

CPC COOPERATIVE PATENT CLASSIFICATION

H ELECTRICITY

(NOTE omitted)

H01 BASIC ELECTRIC ELEMENTS

(NOTE omitted)

H01L SEMICONDUCTOR DEVICES; ELECTRIC SOLID STATE DEVICES NOT OTHERWISE PROVIDED FOR (use of semiconductor devices for measuring [G01](#); resistors in general [H01C](#); magnets, inductors, transformers [H01F](#); capacitors in general [H01G](#); electrolytic devices [H01G 9/00](#); batteries, accumulators [H01M](#); waveguides, resonators, or lines of the waveguide type [H01P](#); line connectors, current collectors [H01R](#); stimulated-emission devices [H01S](#); electromechanical resonators [H03H](#); loudspeakers, microphones, gramophone pick-ups or like acoustic electromechanical transducers [H04R](#); electric light sources in general [H05B](#); printed circuits, hybrid circuits, casings or constructional details of electrical apparatus, manufacture of assemblages of electrical components [H05K](#); use of semiconductor devices in circuits having a particular application, see the subclass for the application)

NOTES

1. This subclass covers:
 - electric solid state devices which are not covered by any other subclass and details thereof, and includes: semiconductor devices adapted for rectifying, amplifying, oscillating or switching; semiconductor devices sensitive to radiation; electric solid state devices using thermoelectric, superconductive, piezo-electric, electrostrictive, magnetostrictive, galvano-magnetic or bulk negative resistance effects and integrated circuit devices;
 - photoresistors, magnetic field dependent resistors, field effect resistors, capacitors with potential-jump barrier, resistors with potential-jump barrier or surface barrier, incoherent light emitting diodes and thin-film or thick-film circuits;
 - processes and apparatus adapted for the manufacture or treatment of such devices, except where such processes relate to single-step processes for which provision exists elsewhere.
2. In this subclass, the following terms or expressions are used with the meaning indicated:
 - "wafer" means a slice of semiconductor or crystalline substrate material, which can be modified by impurity diffusion (doping), ion implantation or epitaxy, and whose active surface can be processed into arrays of discrete components or integrated circuits;
 - "solid state body" means the body of material within which, or at the surface of which, the physical effects characteristic of the device occur. In thermoelectric devices, it includes all materials in the current path.
Regions in or on the body of the device (other than the solid state body itself), which exert an influence on the solid state body electrically, are considered to be "electrodes" whether or not an external electrical connection is made thereto. An electrode may include several portions and the term includes metallic regions which exert influence on the solid state body through an insulating region (e.g. capacitive coupling) and inductive coupling arrangements to the body. The dielectric region in a capacitive arrangement is regarded as part of the electrode. In arrangements including several portions, only those portions which exert an influence on the solid state body by virtue of their shape, size, or disposition or the material of which they are formed are considered to be part of the electrode. The other portions are considered to be "arrangements for conducting electric current to or from the solid state body" or "interconnections between solid state components formed in or on a common substrate", i.e. leads;
 - "device" means an electric circuit element; where an electric circuit element is one of a plurality of elements formed in or on a common substrate it is referred to as a "component";
 - "complete device" is a device in its fully assembled state which may or may not require further treatment, e.g. electroforming, before it is ready for use but which does not require the addition of further structural units;
 - "parts" includes all structural units which are included in a complete device;
 - "container" is an enclosure forming part of the complete device and is essentially a solid construction in which the body of the device is placed, or which is formed around the body without forming an intimate layer thereon. An enclosure which consists of one or more layers formed on the body and in intimate contact therewith is referred to as an "encapsulation";
 - "integrated circuit" is a device where all components, e.g. diodes, resistors, are built up on a common substrate and form the device including interconnections between the components;
 - "assembly" of a device is the building up of the device from its component constructional units and includes the provision of fillings in containers.
3. In this subclass, both the process or apparatus for the manufacture or treatment of a device and the device itself are classified, whenever both of these are described sufficiently to be of interest.

4. Attention is drawn to Note (3) after the title of section [C](#), which Note indicates to which version of the periodic table of chemical elements the IPC refers. In this subclass, the Periodic System used is the 8 group system indicated by Roman numerals in the Periodic Table thereunder.

WARNINGS

1. The following IPC groups are not in the CPC scheme. The subject matter for these IPC groups is classified in the following CPC groups:

H01L 21/301	covered by	H01L 21/30
H01L 21/328	covered by	H01L 29/66075
H01L 21/329	covered by	H01L 29/66083
H01L 21/33	covered by	H01L 29/66227
H01L 21/331	covered by	H01L 29/66234
H01L 21/332	covered by	H01L 29/66363
H01L 21/334	covered by	H01L 29/66075
H01L 21/335	covered by	H01L 29/66409
H01L 21/336	covered by	H01L 29/66477
H01L 21/337	covered by	H01L 29/66893
H01L 21/338	covered by	H01L 29/66848
H01L 21/339	covered by	H01L 29/66946
H01L 21/36-H01L 21/368	covered by	H01L 21/02107
H01L 21/58	covered by	H01L 24/80
H01L 21/60	covered by	H01L 21/50 , H01L 2021/60
H01L 21/66	covered by	H01L 22/00
H01L 21/603	covered by	H01L 21/50 , H01L 2021/603
H01L 21/607	covered by	H01L 21/50 , H01L 2021/607
H01L 21/8242	covered by	H01L 27/108
H01L 21/8244	covered by	H01L 27/11
H01L 21/8246	covered by	H01L 27/112
H01L 21/98	covered by	H01L 25/50
H01L 29/38	covered by	H01L 29/04-H01L 29/365
H01L 29/96	covered by	H01L 29/68-H01L 29/945
H01L 51/30	covered by	H01L 51/0032
H01L 51/40	covered by	H01L 51/0001
H01L 51/46	covered by	H01L 51/0032
H01L 51/48	covered by	H01L 51/0001
H01L 51/54	covered by	H01L 51/0032

2. In this subclass non-limiting references (in the sense of paragraph 39 of the Guide to the IPC) may still be displayed in the scheme.

21/00 Processes or apparatus adapted for the manufacture or treatment of semiconductor or solid state devices or of parts thereof

21/02 . Manufacture or treatment of semiconductor devices or of parts thereof

21/02002 . . {Preparing wafers}

NOTES

1. This group covers processes for manufacturing wafers prior to the fabrication of any device, i.e. between the sawing of ingots (covered by [B28D](#)) and the cleaning of substrates (covered by [H01L 21/02041](#)).
2. This group does not cover:
 - simple use of grinding or polishing machines [B24B](#)
 - thermal smoothening [H01L 21/324](#)

21/02005 . . . {Preparing bulk and homogeneous wafers}
 21/02008 {Multistep processes}
 21/0201 {Specific process step}
 21/02013 {Grinding, lapping}
 21/02016 {Backside treatment}
 21/02019 {Chemical etching}
 21/02021 {Edge treatment, chamfering}
 21/02024 {Mirror polishing}

21/02027 {Setting crystal orientation}
 21/0203 {Making porous regions on the surface}
 21/02032 {by reclaiming or re-processing}
 21/02035 {Shaping}
 21/02041 . . {Cleaning}
 21/02043 . . . {Cleaning before device manufacture, i.e. Begin-Of-Line process}
 21/02046 {Dry cleaning only ([H01L 21/02085](#) takes precedence)}
 21/02049 {with gaseous HF}
 21/02052 {Wet cleaning only ([H01L 21/02085](#) takes precedence)}
 21/02054 {combining dry and wet cleaning steps ([H01L 21/02085](#) takes precedence)}
 21/02057 . . . {Cleaning during device manufacture}
 21/0206 {during, before or after processing of insulating layers}
 21/02063 {the processing being the formation of vias or contact holes}
 21/02065 {the processing being a planarization of insulating layers}
 21/02068 {during, before or after processing of conductive layers, e.g. polysilicon or amorphous silicon layers}

- 21/02071 {the processing being a delineation, e.g. RIE, of conductive layers}
- 21/02074 {the processing being a planarization of conductive layers}
- 21/02076 . . . {Cleaning after the substrates have been singulated}
- 21/02079 . . . {Cleaning for reclaiming}
- 21/02082 . . . {product to be cleaned}
- 21/02085 {Cleaning of diamond}
- 21/02087 {Cleaning of wafer edges}
- 21/0209 {Cleaning of wafer backside}
- 21/02093 {Cleaning of porous materials}
- 21/02096 . . . {only mechanical cleaning}
- 21/02098 . . . {only involving lasers, e.g. laser ablation}
- 21/02101 . . . {only involving supercritical fluids}
- 21/02104 . . {Forming layers (deposition in general [C23C](#); crystal growth in general [C30B](#))}

WARNING

Groups [H01L 21/02104](#) – [H01L 21/02694](#) are incomplete pending reclassification of documents from groups [H01L 21/06](#), [H01L 21/16](#), and [H01L 21/20](#).

Groups [H01L 21/02104](#) – [H01L 21/02694](#), [H01L 21/06](#), [H01L 21/20](#), and [H01L 21/16](#) should be considered in order to perform a complete search.

- 21/02107 . . . {Forming insulating materials on a substrate}

WARNING

Groups [H01L 21/02107](#) – [H01L 21/02326](#) are incomplete pending reclassification of documents from groups [H01L 21/312](#), [H01L 21/314](#), [H01L 21/316](#), and [H01L 21/318](#).

Groups [H01L 21/02107](#) – [H01L 21/02326](#), [H01L 21/312](#), [H01L 21/314](#), [H01L 21/316](#), and [H01L 21/318](#) should be considered in order to perform a complete search.

- 21/02109 {characterised by the type of layer, e.g. type of material, porous/non-porous, pre-cursors, mixtures or laminates}
- 21/02112 {characterised by the material of the layer}

NOTE

Layers comprising sublayers, i.e. multi-layers, are additionally classified in [H01L 21/022](#); porous layers are additionally classified in [H01L 21/02203](#)

- 21/02115 {the material being carbon, e.g. alpha-C, diamond or hydrogen doped carbon}
- 21/02118 {carbon based polymeric organic or inorganic material, e.g. polyimides, poly cyclobutene or PVC (polymers per se [C08G](#), photoresist per se [G03F](#))}
- 21/0212 {the material being fluoro carbon compounds, e.g. (CF_x)_n, (CH_xF_y)_n or polytetrafluoroethylene}
- 21/02123 {the material containing silicon}

- 21/02126 {the material containing Si, O, and at least one of H, N, C, F, or other non-metal elements, e.g. SiOC, SiOC:H or SiONC}

- 21/02129 {the material being boron or phosphorus doped silicon oxides, e.g. BPSG, BSG or PSG}

NOTE

Halogen, e.g. fluorine, containing BPSG, PSG, BSG, and the like, are additionally classified in [H01L 21/02131](#)

- 21/02131 {the material being halogen doped silicon oxides, e.g. FSG}
- 21/02134 {the material comprising hydrogen silsesquioxane, e.g. HSQ}
- 21/02137 {the material comprising alkyl silsesquioxane, e.g. MSQ}
- 21/0214 {the material being a silicon oxynitride, e.g. SiON or SiON:H}
- 21/02142 {the material containing silicon and at least one metal element, e.g. metal silicate based insulators or metal silicon oxynitrides}
- 21/02145 {the material containing aluminium, e.g. AlSiO_x}
- 21/02148 {the material containing hafnium, e.g. HfSiO_x or HfSiON}
- 21/0215 {the material containing tantalum, e.g. TaSiO_x}
- 21/02153 {the material containing titanium, e.g. TiSiO_x}
- 21/02156 {the material containing at least one rare earth element, e.g. silicate of lanthanides, scandium or yttrium}
- 21/02159 {the material containing zirconium, e.g. ZrSiO_x}
- 21/02161 {the material containing more than one metal element}
- 21/02164 {the material being a silicon oxide, e.g. SiO₂}

NOTE

The formation of silicon oxide layers is classified in this group regardless of the precursor or of the process of formation; in case of explicit statements on doping, on rest-groups, or on material components see [H01L 21/02126](#) and subgroups; deposition of silicon oxide from organic precursors without further statements on film composition is classified here and in [H01L 21/02205](#) and subgroups

- 21/02167 {the material being a silicon carbide not containing oxygen, e.g. SiC, SiC:H or silicon carbonitrides ([H01L 21/02126](#) and [H01L 21/0214](#) take precedence)}

21/0217	{the material being a silicon nitride not containing oxygen, e.g. SixNy or SixByNz (H01L 21/02126 and H01L 21/0214 take precedence)}	21/02227	{formation by a process other than a deposition process}
21/02172	{the material containing at least one metal element, e.g. metal oxides, metal nitrides, metal oxynitrides or metal carbides (materials containing silicon H01L 21/02123 ; metal silicates H01L 21/02142)}	NOTE Subject matter classified in the range of H01L 21/0223 - H01L 21/02249 is additionally classified in H01L 21/02249 , H01L 21/02255 and H01L 21/02252 , depending on the type of reaction		
21/02175	{characterised by the metal (H01L 21/02197 takes precedence)}	21/0223	{formation by oxidation, e.g. oxidation of the substrate}
21/02178	{the material containing aluminium, e.g. Al ₂ O ₃ }	21/02233	{of the semiconductor substrate or a semiconductor layer}
21/02181	{the material containing hafnium, e.g. HfO ₂ }	21/02236	{group IV semiconductor}
21/02183	{the material containing tantalum, e.g. Ta ₂ O ₅ }	21/02238	{silicon in uncombined form, i.e. pure silicon}
21/02186	{the material containing titanium, e.g. TiO ₂ }	21/02241	{III-V semiconductor}
21/02189	{the material containing zirconium, e.g. ZrO ₂ }	21/02244	{of a metallic layer}
21/02192	{the material containing at least one rare earth metal element, e.g. oxides of lanthanides, scandium or yttrium}	21/02247	{formation by nitridation, e.g. nitridation of the substrate}
21/02194	{the material containing more than one metal element}	21/02249	{formation by combined oxidation and nitridation performed simultaneously}
21/02197	{the material having a perovskite structure, e.g. BaTiO ₃ }	21/02252	{formation by plasma treatment, e.g. plasma oxidation of the substrate (after treatment of an insulating film by plasma H01L 21/3105 and subgroups)}
21/022	{the layer being a laminate, i.e. composed of sublayers, e.g. stacks of alternating high-k metal oxides (adhesion layers or buffer layers H01L 21/02304 , H01L 21/02362)}	21/02255	{formation by thermal treatment (H01L 21/02252 takes precedence; after treatment of an insulating film H01L 21/3105 and subgroups)}
21/02203	{the layer being porous}	21/02258	{formation by anodic treatment, e.g. anodic oxidation}
21/02205	{the layer being characterised by the precursor material for deposition}	21/0226	{formation by a deposition process (per se C23C)}
21/02208	{the precursor containing a compound comprising Si}	21/02263	{deposition from the gas or vapour phase}
21/02211	{the compound being a silane, e.g. disilane, methylsilane or chlorosilane}	NOTE This group and subgroups also cover deposition methods in which the gas or vapour is produced by physical means, e.g. ablation from targets or heating of source material		
21/02214	{the compound comprising silicon and oxygen}	21/02266	{deposition by physical ablation of a target, e.g. sputtering, reactive sputtering, physical vapour deposition or pulsed laser deposition}
NOTE This group <u>does not cover</u> mixtures of a silane and oxygen			21/02269	{deposition by thermal evaporation (H01L 21/02293 takes precedence)}
21/02216	{the compound being a molecule comprising at least one silicon-oxygen bond and the compound having hydrogen or an organic group attached to the silicon or oxygen, e.g. a siloxane}	NOTE Subject matter relating to molecular beam epitaxy is classified in this group		
21/02219	{the compound comprising silicon and nitrogen}	21/02271	{deposition by decomposition or reaction of gaseous or vapour phase compounds, i.e. chemical vapour deposition (H01L 21/02266 takes precedence)}
NOTE This group <u>does not cover</u> mixtures of silane and nitrogen			21/02274	{in the presence of a plasma [PECVD]}
21/02222	{the compound being a silazane}			
21/02225	{characterised by the process for the formation of the insulating layer}			

- 21/02277 {the reactions being activated by other means than plasma or thermal, e.g. photo-CVD}
- 21/0228 {deposition by cyclic CVD, e.g. ALD, ALE, pulsed CVD}

NOTE

Subject matter relating to cyclic plasma CVD is additionally classified in [H01L 21/02274](#)

- 21/02282 {liquid deposition, e.g. spin-coating, sol-gel techniques, spray coating}
- 21/02285 {Langmuir-Blodgett techniques}
- 21/02288 {printing, e.g. ink-jet printing ([per se B41J](#))}
- 21/0229 {liquid atomic layer deposition}
- 21/02293 {formation of epitaxial layers by a deposition process ([epitaxial growth per se C30B](#))}

NOTE

Formation of non-epitaxial layers by MBE, ALE, etc. is not covered by this group; for MBE [see H01L 21/02269](#); for ALE [see H01L 21/0228](#)

- 21/02296 {characterised by the treatment performed before or after the formation of the layer ([H01L 21/02227](#) and subgroups take precedence)}

NOTE

This group and subgroups only cover processes which are directly linked to the layer formation; routine anneals, i.e. thermal treatment without further features like a special atmosphere, presence of a plasma, thermally induced chemical reactions, change of phase (crystal structure) etc. are not classified here; for cleaning [see H01L 21/02041](#) and subgroups; for etching processes [see H01L 21/311](#) and subgroups; for planarization processes [see H01L 21/31051](#) and subgroups; for processes to repair etch damage [see H01L 21/3105](#) and subgroups

- 21/02299 {pre-treatment}

NOTE

This group and subgroups cover treatments to improve adhesion or change the surface termination; for etching [see H01L 21/306](#) and subgroups and [H01L 21/311](#) and subgroups

- 21/02301 {in-situ cleaning}

NOTE

Subject matter relating to the cleaning processes for semiconductor devices in general is covered by [H01L 21/02041](#) and subgroups

- 21/02304 {formation of intermediate layers, e.g. buffer layers, layers to improve adhesion, lattice match or diffusion barriers}
- 21/02307 {treatment by exposure to a liquid}
- 21/0231 {treatment by exposure to electromagnetic radiation, e.g. UV light}
- 21/02312 {treatment by exposure to a gas or vapour}
- 21/02315 {treatment by exposure to a plasma}
- 21/02318 {post-treatment}

NOTE

This group only covers processes that are part of the layer formation; treatments which are performed after completion of the insulating layer are covered by [H01L 21/3105](#) and subgroups

- 21/02321 {introduction of substances into an already existing insulating layer ([H01L 21/02227](#) and subgroups take precedence)}

NOTE

processes like the introduction of phosphorus into silicon oxide by diffusion, or doping of an already existing insulating layer are covered by this group and subgroups; for the method of introduction, [see H01L 21/02337](#), [H01L 21/02343](#), [H01L 21/02345](#) and subgroups

- 21/02323 {introduction of oxygen}
- 21/02326 {into a nitride layer, e.g. changing SiN to SiON}
- 21/02329 {introduction of nitrogen}
- 21/02332 {into an oxide layer, e.g. changing SiO to SiON}
- 21/02334 {in-situ cleaning after layer formation, e.g. removing process residues}

NOTE

Subject matter relating to the cleaning processes for semiconductor devices in general is covered by [H01L 21/02041](#) and subgroups

- 21/02337 {treatment by exposure to a gas or vapour}
- 21/0234 {treatment by exposure to a plasma}
- 21/02343 {treatment by exposure to a liquid}
- 21/02345 {treatment by exposure to radiation, e.g. visible light}
- 21/02348 {treatment by exposure to UV light}
- 21/02351 {treatment by exposure to corpuscular radiation, e.g. exposure to electrons, alpha-particles, protons or ions}
- 21/02354 {using a coherent radiation, e.g. a laser}

21/02356	{treatment to change the morphology of the insulating layer, e.g. transformation of an amorphous layer into a crystalline layer}	21/02461	{Phosphides}
21/02359	{treatment to change the surface groups of the insulating layer}	21/02463	{Arsenides}
21/02362	{formation of intermediate layers, e.g. capping layers or diffusion barriers}	21/02466	{Antimonides}
21/02365	. . .	{Forming inorganic semiconducting materials on a substrate (for light-sensitive devices H01L 31/00)}	21/02469	{Group 12/16 materials}
WARNING			21/02472	{Oxides}
Group H01L 21/02365 is incomplete pending reclassification of documents from groups H01L 21/06 , H01L 21/16 , and H01L 21/20			21/02474	{Sulfides}
Groups H01L 21/06 , H01L 21/16 , and H01L 21/20 should be considered in order to perform a complete search.			21/02477	{Selenides}
21/02367	{Substrates}	21/0248	{Tellurides}
21/0237	{Materials}	21/02483	{Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}
21/02373	{Group 14 semiconducting materials}	21/02485	{Other chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}
21/02376	{Carbon, e.g. diamond-like carbon}	21/02488	{Insulating materials}
21/02378	{Silicon carbide}	21/02491	{Conductive materials}
21/02381	{Silicon, silicon germanium, germanium}	21/02494	{Structure}
21/02384	{including tin}	21/02496	{Layer structure}
21/02387	{Group 13/15 materials}	21/02499	{Monolayers}
21/02389	{Nitrides}	21/02502	{consisting of two layers}
21/02392	{Phosphides}	21/02505	{consisting of more than two layers}
21/02395	{Arsenides}	21/02507	{Alternating layers, e.g. superlattice}
21/02398	{Antimonides}	21/0251	{Graded layers}
21/024	{Group 12/16 materials}	21/02513	{Microstructure}
21/02403	{Oxides}	21/02516	{Crystal orientation}
21/02406	{Sulfides}	21/02518	{Deposited layers}
21/02409	{Selenides}	21/02521	{Materials}
21/02411	{Tellurides}	21/02524	{Group 14 semiconducting materials}
21/02414	{Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}	21/02527	{Carbon, e.g. diamond-like carbon}
21/02417	{Chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}	21/02529	{Silicon carbide}
21/0242	{Crystalline insulating materials}	21/02532	{Silicon, silicon germanium, germanium}
21/02422	{Non-crystalline insulating materials, e.g. glass, polymers}	21/02535	{including tin}
21/02425	{Conductive materials, e.g. metallic silicides}	21/02538	{Group 13/15 materials}
21/02428	{Structure}	21/0254	{Nitrides}
21/0243	{Surface structure}	21/02543	{Phosphides}
21/02433	{Crystal orientation}	21/02546	{Arsenides}
21/02436	{Intermediate layers between substrates and deposited layers}	21/02549	{Antimonides}
21/02439	{Materials}	21/02551	{Group 12/16 materials}
21/02441	{Group 14 semiconducting materials}	21/02554	{Oxides}
21/02444	{Carbon, e.g. diamond-like carbon}	21/02557	{Sulfides}
21/02447	{Silicon carbide}	21/0256	{Selenides}
21/0245	{Silicon, silicon germanium, germanium}	21/02562	{Tellurides}
21/02452	{including tin}	21/02565	{Oxide semiconducting materials not being Group 12/16 materials, e.g. ternary compounds}
21/02455	{Group 13/15 materials}	21/02568	{Chalcogenide semiconducting materials not being oxides, e.g. ternary compounds}
21/02458	{Nitrides}	21/0257	{Doping during depositing}
			21/02573	{Conductivity type}
			21/02576	{N-type}
			21/02579	{P-type}
			21/02581	{Transition metal or rare earth elements}
			21/02584	{Delta-doping}
			21/02587	{Structure}
			21/0259	{Microstructure}
			21/02592	{amorphous}
			21/02595	{polycrystalline}
			21/02598	{monocrystalline}

21/02601 {Nanoparticles (fullerenes H01L 51/0046)}	21/0271	. . . {comprising organic layers}
21/02603 {Nanowires}	21/0272 {for lift-off processes}
21/02606 {Nanotubes (carbon nanotubes H01L 51/0048)}	21/0273 {characterised by the treatment of photoresist layers}
21/02609 {Crystal orientation}	21/0274 {Photolithographic processes}
21/02612 {Formation types}	21/0275 {using lasers}
21/02614 {Transformation of metal, e.g. oxidation, nitridation}	21/0276 {using an anti-reflective coating (anti-reflective coating for lithography in general G03F 7/09)}
21/02617 {Deposition types}	21/0277 {Electrolithographic processes}
21/0262 {Reduction or decomposition of gaseous compounds, e.g. CVD}	21/0278 {Röntgenlithographic or X-ray lithographic processes}
21/02623 {Liquid deposition}	21/0279 {Ionlithographic processes}
21/02625 {using melted materials}	21/033	. . . comprising inorganic layers
21/02628 {using solutions}	21/0331 {for lift-off processes}
21/02631 {Physical deposition at reduced pressure, e.g. MBE, sputtering, evaporation}	21/0332 {characterised by their composition, e.g. multilayer masks, materials}
21/02634 {Homoepitaxy}	21/0334 {characterised by their size, orientation, disposition, behaviour, shape, in horizontal or vertical plane}
21/02636 {Selective deposition, e.g. simultaneous growth of mono- and non-monocrystalline semiconductor materials}	21/0335 {characterised by their behaviour during the process, e.g. soluble masks, redeposited masks}
21/02639 {Preparation of substrate for selective deposition}	21/0337 {characterised by the process involved to create the mask, e.g. lift-off masks, sidewalls, or to modify the mask, e.g. pre-treatment, post-treatment}
21/02642 {Mask materials other than SiO ₂ or SiN}	21/0338 {Process specially adapted to improve the resolution of the mask}
21/02645 {Seed materials}	21/04	. . the devices having at least one potential-jump barrier or surface barrier, e.g. PN junction, depletion layer or carrier concentration layer {(multistep manufacturing processes for semiconductor bodies of said devices H01L 29/02 ; multistep manufacturing processes for electrodes of said devices H01L 29/401 ; multistep manufacturing processes for said devices H01L 29/66007)}
21/02647 {Lateral overgrowth}	21/0405	. . . {the devices having semiconductor bodies comprising semiconducting carbon, e.g. diamond, diamond-like carbon (multistep processes for the manufacture of said devices H01L 29/66015)}
21/0265 {Pendeoepitaxy}	NOTE	
21/02653 {Vapour-liquid-solid growth}	This group covers passivation	
21/02656 {Special treatments}	21/041 {Making n- or p-doped regions}
21/02658 {Pretreatments (cleaning in general H01L 21/02041)}	21/0415 {using ion implantation}
21/02661 {In-situ cleaning}	21/042 {Changing their shape, e.g. forming recesses (etching of the semiconductor body H01L 21/302)}
21/02664 {Aftertreatments (planarisation in general H01L 21/304)}	21/0425 {Making electrodes}
21/02667 {Crystallisation or recrystallisation of non-monocrystalline semiconductor materials, e.g. regrowth}	21/043 {Ohmic electrodes}
21/02669 {using crystallisation inhibiting elements}	21/0435 {Schottky electrodes}
21/02672 {using crystallisation enhancing elements}	21/044 {Conductor-insulator-semiconductor electrodes}
21/02675 {using laser beams}	21/0445	. . . {the devices having semiconductor bodies comprising crystalline silicon carbide (multistep processes for the manufacture of said devices H01L 29/66053)}
21/02678 {Beam shaping, e.g. using a mask}	21/045 {passivating silicon carbide surfaces}
21/0268 {Shape of mask}	21/0455 {Making n or p doped regions or layers, e.g. using diffusion}
21/02683 {Continuous wave laser beam}		
21/02686 {Pulsed laser beam}		
21/02689 {using particle beams}		
21/02691 {Scanning of a beam}		
21/02694 {Controlling the interface between substrate and epitaxial layer, e.g. by ion implantation followed by annealing}		
21/02697	. . . {Forming conducting materials on a substrate}		
21/027	. . Making masks on semiconductor bodies for further photolithographic processing not provided for in group H01L 21/18 or H01L 21/34 {(photographic masks or originals per se G03F 1/00 ; registration or positioning of photographic masks or originals G03F 9/00 ; photographic cameras G03B ; control of position G05D 3/00)}		

21/046 {using ion implantation}	21/18	. . . the devices having semiconductor bodies comprising elements of Group IV of the Periodic System or A _{III} B _V compounds with or without impurities, e.g. doping materials { (H01L 21/041 - H01L 21/0425, H01L 21/045 - H01L 21/048 take precedence) }
	NOTE Processes where ion implantation of boron and subsequent annealing does not produce a p-doped region are classified elsewhere, e.g. H01L 21/0445		NOTE This group covers also processes and apparatus which, by using the appropriate technology, are clearly suitable for manufacture or treatment of devices whose bodies comprise elements of Group IV of the Periodic System or A _{III} B _V compounds, even if the material used is not explicitly specified.
21/0465 {using masks}	21/182 {Intermixing or interdiffusion or disordering of III-V heterostructures, e.g. IILD}
21/047 {characterised by the angle between the ion beam and the crystal planes or the main crystal surface}	21/185 {Joining of semiconductor bodies for junction formation}
21/0475 {Changing the shape of the semiconductor body, e.g. forming recesses, (etching of the semiconductor body H01L 21/302) }	21/187 {by direct bonding}
21/048 {Making electrodes}	21/20 Deposition of semiconductor materials on a substrate, e.g. epitaxial growth {solid phase epitaxy}
21/0485 {Ohmic electrodes}		WARNING Group H01L 21/20 is impacted by reclassification into groups H01L 21/02365 – H01L 21/02694 . Groups H01L 21/20 and H01L 21/02365 – H01L 21/02694 should be considered in order to perform a complete search.
21/049 {Conductor-insulator-semiconductor electrodes, e.g. MIS contacts}	21/2003 {Characterised by the substrate (H01L 21/203, H01L 21/205, H01L 21/208 take precedence) }
21/0495 {Schottky electrodes}	21/2007 {Bonding of semiconductor wafers to insulating substrates or to semiconducting substrates using an intermediate insulating layer (H01L 21/2011 takes precedence; bonding of semiconductor wafers to semiconductor wafers for junction formation H01L 21/187) }
21/06	. . . the devices having semiconductor bodies comprising selenium or tellurium in uncombined form other than as impurities in semiconductor bodies of other materials	21/2011 {the substrate being of crystalline insulating material, e.g. sapphire}
21/08 Preparation of the foundation plate	21/2015 {the substrate being of crystalline semiconductor material, e.g. lattice adaptation, heteroepitaxy}
21/10 Preliminary treatment of the selenium or tellurium, its application to the foundation plate, or the subsequent treatment of the combination	21/2018 {Selective epilaxial growth, e.g. simultaneous deposition of mono - and non-mono semiconductor materials}
21/101 {Application of the selenium or tellurium to the foundation plate}	21/2022 {Epitaxial regrowth of non-monocrystalline semiconductor materials, e.g. lateral epitaxy by seeded solidification, solid-state crystallization, solid-state graphoepitaxy, explosive crystallization, grain growth in polycrystalline materials}
21/103 Conversion of the selenium or tellurium to the conductive state	21/2026 {using a coherent energy beam, e.g. laser or electron beam}
21/105 Treatment of the surface of the selenium or tellurium layer after having been made conductive	21/203 using physical deposition, e.g. vacuum deposition, sputtering
21/108 Provision of discrete insulating layers, i.e. non-genetic barrier layers		
21/12 Application of an electrode to the exposed surface of the selenium or tellurium after the selenium or tellurium has been applied to the foundation plate		
21/14 Treatment of the complete device, e.g. by electroforming to form a barrier		
21/145 Ageing		
21/16	. . . the devices having semiconductor bodies comprising cuprous oxide or cuprous iodide		
21/161 {Preparation of the foundation plate, preliminary treatment oxidation of the foundation plate, reduction treatment}		
21/162 {Preliminary treatment of the foundation plate}		
21/164 {Oxidation and subsequent heat treatment of the foundation plate (H01L 21/165 takes precedence) }		
21/165 {Reduction of the copper oxide, treatment of the oxide layer}		
21/167 {Application of a non-genetic conductive layer}		
21/168 {Treatment of the complete device, e.g. electroforming, ageing}		

21/2033	{Epitaxial deposition of elements of Group IV of the Periodic System, e.g. Si, Ge}	21/2258	{Diffusion into or out of $A_{III}B_V$ compounds}
21/2036	{Epitaxial deposition of $A_{III}B_V$ compounds}	21/228	using diffusion into or out of a solid from or into a liquid phase, e.g. alloy diffusion processes {(H01L 21/221 - H01L 21/222 take precedence)}
21/205	using reduction or decomposition of a gaseous compound yielding a solid condensate, i.e. chemical deposition	21/24	Alloying of impurity materials, e.g. doping materials, electrode materials, with a semiconductor body {(H01L 21/182 takes precedence)}
21/2053	{Epitaxial deposition of elements of Group IV of the Periodic System, e.g. Si, Ge}	21/242	{Alloying of doping materials with $A_{III}B_V$ compounds}
21/2056	{Epitaxial deposition of $A_{III}B_V$ compounds}	21/244	{Alloying of electrode materials}
21/208	using liquid deposition	21/246	{with $A_{III}B_V$ compounds}
21/2085	{Epitaxial deposition of $A_{III}B_V$ compounds}	21/248	{Apparatus specially adapted for the alloying}
21/22	Diffusion of impurity materials, e.g. doping materials, electrode materials, into or out of a semiconductor body, or between semiconductor regions; {Interactions between two or more impurities; Redistribution of impurities}	21/26	Bombardment with radiation {(H01L 21/3105 takes precedence)}
21/2205	{from the substrate during epitaxy, e.g. autodoping; Preventing or using autodoping}	21/2605	{using natural radiation, e.g. alpha, beta or gamma radiation}
21/221	{of killers}	21/261	to produce a nuclear reaction transmuting chemical elements
21/2215	{in $A_{III}B_V$ compounds}	21/263	with high-energy radiation (H01L 21/261 takes precedence)
21/222	{Lithium-drift}	21/2633	{for etching, e.g. sputteretching}
21/2225	{Diffusion sources}	21/2636	{for heating, e.g. electron beam heating}
21/223	using diffusion into or out of a solid from or into a gaseous phase {(H01L 21/221 - H01L 21/222 take precedence; diffusion through an applied layer H01L 21/225)}	21/265	producing ion implantation
21/2233	{Diffusion into or out of $A_{III}B_V$ compounds}	21/26506	{in group IV semiconductors}
21/2236	{from or into a plasma phase}	21/26513	{of electrically active species}
21/225	using diffusion into or out of a solid from or into a solid phase, e.g. a doped oxide layer {(H01L 21/221 - H01L 21/222 take precedence)}	21/2652	{Through-implantation}
21/2251	{Diffusion into or out of group IV semiconductors}	21/26526	{Recoil-implantation}
		NOTE	21/26533	{of electrically inactive species in silicon to make buried insulating layers}
		{In groups	21/2654	{in $A_{III}B_V$ compounds}
		H01L 21/2254 - H01L 21/2257	21/26546	{of electrically active species}
		one should consider the main compositional parts of the applied layer just before the diffusion step}	21/26553	{Through-implantation}
21/2252	{using predeposition of impurities into the semiconductor surface, e.g. from a gaseous phase}	21/2656	{characterised by the implantation of both electrically active and inactive species in the same semiconductor region to be doped}
21/2253	{by ion implantation}	21/26566	{of a cluster, e.g. using a gas cluster ion beam}
21/2254	{from or through or into an applied layer, e.g. photoresist, nitrides}	2021/26573	{in diamond}
21/2255	{the applied layer comprising oxides only, e.g. P_2O_5 , PSG, H_3BO_3 , doped oxides}	21/2658	{of a molecular ion, e.g. decaborane}
21/2256	{through the applied layer}	21/26586	{characterised by the angle between the ion beam and the crystal planes or the main crystal surface}
21/2257	{the applied layer being silicon or silicide or SIPOS, e.g. polysilicon, porous silicon}	21/26593	{at a temperature lower than room temperature}
			21/266	using masks {(H01L 21/26586 takes precedence)}
			21/268	using electromagnetic radiation, e.g. laser radiation
			21/2683	{using X-ray lasers}
			21/2686	{using incoherent radiation}
			21/28	Manufacture of electrodes on semiconductor bodies using processes or apparatus not provided for in groups H01L 21/20 - H01L 21/268 {etching for patterning the electrodes H01L 21/311 , H01L 21/3213 ; multistep manufacturing processes for data storage electrodes H01L 29/4011 }

21/28008	{Making conductor-insulator-semiconductor electrodes}	21/28088	{the final conductor layer next to the insulator being a composite, e.g. TiN}
21/28017	{the insulator being formed after the semiconductor body, the semiconductor being silicon}	21/28097	{the final conductor layer next to the insulator being a metallic silicide}
NOTE This group covers deposition of the insulators, including epitaxial insulators, and the conductors within the same process or chamber		21/28105	{the final conductor next to the insulator having a lateral composition or doping variation, or being formed laterally by more than one deposition step}
21/28026	{characterised by the conductor (H01L 21/28176 takes precedence)}	21/28114	{characterised by the sectional shape, e.g. T, inverted-T}
NOTE When the final conductor comprises a superconductor, subject matter is not classified according to the subgroups H01L 21/28035 - H01L 21/28097 . Instead, it is classified in H01L 21/28026		NOTE Documents are also classified in groups H01L 21/28035 - H01L 21/28104 when the composition is also relevant	
21/28035	{the final conductor layer next to the insulator being silicon, e.g. polysilicon, with or without impurities (H01L 21/28105 takes precedence)}	21/28123	{Lithography-related aspects, e.g. sub-lithography lengths; Isolation-related aspects, e.g. to solve problems arising at the crossing with the side of the device isolation; Planarisation aspects}
NOTE A very thin, e.g. silicon, adhesion or seed layer is not considered as the one next to the insulator		21/28132	{conducting part of electrode is defined by a sidewall spacer or a similar technique, e.g. oxidation under mask, plating}
21/28044	{the conductor comprising at least another non-silicon conductive layer}	21/28141	{insulating part of the electrode is defined by a sidewall spacer, e.g. dummy spacer, or a similar technique, e.g. oxidation under mask, plating}
21/28052	{the conductor comprising a silicide layer formed by the silicidation reaction of silicon with a metal layer (formed by metal ion implantation H01L 21/28044)}	21/2815	{part or whole of the electrode is a sidewall spacer or made by a similar technique, e.g. transformation under mask, plating}
21/28061	{the conductor comprising a metal or metallic silicide formed by deposition, e.g. sputter deposition, i.e. without a silicidation reaction (H01L 21/28052 takes precedence)}	21/28158	{Making the insulator}
NOTE To assess the coverage of groups H01L 21/28052 and H01L 21/28061 , barrier layers, e.g. TaSiN, are not considered		21/28167	{on single crystalline silicon, e.g. using a liquid, i.e. chemical oxidation}
21/2807	{the final conductor layer next to the insulator being Si or Ge or C and their alloys except Si}	21/28176	{with a treatment, e.g. annealing, after the formation of the definitive gate conductor}
21/28079	{the final conductor layer next to the insulator being a single metal, e.g. Ta, W, Mo, Al}	21/28185	{with a treatment, e.g. annealing, after the formation of the gate insulator and before the formation of the definitive gate conductor}
		21/28194	{by deposition, e.g. evaporation, ALD, CVD, sputtering, laser deposition (H01L 21/28202 takes precedence)}
		21/28202	{in a nitrogen-containing ambient, e.g. nitride deposition, growth, oxynitridation, NH ₃ nitridation, N ₂ O oxidation, thermal nitridation, RTN, plasma nitridation, RPN}

21/28211	{in a gaseous ambient using an oxygen or a water vapour, e.g. RTO, possibly through a layer (H01L 21/28194 and H01L 21/28202 take precedence)}	21/28568	{the conductive layers comprising transition metals (H01L 21/28518 takes precedence)}
		NOTE thin oxidation layers used as a barrier layer or as a buffer layer, e.g. before the formation of a high-k insulator, are classified here only if important <u>per se</u>	21/28575	{on semiconductor bodies comprising A _{III} B _V compounds}
21/2822	{with substrate doping, e.g. N, Ge, C implantation, before formation of the insulator}	21/28581	{Deposition of Schottky electrodes}
21/28229	{by deposition of a layer, e.g. metal, metal compound or polysilicon, followed by transformation thereof into an insulating layer}	21/28587	{characterised by the sectional shape, e.g. T, inverted T}
21/28238	{with sacrificial oxide}	21/28593	{asymmetrical sectional shape}
21/28247	{passivation or protection of the electrode, e.g. using re-oxidation}	21/288	from a liquid, e.g. electrolytic deposition
21/28255	{the insulator being formed after the semiconductor body, the semiconductor belonging to Group IV and not being elemental silicon, e.g. Ge, SiGe, SiGeC}	21/2885	{using an external electrical current, i.e. electro-deposition}
21/28264	{the insulator being formed after the semiconductor body, the semiconductor being a III-V compound}	21/30	Treatment of semiconductor bodies using processes or apparatus not provided for in groups H01L 21/20 - H01L 21/26 (manufacture of electrodes thereon H01L 21/28)
21/283	Deposition of conductive or insulating materials for electrodes {conducting electric current}	21/3003	{Hydrogenation or deuteration, e.g. using atomic hydrogen from a plasma}
21/285	from a gas or vapour, e.g. condensation	21/3006	{of A _{III} B _V compounds}
21/28506	{of conductive layers}	21/302	to change their surface-physical characteristics or shape, e.g. etching, polishing, cutting
21/28512	{on semiconductor bodies comprising elements of Group IV of the Periodic System}	21/304	Mechanical treatment, e.g. grinding, polishing, cutting {(H01L 21/30625 takes precedence)}
21/28518	{the conductive layers comprising silicides (H01L 21/28537 takes precedence)}	21/3043	{Making grooves, e.g. cutting}
21/28525	{the conductive layers comprising semiconducting material (H01L 21/28518 , H01L 21/28537 take precedence)}	21/3046	{using blasting, e.g. sand-blasting (H01L 21/2633 takes precedence)}
21/28531	{Making of side-wall contacts}	21/306	Chemical or electrical treatment, e.g. electrolytic etching (to form insulating layers H01L 21/31)
21/28537	{Deposition of Schottky electrodes}	21/30604	{Chemical etching}
21/2855	{by physical means, e.g. sputtering, evaporation (H01L 21/28518 - H01L 21/28537 and H01L 21/28568 take precedence)}	21/30608	{Anisotropic liquid etching (H01L 21/3063 takes precedence)}
21/28556	{by chemical means, e.g. CVD, LPCVD, PECVD, laser CVD (H01L 21/28518 - H01L 21/28537 and H01L 21/28568 take precedence)}	21/30612	{Etching of A _{III} B _V compounds}
21/28562	{Selective deposition}	21/30617	{Anisotropic liquid etching}
			21/30621	{Vapour phase etching}
			21/30625	{With simultaneous mechanical treatment, e.g. mechanico-chemical polishing}
			21/3063	Electrolytic etching
			21/30635	{of A _{III} B _V compounds}
			21/3065	Plasma etching; Reactive-ion etching
			21/30655	{comprising alternated and repeated etching and passivation steps, e.g. Bosch process}
			21/308	using masks (H01L 21/3063 , H01L 21/3065 take precedence)
			21/3081	{characterised by their composition, e.g. multilayer masks, materials}
			21/3083	{characterised by their size, orientation, disposition, behaviour, shape, in horizontal or vertical plane}
			21/3085	{characterised by their behaviour during the process, e.g. soluble masks, redeposited masks}

- 21/3086 {characterised by the process involved to create the mask, e.g. lift-off masks, sidewalls, or to modify the mask, e.g. pre-treatment, post-treatment}
- 21/3088 {Process specially adapted to improve the resolution of the mask}
- 21/31 to form insulating layers thereon, e.g. for masking or by using photolithographic techniques ([encapsulating layers H01L 21/56](#)); After treatment of these layers; Selection of materials for these layers
- 21/3105 After-treatment
- 21/31051 {Planarisation of the insulating layers ([H01L 21/31058 takes precedence](#))}
- 21/31053 {involving a dielectric removal step}
- 21/31055 {the removal being a chemical etching step, e.g. dry etching ([etching per se H01L 21/311](#))}
- 21/31056 {the removal being a selective chemical etching step, e.g. selective dry etching through a mask}
- 21/31058 {of organic layers}
- 21/311 Etching the insulating layers {by chemical or physical means ([H01L 21/31058 takes precedence](#))}
- 21/31105 {Etching inorganic layers}
- 21/31111 {by chemical means}
- 21/31116 {by dry-etching}
- 21/31122 {of layers not containing Si, e.g. PZT, Al₂O₃}
- 21/31127 {Etching organic layers}
- 21/31133 {by chemical means}
- 21/31138 {by dry-etching}
- 21/31144 {using masks}
- 21/3115 Doping the insulating layers
- 21/31155 {by ion implantation}
- 21/312 Organic layers, e.g. photoresist ([H01L 21/3105](#), [H01L 21/32 take precedence](#); [photoresists per se G03C](#))
- (Frozen)

WARNING

Groups [H01L 21/312](#) – [H01L 21/3128](#) are no longer used for the classification of documents as of May 1, 2011. The content of these groups is being reclassified into groups [H01L 21/02107](#) – [H01L 21/02326](#).

Groups [H01L 21/02107](#) – [H01L 21/02326](#) should be considered in order to perform a complete search.

- 21/3121 {Layers comprising organo-silicon compounds} (Frozen)
- 21/3122 {layers comprising polysiloxane compounds} (Frozen)
- 21/3124 {layers comprising hydrogen silsesquioxane} (Frozen)

- 21/3125 {layers comprising silazane compounds} (Frozen)
- 21/3127 {Layers comprising fluoro (hydro)carbon compounds, e.g. polytetrafluoroethylene} (Frozen)
- 21/3128 {by Langmuir-Blodgett techniques} (Frozen)
- 21/314 Inorganic layers ([H01L 21/3105](#), [H01L 21/32 take precedence](#)) (Frozen)

WARNING

Groups [H01L 21/314](#) – [H01L 21/3185](#) are no longer used for the classification of documents as of May 1, 2011. The content of these group is being reclassified into group [H01L 21/02107](#) – [H01L 21/02326](#).

Groups [H01L 21/02107](#) – [H01L 21/02326](#) should be considered in order to perform a complete search.

- 21/3141 {Deposition using atomic layer deposition techniques [ALD]} (Frozen)
- 21/3142 {of nano-laminates, e.g. alternating layers of Al₂O₃-HfO₂} (Frozen)
- 21/3143 {composed of alternated layers or of mixtures of nitrides and oxides or of oxinitrides, e.g. formation of oxinitride by oxidation of nitride layers} (Frozen)
- 21/3144 {on silicon} (Frozen)
- 21/3145 {formed by deposition from a gas or vapour} (Frozen)
- 21/3146 {Carbon layers, e.g. diamond-like layers} (Frozen)
- 21/3147 {Epitaxial deposition of insulating materials} (Frozen)
- 21/3148 {Silicon Carbide layers} (Frozen)
- 2021/3149 {Langmuir-Blodgett techniques} (Frozen)
- 21/316 composed of oxides or glassy oxides or oxide based glass (Frozen)

WARNING

Group [H01L 21/316](#) is no longer used for the classification of documents as of May 1, 2011. The content of this group is being reclassified into groups [H01L 21/02107](#) – [H01L 21/02326](#).

Groups [H01L 21/02107](#) – [H01L 21/02326](#) should be considered in order to perform a complete search.

- 21/31604 {Deposition from a gas or vapour ([H01L 21/31691](#), [H01L 21/31695 take precedence](#))} (Frozen)
- 21/31608 {Deposition of SiO₂ ([H01L 21/31625](#), [H01L 21/31629](#) and [H01L 21/31633 take precedence](#))} (Frozen)

21/31612 {on a silicon body} (Frozen)	21/3205 Deposition of non-insulating-, e.g. conductive- or resistive-, layers on insulating layers; After-treatment of these layers (manufacture of electrodes H01L 21/28)
21/31616 {Deposition of Al ₂ O ₃ } (Frozen)	21/32051 {Deposition of metallic or metal-silicide layers}
21/3162 {on a silicon body} (Frozen)	21/32053 {of metal-silicide layers}
21/31625 {Deposition of boron or phosphorus doped silicon oxide, e.g. BSG, PSG, BPSG} (Frozen)	21/32055 {Deposition of semiconductive layers, e.g. poly - or amorphous silicon layers}
21/31629 {Deposition of halogen doped silicon oxide, e.g. fluorine doped silicon oxide} (Frozen)	21/32056 {Deposition of conductive or semi-conductive organic layers (H01L 21/32058 takes precedence)}
21/31633 {Deposition of carbon doped silicon oxide, e.g. SiOC} (Frozen)	21/32058 {Deposition of superconductive layers}
21/31637 {Deposition of Tantalum oxides, e.g. Ta ₂ O ₅ } (Frozen)	21/321 After treatment
21/31641 {Deposition of Zirconium oxides, e.g. ZrO ₂ } (Frozen)	21/32105 {Oxidation of silicon-containing layers}
21/31645 {Deposition of Hafnium oxides, e.g. HfO ₂ } (Frozen)	21/3211 {Nitridation of silicon-containing layers}
21/3165 {formed by oxidation (H01L 21/31691, H01L 21/31695 take precedence)}	21/32115 {Planarisation}
21/31654 {of semiconductor materials, e.g. the body itself} (Frozen)	21/3212 {by chemical mechanical polishing [CMP]}
21/31658 {by thermal oxidation, e.g. of SiGe} (Frozen)	21/32125 {by simultaneously passing an electrical current, i.e. electrochemical mechanical polishing, e.g. ECMP}
21/31662 {of silicon in uncombined form} (Frozen)	21/3213 Physical or chemical etching of the layers, e.g. to produce a patterned layer from a pre-deposited extensive layer
21/31666 {of AIII BV compounds} (Frozen)	21/32131 {by physical means only}
21/3167 {of anodic oxidation} (Frozen)	21/32132 {of silicon-containing layers}
21/31675 {of silicon} (Frozen)	21/32133 {by chemical means only}
21/31679 {of AIII BV compounds} (Frozen)	21/32134 {by liquid etching only}
21/31683 {of metallic layers, e.g. Al deposited on the body, e.g. formation of multi-layer insulating structures} (Frozen)	21/32135 {by vapour etching only}
21/31687 {by anodic oxidation} (Frozen)	21/32136 {using plasmas}
21/31691 {with perovskite structure} (Frozen)	21/32137 {of silicon-containing layers}
21/31695 {Deposition of porous oxides or porous glassy oxides or oxide based porous glass} (Frozen)	21/32138 {pre- or post-treatments, e.g. anti-corrosion processes}
21/318 composed of nitrides (Frozen)	21/32139 {using masks}
<p>WARNING</p> <p>Group H01L 21/318 is no longer used for the classification of documents as of May 1, 2011. The content of this group is being reclassified into groups H01L 21/02107 – H01L 21/02326.</p> <p>Groups H01L 21/02107 – H01L 21/02326 should be considered in order to perform a complete search.</p>	
21/3185 {of siliconnitrides} (Frozen)	21/3215 Doping the layers
21/32 using masks	21/32155 {Doping polycrystalline - or amorphous silicon layers}
	21/322 to modify their internal properties, e.g. to produce internal imperfections
	21/3221 {of silicon bodies, e.g. for gettering}
	21/3223 {using cavities formed by hydrogen or noble gas ion implantation}
	21/3225 {Thermally inducing defects using oxygen present in the silicon body for intrinsic gettering (H01L 21/3226 takes precedence)}
	NOTE
	Gettering using both extrinsic and intrinsic gettering techniques is classified in both H01L 21/3221 and H01L 21/3225
	21/3226 {of silicon on insulator}
	21/3228 {of AIII BV compounds, e.g. to make them semi-insulating}

- 21/324 Thermal treatment for modifying the properties of semiconductor bodies, e.g. annealing, sintering ([H01L 21/20](#) - [H01L 21/288](#) and [H01L 21/302](#) - [H01L 21/322](#) take precedence)
- 21/3242 {for the formation of PN junctions without addition of impurities ([H01L 21/22](#) takes precedence)}
- 21/3245 {of $A_{III}B_V$ compounds}
- 21/3247 {for altering the shape, e.g. smoothing the surface}
- WARNING**
- Group [H01L 21/3247](#) is incomplete pending reclassification of documents from group [H01L 21/324](#).
- Groups [H01L 21/324](#) and [H01L 21/3247](#) should be considered in order to perform a complete search.
- 21/326 Application of electric currents or fields, e.g. for electroforming ([H01L 21/20](#) - [H01L 21/288](#) and [H01L 21/302](#) - [H01L 21/324](#) take precedence)
- 21/34 . . . the devices having semiconductor bodies not provided for in groups {[H01L 21/0405](#), [H01L 21/0445](#)}, [H01L 21/06](#), [H01L 21/16](#) and [H01L 21/18](#) with or without impurities, e.g. doping materials
- 21/38 Diffusion of impurity materials, e.g. doping materials, electrode materials, into or out of a semiconductor body, or between semiconductor regions
- 21/383 using diffusion into or out of a solid from or into a gaseous phase
- 21/385 using diffusion into or out of a solid from or into a solid phase, e.g. a doped oxide layer
- 21/388 using diffusion into or out of a solid from or into a liquid phase, e.g. alloy diffusion processes
- 21/40 Alloying of impurity materials, e.g. doping materials, electrode materials, with a semiconductor body
- 21/42 Bombardment with radiation
- 21/423 with high-energy radiation
- 21/425 producing ion implantation
- 21/426 using masks
- 21/428 using electromagnetic radiation, e.g. laser radiation
- 21/44 Manufacture of electrodes on semiconductor bodies using processes or apparatus not provided for in groups [H01L 21/38](#) - [H01L 21/428](#)
- 21/441 Deposition of conductive or insulating materials for electrodes
- 21/443 from a gas or vapour, e.g. condensation
- 21/445 from a liquid, e.g. electrolytic deposition
- 21/447 involving the application of pressure, e.g. thermo-compression bonding
- 21/449 involving the application of mechanical vibrations, e.g. ultrasonic vibrations
- 21/46 Treatment of semiconductor bodies using processes or apparatus not provided for in groups [H01L 21/428](#) (manufacture of electrodes thereon [H01L 21/44](#))
- 21/461 to change their surface-physical characteristics or shape, e.g. etching, polishing, cutting
- 21/463 Mechanical treatment, e.g. grinding, ultrasonic treatment
- 21/465 Chemical or electrical treatment, e.g. electrolytic etching (to form insulating layers [H01L 21/469](#))
- 21/467 using masks
- 21/469 to form insulating layers thereon, e.g. for masking or by using photolithographic techniques (encapsulating layers [H01L 21/56](#)); After-treatment of these layers
- 21/47 Organic layers, e.g. photoresist ([H01L 21/475](#), [H01L 21/4757](#) take precedence)
- 21/471 Inorganic layers ([H01L 21/475](#), [H01L 21/4757](#) take precedence)
- 21/473 composed of oxides or glassy oxides or oxide based glass
- 21/475 using masks
- 21/4757 After-treatment
- 21/47573 {Etching the layer}
- 21/47576 {Doping the layer}
- 21/4763 Deposition of non-insulating, e.g. conductive -, resistive -, layers on insulating layers; After-treatment of these layers (manufacture of electrodes [H01L 21/28](#), {[H01L 21/44](#)})
- 21/47635 {After-treatment of these layers}
- 21/477 Thermal treatment for modifying the properties of semiconductor bodies, e.g. annealing, sintering ([H01L 21/38](#) - [H01L 21/449](#) and [H01L 21/461](#) - [H01L 21/475](#) take precedence)
- 21/479 Application of electric currents or fields, e.g. for electroforming ([H01L 21/38](#) - [H01L 21/449](#) and [H01L 21/461](#) - [H01L 21/475](#) take precedence)
- 21/48 . . . Manufacture or treatment of parts, e.g. containers, prior to assembly of the devices, using processes not provided for in a single one of the subgroups [H01L 21/06](#) - [H01L 21/326](#)
- NOTE**
- In this group, the expression "treatment" covers also the removal of leads from parts
- 21/4803 {Insulating or insulated parts, e.g. mountings, containers, diamond heatsinks ([H01L 21/4846](#) takes precedence; printed circuit boards [H05K 1/00](#))}
- 21/4807 {Ceramic parts}
- 21/481 {Insulating layers on insulating parts, with or without metallisation}
- 21/4814 {Conductive parts}
- 21/4817 {for containers, e.g. caps ([H01L 21/4871](#) takes precedence)}

21/4821	{Flat leads, e.g. lead frames with or without insulating supports}	21/54	Providing fillings in containers, e.g. gas fillings
21/4825	{Connection or disconnection of other leads to or from flat leads, e.g. wires, bumps, other flat leads}	21/56	Encapsulations, e.g. encapsulation layers, coatings
21/4828	{Etching (etching for cleaning without patterning H01L 21/4835)}	21/561	{Batch processing}
21/4832	{Etching a temporary substrate after encapsulation process to form leads}	21/563	{Encapsulation of active face of flip-chip device, e.g. underfilling or underencapsulation of flip-chip, encapsulation preform on chip or mounting substrate}
21/4835	{Cleaning, e.g. removing of solder}	21/565	{Moulds}
21/4839	{Assembly of a flat lead with an insulating support, e.g. for TAB}	21/566	{Release layers for moulds, e.g. release layers, layers against residue during moulding}
21/4842	{Mechanical treatment, e.g. punching, cutting, deforming, cold welding}	21/568	{Temporary substrate used as encapsulation process aid (H01L 21/4832 and H01L 21/566 take precedence)}
21/4846	{Leads on or in insulating or insulated substrates, e.g. metallisation (H01L 21/4821 takes precedence; metallisation of ceramics in general C04B 41/51 ; printed circuits H05K 3/00)}	2021/60	{Attaching or detaching leads or other conductive members, to be used for carrying current to or from the device in operation}
21/485	{Adaptation of interconnections, e.g. engineering charges, repair techniques}	2021/60007	{involving a soldering or an alloying process}
21/4853	{Connection or disconnection of other leads to or from a metallisation, e.g. pins, wires, bumps}	2021/60015	{using plate connectors, e.g. layer, film}
21/4857	{Multilayer substrates (multilayer metallisation on monolayer substrate H01L 21/4846)}	2021/60022	{using bump connectors, e.g. for flip chip mounting}
21/486	{Via connections through the substrate with or without pins}	2021/6003	{Apparatus therefor}
21/4864	{Cleaning, e.g. removing of solder}	2021/60037	{Right-up bonding}
21/4867	{Applying pastes or inks, e.g. screen printing (H01L 21/486 takes precedence)}	2021/60045	{Pre-treatment step of the bump connectors prior to bonding}
21/4871	{Bases, plates or heatsinks}	2021/60052	{Oxide removing step, e.g. flux, rosin}
21/4875	{Connection or disconnection of other leads to or from bases or plates}	2021/6006	{with temporary supporting member not part of an apparatus, e.g. removable coating, film or substrate}
21/4878	{Mechanical treatment, e.g. deforming}	2021/60067	{Aligning the bump connectors with the mounting substrate}
21/4882	{Assembly of heatsink parts}	2021/60075	{involving active alignment, i.e. by apparatus steering, e.g. using alignment marks, sensors}
21/4885	{Wire-like parts or pins (wire ball formation B23K 20/00 ; methods related to connecting semiconductor or other solid state bodies H01L 24/00)}	2021/60082	{involving passive alignment, e.g. using surface energy, chemical reactions, thermal equilibrium}
21/4889	{Connection or disconnection of other leads to or from wire-like parts, e.g. wires}	2021/6009	{involving guiding structures, e.g. structures that are left at least partly in the bonded product, spacers}
21/4892	{Cleaning}	2021/60097	{Applying energy, e.g. for the soldering or alloying process}
21/4896	{Mechanical treatment, e.g. cutting, bending}	2021/60105	{using electromagnetic radiation}
21/50	Assembly of semiconductor devices using processes or apparatus not provided for in a single one of the subgroups H01L 21/06 - H01L 21/326 , {e.g. sealing of a cap to a base of a container}	2021/60112	{Coherent radiation, i.e. laser beam}
NOTE Arrangements for connecting or disconnecting semiconductor or other solid state bodies, or methods related thereto, other than those arrangements or methods covered by the following subgroups, are covered by H01L 24/00			2021/6012	{Incoherent radiation, e.g. polychromatic heating lamp}
			2021/60127	{Induction heating, i.e. eddy currents}
			2021/60135	{using convection, e.g. reflow oven}
			2021/60142	{with a graded temperature profile}
			2021/6015	{using conduction, e.g. chuck heater, thermocompression}
			2021/60157	{with a graded temperature profile}
			2021/60165	{using an electron beam}
21/52	Mounting semiconductor bodies in containers	2021/60172	{using static pressure}

2021/6018	{Unidirectional static pressure}	21/67	Apparatus specially adapted for handling semiconductor or electric solid state devices during manufacture or treatment thereof; Apparatus specially adapted for handling wafers during manufacture or treatment of semiconductor or electric solid state devices or components {;
2021/60187	{Isostatic pressure, e.g. degassing using vacuum or pressurised liquid}			Apparatus not specifically provided for elsewhere (processes per se H01L 21/30 , H01L 21/46 , H01L 23/00 ; simple temporary support means, e.g. using adhesives, electric or magnetic means H01L 21/68 , H01L 21/302 ; apparatus for manufacturing arrangements for connecting or disconnecting semiconductor or solid-state bodies and for methods related thereto H01L 24/74 ;)}
2021/60195	{using dynamic pressure, e.g. ultrasonic or thermosonic bonding}			NOTE
2021/60202	{using a protective atmosphere, e.g. with forming or shielding gas}			In this subgroup the term substrate designates a semiconductor or electric solid state device or component, or a wafer
2021/6021	{using an autocatalytic reaction}			
2021/60217	{Detaching bump connectors, e.g. after testing}			
2021/60225	{Arrangement of bump connectors prior to mounting}			
2021/60232	{wherein the bump connectors are disposed only on the semiconductor chip}			
2021/6024	{wherein the bump connectors are disposed only on the mounting substrate}			
2021/60247	{wherein the bump connectors are disposed on both the semiconductor chip and the mounting substrate, e.g. bump to bump}	21/67005	{Apparatus not specifically provided for elsewhere (processes per se H01L 21/30 , H01L 21/46 , H01L 23/00 ; simple temporary support means, e.g. using adhesives, electric or magnetic means H01L 21/68 , H01L 21/302)}
2021/60255	{wherein the bump connectors are provided as prepeg, e.g. are provided in an insulating plate member}	21/67011	{Apparatus for manufacture or treatment (processes H01L 21/30 , H01L 21/46 ; for production or after-treatment of single crystals or homogeneous polycrystalline material C30B 35/00)}
2021/60262	{Lateral distribution of bump connectors prior to mounting}	21/67017	{Apparatus for fluid treatment (H01L 21/67126 , H01L 21/6715 take precedence)}
2021/6027	{Mounting on semiconductor conductive members}	21/67023	{for general liquid treatment, e.g. etching followed by cleaning}
2021/60277	{involving the use of conductive adhesives}	21/67028	{for cleaning followed by drying, rinsing, stripping, blasting or the like}
2021/60285	{involving the use of mechanical auxiliary parts without the use of an alloying of soldering process, e.g. pressure contacts}	21/67034	{for drying}
2021/60292	{involving the use of an electron or laser beam}	21/6704	{for wet cleaning or washing}
2021/603	{involving the application of pressure, e.g. thermo-compression bonding}	21/67046	{using mainly scrubbing means, e.g. brushes}
2021/607	{involving the application of mechanical vibrations, e.g. ultrasonic vibrations}	21/67051	{using mainly spraying means, e.g. nozzles}
21/62	the devices having no potential-jump barriers or surface barriers	21/67057	{with the semiconductor substrates being dipped in baths or vessels}
21/64	Manufacture or treatment of solid state devices other than semiconductor devices, or of parts thereof, not peculiar to a single device provided for in groups H01L 31/00 - H01L 51/00	21/67063	{for etching}
			21/67069	{for drying etching}
			21/67075	{for wet etching}
			21/6708	{using mainly spraying means, e.g. nozzles}
			21/67086	{with the semiconductor substrates being dipped in baths or vessels}
			21/67092	{Apparatus for mechanical treatment (or grinding or cutting, see the relevant groups in subclasses B24B or B28D)}
			21/67098	{Apparatus for thermal treatment}
			21/67103	{mainly by conduction}
			21/67109	{mainly by convection}
			21/67115	{mainly by radiation}
			21/67121	{Apparatus for making assemblies not otherwise provided for, e.g. package constructions}
			21/67126	{Apparatus for sealing, encapsulating, glassing, decapsulating or the like (processes H01L 23/02 , H01L 23/28)}

- 21/67132 {Apparatus for placing on an insulating substrate, e.g. tape}
- 21/67138 {Apparatus for wiring semiconductor or solid state device}
- 21/67144 {Apparatus for mounting on conductive members, e.g. leadframes or conductors on insulating substrates}
- 21/6715 {Apparatus for applying a liquid, a resin, an ink or the like ([H01L 21/67126 takes precedence](#))}
- 21/67155 {Apparatus for manufacturing or treating in a plurality of work-stations}
- 21/67161 {characterized by the layout of the process chambers}
- 21/67167 {surrounding a central transfer chamber}
- 21/67173 {in-line arrangement}
- 21/67178 {vertical arrangement}
- 21/67184 {characterized by the presence of more than one transfer chamber}
- 21/6719 {characterized by the construction of the processing chambers, e.g. modular processing chambers}
- 21/67196 {characterized by the construction of the transfer chamber}
- 21/67201 {characterized by the construction of the load-lock chamber}
- 21/67207 {comprising a chamber adapted to a particular process}
- 21/67213 {comprising at least one ion or electron beam chamber ([coating by ion implantation C23C](#); [ion or electron beam tubes H01J 37/00](#))}
- 21/67219 {comprising at least one polishing chamber ([polishing apparatuses B24B](#))}
- 21/67225 {comprising at least one lithography chamber ([lithographic apparatuses G03F 7/00](#))}
- 21/6723 {comprising at least one plating chamber ([electroless plating apparatuses C23C](#), [electroplating apparatuses C25D](#))}
- 21/67236 {the substrates being processed being not semiconductor wafers, e.g. leadframes or chips}
- 21/67242 . . . {Apparatus for monitoring, sorting or marking ([testing or measuring during manufacture H01L 22/00](#), [marks per se H01L 23/544](#); [testing individual semiconductor devices G01R 31/26](#))}
- 21/67248 {Temperature monitoring}
- 21/67253 {Process monitoring, e.g. flow or thickness monitoring}
- 21/67259 {Position monitoring, e.g. misposition detection or presence detection}
- 21/67265 {of substrates stored in a container, a magazine, a carrier, a boat or the like}
- 21/67271 {Sorting devices}
- 21/67276 {Production flow monitoring, e.g. for increasing throughput ([program-control systems per se G05B 19/00](#), [e.g. total factory control G05B 19/418](#))}
- 21/67282 {Marking devices}
- 21/67288 {Monitoring of warpage, curvature, damage, defects or the like}
- 21/67294 {using identification means, e.g. labels on substrates or labels on containers}
- 21/673 . . . using specially adapted carriers {or holders; [Fixing the workpieces on such carriers or holders \(holders for supporting a complete device in operation H01L 23/32\)](#)}
- 21/67303 . . . {Vertical boat type carrier whereby the substrates are horizontally supported, e.g. comprising rod-shaped elements}
- 21/67306 {characterized by a material, a roughness, a coating or the like}
- 21/67309 {characterized by the substrate support}
- 21/67313 . . . {Horizontal boat type carrier whereby the substrates are vertically supported, e.g. comprising rod-shaped elements}
- 21/67316 {characterized by a material, a roughness, a coating or the like}
- 21/6732 . . . {Vertical carrier comprising wall type elements whereby the substrates are horizontally supported, e.g. comprising sidewalls}
- 21/67323 {characterized by a material, a roughness, a coating or the like}
- 21/67326 . . . {Horizontal carrier comprising wall type elements whereby the substrates are vertically supported, e.g. comprising sidewalls}
- 21/6733 {characterized by a material, a roughness, a coating or the like}
- 21/67333 . . . {Trays for chips ([magazine for components H05K 13/0084](#))}
- 21/67336 {characterized by a material, a roughness, a coating or the like}
- 21/6734 . . . {specially adapted for supporting large square shaped substrates ([containers and packaging elements for glass sheets B65D 85/48](#), [transporting of glass products during their manufacture C03B 35/00](#))}
- 21/67343 {characterized by a material, a roughness, a coating or the like}
- 21/67346 . . . {characterized by being specially adapted for supporting a single substrate or by comprising a stack of such individual supports}
- 21/6735 . . . {Closed carriers}
- 21/67353 {specially adapted for a single substrate}
- 21/67356 {specially adapted for containing chips, dies or ICs}
- 21/67359 {specially adapted for containing masks, reticles or pellicles}
- 21/67363 {specially adapted for containing substrates other than wafers ([H01L 21/67356](#), [H01L 21/67359 take precedence](#))}
- 21/67366 {characterised by materials, roughness, coatings or the like ([materials relating to an injection moulding process B29C 45/00](#); [chemical composition of materials C08L 51/00](#))}
- 21/67369 {characterised by shock absorbing elements, e.g. retainers or cushions}
- 21/67373 {characterised by locking systems}
- 21/67376 {characterised by sealing arrangements}
- 21/67379 {characterised by coupling elements, kinematic members, handles or elements to be externally gripped}

- 21/67383 {characterised by substrate supports}
 - 21/67386 {characterised by the construction of the closed carrier}
 - 21/67389 {characterised by atmosphere control}
 - 21/67393 {characterised by the presence of atmosphere modifying elements inside or attached to the closed carrier}
 - 21/67396 {characterised by the presence of antistatic elements}
 - 21/677 . . . for conveying, e.g. between different workstations
 - 21/67703 . . . {between different workstations}
 - 21/67706 {Mechanical details, e.g. roller, belt ([H01L 21/67709 takes precedence](#))}
 - 21/67709 {using magnetic elements}
 - 21/67712 {the substrate being handled substantially vertically}
 - 21/67715 {Changing the direction of the conveying path}
 - 21/67718 {Changing orientation of the substrate, e.g. from a horizontal position to a vertical position}
 - 21/67721 {the substrates to be conveyed not being semiconductor wafers or large planar substrates, e.g. chips, lead frames ([H01L 21/6773 takes precedence](#))}
 - 21/67724 {by means of a cart or a vehicle}
 - 21/67727 {using a general scheme of a conveying path within a factory}
 - 21/6773 {Conveying cassettes, containers or carriers}
 - 21/67733 {Overhead conveying}
 - 21/67736 {Loading to or unloading from a conveyor}
 - 21/67739 . . . {into and out of processing chamber}
 - 21/67742 {Mechanical parts of transfer devices ([robots in general in B25J](#))}
 - 21/67745 {characterized by movements or sequence of movements of transfer devices}
 - 21/67748 {horizontal transfer of a single workpiece}
 - 21/67751 {vertical transfer of a single workpiece}
 - 21/67754 {horizontal transfer of a batch of workpieces}
 - 21/67757 {vertical transfer of a batch of workpieces}
 - 21/6776 {Continuous loading and unloading into and out of a processing chamber, e.g. transporting belts within processing chambers}
 - 21/67763 . . . {the wafers being stored in a carrier, involving loading and unloading ([H01L 21/6779 takes precedence](#))}
 - 21/67766 {Mechanical parts of transfer devices ([robots in general in B25J](#))}
 - 21/67769 {Storage means}
 - 21/67772 {involving removal of lid, door, cover}
 - 21/67775 {Docking arrangements}
 - 21/67778 {involving loading and unloading of wafers}
 - 21/67781 {Batch transfer of wafers}
 - 21/67784 . . . {using air tracks}
 - 21/67787 {with angular orientation of the workpieces}
 - 21/6779 {the workpieces being stored in a carrier, involving loading and unloading}
 - 21/67793 . . . {with orientating and positioning by means of a vibratory bowl or track}
 - 21/67796 . . . {with angular orientation of workpieces ([H01L 21/67787](#) and [H01L 21/67793 take precedence](#))}
 - 21/68 . . . for positioning, orientation or alignment
 - 21/681 . . . {using optical controlling means}
 - 21/682 . . . {Mask-wafer alignment ([in general G03F 7/70, G03F 9/70](#))}
 - 21/683 . . . for supporting or gripping ([for conveying H01L 21/677, for positioning, orientation or alignment H01L 21/68](#))
 - 21/6831 . . . {using electrostatic chucks}
 - 21/6833 {Details of electrostatic chucks}
 - 21/6835 . . . {using temporarily an auxiliary support}
- NOTE**
- [H01L 21/6835](#), details of the apparatus are to be further indexed using the indexing codes chosen from [H01L 2221/68304](#) and subgroups
- 21/6836 {Wafer tapes, e.g. grinding or dicing support tapes ([adhesive tapes in general C09J 7/20](#))}
 - 21/6838 . . . {with gripping and holding devices using a vacuum; Bernoulli devices}
 - 21/687 . . . using mechanical means, e.g. chucks, clamps or pinches ([using electrostatic chucks H01L 21/6831](#))}
 - 21/68707 {the wafers being placed on a robot blade, or gripped by a gripper for conveyance}
 - 21/68714 {the wafers being placed on a susceptor, stage or support}
 - 21/68721 {characterised by edge clamping, e.g. clamping ring}
 - 21/68728 {characterised by a plurality of separate clamping members, e.g. clamping fingers}
 - 21/68735 {characterised by edge profile or support profile}
 - 21/68742 {characterised by a lifting arrangement, e.g. lift pins}
 - 21/6875 {characterised by a plurality of individual support members, e.g. support posts or protrusions}
 - 21/68757 {characterised by a coating or a hardness or a material}
 - 21/68764 {characterised by a movable susceptor, stage or support, others than those only rotating on their own vertical axis, e.g. susceptors on a rotating carousel}
 - 21/68771 {characterised by supporting more than one semiconductor substrate}
 - 21/68778 {characterised by supporting substrates others than wafers, e.g. chips}
 - 21/68785 {characterised by the mechanical construction of the susceptor, stage or support}
 - 21/68792 {characterised by the construction of the shaft}

- 21/70 Manufacture or treatment of devices consisting of a plurality of solid state components formed in or on a common substrate or of parts thereof; Manufacture of integrated circuit devices or of parts thereof ([{multistep manufacturing processes of assemblies consisting of a plurality of individual semiconductor or other solid state devices H01L 25/00; }](#) manufacture of assemblies consisting of preformed electrical components [H05K 3/00](#), [H05K 13/00](#))
- 21/702 {of thick-or thin-film circuits or parts thereof}
- 21/705 {of thick-film circuits or parts thereof}
- 21/707 {of thin-film circuits or parts thereof}
- 21/71 Manufacture of specific parts of devices defined in group [H01L 21/70](#) ([{H01L 21/0405, H01L 21/0445}](#) , [H01L 21/28](#), [H01L 21/44](#), [H01L 21/48](#) take precedence)
- 21/74 Making of {localized} buried regions, e.g. buried collector layers, internal connections {substrate contacts}
- 21/743 {Making of internal connections, substrate contacts}
- 21/746 {for AIII-BV integrated circuits}
- 21/76 Making of isolation regions between components
- 21/7602 {between components manufactured in an active substrate comprising SiC compounds}
- 21/7605 {between components manufactured in an active substrate comprising AIII BV compounds}
- 21/7607 {between components manufactured in an active substrate comprising A_{II}BV_I compounds}
- 21/761 PN junctions
- 21/762 Dielectric regions {, e.g. EPIC dielectric isolation, LOCOS; Trench refilling techniques, SOI technology, use of channel stoppers}
- 21/76202 {using a local oxidation of silicon, e.g. LOCOS, SWAMI, SILO ([H01L 21/76235](#) takes precedence; together with vertical isolation, e.g. LOCOS in a SOI substrate, [H01L 21/76264](#))}
- 21/76205 {in a region being recessed from the surface, e.g. in a recess, groove, tub or trench region}
- 21/76208 {using auxiliary pillars in the recessed region, e.g. to form LOCOS over extended areas}
- 21/7621 {the recessed region having a shape other than rectangular, e.g. rounded or oblique shape ([H01L 21/76208](#) takes precedence)}
- 21/76213 {introducing electrical inactive or active impurities in the local oxidation region, e.g. to alter LOCOS oxide growth characteristics or for additional isolation purpose}
- 21/76216 {introducing electrical active impurities in the local oxidation region for the sole purpose of creating channel stoppers}
- 21/76218 {introducing both types of electrical active impurities in the local oxidation region for the sole purpose of creating channel stoppers, e.g. for isolation of complementary doped regions}
- 21/76221 {with a plurality of successive local oxidation steps}
- 21/76224 {using trench refilling with dielectric materials ([trench filling with polycrystalline silicon H01L 21/763; together with vertical isolation, e.g. trench refilling in a SOI substrate H01L 21/76264](#))}
- 21/76227 {the dielectric materials being obtained by full chemical transformation of non-dielectric materials, such as polycrystalline silicon, metals}
- 21/76229 {Concurrent filling of a plurality of trenches having a different trench shape or dimension, e.g. rectangular and V-shaped trenches, wide and narrow trenches, shallow and deep trenches}
- 21/76232 {of trenches having a shape other than rectangular or V-shape, e.g. rounded corners, oblique or rounded trench walls ([H01L 21/76229](#) takes precedence)}
- 21/76235 {trench shape altered by a local oxidation of silicon process step, e.g. trench corner rounding by LOCOS}
- 21/76237 {introducing impurities in trench side or bottom walls, e.g. for forming channel stoppers or alter isolation behavior}
- 21/7624 {using semiconductor on insulator [SOI] technology ([H01L 21/76297](#) takes precedence; manufacture of integrated circuits on insulating substrates [H01L 21/84](#); silicon on sapphire [SOS] technology [H01L 21/86](#))}
- 21/76243 {using silicon implanted buried insulating layers, e.g. oxide layers, i.e. SIMOX techniques}
- 21/76245 {using full isolation by porous oxide silicon, i.e. FIPOS techniques}
- 21/76248 {using lateral overgrowth techniques, i.e. ELO techniques}
- 21/76251 {using bonding techniques}
- 21/76254 {with separation/delamination along an ion implanted layer, e.g. Smart-cut, Unibond}
- 21/76256 {using silicon etch back techniques, e.g. BESOI, ELTRAN}
- 21/76259 {with separation/delamination along a porous layer}
- 21/76262 {using selective deposition of single crystal silicon, i.e. SEG techniques}
- 21/76264 {SOI together with lateral isolation, e.g. using local oxidation of silicon, or dielectric or polycrystalline material refilled trench or air gap isolation regions, e.g. completely isolated semiconductor islands}

21/76267	{ Vertical isolation by silicon implanted buried insulating layers, e.g. oxide layers, i.e. SIMOX techniques }	21/76814	{ post-treatment or after-treatment, e.g. cleaning or removal of oxides on underlying conductors }
21/7627	{ Vertical isolation by full isolation by porous oxide silicon, i.e. FIPOS techniques }	21/76816	{ Aspects relating to the layout of the pattern or to the size of vias or trenches (layout of the interconnections per se H01L 23/528 ; CAD of ICs G06F 30/00) }
21/76272	{ Vertical isolation by lateral overgrowth techniques, i.e. ELO techniques }	21/76817	{ using printing or stamping techniques }
21/76275	{ Vertical isolation by bonding techniques }	21/76819	{ Smoothing of the dielectric (planarisation of insulating materials per se H01L 21/31051) }
21/76278	{ Vertical isolation by selective deposition of single crystal silicon, i.e. SEG techniques }	21/7682	{ the dielectric comprising air gaps }
21/76281	{ Lateral isolation by selective oxidation of silicon }	21/76822	{ Modification of the material of dielectric layers, e.g. grading, after-treatment to improve the stability of the layers, to increase their density etc. }
21/76283	{ Lateral isolation by refilling of trenches with dielectric material }	21/76823	{ transforming an insulating layer into a conductive layer }
21/76286	{ Lateral isolation by refilling of trenches with polycrystalline material }	21/76825	{ by exposing the layer to particle radiation, e.g. ion implantation, irradiation with UV light or electrons etc. (plasma treatment H01L 21/76826) }
21/76289	{ Lateral isolation by air gap }	21/76826	{ by contacting the layer with gases, liquids or plasmas }
21/76291	{ Lateral isolation by field effect }	21/76828	{ thermal treatment }
21/76294	{ using selective deposition of single crystal silicon, i.e. SEG techniques }	21/76829	{ characterised by the formation of thin functional dielectric layers, e.g. dielectric etch-stop, barrier, capping or liner layers }
21/76297	{ Dielectric isolation using EPIC techniques, i.e. epitaxial passivated integrated circuit }	21/76831	{ in via holes or trenches, e.g. non-conductive sidewall liners }
21/763	Polycrystalline semiconductor regions { (H01L 21/76264 takes precedence) }	21/76832	{ Multiple layers }
21/764	Air gaps { (H01L 21/76264 takes precedence) }	21/76834	{ formation of thin insulating films on the sidewalls or on top of conductors (H01L 21/76831 takes precedence) }
21/765	by field effect { (H01L 21/76264 takes precedence) }	21/76835	{ Combinations of two or more different dielectric layers having a low dielectric constant (H01L 21/76832 takes precedence) }
21/768	Applying interconnections to be used for carrying current between separate components within a device { comprising conductors and dielectrics }	21/76837	{ Filling up the space between adjacent conductive structures; Gap-filling properties of dielectrics }
NOTE			21/76838	{ characterised by the formation and the after-treatment of the conductors (etching for patterning the conductors H01L 21/3213) }
Groups			NOTE		
H01L 21/768 - H01L 21/76898 cover multi-step processes for manufacturing interconnections. Information peculiar to single-step processes should also be classified in the corresponding group, e.g.			When the interconnect is also used as the conductor part of a conductor insulator semiconductor electrode (gate level interconnections), documents are classified in the relevant electrode manufacture groups, e.g. H01L 21/28026		
• cleaning H01L 21/02041					
• etching H01L 21/311 , H01L 21/3213					
• masking H01L 21/027 , H01L 21/033 , H01L 21/31144 , H01L 21/32139					
• planarizing H01L 21/3105 , H01L 21/321					
21/76801	{ characterised by the formation and the after-treatment of the dielectrics, e.g. smoothing }	21/7684	{ Smoothing; Planarisation }
21/76802	{ by forming openings in dielectrics }	21/76841	{ Barrier, adhesion or liner layers }
21/76804	{ by forming tapered via holes }	21/76843	{ formed in openings in a dielectric }
21/76805	{ the opening being a via or contact hole penetrating the underlying conductor }	21/76844	{ Bottomless liners }
21/76807	{ for dual damascene structures }	21/76846	{ Layer combinations }
21/76808	{ involving intermediate temporary filling with material }	21/76847	{ the layer being positioned within the main fill metal }
21/7681	{ involving one or more buried masks }	21/76849	{ the layer being positioned on top of the main fill metal }
21/76811	{ involving multiple stacked pre-patterned masks }			
21/76813	{ involving a partial via etch }			

21/7685	{the layer covering a conductive structure (H01L 21/76849 takes precedence)}	21/76888	{By rendering at least a portion of the conductor non conductive, e.g. oxidation}
21/76852	{the layer also covering the sidewalls of the conductive structure}	21/76889	{by forming silicides of refractory metals}
21/76853	{characterized by particular after-treatment steps}	21/76891	{by using superconducting materials}
21/76855	{After-treatment introducing at least one additional element into the layer}	21/76892	{modifying the pattern}
21/76856	{by treatment in plasmas or gaseous environments, e.g. nitriding a refractory metal liner}	21/76894	{using a laser, e.g. laser cutting, laser direct writing, laser repair}
21/76858	{by diffusing alloying elements}	21/76895	{Local interconnects; Local pads, as exemplified by patent document EP0896365}
21/76859	{by ion implantation}	21/76897	{Formation of self-aligned vias or contact plugs, i.e. involving a lithographically uncritical step (self-aligned silicidation on field effect transistors H01L 29/665)}
21/76861	{Post-treatment or after-treatment not introducing additional chemical elements into the layer}	21/76898	{formed through a semiconductor substrate}
21/76862	{Bombardment with particles, e.g. treatment in noble gas plasmas; UV irradiation}	21/77	Manufacture or treatment of devices consisting of a plurality of solid state components or integrated circuits formed in, or on, a common substrate (electrically programmable read-only memories or multistep manufacturing processes therefor H01L 27/115)
21/76864	{Thermal treatment}	NOTE		
21/76865	{Selective removal of parts of the layer (H01L 21/76844 takes precedence)}	Integration processes for the manufacture of devices of the type classified in H01L 27/14 - H01L 27/32 are not classified in this group and its sub-groups. Instead, as they are peculiar to said devices, they are classified together with the devices Multistep processes for manufacturing memory structures in general using field effect technology are covered by H01L 27/1052 ; Multistep processes for manufacturing dynamic random access memory structures are covered by H01L 27/10844 ; Multistep processes for manufacturing static random access memory structures are covered by H01L 27/11 ; Multistep processes for manufacturing read-only memory structures are covered by H01L 27/112 ; Multistep processes for manufacturing electrically programmable read-only memory structures are covered by H01L 27/115		
21/76867	{characterized by methods of formation other than PVD, CVD or deposition from a liquids (PVD H01L 21/2855 ; CVD H01L 21/28556 ; deposition from liquids H01L 21/288)}			
21/76868	{Forming or treating discontinuous thin films, e.g. repair, enhancement or reinforcement of discontinuous thin films}			
21/7687	{Thin films associated with contacts of capacitors}			
21/76871	{Layers specifically deposited to enhance or enable the nucleation of further layers, i.e. seed layers}			
21/76873	{for electroplating}			
21/76874	{for electroless plating}			
21/76876	{for deposition from the gas phase, e.g. CVD}			
21/76877	{Filling of holes, grooves or trenches, e.g. vias, with conductive material}			
21/76879	{by selective deposition of conductive material in the vias, e.g. selective C.V.D. on semiconductor material, plating (plating on semiconductors in general H01L 21/288)}	2021/775	{comprising a plurality of TFTs on a non-semiconducting substrate, e.g. driving circuits for AMLCDs}
21/7688	{by deposition over sacrificial masking layer, e.g. lift-off (lift-off per se H01L 21/0272)}	21/78	with subsequent division of the substrate into plural individual devices (cutting to change the surface-physical characteristics or shape of semiconductor bodies H01L 21/304)
21/76882	{Reflowing or applying of pressure to better fill the contact hole}	21/7806	{involving the separation of the active layers from a substrate}
21/76883	{Post-treatment or after-treatment of the conductive material}	21/7813	{leaving a reusable substrate, e.g. epitaxial lift off}
21/76885	{By forming conductive members before deposition of protective insulating material, e.g. pillars, studs}	21/782	to produce devices, each consisting of a single circuit element (H01L 21/82 takes precedence)
21/76886	{Modifying permanently or temporarily the pattern or the conductivity of conductive members, e.g. formation of alloys, reduction of contact resistances}	21/784	the substrate being a semiconductor body
			21/786	the substrate being other than a semiconductor body, e.g. insulating body
			21/82	to produce devices, e.g. integrated circuits, each consisting of a plurality of components

21/8206	{the substrate being a semiconductor, using diamond technology (H01L 21/8258 takes precedence)}	21/823462	{with a particular manufacturing method of the gate insulating layers, e.g. different gate insulating layer thicknesses, particular gate insulator materials or particular gate insulator implants}
21/8213	{the substrate being a semiconductor, using SiC technology (H01L 21/8258 takes precedence)}	21/823468	{with a particular manufacturing method of the gate sidewall spacers, e.g. double spacers, particular spacer material or shape}
21/822	the substrate being a semiconductor, using silicon technology (H01L 21/8258 takes precedence)	21/823475	{interconnection or wiring or contact manufacturing related aspects}
21/8221	{Three dimensional integrated circuits stacked in different levels}	21/823481	{isolation region manufacturing related aspects, e.g. to avoid interaction of isolation region with adjacent structure}
21/8222	Bipolar technology	21/823487	{with a particular manufacturing method of vertical transistor structures, i.e. with channel vertical to the substrate surface (with a current flow parallel to the substrate surface H01L 21/823431)}
21/8224	comprising a combination of vertical and lateral transistors	21/823493	{with a particular manufacturing method of the wells or tubs, e.g. twin tubs, high energy well implants, buried implanted layers for lateral isolation [BILLI]}
21/8226	comprising merged transistor logic or integrated injection logic	21/8236	Combination of enhancement and depletion transistors
21/8228	Complementary devices, e.g. complementary transistors	21/8238	Complementary field-effect transistors, e.g. CMOS
21/82285	{Complementary vertical transistors}	21/823807	{with a particular manufacturing method of the channel structures, e.g. channel implants, halo or pocket implants, or channel materials}
21/8229	Memory structures	21/823814	{with a particular manufacturing method of the source or drain structures, e.g. specific source or drain implants or silicided source or drain structures or raised source or drain structures}
21/8232	Field-effect technology	21/823425	{manufacturing common source or drain regions between a plurality of conductor-insulator-semiconductor structures}
21/8234	MIS technology {, i.e. integration processes of field effect transistors of the conductor-insulator-semiconductor type}	21/823431	{with a particular manufacturing method of transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}
21/823406	{Combination of charge coupled devices, i.e. CCD, or BBD}	21/823437	{with a particular manufacturing method of the gate conductors, e.g. particular materials, shapes}
21/823412	{with a particular manufacturing method of the channel structures, e.g. channel implants, halo or pocket implants, or channel materials}	21/823443	{silicided or salicided gate conductors}
21/823418	{with a particular manufacturing method of the source or drain structures, e.g. specific source or drain implants or silicided source or drain structures or raised source or drain structures}	21/82345	{gate conductors with different gate conductor materials or different gate conductor implants, e.g. dual gate structures}
21/823425	{manufacturing common source or drain regions between a plurality of conductor-insulator-semiconductor structures}	21/823456	{gate conductors with different shapes, lengths or dimensions}
21/823431	{with a particular manufacturing method of transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}		
21/823437	{with a particular manufacturing method of the gate conductors, e.g. particular materials, shapes}		
21/823443	{silicided or salicided gate conductors}		
21/82345	{gate conductors with different gate conductor materials or different gate conductor implants, e.g. dual gate structures}		
21/823456	{gate conductors with different shapes, lengths or dimensions}		
		21/823828	{with a particular manufacturing method of the gate conductors, e.g. particular materials, shapes}
		21/823835	{silicided or salicided gate conductors}
		21/823842	{gate conductors with different gate conductor materials or different gate conductor implants, e.g. dual gate structures}
		21/82385	{gate conductors with different shapes, lengths or dimensions}

21/823857	{with a particular manufacturing method of the gate insulating layers, e.g. different gate insulating layer thicknesses, particular gate insulator materials or particular gate insulator implants}	22/10	. {Measuring as part of the manufacturing process (burn-in G01R 31/2855)}
21/823864	{with a particular manufacturing method of the gate sidewall spacers, e.g. double spacers, particular spacer material or shape}	22/12	. . {for structural parameters, e.g. thickness, line width, refractive index, temperature, warp, bond strength, defects, optical inspection, electrical measurement of structural dimensions, metallurgic measurement of diffusions (electrical measurement of diffusions H01L 22/14)}
21/823871	{interconnection or wiring or contact manufacturing related aspects}	22/14	. . {for electrical parameters, e.g. resistance, deep-levels, CV, diffusions by electrical means}
21/823878	{isolation region manufacturing related aspects, e.g. to avoid interaction of isolation region with adjacent structure}	22/20	. {Sequence of activities consisting of a plurality of measurements, corrections, marking or sorting steps}
21/823885	{with a particular manufacturing method of vertical transistor structures, i.e. with channel vertical to the substrate surface (with a current flow parallel to the substrate surface H01L 21/823821)}	22/22	. . {Connection or disconnection of sub-entities or redundant parts of a device in response to a measurement (testing and repair of stores after manufacture including at wafer scale G11C 29/00 ; fuses per se H01L 23/525)}
21/823892	{with a particular manufacturing method of the wells or tubs, e.g. twin tubs, high energy well implants, buried implanted layers for lateral isolation [BILLI]}	22/24	. . {Optical enhancement of defects or not directly visible states, e.g. selective electrolytic deposition, bubbles in liquids, light emission, colour change (voltage contrast G01R 31/311)}
21/8239	Memory structures	22/26	. . {Acting in response to an ongoing measurement without interruption of processing, e.g. endpoint detection, in-situ thickness measurement (endpoint detection arrangements in CMP apparatus B24B 37/013 , in discharge apparatus H01J 37/32)}
21/8248	Combination of bipolar and field-effect technology	22/30	. {Structural arrangements specially adapted for testing or measuring during manufacture or treatment, or specially adapted for reliability measurements}
21/8249	Bipolar and MOS technology	22/32	. . {Additional lead-in metallisation on a device or substrate, e.g. additional pads or pad portions, lines in the scribe line, sacrificed conductors (arrangements for conducting electric current to or from the solid state body in operation H01L 23/48)}
21/8252	the substrate being a semiconductor, using III-V technology (H01L 21/8258 takes precedence)	22/34	. . {Circuits for electrically characterising or monitoring manufacturing processes, e. g. whole test die, wafers filled with test structures, on-board-devices incorporated on each die, process control monitors or pad structures thereof, devices in scribe line (switching, multiplexing, gating devices G01R 19/25 ; process control with lithography, e.g. dose control, G03F 7/20 ; structures for alignment control by optical means G03F 7/0633)}
21/8254	the substrate being a semiconductor, using II-VI technology (H01L 21/8258 takes precedence)		
21/8256	the substrate being a semiconductor, using technologies not covered by one of groups { H01L 21/8206 , H01L 21/8213 }, H01L 21/822 , H01L 21/8252 and H01L 21/8254 (H01L 21/8258 takes precedence)		
21/8258	the substrate being a semiconductor, using a combination of technologies covered by { H01L 21/8206 , H01L 21/8213 }, H01L 21/822 , H01L 21/8252 , H01L 21/8254 or H01L 21/8256	23/00	Details of semiconductor or other solid state devices (H01L 25/00 takes precedence ; structural arrangements for testing or measuring during manufacture or treatment, or for reliability measurements H01L 22/00; arrangements for connecting or disconnecting semiconductor or solid-state bodies, or methods related thereto H01L 24/00; finger print sensors G06K 9/00006)
21/84	the substrate being other than a semiconductor body, e.g. being an insulating body		NOTE
21/845	{including field-effect transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}		This group does not cover :
21/86	the insulating body being sapphire, e.g. silicon on sapphire structure, i.e. SOS		<ul style="list-style-type: none"> • details of semiconductor bodies or of electrodes of devices provided for in group H01L 29/00, which details are covered by that group; • details peculiar to devices provided for in a single main group of groups
22/00	{Testing or measuring during manufacture or treatment; Reliability measurements, i.e. testing of parts without further processing to modify the parts as such; Structural arrangements therefor}		

H01L

H01L 23/00
(continued)

[H01L 31/00](#) - [H01L 51/00](#), which details are covered by those groups.

- 23/02 . Containers; Seals ([H01L 23/12](#), [H01L 23/34](#), [H01L 23/48](#), [H01L 23/552](#), {[H01L 23/66](#)} take precedence; {for memories [G11C](#)})
- 23/04 . . characterised by the shape {of the container or parts, e.g. caps, walls}
- 23/041 . . . {the container being a hollow construction having no base used as a mounting for the semiconductor body}
- 23/043 . . . the container being a hollow construction and having a conductive base as a mounting as well as a lead for the semiconductor body
- 23/045 the other leads having an insulating passage through the base
- 23/047 the other leads being parallel to the base
- 23/049 the other leads being perpendicular to the base
- 23/051 another lead being formed by a cover plate parallel to the base plate, e.g. sandwich type
- 23/053 . . . the container being a hollow construction and having an insulating {or insulated} base as a mounting for the semiconductor body
- 23/055 the leads having a passage through the base {([H01L 23/057](#) takes precedence)}
- 23/057 the leads being parallel to the base
- 23/06 . . characterised by the material of the container or its electrical properties
- 23/08 . . . the material being an electrical insulator, e.g. glass
- 23/10 . . characterised by the material or arrangement of seals between parts, e.g. between cap and base of the container or between leads and walls of the container
- 23/12 . Mountings, e.g. non-detachable insulating substrates
- 23/13 . . characterised by the shape
- 23/14 . . characterised by the material or its electrical properties {([printed circuit boards H05K 1/00](#))}
- 23/142 . . . {Metallic substrates having insulating layers}
- 23/145 . . . {Organic substrates, e.g. plastic}
- 23/147 . . . {Semiconductor insulating substrates (semiconductor conductive substrates [H01L 23/4926](#))}
- 23/15 . . . Ceramic or glass substrates {([H01L 23/142](#), [H01L 23/145](#), [H01L 23/147](#) take precedence)}
- 23/16 . Fillings or auxiliary members in containers {or encapsulations}, e.g. centering rings ([H01L 23/42](#), [H01L 23/552](#) take precedence)
- 23/18 . . Fillings characterised by the material, its physical or chemical properties, or its arrangement within the complete device

NOTE

Group [H01L 23/26](#) takes precedence over groups [H01L 23/20](#) - [H01L 23/24](#)

- 23/20 . . . gaseous at the normal operating temperature of the device
- 23/22 . . . liquid at the normal operating temperature of the device
- 23/24 . . . solid or gel at the normal operating temperature of the device {([H01L 23/3135](#) takes precedence)}

- 23/26 . . . including materials for absorbing or reacting with moisture or other undesired substances {, e.g. getters}
- 23/28 . Encapsulations, e.g. encapsulating layers, coatings, {e.g. for protection} ([H01L 23/552](#) takes precedence; {insulating layers for contacts or interconnections [H01L 23/5329](#)})
- 23/29 . . characterised by the material {, e.g. carbon (interlayer dielectrics [H01L 23/5329](#))}
- 23/291 . . . {Oxides or nitrides or carbides, e.g. ceramics, glass}
- 23/293 . . . {Organic, e.g. plastic}
- 23/295 {containing a filler ([H01L 23/296](#) takes precedence)}
- 23/296 {Organo-silicon compounds}
- 23/298 . . . {Semiconductor material, e.g. amorphous silicon}
- 23/31 . . characterised by the arrangement {or shape}
- 23/3107 . . . {the device being completely enclosed}
- 23/3114 {the device being a chip scale package, e.g. CSP}
- 23/3121 {a substrate forming part of the encapsulation}
- 23/3128 {the substrate having spherical bumps for external connection}
- 23/3135 {Double encapsulation or coating and encapsulation}
- 23/3142 {Sealing arrangements between parts, e.g. adhesion promoters}
- 23/315 {the encapsulation having a cavity}
- 23/3157 . . . {Partial encapsulation or coating (mask layer used as insulation layer [H01L 21/31](#))}
- 23/3164 {the coating being a foil}
- 23/3171 {the coating being directly applied to the semiconductor body, e.g. passivation layer ([H01L 23/3178](#) takes precedence)}
- 23/3178 {Coating or filling in grooves made in the semiconductor body}
- 23/3185 {the coating covering also the sidewalls of the semiconductor body}
- 23/3192 {Multilayer coating}
- 23/32 . Holders for supporting the complete device in operation, i.e. detachable fixtures ([H01L 23/40](#) takes precedence)
- 23/34 . Arrangements for cooling, heating, ventilating or temperature compensation {; Temperature sensing arrangements (thermal treatment apparatus [H01L 21/00](#))}
- 23/345 . . {Arrangements for heating (thermal treatment apparatus [H01L 21/00](#))}
- 23/36 . . Selection of materials, or shaping, to facilitate cooling or heating, e.g. heatsinks {([H01L 23/28](#), [H01L 23/40](#), [H01L 23/42](#), [H01L 23/44](#), [H01L 23/46](#) take precedence; heating [H01L 23/345](#))}
- 23/367 . . . Cooling facilitated by shape of device {([H01L 23/38](#), [H01L 23/40](#), [H01L 23/42](#), [H01L 23/44](#), [H01L 23/46](#) take precedence)}
- 23/3672 {Foil-like cooling fins or heat sinks (being part of lead-frames [H01L 23/49568](#))}
- 23/3675 {characterised by the shape of the housing}
- 23/3677 {Wire-like or pin-like cooling fins or heat sinks}

- 23/373 . . . Cooling facilitated by selection of materials for the device {or materials for thermal expansion adaptation, e.g. carbon}
- 23/3731 {Ceramic materials or glass ([H01L 23/3732](#), [H01L 23/3733](#), [H01L 23/3735](#), [H01L 23/3737](#), [H01L 23/3738](#) take precedence)}
- 23/3732 {Diamonds}
- 23/3733 {having a heterogeneous or anisotropic structure, e.g. powder or fibres in a matrix, wire mesh, porous structures ([H01L 23/3732](#), [H01L 23/3737](#) take precedence)}
- 23/3735 {Laminates or multilayers, e.g. direct bond copper ceramic substrates}
- 23/3736 {Metallic materials ([H01L 23/3732](#), [H01L 23/3733](#), [H01L 23/3735](#), [H01L 23/3737](#), [H01L 23/3738](#) take precedence)}
- 23/3737 {Organic materials with or without a thermoconductive filler}
- 23/3738 {Semiconductor materials}
- 23/38 . . Cooling arrangements using the Peltier effect
- 23/40 . . Mountings or securing means for detachable cooling or heating arrangements {(heating [H01L 23/345](#)); fixed by friction, plugs or springs}
- 23/4006 . . . {with bolts or screws}
- 23/4012 {for stacked arrangements of a plurality of semiconductor devices ([assemblies per se](#) [H01L 25/00](#))}
- 2023/4018 {characterised by the type of device to be heated or cooled}
- 2023/4025 {Base discrete devices, e.g. presspack, disc-type transistors}
- 2023/4031 {Packaged discrete devices, e.g. to-3 housings, diodes}
- 2023/4037 {characterised by thermal path or place of attachment of heatsink}
- 2023/4043 {heatsink to have chip}
- 2023/405 {heatsink to package}
- 2023/4056 {heatsink to additional heatsink}
- 2023/4062 {heatsink to or through board or cabinet}
- 2023/4068 {Heatconductors between device and heatsink, e.g. compliant heat-spreaders, heat-conducting bands}
- 2023/4075 {Mechanical elements}
- 2023/4081 {Compliant clamping elements not primarily serving heat-conduction}
- 2023/4087 {Mounting accessories, interposers, clamping or screwing parts}
- 23/4093 . . . {Snap-on arrangements, e.g. clips}
- 23/42 . . Fillings or auxiliary members in containers {or encapsulations} selected or arranged to facilitate heating or cooling
- 23/427 . . . Cooling by change of state, e.g. use of heat pipes {(by liquefied gas [H01L 23/445](#))}
- 23/4275 {by melting or evaporation of solids}
- 23/433 . . . Auxiliary members {in containers} characterised by their shape, e.g. pistons
- 23/4332 {Bellows}
- 23/4334 {Auxiliary members in encapsulations ([H01L 23/49568](#) takes precedence)}
- 23/4336 {in combination with jet impingement}
- 23/4338 {Pistons, e.g. spring-loaded members}
- 23/44 . . the complete device being wholly immersed in a fluid other than air {([H01L 23/427](#) takes precedence)}
- 23/445 . . . {the fluid being a liquefied gas, e.g. in a cryogenic vessel}
- 23/46 . . involving the transfer of heat by flowing fluids ([H01L 23/42](#), [H01L 23/44](#) take precedence)
- 23/467 . . . by flowing gases, e.g. air {([H01L 23/473](#) takes precedence)}
- 23/473 . . . by flowing liquids {([H01L 23/4332](#), [H01L 23/4338](#) take precedence)}
- 23/4735 {Jet impingement ([H01L 23/4336](#) takes precedence)}
- 23/48 . Arrangements for conducting electric current to or from the solid state body in operation, e.g. leads, terminal arrangements {; Selection of materials therefor}
- NOTE**
Arrangements for connecting or disconnecting semiconductor or other solid state bodies, or methods related thereto, other than those arrangements or methods covered by the following subgroups, are covered by [H01L 24/00](#)
- 23/481 . . {Internal lead connections, e.g. via connections, feedthrough structures}
- 23/482 . . consisting of lead-in layers inseparably applied to the semiconductor body {(electrodes [H01L 29/40](#))}
- 23/4821 . . . {Bridge structure with air gap}
- 23/4822 . . . {Beam leads}
- 23/4824 . . . {Pads with extended contours, e.g. grid structure, branch structure, finger structure}
- 23/4825 . . . {for devices consisting of semiconductor layers on insulating or semi-insulating substrates, e.g. silicon on sapphire devices, i.e. SOS}
- 23/4827 . . . {Materials}
- 23/4828 {Conductive organic material or pastes, e.g. conductive adhesives, inks}
- 23/485 . . . consisting of layered constructions comprising conductive layers and insulating layers, e.g. planar contacts {([H01L 23/4821](#), [H01L 23/4822](#), [H01L 23/4824](#), [H01L 23/4825](#) take precedence; materials [H01L 23/532](#), bond pads [H01L 24/02](#), bump connectors [H01L 24/10](#))}
- 23/4855 {Overhang structure}
- 23/488 . . consisting of soldered {or bonded} constructions {(bump connectors [H01L 24/01](#))}
- 23/49 . . . wire-like {arrangements or pins or rods (using optical fibres [H01L 23/48](#); pins attached to insulating substrates [H01L 23/49811](#))}
- 23/492 . . . Bases or plates {or solder therefor}
- 23/4922 {having a heterogeneous or anisotropic structure}
- 23/4924 {characterised by the materials}
- 23/4926 {the materials containing semiconductor material}
- 23/4928 {the materials containing carbon}
- 23/495 . . . Lead-frames {or other flat leads ([H01L 23/498](#) takes precedence; lead frame interconnections between components [H01L 23/52](#))}
- 23/49503 {characterised by the die pad}

- 23/49506 {an insulative substrate being used as a diepad, e.g. ceramic, plastic ([H01L 23/49531](#) takes precedence)}
- 23/4951 {Chip-on-leads or leads-on-chip techniques, i.e. inner lead fingers being used as die pad}
- 23/49513 {having bonding material between chip and die pad}
- 23/49517 {Additional leads}
- 23/4952 {the additional leads being a bump or a wire}
- 23/49524 {the additional leads being a tape carrier or flat leads}
- 23/49527 {the additional leads being a multilayer}
- 23/49531 {the additional leads being a wiring board}
- 23/49534 {Multi-layer}
- 23/49537 {Plurality of lead frames mounted in one device}
- 23/49541 {Geometry of the lead-frame}
- 23/49544 {Deformation absorbing parts in the lead frame plane, e.g. meanderline shape ([H01L 23/49562](#) takes precedence)}
- 23/49548 {Cross section geometry ([H01L 23/49562](#) takes precedence)}
- 23/49551 {characterised by bent parts}
- 23/49555 {the bent parts being the outer leads}
- 23/49558 {Insulating layers on lead frames, e.g. bridging members}
- 23/49562 {for devices being provided for in [H01L 29/00](#)}
- 23/49565 {Side rails of the lead frame, e.g. with perforations, sprocket holes}
- 23/49568 {specifically adapted to facilitate heat dissipation}
- 23/49572 {consisting of thin flexible metallic tape with or without a film carrier ([H01L 23/49503](#) - [H01L 23/49568](#) and [H01L 23/49575](#) - [H01L 23/49579](#) take precedence)}
- 23/49575 {Assemblies of semiconductor devices on lead frames}
- 23/49579 {characterised by the materials of the lead frames or layers thereon}
- 23/49582 {Metallic layers on lead frames}
- 23/49586 {Insulating layers on lead frames}
- 23/49589 {Capacitor integral with or on the leadframe}
- 23/49593 {Battery in combination with a leadframe}
- 23/49596 {Oscillators in combination with lead-frames}
- 23/498 Leads, {i.e. metallisations or lead-frames} on insulating substrates, {e.g. chip carriers (shape of the substrate [H01L 23/13](#))}
- 23/49805 {the leads being also applied on the sidewalls or the bottom of the substrate, e.g. leadless packages for surface mounting}
- 23/49811 {Additional leads joined to the metallisation on the insulating substrate, e.g. pins, bumps, wires, flat leads ([H01L 23/49827](#) takes precedence)}
- 23/49816 {Spherical bumps on the substrate for external connection, e.g. ball grid arrays [BGA]}
- 23/49822 {Multilayer substrates ([multilayer metallisation on monolayer substrate H01L 23/498](#))}
- 23/49827 {Via connections through the substrates, e.g. pins going through the substrate, coaxial cables ([H01L 23/49822](#), [H01L 23/49833](#), [H01L 23/4985](#), [H01L 23/49861](#) take precedence)}
- 23/49833 {the chip support structure consisting of a plurality of insulating substrates}
- 23/49838 {Geometry or layout}
- 23/49844 {for devices being provided for in [H01L 29/00](#)}
- 23/4985 {Flexible insulating substrates ([H01L 23/49572](#) and [H01L 23/49855](#) take precedence)}
- 23/49855 {for flat-cards, e.g. credit cards ([cards per se G06K 19/00](#))}
- 23/49861 {Lead-frames fixed on or encapsulated in insulating substrates ([H01L 23/4985](#), [H01L 23/49805](#) take precedence)}
- 23/49866 {characterised by the materials (materials of the substrates [H01L 23/14](#), of the lead-frames [H01L 23/49579](#))}
- 23/49872 {the conductive materials containing semiconductor material}
- 23/49877 {Carbon, e.g. fullerenes ([superconducting fullerenes H01L 39/123](#))}
- 23/49883 {the conductive materials containing organic materials or pastes, e.g. for thick films ([for printed circuits H05K 1/092](#))}
- 23/49888 {the conductive materials containing superconducting material}
- 23/49894 {Materials of the insulating layers or coatings}
- 23/50 for integrated circuit devices, {e.g. power bus, number of leads} ([H01L 23/482](#) - [H01L 23/498](#) take precedence)
- 23/52 Arrangements for conducting electric current within the device in operation from one component to another {, i.e. interconnections, e.g. wires, lead frames ([optical interconnections G02B 6/00](#))}
- 23/522 including external interconnections consisting of a multilayer structure of conductive and insulating layers inseparably formed on the semiconductor body
- 23/5221 {Crossover interconnections}
- 23/5222 {Capacitive arrangements or effects of, or between wiring layers ([other capacitive arrangements H01L 23/642](#))}
- 23/5223 {Capacitor integral with wiring layers}
- 23/5225 {Shielding layers formed together with wiring layers}
- 23/5226 {Via connections in a multilevel interconnection structure}
- 23/5227 {Inductive arrangements or effects of, or between, wiring layers ([other inductive arrangements H01L 23/645](#))}
- 23/5228 {Resistive arrangements or effects of, or between, wiring layers ([other resistive arrangements H01L 23/647](#))}
- 23/525 with adaptable interconnections
- 23/5252 {comprising anti-fuses, i.e. connections having their state changed from non-conductive to conductive}

- 23/5254 {the change of state resulting from the use of an external beam, e.g. laser beam or ion beam}
- 23/5256 {comprising fuses, i.e. connections having their state changed from conductive to non-conductive}
- 23/5258 {the change of state resulting from the use of an external beam, e.g. laser beam or ion beam}
- 23/528 . . . {Geometry or} layout of the interconnection structure {(H01L 27/0207 takes precedence; algorithms G06F 30/00)}
- 23/5283 {Cross-sectional geometry}
- 23/5286 {Arrangements of power or ground buses}
- 23/532 . . . characterised by the materials
- 23/53204 {Conductive materials}
- 23/53209 {based on metals, e.g. alloys, metal silicides (H01L 23/53285 takes precedence)}
- 23/53214 {the principal metal being aluminium}
- 23/53219 {Aluminium alloys}
- 23/53223 {Additional layers associated with aluminium layers, e.g. adhesion, barrier, cladding layers}
- 23/53228 {the principal metal being copper}
- 23/53233 {Copper alloys}
- 23/53238 {Additional layers associated with copper layers, e.g. adhesion, barrier, cladding layers}
- 23/53242 {the principal metal being a noble metal, e.g. gold}
- 23/53247 {Noble-metal alloys}
- 23/53252 {Additional layers associated with noble-metal layers, e.g. adhesion, barrier, cladding layers}
- 23/53257 {the principal metal being a refractory metal}
- 23/53261 {Refractory-metal alloys}
- 23/53266 {Additional layers associated with refractory-metal layers, e.g. adhesion, barrier, cladding layers}
- 23/53271 {containing semiconductor material, e.g. polysilicon}
- 23/53276 {containing carbon, e.g. fullerenes (superconducting fullerenes H01L 39/123)}
- 23/5328 {containing conductive organic materials or pastes, e.g. conductive adhesives, inks}
- 23/53285 {containing superconducting materials}
- 23/5329 {Insulating materials}
- 23/53295 {Stacked insulating layers}
- 23/535 . . . including internal interconnections, e.g. cross-under constructions {(internal lead connections H01L 23/481)}
- 23/538 . . . the interconnection structure between a plurality of semiconductor chips being formed on, or in, insulating substrates ({H05K takes precedence; manufacture or treatment H01L 21/4846} ; mountings per se H01L 23/12; {materials H01L 23/49866})
- 23/5381 . . . {Crossover interconnections, e.g. bridge stepovers}
- 23/5382 . . . {Adaptable interconnections, e.g. for engineering changes}
- 23/5383 . . . {Multilayer substrates (H01L 23/5385 takes precedence; multilayer metallisation on monolayer substrates H01L 23/538)}
- 23/5384 . . . {Conductive vias through the substrate with or without pins, e.g. buried coaxial conductors (H01L 23/5383, H01L 23/5385 take precedence; pins attached to insulating substrates H01L 23/49811)}
- 23/5385 . . . {Assembly of a plurality of insulating substrates}
- 23/5386 . . . {Geometry or layout of the interconnection structure}
- 23/5387 . . . {Flexible insulating substrates (H01L 23/5388 takes precedence)}
- 23/5388 . . . {for flat cards, e.g. credit cards (cards per se G06K 19/00)}
- 23/5389 . . . {the chips being integrally enclosed by the interconnect and support structures}
- 23/544 . Marks applied to semiconductor devices {or parts}, e.g. registration marks, {alignment structures, wafer maps (test patterns for characterising or monitoring manufacturing processes H01L 22/00)}
- NOTE**
- When classifying in group H01L 23/544, details are to be further indexed by using the indexing codes chosen from H01L 2223/544 and subgroups
- 23/552 . Protection against radiation, e.g. light {or electromagnetic waves}
- 23/556 . . against alpha rays
- 23/562 . {Protection against mechanical damage (H01L 23/02, H01L 23/28 take precedence)}
- 23/564 . {Details not otherwise provided for, e.g. protection against moisture (getters H01L 23/26)}
- 23/57 . {Protection from inspection, reverse engineering or tampering}
- 23/573 . . {using passive means}
- 23/576 . . {using active circuits}
- 23/58 . Structural electrical arrangements for semiconductor devices not otherwise provided for {, e.g. in combination with batteries (H01L 23/49593, H01L 23/49596 take precedence)}
- 23/585 . . {comprising conductive layers or plates or strips or rods or rings (H01L 23/60, H01L 23/62, H01L 23/64, H01L 23/66 take precedence)}
- 23/60 . . Protection against electrostatic charges or discharges, e.g. Faraday shields
- 23/62 . . Protection against overvoltage, e.g. fuses, shunts
- 23/64 . . Impedance arrangements
- 23/642 . . . {Capacitive arrangements (H01L 23/49589, H01L 23/645, H01L 23/647, H01L 23/66 take precedence; capacitive effects between wiring layers on the semiconductor body H01L 23/5222)}
- 23/645 . . . {Inductive arrangements (H01L 23/647, H01L 23/66 take precedence)}
- 23/647 . . . {Resistive arrangements (H01L 23/66, H01L 23/62 take precedence)}
- 23/66 . . . High-frequency adaptations
- NOTE**
- When classifying in group H01L 23/66, details are to be further indexed by using the

indexing codes chosen from [H01L 2223/66](#) and subgroups

24/02

- . . {Bonding areas (on insulating substrates, e.g. chip carriers, [H01L 23/49816](#), [H01L 23/49838](#), [H01L 23/5389](#)); Manufacturing methods related thereto}

WARNING

Groups [H01L 24/02](#) – [H01L 24/09](#) are incomplete pending reclassification of documents from groups [H01L 24/02](#) and [H01L 24/10](#).

Groups [H01L 24/02](#) – [H01L 24/09](#) and [H01L 24/10](#) should be considered in order to perform a complete search.

24/00 {Arrangements for connecting or disconnecting semiconductor or solid-state bodies; Methods or apparatus related thereto}

NOTES

1. This group does not cover:

- details of semiconductor bodies or of electrodes of devices provided for in group [H01L 29/00](#), which details are covered by that group;
- details peculiar to devices provided for in a single main group of groups [H01L 31/00](#) - [H01L 51/00](#), which details are covered by those groups.
- printed circuits, which are covered by groups [H05K 1/00](#) - [H05K 1/189](#);
- apparatus or manufacturing processes for printed circuits, which are covered by groups [H05K 3/00](#) - [H05K 3/4685](#);
- manufacture or treatment of parts, which are covered by group [H01L 21/48](#) and subgroups except [H01L 21/4885](#) - [H01L 21/4896](#);
- assemblies of semiconductor devices, which are covered by groups [H01L 21/50](#) - [H01L 21/568](#);
- applying interconnections to be used for carrying current between separate components within a device, which is covered by group [H01L 21/768](#) and subgroups;
- containers or seals, which are covered by groups [H01L 23/02](#) - [H01L 23/10](#);
- mountings, which are covered by groups [H01L 23/12](#) - [H01L 23/15](#) and subgroups;
- arrangements for cooling, heating, ventilating or temperature compensation, which are covered by groups [H01L 23/34](#) - [H01L 23/4735](#);
- arrangements for conducting electric current, which are covered by groups [H01L 23/48](#) - [H01L 23/50](#), and by groups [H01L 23/52](#) - [H01L 23/5389](#);
- structural electrical arrangements, which are covered by groups [H01L 24/80](#) - [H01L 23/66](#);
- assemblies of semiconductor or other solid state devices, which are covered by groups [H01L 25/00](#) - [H01L 25/18](#).

2. In this group the following indexing codes are used : [H01L 24/00](#), [H01L 2224/00](#), [H01L 2924/00](#), and subgroups thereof

24/03

- . . . {Manufacturing methods}

24/04

- . . . {Structure, shape, material or disposition of the bonding areas prior to the connecting process}

24/05

- {of an individual bonding area}

24/06

- {of a plurality of bonding areas}

24/07

- . . . {Structure, shape, material or disposition of the bonding areas after the connecting process}

24/08

- {of an individual bonding area}

24/09

- {of a plurality of bonding areas}

24/10

- . . {Bump connectors (bumps on insulating substrates, e.g. chip carriers, [H01L 23/49816](#)); Manufacturing methods related thereto}

24/11

- . . . {Manufacturing methods (for bumps on insulating substrates [H01L 21/4853](#))}

24/12

- . . . {Structure, shape, material or disposition of the bump connectors prior to the connecting process}

24/13

- {of an individual bump connector}

24/14

- {of a plurality of bump connectors}

24/15

- . . . {Structure, shape, material or disposition of the bump connectors after the connecting process}

24/16

- {of an individual bump connector}

24/17

- {of a plurality of bump connectors}

24/18

- . . {High density interconnect [HDI] connectors; Manufacturing methods related thereto (interconnection structure between a plurality of semiconductor chips [H01L 23/5389](#))}

WARNING

Groups [H01L 24/18](#) – [H01L 24/25](#) are incomplete pending reclassification of documents from groups [H01L 24/18](#) and [H01L 24/82](#).

Groups [H01L 24/18](#) – [H01L 24/25](#) and [H01L 24/82](#) should be considered in order to perform a complete search.

24/19

- . . . {Manufacturing methods of high density interconnect preforms}

24/20

- . . . {Structure, shape, material or disposition of high density interconnect preforms}

24/23

- . . . {Structure, shape, material or disposition of the high density interconnect connectors after the connecting process}

24/24

- {of an individual high density interconnect connector}

24/25

- {of a plurality of high density interconnect connectors}

24/26

- . . {Layer connectors, e.g. plate connectors, solder or adhesive layers; Manufacturing methods related thereto}

24/01

- . {Means for bonding being attached to, or being formed on, the surface to be connected, e.g. chip-to-package, die-attach, "first-level" interconnects; Manufacturing methods related thereto}

- 24/27 . . . {Manufacturing methods}
- 24/28 . . . {Structure, shape, material or disposition of the layer connectors prior to the connecting process}
- 24/29 {of an individual layer connector}
- 24/30 {of a plurality of layer connectors}
- 24/31 . . . {Structure, shape, material or disposition of the layer connectors after the connecting process}
- 24/32 {of an individual layer connector}
- 24/33 {of a plurality of layer connectors}
- 24/34 . . {Strap connectors, e.g. copper straps for grounding power devices; Manufacturing methods related thereto}

WARNING

Groups [H01L 24/34](#) – [H01L 24/41](#) are incomplete pending reclassification of documents from groups [H01L 24/34](#), [H01L 24/01](#), [H01L 24/42](#), and [H01L 24/85](#).

Groups [H01L 24/34](#) – [H01L 24/41](#) and [H01L 24/01](#), [H01L 24/42](#), [H01L 24/85](#) should be considered in order to perform a complete search.

- 24/35 . . . {Manufacturing methods}
- 24/36 . . . {Structure, shape, material or disposition of the strap connectors prior to the connecting process}
- 24/37 {of an individual strap connector}
- 24/38 {of a plurality of strap connectors}
- 24/39 . . . {Structure, shape, material or disposition of the strap connectors after the connecting process}
- 24/40 {of an individual strap connector}
- 24/41 {of a plurality of strap connectors}
- 24/42 . . {Wire connectors; Manufacturing methods related thereto}
- 24/43 . . . {Manufacturing methods}
- 24/44 . . . {Structure, shape, material or disposition of the wire connectors prior to the connecting process}
- 24/45 {of an individual wire connector}
- 24/46 {of a plurality of wire connectors}
- 24/47 . . . {Structure, shape, material or disposition of the wire connectors after the connecting process}
- 24/48 {of an individual wire connector}
- 24/49 {of a plurality of wire connectors}
- 24/50 . . {Tape automated bonding [TAB] connectors, i.e. film carriers; Manufacturing methods related thereto (thin flexible metallic tape with or without a film carrier [H01L 23/49572](#), flexible insulating substrates [H01L 23/4985](#), [H01L 23/5387](#))}

WARNING

Group [H01L 24/50](#) is incomplete pending reclassification of documents from group [H01L 24/86](#).

Groups [H01L 24/50](#) and [H01L 24/86](#) should be considered in order to perform a complete search.

- 24/63 . . {Connectors not provided for in any of the groups [H01L 24/10](#) - [H01L 24/50](#) and subgroups; Manufacturing methods related thereto}
- 24/64 . . . {Manufacturing methods}

- 24/65 . . . {Structure, shape, material or disposition of the connectors prior to the connecting process}
- 24/66 {of an individual connector}
- 24/67 {of a plurality of connectors}
- 24/68 . . . {Structure, shape, material or disposition of the connectors after the connecting process}
- 24/69 {of an individual connector}
- 24/70 {of a plurality of connectors}
- 24/71 . {Means for bonding not being attached to, or not being formed on, the surface to be connected (holders for supporting the complete device in operation [H01L 23/32](#))}
- 24/72 . . {Detachable connecting means consisting of mechanical auxiliary parts connecting the device, e.g. pressure contacts using springs or clips}
- 24/73 . {Means for bonding being of different types provided for in two or more of groups [H01L 24/10](#), [H01L 24/18](#), [H01L 24/26](#), [H01L 24/34](#), [H01L 24/42](#), [H01L 24/50](#), [H01L 24/63](#), [H01L 24/71](#)}
- 24/74 . {Apparatus for manufacturing arrangements for connecting or disconnecting semiconductor or solid-state bodies}
- 24/741 . . {Apparatus for manufacturing means for bonding, e.g. connectors}
- 24/742 . . . {Apparatus for manufacturing bump connectors}
- 24/743 . . . {Apparatus for manufacturing layer connectors}
- 24/744 . . . {Apparatus for manufacturing strap connectors}
- 24/745 . . . {Apparatus for manufacturing wire connectors}
- 24/75 . . {Apparatus for connecting with bump connectors or layer connectors}
- 24/76 . . {Apparatus for connecting with build-up interconnects}
- 24/77 . . {Apparatus for connecting with strap connectors}
- 24/78 . . {Apparatus for connecting with wire connectors}
- 24/79 . . {Apparatus for Tape Automated Bonding [TAB]}
- 24/799 . . {Apparatus for disconnecting}
- 24/80 . {Methods for connecting semiconductor or other solid state bodies using means for bonding being attached to, or being formed on, the surface to be connected}
- 24/81 . . {using a bump connector}
- 24/82 . . {by forming build-up interconnects at chip-level, e.g. for high density interconnects [HDI] (interconnection structure between a plurality of semiconductor chips [H01L 23/5389](#))}
- 24/83 . . {using a layer connector}
- 24/84 . . {using a strap connector}

WARNING

Group [H01L 24/84](#) is incomplete pending reclassification of documents from group [H01L 24/85](#).

Group [H01L 24/84](#) and [H01L 24/85](#) should be considered in order to perform a complete search.

- 24/85 . . {using a wire connector (wire bonding in general [B23K 20/004](#))}
- 24/86 . . {using tape automated bonding [TAB]}

- 24/89 . . {using at least one connector not provided for in any of the groups [H01L 24/81](#) - [H01L 24/86](#)}
- 24/90 . {Methods for connecting semiconductor or solid state bodies using means for bonding not being attached to, or not being formed on, the body surface to be connected, e.g. pressure contacts using springs or clips}
- 24/91 . {Methods for connecting semiconductor or solid state bodies including different methods provided for in two or more of groups [H01L 24/80](#) - [H01L 24/90](#)}
- 24/92 . . {Specific sequence of method steps}
- 24/93 . {Batch processes}
- WARNING**
- Group [H01L 24/93](#) is incomplete pending reclassification of documents from groups [H01L 24/80](#) - [H01L 24/90](#).
- Groups [H01L 24/93](#) and [H01L 24/80](#) - [H01L 24/90](#) should be considered in order to perform a complete search.
- 24/94 . . {at wafer-level, i.e. with connecting carried out on a wafer comprising a plurality of undiced individual devices}
- 24/95 . . {at chip-level, i.e. with connecting carried out on a plurality of singulated devices, i.e. on diced chips}
- 24/96 . . . {the devices being encapsulated in a common layer, e.g. neo-wafer or pseudo-wafer, said common layer being separable into individual assemblies after connecting}
- 24/97 . . . {the devices being connected to a common substrate, e.g. interposer, said common substrate being separable into individual assemblies after connecting}
- 24/98 . {Methods for disconnecting semiconductor or solid-state bodies}
- 25/00 Assemblies consisting of a plurality of individual semiconductor or other solid state devices (; Multistep manufacturing processes thereof){devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#); photovoltaic modules or arrays of photovoltaic cells [H01L 31/042](#) (; panels or arrays of photo electrochemical cells [H01G 9/2068](#))}**
- 25/03 . all the devices being of a type provided for in the same subgroup of groups [H01L 27/00](#) - [H01L 51/00](#), e.g. assemblies of rectifier diodes
- 25/04 . . the devices not having separate containers
- 25/041 . . . {the devices being of a type provided for in group [H01L 31/00](#)}
- 25/042 {the devices being arranged next to each other (solar cells [H01L 31/042](#))}
- 25/043 {Stacked arrangements of devices}
- 25/046 . . . {the devices being of a type provided for in group [H01L 51/00](#)}
- 25/047 {the devices being of a type provided for in group [H01L 51/42](#), e.g. photovoltaic modules based on organic solar cells}
- 25/048 {the devices being of a type provided for in group [H01L 51/50](#), e.g. assembly of organic light emitting devices}
- 25/065 . . . the devices being of a type provided for in group [H01L 27/00](#)
- NOTE**
- Group [H01L 25/0652](#) takes precedence over groups [H01L 25/0655](#) and [H01L 25/0657](#)
- 25/0652 {the devices being arranged next and on each other, i.e. mixed assemblies}
- 25/0655 {the devices being arranged next to each other}
- 25/0657 {Stacked arrangements of devices}
- 25/07 . . . the devices being of a type provided for in group [H01L 29/00](#)
- NOTE**
- Group [H01L 25/071](#) takes precedence over groups [H01L 25/072](#) - [H01L 25/074](#)
- 25/071 {the devices being arranged next and on each other, i.e. mixed assemblies}
- 25/072 {the devices being arranged next to each other}
- 25/073 {Apertured devices mounted on one or more rods passed through the apertures}
- 25/074 {Stacked arrangements of non-apertured devices}
- 25/075 . . . the devices being of a type provided for in group [H01L 33/00](#)
- 25/0753 {the devices being arranged next to each other}
- 25/0756 {Stacked arrangements of devices}
- 25/10 . . the devices having separate containers
- 25/105 . . . {the devices being of a type provided for in group [H01L 27/00](#)}
- NOTE**
- When classifying in group [H01L 25/105](#), details of the assemblies are to be further indexed by using the indexing codes chosen from [H01L 2225/1005](#) and subgroups
- 25/11 . . . the devices being of a type provided for in group [H01L 29/00](#)
- NOTE**
- Group [H01L 25/112](#) takes precedence over groups [H01L 25/115](#) and [H01L 25/117](#)
- 25/112 {Mixed assemblies}
- 25/115 {the devices being arranged next to each other}
- 25/117 {Stacked arrangements of devices}
- 25/13 . . . the devices being of a type provided for in group [H01L 33/00](#)
- 25/16 . the devices being of types provided for in two or more different main groups of [H01L 27/00](#) - [H01L 49/00](#) {and [H01L 51/00](#)}, e.g. forming hybrid circuits {(interconnections for hybrid circuits [H01L 23/5389](#))}
- 25/162 . . {the devices being mounted on two or more different substrates}
- 25/165 . . {Containers}
- 25/167 . . {comprising optoelectronic devices, e.g. LED, photodiodes}

25/18	the devices being of types provided for in two or more different subgroups of the same main group of groups H01L 27/00 - H01L 51/00 {comprising devices provided for in H01L 27/144 and subgroups, see H01L 27/144 and subgroups}	27/0244 {I2L structures integrated in combination with analog structures}
25/50	{Multistep manufacturing processes of assemblies consisting of devices, each device being of a type provided for in group H01L 27/00 or H01L 29/00 (H01L 21/50 takes precedence)}	27/0248	. . . {for electrical or thermal protection, e.g. electrostatic discharge [ESD] protection}
27/00	Devices consisting of a plurality of semiconductor or other solid-state components formed in or on a common substrate (details thereof H01L 23/00 , H01L 29/00 - H01L 51/00 ; assemblies consisting of a plurality of individual solid state devices H01L 25/00)	27/0251 {for MOS devices}
	NOTES	27/0255 {using diodes as protective elements}
	1. In this group, with the exception of groups H01L 27/115 - H01L 27/11597 , the last place priority rule is applied, i.e. at each hierarchical level, in the absence of an indication to the contrary, classification is made in the last appropriate place.	27/0259 {using bipolar transistors as protective elements}
	2. When classifying in this group, subject matter relating to electrically programmable read-only memories is classified in group H01L 27/115 , irrespective of the last place priority rule.	27/0262 {including a PNP transistor and a NPN transistor, wherein each of said transistors has its base coupled to the collector of the other transistor, e.g. silicon controlled rectifier [SCR] devices}
27/01	comprising only passive thin-film or thick-film elements formed on a common insulating substrate {(passive two-terminal components without a potential-jump or surface barrier for integrated circuits, details thereof and multistep manufacturing processes therefor H01L 28/00)}	27/0266 {using field effect transistors as protective elements}
	NOTE	27/027 {specially adapted to provide an electrical current path other than the field effect induced current path}
	In groups H01L 27/01 - H01L 27/26 , in the absence of an indication to the contrary, classification is made in the last appropriate place.	27/0274 {involving a parasitic bipolar transistor triggered by the electrical biasing of the gate electrode of the field effect transistor, e.g. gate coupled transistors}
27/013	. . {Thick-film circuits}	27/0277 {involving a parasitic bipolar transistor triggered by the local electrical biasing of the layer acting as base of said parasitic bipolar transistor}
27/016	. . {Thin-film circuits}	27/0281 {field effect transistors in a "Darlington-like" configuration}
27/02	including semiconductor components specially adapted for rectifying, oscillating, amplifying or switching and having at least one potential-jump barrier or surface barrier; including integrated passive circuit elements with at least one potential-jump barrier or surface barrier	27/0285 {bias arrangements for gate electrode of field effect transistors, e.g. RC networks, voltage partitioning circuits (H01L 27/0281 takes precedence)}
27/0203	. . {Particular design considerations for integrated circuits}	27/0288 {using passive elements as protective elements, e.g. resistors, capacitors, inductors, spark-gaps}
27/0207	. . . {Geometrical layout of the components, e.g. computer aided design; custom LSI, semi-custom LSI, standard cell technique}	27/0292 {using a specific configuration of the conducting means connecting the protective devices, e.g. ESD buses}
27/0211 {adapted for requirements of temperature}	27/0296 {involving a specific disposition of the protective devices}
27/0214	. . . {for internal polarisation, e.g. I2L}	27/04	. . the substrate being a semiconductor body
27/0218 {of field effect structures}	27/06	. . . including a plurality of individual components in a non-repetitive configuration
27/0222 {Charge pumping, substrate bias generation structures}	27/0605 {integrated circuits made of compound material, e.g. A _{III} B _V }
27/0225 {Charge injection in static induction transistor logic structures [SITL]}	27/0611 {integrated circuits having a two-dimensional layout of components without a common active region}
27/0229 {of bipolar structures}	27/0617 {comprising components of the field-effect type (H01L 27/0251 takes precedence)}
27/0233 {Integrated injection logic structures [I2L]}	27/0623 {in combination with bipolar transistors}
27/0237 {using vertical injector structures}	27/0629 {in combination with diodes, or resistors, or capacitors}
27/024 {using field effect injector structures}	27/0635 {in combination with bipolar transistors and diodes, or resistors, or capacitors}
		27/0641 {without components of the field effect type}
		27/0647 {Bipolar transistors in combination with diodes, or capacitors, or resistors, e.g. vertical bipolar transistor and bipolar lateral transistor and resistor}

27/0652	{ Vertical bipolar transistor in combination with diodes, or capacitors, or resistors }	27/0811	{ MIS diodes }
27/0658	{ Vertical bipolar transistor in combination with resistors or capacitors }	27/0814	{ Diodes only }
27/0664	{ Vertical bipolar transistor in combination with diodes }	27/0817	{ Thyristors only }
27/067	{ Lateral bipolar transistor in combination with diodes, or capacitors, or resistors }	27/082	including bipolar components only
27/0676	{ comprising combinations of diodes, or capacitors or resistors }	27/0821	{ Combination of lateral and vertical transistors only }
27/0682	{ comprising combinations of capacitors and resistors }	27/0823	{ including vertical bipolar transistors only }
27/0688	{ Integrated circuits having a three-dimensional layout }	27/0825	{ Combination of vertical direct transistors of the same conductivity type having different characteristics, (e.g. Darlington transistors) }
27/0694	{ comprising components formed on opposite sides of a semiconductor substrate }	27/0826	{ Combination of vertical complementary transistors }
27/07	the components having an active region in common	27/0828	{ Combination of direct and inverse vertical transistors }
27/0705	{ comprising components of the field effect type }	27/085	including field-effect components only
27/0711	{ in combination with bipolar transistors and diodes, or capacitors, or resistors }	27/088	the components being field-effect transistors with insulated gate
27/0716	{ in combination with vertical bipolar transistors and diodes, or capacitors, or resistors }	27/0883	{ Combination of depletion and enhancement field effect transistors }
27/0722	{ in combination with lateral bipolar transistors and diodes, or capacitors, or resistors }	27/0886	{ including transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET }
27/0727	{ in combination with diodes, or capacitors or resistors }	27/092	complementary MIS field-effect transistors
27/0733	{ in combination with capacitors only }	27/0921	{ Means for preventing a bipolar, e.g. thyristor, action between the different transistor regions, e.g. Latchup prevention }
27/0738	{ in combination with resistors only }	27/0922	{ Combination of complementary transistors having a different structure, e.g. stacked CMOS, high-voltage and low-voltage CMOS }
27/0744	{ without components of the field effect type }	27/0924	{ including transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET }
27/075	{ Bipolar transistors in combination with diodes, or capacitors, or resistors, e.g. lateral bipolar transistor, and vertical bipolar transistor and resistor }	27/0925	{ comprising an N-well only in the substrate }
27/0755	{ Vertical bipolar transistor in combination with diodes, or capacitors, or resistors }	27/0927	{ comprising a P-well only in the substrate }
27/0761	{ Vertical bipolar transistor in combination with diodes only }	27/0928	{ comprising both N- and P- wells in the substrate, e.g. twin-tub }
27/0766	{ with Schottky diodes only }	27/095	the components being Schottky barrier gate field-effect transistors
27/0772	{ Vertical bipolar transistor in combination with resistors only }	27/098	the components being PN junction gate field-effect transistors
27/0777	{ Vertical bipolar transistor in combination with capacitors only }	27/10	including a plurality of individual components in a repetitive configuration
27/0783	{ Lateral bipolar transistors in combination with diodes, or capacitors, or resistors }	27/101	{ including resistors or capacitors only }
27/0788	{ comprising combinations of diodes or capacitors or resistors }	27/102	including bipolar components
27/0794	{ Combinations of capacitors and resistors }	27/1021	{ including diodes only }
27/08	including only semiconductor components of a single kind	27/1022	{ including bipolar transistors }
27/0802	{ Resistors only }	27/1023	{ Bipolar dynamic random access memory structures }
27/0805	{ Capacitors only }	27/1024	{ Arrays of single bipolar transistors only, e.g. read only memory structures }
27/0808	{ Varactor diodes }	27/1025	{ Static bipolar memory cell structures }
			27/1026	{ Bipolar electrically programmable memory structures (using fuses H01L 23/525) }
			27/1027	{ Thyristors }

27/1028	{Double base diodes}	27/10867	{with at least one step of making a connection between transistor and capacitor, e.g. buried strap}
27/105	including field-effect components			
		NOTE			
		In this group and its subgroups classification is made in any appropriate place	27/1087	{with at least one step of making the trench}
27/1052	{Memory structures and multistep manufacturing processes therefor not provided for in groups H01L 27/1055 - H01L 27/112 }	27/10873	{with at least one step of making the transistor}
27/1055	{comprising charge coupled devices of the so-called bucket brigade type}	27/10876	{the transistor having a trench structure in the substrate (vertical transistor in combination with a capacitor formed in a substrate trench H01L 27/10864)}
27/1057	{comprising charge coupled devices [CCD] or charge injection devices [CID]}	27/10879	{the transistor being of the FinFET type}
27/108	Dynamic random access memory structures	27/10882	{with at least one step of making a data line}
27/10802	{comprising floating-body transistors, e.g. floating-body cells}	27/10885	{with at least one step of making a bit line}
27/10805	{with one-transistor one-capacitor memory cells}	27/10888	{with at least one step of making a bit line contact}
27/10808	{the storage electrode stacked over transistor}	27/10891	{with at least one step of making a word line}
27/10811	{with bit line higher than capacitor}	27/10894	{with simultaneous manufacture of periphery and memory cells}
27/10814	{with capacitor higher than bit line level}	27/10897	{Peripheral structures}
27/10817	{the storage electrode having multiple wings}	27/11	Static random access memory structures
27/1082	{the capacitor extending under transfer transistor area}	27/1104	{the load element being a MOSFET transistor}
27/10823	{the transistor having a trench structure in the substrate}	27/1108	{the load element being a thin film transistor}
27/10826	{the transistor being of the FinFET type}	27/1112	{the load element being a resistor (resistors for integrated circuits H01L 28/20, H01L 29/8605)}
27/10829	{the capacitor being in a substrate trench}	27/1116	{Peripheral circuit region}
27/10832	{the capacitor extending under or around transfer transistor area}	27/112	Read-only memory structures {[ROM] and multistep manufacturing processes therefor}
27/10835	{having storage electrode extension stacked over transistor}	27/11206	{Programmable ROM [PROM], e.g. memory cells comprising a transistor and a fuse or an antifuse}
27/10838	{the capacitor and the transistor being in one trench}	27/11213	{ROM only}
27/10841	{the transistor being vertical}	27/1122	{with source and drain on the same level, e.g. lateral transistors}
27/10844	{Multistep manufacturing methods}	27/11226	{Source or drain contact programmed}
27/10847	{for structures comprising one transistor one-capacitor memory cells}	27/11233	{Gate programmed, e.g. different gate material or no gate}
27/1085	{with at least one step of making the capacitor or connections thereto}	27/1124	{Gate contact programmed}
27/10852	{the capacitor extending over the access transistor}	27/11246	{Gate dielectric programmed, e.g. different thickness}
27/10855	{with at least one step of making a connection between transistor and capacitor, e.g. plug}	27/11253	{Doping programmed, e.g. mask ROM}
27/10858	{the capacitor extending under the access transistor area}	27/1126	{Entire channel doping programmed}
27/10861	{the capacitor being in a substrate trench}	27/11266	{Source or drain doping programmed}
27/10864	{in combination with a vertical transistor}	27/11273	{with source and drain on different levels, e.g. vertical channel}
			27/1128	{with transistors on different levels, e.g. 3D ROM}
			27/11286	{Peripheral circuit regions}
			27/11293	{of memory structures of the ROM-only type}

27/115	Electrically programmable read-only memories; Multistep manufacturing processes therefor	27/11563	with charge-trapping gate insulators, e.g. MNOS or NROM
27/11502	with ferroelectric memory capacitors	27/11565	characterised by the top-view layout
27/11504	characterised by the top-view layout	27/11568	characterised by the memory core region (three-dimensional arrangements H01L 27/11578)
27/11507	characterised by the memory core region	27/1157	with cell select transistors, e.g. NAND
27/11509	characterised by the peripheral circuit region	27/11573	characterised by the peripheral circuit region
27/11512	characterised by the boundary region between the core and peripheral circuit regions	27/11575	characterised by the boundary region between the core and peripheral circuit regions
27/11514	characterised by the three-dimensional arrangements, e.g. with cells on different height levels	27/11578	characterised by three-dimensional arrangements, e.g. with cells on different height levels
27/11517	with floating gate	27/1158	with source and drain on different levels, e.g. with sloping channels
27/11519	characterised by the top-view layout	27/11582	the channels comprising vertical portions, e.g. U-shaped channels
27/11521	characterised by the memory core region (three-dimensional arrangements H01L 27/11551)	27/11585	with the gate electrodes comprising a layer used for its ferroelectric memory properties, e.g. metal-ferroelectric-semiconductor [MFS] or metal-ferroelectric-metal-insulator-semiconductor [MFMS]
27/11524	with cell select transistors, e.g. NAND	27/11587	characterised by the top-view layout
27/11526	characterised by the peripheral circuit region	27/1159	characterised by the memory core region
27/11529	of memory regions comprising cell select transistors, e.g. NAND	27/11592	characterised by the peripheral circuit region
27/11531	Simultaneous manufacturing of periphery and memory cells	27/11595	characterised by the boundary region between core and peripheral circuit regions
27/11534	including only one type of peripheral transistor	27/11597	characterised by three-dimensional arrangements, e.g. cells on different height levels
27/11536	with a control gate layer also being used as part of the peripheral transistor	27/118	Masterslice integrated circuits
27/11539	with an inter-gate dielectric layer also being used as part of the peripheral transistor	27/11801	{using bipolar technology}
27/11541	with a floating-gate layer also being used as part of the peripheral transistor	27/11803	{using field effect technology}
27/11543	with a tunnel dielectric layer also being used as part of the peripheral transistor	2027/11805	{A3B5 or A3B6 gate arrays}
27/11546	including different types of peripheral transistor	27/11807	{CMOS gate arrays}
27/11548	characterised by the boundary region between the core and peripheral circuit regions	2027/11809	{Microarchitecture}
27/11551	characterised by three-dimensional arrangements, e.g. with cells on different height levels	2027/11811	{Basic cell P to N transistor count}
27/11553	with source and drain on different levels, e.g. with sloping channels	2027/11812	{4-T CMOS basic cell}
27/11556	the channels comprising vertical portions, e.g. U-shaped channels	2027/11814	{5-T CMOS basic cell}
27/11558	the control gate being a doped region, e.g. single-poly memory cells	2027/11816	{6-T CMOS basic cell}
27/1156	the floating gate being an electrode shared by two or more components	2027/11818	{7-T CMOS basic cell}
			2027/1182	{8-T CMOS basic cell}
			2027/11822	{relative P to N transistor sizes}
			2027/11824	{for current drive capability}
			2027/11825	{for delay time adaptation}
			2027/11827	{for capacitive loading}
			2027/11829	{Isolation techniques}
			2027/11831	{FET isolation}
			2027/11833	{LOCOS}
			2027/11835	{Degree of specialisation for implementing specific functions}
			2027/11837	{Implementation of digital circuits}

2027/11838	{Implementation of memory functions}	27/1214	{comprising a plurality of TFTs formed on a non-semiconducting substrate, e.g. driving circuits for AMLCDs}
2027/1184	{Implementation of analog circuits}			WARNING
2027/11842	{Resistors and capacitors}			Group H01L 27/1218 – H01L 27/1296 are incomplete pending reclassification of documents from group H01L 27/1214 .
2027/11844	{Hybrid analog or digital}			Groups H01L 27/1218 – H01L 27/1296 and H01L 27/1214 should be considered in order to perform a complete search.
2027/11846	{Embedded IO cells}			
2027/11848	{Transmission gate}			
2027/1185	{Porous cells, i.e. pass-through elements}			
2027/11851	{Technology used, i.e. design rules}	27/1218	{with a particular composition or structure of the substrate}
2027/11853	{Sub-micron technology}	27/1222	{with a particular composition, shape or crystalline structure of the active layer}
2027/11855	{Twin-tub technology}	27/1225	{with semiconductor materials not belonging to the group IV of the periodic table, e.g. InGaZnO}
2027/11857	{SOS, SOI technology}	27/1229	{with different crystal properties within a device or between different devices}
2027/11859	{Connectibility characteristics, i.e. diffusion and polysilicon geometries}	27/1233	{with different thicknesses of the active layer in different devices}
2027/11861	{Substrate and well contacts}	27/1237	{with a different composition, shape, layout or thickness of the gate insulator in different devices}
2027/11862	{Horizontal or vertical grid line density}	27/124	{with a particular composition, shape or layout of the wiring layers specially adapted to the circuit arrangement, e.g. scanning lines in LCD pixel circuits (wiring structures per se H01L 23/52)}
2027/11864	{Yield or reliability}	27/1244	{for preventing breakage, peeling or short circuiting}
2027/11866	{Gate electrode terminals or contacts}	27/1248	{with a particular composition or shape of the interlayer dielectric specially adapted to the circuit arrangement}
2027/11868	{Macro-architecture}	27/1251	{comprising TFTs having a different architecture, e.g. top- and bottom gate TFTs}
2027/1187	{Number of core or basic cells in the macro (RAM, ROM)}	27/1255	{integrated with passive devices, e.g. auxiliary capacitors}
2027/11872	{Distribution function, e.g. Sea of Gates}	27/1259	{Multistep manufacturing methods}
2027/11874	{Layout specification, i.e. inner core region}	27/1262	{with a particular formation, treatment or coating of the substrate}
2027/11875	{Wiring region, routing}	27/1266	{the substrate on which the devices are formed not being the final device substrate, e.g. using a temporary substrate}
2027/11877	{Avoiding clock-skew or clock-delay}	27/127	{with a particular formation, treatment or patterning of the active layer specially adapted to the circuit arrangement}
2027/11879	{Data lines (buses)}	27/1274	{using crystallisation of amorphous semiconductor or recrystallisation of crystalline semiconductor}
2027/11881	{Power supply lines}	27/1277	{using a crystallisation promoting species, e.g. local introduction of Ni catalyst}
2027/11883	{Levels of metallisation}	27/1281	{by using structural features to control crystal growth, e.g. placement of grain filters}
2027/11885	{Two levels of metal}	27/1285	{using control of the annealing or irradiation parameters, e.g. using different scanning direction or intensity for different transistors}
2027/11887	{Three levels of metal}			
2027/11888	{More than 3 levels of metal}			
2027/1189	{Latch-up prevention}			
2027/11892	{Noise prevention (crosstalk)}			
2027/11894	{Radiation hardened circuits}			
27/11896	{using combined field effect/bipolar technology}			
27/11898	{Input and output buffer/driver structures}			
27/12	the substrate being other than a semiconductor body, e.g. an insulating body			
27/1203	{the substrate comprising an insulating body on a semiconductor body, e.g. SOI (three-dimensional layout H01L 27/0688)}			
27/1207	{combined with devices in contact with the semiconductor body, i.e. bulk/SOI hybrid circuits}			
27/1211	{combined with field-effect transistors with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}			

- 27/1288 {employing particular masking sequences or specially adapted masks, e.g. half-tone mask}
- 27/1292 {using liquid deposition, e.g. printing}
- 27/1296 {adapted to increase the uniformity of device parameters}
- 27/13 . . . combined with thin-film or thick-film passive components
- 27/14 . . including semiconductor components sensitive to infra-red radiation, light, electromagnetic radiation of shorter wavelength or corpuscular radiation and specially adapted either for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation (radiation-sensitive components structurally associated with one or more electric light sources only [H01L 31/14](#); couplings of light guides with optoelectronic elements [G02B 6/42](#))
- 27/142 . . Energy conversion devices (photovoltaic modules or arrays of single photovoltaic cells comprising bypass diodes integrated or directly associated with the devices [H01L 31/0443](#); photovoltaic modules composed of a plurality of thin film solar cells deposited on the same substrate [H01L 31/046](#))
- 27/1421 . . . {comprising bypass diodes integrated or directly associated with the device, e.g. bypass diode integrated or formed in or on the same substrate as the solar cell}
- 27/144 . . Devices controlled by radiation
- 27/1443 . . . {with at least one potential jump or surface barrier}
- 27/1446 . . . {in a repetitive configuration}
- 27/146 . . . Imager structures
- WARNING**
- Groups [H01L 27/146](#) – [H01L 27/14893](#) are incomplete pending reclassification of documents from groups [H04N 5/3696](#) and [H04N 9/045](#).
- Groups [H04N 5/3696](#), [H04N 9/045](#), and [H01L 27/146](#) – [H01L 27/14893](#) should be considered in order to perform a complete search.
- 27/14601 {Structural or functional details thereof}
- 27/14603 {Special geometry or disposition of pixel-elements, address-lines or gate-electrodes}
- 27/14605 {Structural or functional details relating to the position of the pixel elements, e.g. smaller pixel elements in the center of the imager compared to pixel elements at the periphery}
- 27/14607 {Geometry of the photosensitive area}
- 27/14609 {Pixel-elements with integrated switching, control, storage or amplification elements (scanning details of imagers [H04N 3/15](#); circuitry of imagers [H04N 5/369](#))}
- 27/1461 {characterised by the photosensitive area}
- 27/14612 {involving a transistor}
- 27/14614 {having a special gate structure}
- 27/14616 {characterised by the channel of the transistor, e.g. channel having a doping gradient}
- 27/14618 {Containers}
- 27/1462 {Coatings}
- 27/14621 {Colour filter arrangements}
- 27/14623 {Optical shielding}
- 27/14625 {Optical elements or arrangements associated with the device}
- 27/14627 {Microlenses}
- 27/14629 {Reflectors}
- 27/1463 {Pixel isolation structures}
- 27/14632 {Wafer-level processed structures}
- 27/14634 {Assemblies, i.e. Hybrid structures}
- 27/14636 {Interconnect structures}
- 27/14638 {Structures specially adapted for transferring the charges across the imager perpendicular to the imaging plane}
- 27/1464 {Back illuminated imager structures}
- 27/14641 {Electronic components shared by two or more pixel-elements, e.g. one amplifier shared by two pixel elements}
- 27/14643 {Photodiode arrays; MOS imagers}
- 27/14645 {Colour imagers}
- 27/14647 {Multicolour imagers having a stacked pixel-element structure, e.g. npn, npnpn or MQW elements}
- 27/14649 {Infra-red imagers}
- 27/1465 {of the hybrid type}
- 27/14652 {Multispectral infra-red imagers, having a stacked pixel-element structure, e.g. npn, npnpn or MQW structures}
- 27/14654 {Blooming suppression}
- 27/14656 {Overflow drain structures}
- 27/14658 {X-ray, gamma-ray or corpuscular radiation imagers (measuring X-, gamma- or corpuscular radiation [G01T 1/00](#))}
- 27/14659 {Direct radiation imagers structures}
- 27/14661 {of the hybrid type}
- 27/14663 {Indirect radiation imagers, e.g. using luminescent members}
- 27/14665 {Imagers using a photoconductor layer}
- 27/14667 {Colour imagers}
- 27/14669 {Infra-red imagers}
- 27/1467 {of the hybrid type}
- 27/14672 {Blooming suppression}
- 27/14674 {Overflow drain structures}
- 27/14676 {X-ray, gamma-ray or corpuscular radiation imagers (measuring X-, gamma- or corpuscular radiation [G01T 1/00](#))}
- 27/14678 {Contact-type imagers}
- 27/14679 {Junction field effect transistor [JFET] imagers; static induction transistor [SIT] imagers}
- 27/14681 {Bipolar transistor imagers}
- 27/14683 {Processes or apparatus peculiar to the manufacture or treatment of these devices or parts thereof (not peculiar thereto [H01L 21/00](#))}
- 27/14685 {Process for coatings or optical elements}
- 27/14687 {Wafer level processing}
- 27/14689 {MOS based technologies}
- 27/1469 {Assemblies, i.e. hybrid integration}
- 27/14692 {Thin film technologies, e.g. amorphous, poly, micro- or nanocrystalline silicon}

- 27/14694 {The active layers comprising only $A_{III}B_V$ compounds, e.g. GaAs, InP}
- 27/14696 {The active layers comprising only $A_{II}B_{VI}$ compounds, e.g. CdS, ZnS, CdTe}
- 27/14698 {Post-treatment for the devices, e.g. annealing, impurity-gettering, shor-circuit elimination, recrystallisation}
- 27/148 Charge coupled imagers {(individual charge coupled devices [H01L 29/765](#))}
- 27/14806 {Structural or functional details thereof}
- 27/14812 {Special geometry or disposition of pixel-elements, address lines or gate-electrodes}
- 27/14818 {Optical shielding}
- 27/14825 {Linear CCD imagers}
- 27/14831 {Area CCD imagers}
- 27/14837 {Frame-interline transfer}
- 27/14843 {Interline transfer}
- 27/1485 {Frame transfer}
- 27/14856 {Time-delay and integration}
- 27/14862 {CID imagers}
- 27/14868 {CCD or CID colour imagers}
- 27/14875 {Infra-red CCD or CID imagers}
- 27/14881 {of the hybrid type}
- 27/14887 {Blooming suppression}
- 27/14893 {comprising a photoconductive layer deposited on the CCD structure}
- 27/15 including semiconductor components with at least one potential-jump barrier or surface barrier specially adapted for light emission {(monolithically integrated components including semiconductor laser components [H01S 5/026](#))}
- 27/153 {in a repetitive configuration, e.g. LED bars}
- 27/156 {two-dimensional arrays}
- 27/16 including thermoelectric components with or without a junction of dissimilar materials; including thermomagnetic components (using the Peltier effect only for cooling of semiconductor or other solid state devices [H01L 23/38](#))
- 27/18 including components exhibiting superconductivity
- 27/20 including piezo-electric components; including electrostrictive components; including magnetostrictive components
- 27/22 including components using galvano-magnetic effects, e.g. Hall effects; using similar magnetic field effects
- 27/222 {Magnetic non-volatile memory structures, e.g. MRAM}
- 27/224 {comprising two-terminal components, e.g. diodes, MIM elements}
- 27/226 {comprising multi-terminal components, e.g. transistors}
- 27/228 {of the field-effect transistor type}
- 27/24 including solid state components for rectifying, amplifying or switching without a potential-jump barrier or surface barrier, {e.g. resistance switching non-volatile memory structures}
- 27/2409 {comprising two-terminal selection components, e.g. diodes}
- 27/2418 {of the metal-insulator-metal type}
- 27/2427 {of the Ovonic threshold switching type}
- 27/2436 {comprising multi-terminal selection components, e.g. transistors}
- 27/2445 {of the bipolar type}
- 27/2454 {of the vertical channel field-effect transistor type}
- 27/2463 {Arrangements comprising multiple bistable or multistable switching components of the same type on a plane parallel to the substrate, e.g. cross-point arrays, details of the horizontal layout}
- 27/2472 {the switching components having a common active material layer}
- 27/2481 {arranged in a direction perpendicular to the substrate, e.g. 3D cell arrays, details of the vertical layout}
- 27/249 {the switching components being connected to a common vertical conductor}
- 27/26 including bulk negative resistance effect components
- 27/265 {Gunn effect devices}
- 27/28 including components using organic materials as the active part, or using a combination of organic materials with other materials as the active part
- 27/281 {Integrated circuits having a three-dimensional layout}
- 27/283 {comprising components of the field-effect type}
- 27/285 {Integrated circuits with a common active layer, e.g. cross point devices}
- 27/286 {with an active region comprising an inorganic semiconductor}
- 27/288 {Combination of organic light sensitive components with organic light emitting components, e.g. optocoupler}
- 27/30 with components specially adapted for sensing infra-red radiation, light, electromagnetic radiation of shorter wavelength, or corpuscular radiation; with components specially adapted for either the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation {(combination of organic light sensitive components with organic light emitting components, e.g. optocoupler [H01L 27/288](#))}
- 27/301 {Energy conversion devices}
- 27/302 {comprising multiple junctions, e.g. tandem cells}
- 27/304 {in form of a fiber or a tube, e.g. photovoltaic fibers}
- 27/305 {Devices controlled by radiation}
- 27/307 {Imager structures}

WARNING

Group [H01L 27/307](#) is incomplete pending reclassification of documents from groups [H04N 5/3696](#) and [H04N 9/045](#).

Groups [H04N 5/3696](#), [H04N 9/045](#), and [H01L 27/307](#) should be considered in order to perform a complete search.

- 27/308 {Devices specially adapted for detecting X-ray radiation ([measuring X-radiation G01T 1/00](#))}

- 27/32 . . . with components specially adapted for light emission, e.g. flat-panel displays using organic light-emitting diodes [OLED] {(combination of organic light sensitive components with organic light emitting components, e.g. optocoupler [H01L 27/288](#))}
- 27/3202 . . . {OLEDs electrically connected in parallel}
- 27/3204 . . . {OLEDs electrically connected in series}
- 27/3206 . . . {Multi-colour light emission}
- 27/3209 {using stacked OLED}
- 27/3211 {using RGB sub-pixels}
- 27/3213 {using more than three sub-pixels, e.g. RGBW}
- 27/3216 {the areas of RGB sub-pixels being different}
- 27/3218 {characterised by the geometrical arrangement of the RGB sub-pixels}
- 27/322 {using colour filters or colour changing media [CCM]}
- 27/3223 . . . {combined with dummy elements, i.e. non-functional features}
- 27/3225 . . . {OLED integrated with another component ([H01L 27/3223](#) takes precedence)}
- 27/3227 {the other component being a light sensitive element, e.g. inorganic solar cell, inorganic photodiode ([H01L 27/288](#) takes precedence)}
- 27/323 {the other component being a touch screen}
- 27/3232 {the other component being a light modulating element, e.g. electrochromic element, photochromic element, liquid crystal element}
- 27/3234 {the other component being an imager structure ([H01L 27/146](#) takes precedence)}
- 27/3237 . . . {Displays not provided for in group [H01L 27/3241](#) and subgroups, e.g. segment-type displays}
- 27/3239 {Light emitting logos}
- 27/3241 . . . {Matrix-type displays}
- 27/3244 {Active matrix displays}
- 27/3246 {Pixel defining structures, e.g. banks}

WARNING

Group [H01L 27/3246](#) is incomplete pending reclassification of documents from group [H01L 27/3295](#).

Groups [H01L 27/3295](#) and [H01L 27/3246](#) should be considered in order to perform a complete search.

- 27/3248 {Connection of the pixel electrode to the TFT}
- 27/3251 {Double substrate, i.e. with OLED and TFT on different substrates}
- 27/3253 {Electrical connection of the two substrates}
- 27/3255 {Chiplets}
- 27/3258 {Insulating layers formed between TFT elements and OLED elements}
- 27/326 {special geometry or disposition of pixel-elements}
- 27/3262 {of TFT}
- 27/3265 {of capacitor}

- 27/3267 {Dual display, i.e. having two independent displays}
- 27/3269 {Including photosensors to control luminance}
- 27/3272 {Shielding, e.g. of TFT}
- 27/3274 {including organic thin film transistors [OTFT]}
- 27/3276 {Wiring lines}

WARNING

Group [H01L 27/3276](#) is incomplete pending reclassification of documents from group [H01L 27/3297](#).

Groups [H01L 27/3297](#) and [H01L 27/3276](#) should be considered in order to perform a complete search.

- 27/3279 {comprising structures specially adapted for lowering the resistance}
- 27/3281 {Passive matrix displays}
- 27/3283 {including banks or shadow masks}

WARNING

Group [H01L 27/3283](#) is incomplete pending reclassification of documents from group [H01L 27/3295](#).

Groups [H01L 27/3295](#) and [H01L 27/3283](#) should be considered in order to perform a complete search.

- 27/3286 {Dual display, i.e. having two independent displays}
- 27/3288 {Wiring lines}

WARNING

Group [H01L 27/3288](#) is incomplete pending reclassification of documents from group [H01L 27/3297](#).

Groups [H01L 27/3297](#) and [H01L 27/3288](#) should be considered in order to perform a complete search.

- 27/329 {comprising structures specially adapted for lowering the resistance}
- 27/3293 {Tiled displays}
- 27/3295 {including banks or shadow masks}

(Frozen)

WARNING

Group [H01L 27/3295](#) is no longer used for the classification of documents as of January 1, 2020.

The content of this group is being reclassified into groups [H01L 27/3246](#) and [H01L 27/3283](#).

Groups [H01L 27/3295](#), [H01L 27/3246](#) and [H01L 27/3283](#) should be considered in order to perform a complete search.

27/3297 {Wiring lines, e.g. power supply lines}
(Frozen)

WARNING

Group [H01L 27/3297](#) is no longer used for the classification of documents as of January 1, 2020.

The content of this group is being reclassified into groups [H01L 27/3276](#) and [H01L 27/3288](#).

Groups [H01L 27/3297](#), [H01L 27/3276](#) and [H01L 27/3288](#) should be considered in order to perform a complete search.

- 28/00** {Passive two-terminal components without a potential-jump or surface barrier for integrated circuits; Details thereof; Multistep manufacturing processes therefor (testing or measuring during manufacture [H01L 22/00](#); integration methods [H01L 21/70](#); integrated circuits [H01L 27/00](#); two-terminal components with a potential-jump or surface barrier [H01L 29/00](#); resistors in general [H01C](#); inductors in general [H01F](#); capacitors in general [H01G](#))}
- 28/10 . {Inductors}
 - 28/20 . {Resistors}
 - 28/22 . . {with an active material comprising carbon, e.g. diamond or diamond-like carbon [DLC]}
 - 28/24 . . {with an active material comprising a refractory, transition or noble metal, metal compound or metal alloy, e.g. silicides, oxides, nitrides}
 - 28/26 . . {with an active material comprising an organic conducting material, e.g. conducting polymers}
 - 28/40 . {Capacitors}
 - 28/55 . . {with a dielectric comprising a perovskite structure material}
 - 28/56 . . . {the dielectric comprising two or more layers, e.g. comprising buffer layers, seed layers, gradient layers}
 - 28/57 . . . {comprising a barrier layer to prevent diffusion of hydrogen or oxygen}
 - 28/60 . . {Electrodes}
 - 28/65 . . . {comprising a noble metal or a noble metal oxide, e.g. platinum (Pt), ruthenium (Ru), ruthenium dioxide (RuO₂), iridium (Ir), iridium dioxide (IrO₂)}
 - 28/75 . . . {comprising two or more layers, e.g. comprising a barrier layer and a metal layer}
 - 28/82 . . . {with an enlarged surface, e.g. formed by texturisation}
 - 28/84 {being a rough surface, e.g. using hemispherical grains}
 - 28/86 {having horizontal extensions}
 - 28/87 {made by depositing layers, e.g. by depositing alternating conductive and insulating layers}
 - 28/88 {made by patterning layers, e.g. by etching conductive layers}
 - 28/90 {having vertical extensions}
 - 28/91 {made by depositing layers, e.g. by depositing alternating conductive and insulating layers}
 - 28/92 {made by patterning layers, e.g. by etching conductive layers}

29/00

Semiconductor devices adapted for rectifying, amplifying, oscillating or switching, or capacitors or resistors with at least one potential-jump barrier or surface barrier, e.g. PN junction depletion layer or carrier concentration layer; Details of semiconductor bodies or of electrodes thereof; {Multistep manufacturing processes therefor} ([H01L 31/00](#) - [H01L 47/00](#), [H01L 51/05](#) take precedence; processes or apparatus adapted for the manufacture or treatment thereof or of parts thereof [H01L 21/00](#); details other than of semiconductor bodies or of electrodes thereof [H01L 23/00](#); devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#); {passive two-terminal components without a potential-jump or surface barrier for integrated circuits, details thereof and multistep manufacturing processes therefor [H01L 28/00](#); } resistors in general [H01C](#); capacitors in general [H01G](#), {e.g. ceramic barrier-layer capacitors [H01G 4/1272](#)})

NOTE

In this main group, classification is made both in groups [H01L 29/02](#) - [H01L 29/51](#) and in groups [H01L 29/66](#) - [H01L 29/94](#) if both of these sets of groups are relevant.

- 29/02 . Semiconductor bodies {; Multistep manufacturing processes therefor}
- 29/04 . . characterised by their crystalline structure, e.g. polycrystalline, cubic or particular orientation of crystalline planes (characterised by physical imperfections [H01L 29/30](#))
- 29/045 . . . {by their particular orientation of crystalline planes}
- 29/06 . . characterised by their shape; characterised by the shapes, relative sizes, or dispositions of the semiconductor regions {; characterised by the concentration or distribution of impurities within semiconductor regions}
- 29/0603 . . . {characterised by particular constructional design considerations, e.g. for preventing surface leakage, for controlling electric field concentration or for internal isolations regions (isolation regions between components [H01L 21/76](#); design considerations for integrated circuits [H01L 27/00](#); geometrical design considerations for devices [H01L 29/0657](#))}
- 29/0607 {for preventing surface leakage or controlling electric field concentration}
- 29/0611 {for increasing or controlling the breakdown voltage of reverse biased devices ([H01L 29/0661](#) takes precedence)}
- 29/0615 {by the doping profile or the shape or the arrangement of the PN junction, or with supplementary regions, e.g. junction termination extension [JTE] (LDD or drain offset regions [H01L 29/7833](#))}
- 29/0619 {with a supplementary region doped oppositely to or in rectifying contact with the semiconductor containing or contacting region, e.g. guard rings with PN or Schottky junction}

29/0623	{Buried supplementary region, e.g. buried guard ring (multi-RESURF H01L 29/0634)}	29/0826	{Pedestal collectors}
29/0626	{with a localised breakdown region, e.g. built-in avalanching region (in self-protected thyristors H01L 29/7424)}	29/083	{Anode or cathode regions of thyristors or gated bipolar-mode devices}
29/063	{Reduced surface field [RESURF] pn-junction structures}	29/0834	{Anode regions of thyristors or gated bipolar-mode devices, e.g. supplementary regions surrounding anode regions}
29/0634	{Multiple reduced surface field (multi-RESURF) structures, e.g. double RESURF, charge compensation, cool, superjunction (SJ), 3D-RESURF, composite buffer (CB) structures}	29/0839	{Cathode regions of thyristors}
29/0638	{for preventing surface leakage due to surface inversion layer, e.g. with channel stopper (channel stoppers in combination with isolation region for integrated circuits H01L 21/762)}	29/0843	{Source or drain regions of field-effect devices}
29/0642	{Isolation within the component, i.e. internal isolation}	29/0847	{of field-effect transistors with insulated gate (H01L 29/0653 takes precedence; with a passive supplementary region between source or drain and substrate related to punch-through, capacity or isolation phenomena H01L 29/1079 ; with LDD or DDD structure H01L 29/7833 ; for thin film transistors H01L 29/78618)}
29/0646	{PN junctions}	29/0852	{of DMOS transistors}
29/0649	{Dielectric regions, e.g. SiO ₂ regions, air gaps}	WARNING		
29/0653	{adjoining the input or output region of a field-effect device, e.g. the source or drain region}	Groups H01L 29/0852 – H01L 29/0886 are incomplete pending reclassification of documents from group H01L 29/0847 and H01L 29/7801 .		
29/0657	{characterised by the shape of the body}	Groups H01L 29/0852 – H01L 29/0886 and H01L 29/0847 , H01L 29/7801 should be considered in order to perform a complete search.		
29/0661	{specially adapted for altering the breakdown voltage by removing semiconductor material at, or in the neighbourhood of, a reverse biased junction, e.g. by bevelling, moat etching, depletion etching}	29/0856	{Source regions}
29/0665	{the shape of the body defining a nanostructure (nanotechnology per se B82B)}	29/086	{Impurity concentration or distribution}
29/0669	{Nanowires or nanotubes (carbon nanotubes as material of solid-state device active part H01L 51/0048)}	29/0865	{Disposition}
29/0673	{oriented parallel to a substrate}	29/0869	{Shape (cell layout H01L 29/0696)}
29/0676	{oriented perpendicular or at an angle to a substrate}	29/0873	{Drain regions}
29/068	{comprising a junction}	29/0878	{Impurity concentration or distribution}
29/0684	{characterised by the shape, relative sizes or dispositions of the semiconductor regions or junctions between the regions}	29/0882	{Disposition}
29/0688	{characterised by the particular shape of a junction between semiconductor regions}	29/0886	{Shape}
29/0692	{Surface layout}	29/0891	{of field-effect transistors with Schottky gate}
29/0696	{of cellular field-effect devices, e.g. multicellular DMOS transistors or IGBTs}	29/0895	{Tunnel injectors}
29/08	with semiconductor regions connected to an electrode carrying current to be rectified, amplified or switched and such electrode being part of a semiconductor device which comprises three or more electrodes	29/10	with semiconductor regions connected to an electrode not carrying current to be rectified, amplified or switched and such electrode being part of a semiconductor device which comprises three or more electrodes
29/0804	{Emitter regions of bipolar transistors}	29/1004	{Base region of bipolar transistors}
29/0808	{of lateral transistors}	29/1008	{of lateral transistors}
29/0813	{Non-interconnected multi-emitter structures}	29/1012	{Base regions of thyristors (H01L 29/083 takes precedence)}
29/0817	{of heterojunction bipolar transistors (H01L 29/7375 takes precedence)}	29/1016	{Anode base regions of thyristors}
29/0821	{Collector regions of bipolar transistors}	29/102	{Cathode base regions of thyristors}
			29/1025	{Channel region of field-effect devices}
			29/1029	{of field-effect transistors}
			29/1033	{with insulated gate, e.g. characterised by the length, the width, the geometric contour or the doping structure (with channel and gate aligned in the lengthwise direction H01L 29/42376 ; with buried channel H01L 29/7838)}

- 29/1037 {and non-planar channel (resulting from the gate electrode disposition, e.g. within a trench, [H01L 29/42356](#))}
- 29/1041 {with a non-uniform doping structure in the channel region surface}
- 29/1045 {the doping structure being parallel to the channel length, e.g. DMOS like}
- 29/105 {with vertical doping variation ([H01L 29/7827](#) takes precedence)}
- 29/1054 {with a variation of the composition, e.g. channel with strained layer for increasing the mobility}
- 29/1058 {with PN junction gate}
- 29/1062 {of charge coupled devices}
- 29/1066 {Gate region of field-effect devices with PN junction gate}
- 29/107 {Substrate region of field-effect devices}
- 29/1075 {of field-effect transistors}
- 29/1079 {with insulated gate}
- 29/1083 {with an inactive supplementary region, e.g. for preventing punch-through, improving capacity effect or leakage current}
- 29/1087 {characterised by the contact structure of the substrate region, e.g. for controlling or preventing bipolar effect}
- 29/1091 {of charge coupled devices}
- 29/1095 {Body region, i.e. base region, of DMOS transistors or IGBTs ([cell layout H01L 29/0696](#))}
- 29/12 . . . characterised by the materials of which they are formed
- 29/122 . . . {Single quantum well structures (single heterojunctions, couples of materials [H01L 29/165](#), [H01L 29/205](#), [H01L 29/225](#), [H01L 29/267](#))}
- 29/125 {Quantum wire structures}
- 29/127 {Quantum box structures}
- 29/15 . . . Structures with periodic or quasi periodic potential variation, e.g. multiple quantum wells, superlattices (such structures applied for the control of light [G02F 1/017](#), applied in semiconductor lasers [H01S 5/34](#))
- NOTE**
- Group [H01L 29/15](#) takes precedence over groups [H01L 29/16](#) - [H01L 29/26](#).
- 29/151 {Compositional structures ([H01L 29/157](#) and [H01L 29/158](#) take precedence)}
- 29/152 {with quantum effects only in vertical direction, i.e. layered structures with quantum effects solely resulting from vertical potential variation}
- 29/154 {comprising at least one long range structurally disordered material, e.g. one-dimensional vertical amorphous superlattices}
- 29/155 {Comprising only semiconductor materials ([H01L 29/154](#) takes precedence)}
- 29/157 {Doping structures, e.g. doping superlattices, nipi superlattices ([delta doping in general H01L 29/365](#))}
- 29/158 {Structures without potential periodicity in a direction perpendicular to a major surface of the substrate, i.e. vertical direction, e.g. lateral superlattices, lateral surface superlattices [LSS]}
- 29/16 . . . including, apart from doping materials or other impurities, only elements of Group IV of the Periodic System
- 29/1602 {Diamond}
- 29/1604 {Amorphous materials}
- 29/1606 {Graphene}
- 29/1608 {Silicon carbide}
- 29/161 including two or more of the elements provided for in group [H01L 29/16](#) {, e.g. alloys ([H01L 29/1604](#) takes precedence)}
- 29/165 in different semiconductor regions {, e.g. heterojunctions}
- 29/167 further characterised by the doping material {([H01L 29/1604](#) takes precedence)}
- 29/18 . . . Selenium or tellurium only, apart from doping materials or other impurities
- 29/185 {Amorphous materials}
- 29/20 . . . including, apart from doping materials or other impurities, only $A_{III}B_V$ compounds
- 29/2003 {Nitride compounds}
- 29/2006 {Amorphous materials}
- 29/201 including two or more compounds {, e.g. alloys ([H01L 29/2006](#) takes precedence)}
- 29/205 in different semiconductor regions {, e.g. heterojunctions}
- 29/207 further characterised by the doping material {([H01L 29/2006](#) takes precedence)}
- 29/22 . . . including, apart from doping materials or other impurities, only $A_{II}B_{VI}$ compounds
- 29/2203 {Cd X compounds being one element of the 6th group of the Periodic System ([H01L 29/2206](#) takes precedence)}
- 29/2206 {Amorphous materials}
- 29/221 including two or more compounds {, e.g. alloys ([H01L 29/2206](#) takes precedence)}
- 29/225 in different semiconductor regions {, e.g. heterojunctions}
- 29/227 further characterised by the doping material {([H01L 29/2206](#) takes precedence)}
- 29/24 . . . including, apart from doping materials or other impurities, only semiconductor materials not provided for in groups [H01L 29/16](#), [H01L 29/18](#), [H01L 29/20](#), [H01L 29/22](#) (including organic materials [H01L 51/00](#))
- 29/242 { $A_I B_{VI}$ or $A_I B_{VII}$ compounds, e.g. Cu_2O , $Cu I$ ([H01L 29/247](#) takes precedence)}
- 29/245 {Pb compounds, e.g. PbO ([H01L 29/247](#) takes precedence)}
- 29/247 {Amorphous materials}
- 29/26 . . . including, apart from doping materials or other impurities, elements provided for in two or more of the groups [H01L 29/16](#), [H01L 29/18](#), [H01L 29/20](#), [H01L 29/22](#), [H01L 29/24](#) {, e.g. alloys}
- 29/263 {Amorphous materials}

- 29/267 in different semiconductor regions {, e.g. heterojunctions ([H01L 29/263](#) takes precedence)}
- 29/30 . . characterised by physical imperfections; having polished or roughened surface
- 29/32 . . . the imperfections being within the semiconductor body
- 29/34 . . . the imperfections being on the surface
- 29/36 . . characterised by the concentration or distribution of impurities {in the bulk material (within semiconductor regions [H01L 29/06](#))}
- 29/365 . . . {Planar doping, e.g. atomic-plane doping, delta-doping}
- 29/40 . Electrodes {; Multistep manufacturing processes therefor}
- 29/401 . . {Multistep manufacturing processes}

WARNING

Group [H01L 29/401](#) is impacted by reclassification into groups [H01L 29/4011](#), [H01L 29/40111](#), [H01L 29/40114](#) and [H01L 29/40117](#).

Groups [H01L 29/401](#), [H01L 29/4011](#), [H01L 29/40111](#), [H01L 29/40114](#) and [H01L 29/40117](#) should be considered in order to perform a complete search.

- 29/4011 . . . {for data storage electrodes}

WARNING

Group [H01L 29/4011](#) is incomplete pending reclassification of documents from group [H01L 29/401](#).

Group [H01L 29/401](#) and [H01L 29/4011](#) should be considered in order to perform a complete search.

- 29/40111 {the electrodes comprising a layer which is used for its ferroelectric properties}

WARNING

Group [H01L 29/40111](#) is incomplete pending reclassification of documents from group [H01L 29/401](#).

Group [H01L 29/401](#) and [H01L 29/40111](#) should be considered in order to perform a complete search.

- 29/40114 {the electrodes comprising a conductor-insulator-conductor-insulator-semiconductor structure}

WARNING

Group [H01L 29/40114](#) is incomplete pending reclassification of documents from group [H01L 29/401](#).

Group [H01L 29/401](#) and [H01L 29/40114](#) should be considered in order to perform a complete search.

- 29/40117 {the electrodes comprising a charge-trapping insulator}

WARNING

Group [H01L 29/40117](#) is incomplete pending reclassification of documents from group [H01L 29/401](#).

Group [H01L 29/401](#) and [H01L 29/40117](#) should be considered in order to perform a complete search.

- 29/402 . . {Field plates}
- 29/404 . . . {Multiple field plate structures}
- 29/405 . . . {Resistive arrangements, e.g. resistive or semi-insulating field plates}
- 29/407 . . . {Recessed field plates, e.g. trench field plates, buried field plates}
- 29/408 . . {with an insulating layer with a particular dielectric or electrostatic property, e.g. with static charges or for controlling trapped charges or moving ions, or with a plate acting on the insulator potential or the insulator charges, e.g. for controlling charges effect or potential distribution in the insulating layer, or with a semi-insulating layer contacting directly the semiconductor surface}
- 29/41 . . characterised by their shape, relative sizes or dispositions
- 29/413 . . . {Nanosized electrodes, e.g. nanowire electrodes comprising one or a plurality of nanowires (transparent electrodes comprising carbon nano-tubes [H01L 51/444](#), nanotechnology per se [B82B](#); nanosized carbon materials, e.g. carbon nanotubes, per se [C01B 32/15](#))}
- 29/417 . . . carrying the current to be rectified, amplified or switched
- 29/41708 {Emitter or collector electrodes for bipolar transistors}
- 29/41716 {Cathode or anode electrodes for thyristors}
- 29/41725 {Source or drain electrodes for field effect devices (with monocrystalline semiconductor on source/drain region [H01L 29/0843](#))}
- 29/41733 {for thin film transistors with insulated gate}
- 29/41741 {for vertical or pseudo-vertical devices}

NOTE

A pseudo-vertical device is a device with the drain and source electrodes on the same main surface and where the main current is vertical at least in a part of its path

- 29/4175 {for lateral devices where the connection to the source or drain region is done through at least one part of the semiconductor substrate thickness, e.g. with connecting sink or with via-hole}

NOTE

The sink or via-hole leading to the source or drain region is considered to form part of the source or drain electrode

29/41758	{for lateral devices with structured layout for source or drain region, i.e. the source or drain region having cellular, interdigitated or ring structure or being curved or angular (H01L 29/41733 - H01L 29/4175 take precedence)}	29/4236	{within a trench, e.g. trench gate electrode, groove gate electrode}
NOTE Interdigitated structure means that at least one of the source or drain region has two or more fingers		29/42364	{characterised by the insulating layer, e.g. thickness or uniformity (H01L 29/42324 and H01L 29/4234 take precedence)}
29/41766	{with at least part of the source or drain electrode having contact below the semiconductor surface, e.g. the source or drain electrode formed at least partially in a groove or with inclusions of conductor inside the semiconductor (H01L 29/41733 - H01L 29/41758 take precedence)}	29/42368	{the thickness being non-uniform}
29/41775	{characterised by the proximity or the relative position of the source or drain electrode and the gate electrode, e.g. the source or drain electrode separated from the gate electrode by side-walls or spreading around or above the gate electrode}	29/42372	{characterised by the conducting layer, e.g. the length, the sectional shape or the lay-out (H01L 29/42324 takes precedence)}
29/41783	{Raised source or drain electrodes self aligned with the gate}	29/42376	{characterised by the length or the sectional shape}
29/41791	{for transistors with a horizontal current flow in a vertical sidewall, e.g. FinFET, MuGFET}	29/4238	{characterised by the surface lay-out}
29/423	not carrying the current to be rectified, amplified or switched	29/42384	{for thin film field effect transistors, e.g. characterised by the thickness or the shape of the insulator or the dimensions, the shape or the lay-out of the conductor}
29/42304	{Base electrodes for bipolar transistors}	2029/42388	{characterised by the shape of the insulating material}
29/42308	{Gate electrodes for thyristors}	29/42392	{fully surrounding the channel, e.g. gate-all-around}
29/42312	{Gate electrodes for field effect devices}	29/42396	{for charge coupled devices}
29/42316	{for field-effect transistors}	29/43	characterised by the materials of which they are formed
29/4232	{with insulated gate}	29/432	{Heterojunction gate for field effect devices}
29/42324	{Gate electrodes for transistors with a floating gate}	29/435	{Resistive materials for field effect devices, e.g. resistive gate for MOSFET or MESFET}
29/42328	{with at least one additional gate other than the floating gate and the control gate, e.g. program gate, erase gate or select gate}	29/437	{Superconductor materials}
29/42332	{with the floating gate formed by two or more non connected parts, e.g. multi-particles floating gate}	29/45	Ohmic electrodes
29/42336	{with one gate at least partly formed in a trench}	29/452	{on AIII-BV compounds}
29/4234	{Gate electrodes for transistors with charge trapping gate insulator}	29/454	{on thin film AIII-BV compounds}
29/42344	{with at least one additional gate, e.g. program gate, erase gate or select gate}	29/456	{on silicon}
29/42348	{with trapping site formed by at least two separated sites, e.g. multi-particles trapping site}	29/458	{for thin film silicon, e.g. source or drain electrode}
29/42352	{with the gate at least partly formed in a trench}	29/47	Schottky barrier electrodes (H01L 29/435 takes precedence)}
29/42356	{Disposition, e.g. buried gate electrode (H01L 29/42324 and H01L 29/4234 take precedence)}	29/475	{on AIII-BV compounds}
		29/49	Metal-insulator-semiconductor electrodes, {e.g. gates of MOSFET (H01L 29/435 takes precedence)}
		NOTE This group covers also devices using any other conductor material in place of metal	
		29/4908	{for thin film semiconductor, e.g. gate of TFT}
		29/4916	{the conductor material next to the insulator being a silicon layer, e.g. polysilicon doped with boron, phosphorus or nitrogen (H01L 29/4908 , H01L 29/4983 take precedence)}
		29/4925	{with a multiple layer structure, e.g. several silicon layers with different crystal structure or grain arrangement (with only a vertical doping structure or vertical doping variation H01L 29/4916)}
		29/4933	{with a silicide layer contacting the silicon layer, e.g. Polycide gate (with a barrier layer between the silicide and silicon layers H01L 29/4941)}

- 29/4941 {with a barrier layer between the silicon and the metal or metal silicide upper layer, e.g. Silicide/TiN/Polysilicon}
- 29/495 {the conductor material next to the insulator being a simple metal, e.g. W, Mo ([H01L 29/4908](#), [H01L 29/4983](#) take precedence)}
- 29/4958 {with a multiple layer structure}
- 29/4966 {the conductor material next to the insulator being a composite material, e.g. organic material, TiN, MoSi₂ ([H01L 29/4908](#), [H01L 29/4983](#) take precedence)}
- 29/4975 {being a silicide layer, e.g. TiSi₂}
- 29/4983 {with a lateral structure, e.g. a Polysilicon gate with a lateral doping variation or with a lateral composition variation or characterised by the sidewalls being composed of conductive, resistive or dielectric material}
- 29/4991 {comprising an air gap}
- WARNING**
- Group [H01L 29/4991](#) is incomplete pending reclassification of documents from group [H01L 29/4983](#).
- Groups [H01L 29/4991](#) and [H01L 29/4983](#) should be considered in order to perform a complete search.
- 29/51 Insulating materials associated therewith {for MIS structures on thin film semiconductor [H01L 29/4908](#)}
- 29/511 {with a compositional variation, e.g. multilayer structures ([H01L 29/516](#) takes precedence)}
- 29/512 {the variation being parallel to the channel plane}
- 29/513 {the variation being perpendicular to the channel plane}
- 29/515 {with cavities, e.g. containing a gas}
- 29/516 {with at least one ferroelectric layer}
- 29/517 {the insulating material comprising a metallic compound, e.g. metal oxide, metal silicate ([H01L 29/518](#) takes precedence)}
- 29/518 {the insulating material containing nitrogen, e.g. nitride, oxynitride, nitrogen-doped material}
- 29/66 Types of semiconductor device {; Multistep manufacturing processes therefor}
- 29/66007 {Multistep manufacturing processes}
- 29/66015 {of devices having a semiconductor body comprising semiconducting carbon, e.g. diamond, diamond-like carbon, graphene}
- 29/66022 {the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}
- 29/6603 {Diodes}
- 29/66037 {the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}
- 29/66045 {Field-effect transistors}
- 29/66053 {of devices having a semiconductor body comprising crystalline silicon carbide}
- 29/6606 {the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}
- 29/66068 {the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}
- 29/66075 {of devices having semiconductor bodies comprising group 14 or group 13/15 materials (comprising semiconducting carbon [H01L 29/66015](#); comprising crystalline silicon carbide [H01L 29/66053](#))}
- 29/66083 {the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}
- 29/6609 {Diodes}
- 29/66098 {Breakdown diodes}
- 29/66106 {Zener diodes}
- 29/66113 {Avalanche diodes}
- 29/66121 {Multilayer diodes, e.g. PNP diodes}
- 29/66128 {Planar diodes}
- 29/66136 {PN junction diodes}
- 29/66143 {Schottky diodes}
- 29/66151 {Tunnel diodes (group 13/15 resonant tunneling diodes [H01L 29/66219](#))}
- 29/66159 {Transit time diodes, e.g. IMPATT, TRAPATT diodes}
- 29/66166 {Resistors with PN junction}
- 29/66174 {Capacitors with PN or Schottky junction, e.g. varactors (capacitors with PN junction combined with MOS control [H01L 29/66189](#))}
- 29/66181 {Conductor-insulator-semiconductor capacitors, e.g. trench capacitors}
- 29/66189 {with PN junction, e.g. hybrid capacitors}
- 29/66196 {with an active layer made of a group 13/15 material}
- 29/66204 {Diodes}
- 29/66212 {Schottky diodes}
- 29/66219 {with a heterojunction, e.g. resonant tunneling diodes [RTD]}
- 29/66227 {the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}
- 29/66234 {Bipolar junction transistors [BJT]}
- 29/66242 {Heterojunction transistors [HBT] (with an active layer made of a group 13/15 material [H01L 29/66318](#))}

29/6625	{Lateral transistors (H01L 29/66242 and H01L 29/66265 take precedence)}	29/66446	{with an active layer made of a group 13/15 material, e.g. group 13/15 velocity modulation transistor [VMT], group 13/15 negative resistance FET [NERFET]}
29/66257	{Schottky transistors}			
29/66265	{Thin film bipolar transistors (H01L 29/66242 takes precedence)}	29/66454	{Static induction transistors [SIT], e.g. permeable base transistors [PBT]}
29/66272	{Silicon vertical transistors (H01L 29/66242 , H01L 29/66257 and H01L 29/66265 take precedence)}	29/66462	{with a heterojunction interface channel or gate, e.g. HFET, HIGFET, SISFET, HJFET, HEMT}
29/6628	{Inverse transistors}	29/66469	{with one- or zero-dimensional channel, e.g. quantum wire field-effect transistors, in-plane gate transistors [IPG], single electron transistors [SET], Coulomb blockade transistors, striped channel transistors}
29/66287	{with a single crystalline emitter, collector or base including extrinsic, link or graft base formed on the silicon substrate, e.g. by epitaxy, recrystallisation, after insulating device isolation (H01L 29/6628 takes precedence)}	29/66477	{with an insulated gate, i.e. MISFET}
29/66295	{with main current going through the whole silicon substrate, e.g. power bipolar transistor}	29/66484	{with multiple gate, at least one gate being an insulated gate (H01L 29/66742 takes precedence)}
29/66303	{with multi-emitter, e.g. interdigitated, multi-cellular or distributed emitter}	29/66492	{with a pocket or a lightly doped drain selectively formed at the side of the gate}
29/6631	{with an active layer made of a group 13/15 material}	29/665	{using self aligned silicidation, i.e. salicide (formation of conductive layers comprising silicides H01L 21/28518)}
29/66318	{Heterojunction transistors}	29/66507	{providing different silicide thicknesses on the gate and on source or drain}
29/66325	{controlled by field-effect, e.g. insulated gate bipolar transistors [IGBT]}	29/66515	{using self aligned selective metal deposition simultaneously on the gate and on source or drain}
29/66333	{Vertical insulated gate bipolar transistors}	29/66522	{with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence)}
29/6634	{with a recess formed by etching in the source/emitter contact region (H01L 29/66348 takes precedence; etching of semiconductor bodies H01L 21/302)}	29/6653	{using the removal of at least part of spacer, e.g. disposable spacer}
29/66348	{with a recessed gate}	29/66537	{using a self aligned punch through stopper or threshold implant under the gate region (H01L 29/66606 takes precedence)}
29/66356	{Gated diodes, e.g. field controlled diodes [FCD], static induction thyristors [SITh], field controlled thyristors [FCTh]}	29/66545	{using a dummy, i.e. replacement gate in a process wherein at least a part of the final gate is self aligned to the dummy gate}
29/66363	{Thyristors}	29/66553	{using inside spacers, permanent or not}
29/66371	{structurally associated with another device, e.g. built-in diode (making integrated circuits H01L 21/82)}	29/6656	{using multiple spacer layers, e.g. multiple sidewall spacers}
29/66378	{the other device being a controlling field-effect device}	29/66568	{Lateral single gate silicon transistors}
29/66386	{Bidirectional thyristors}	29/66575	{where the source and drain or source and drain extensions are self-aligned to the sides of the gate (H01L 29/66606 takes precedence)}
29/66393	{Lateral or planar thyristors}	29/66583	{with initial gate mask or masking layer complementary to the prospective gate location, e.g. with dummy source and drain contacts}
29/66401	{with an active layer made of a group 13/15 material}			
29/66409	{Unipolar field-effect transistors}			
29/66416	{Static induction transistors [SIT] (with an active layer made of a group 13/15 material H01L 29/66454)}			
29/66424	{Permeable base transistors [PBT]}			
29/66431	{with a heterojunction interface channel or gate, e.g. HFET, HIGFET, SISFET, HJFET, HEMT (with an active layer made of a group 13/15 material H01L 29/66462)}			
29/66439	{with a one- or zero-dimensional channel, e.g. quantum wire FET, in-plane gate transistor [IPG], single electron transistor [SET], striped channel transistor, Coulomb blockade transistor (with an active layer made of a group 13/15 material H01L 29/66469)}			

29/6659	{with both lightly doped source and drain extensions and source and drain self-aligned to the sides of the gate, e.g. lightly doped drain [LDD] MOSFET, double diffused drain [DDD] MOSFET}	29/66719	{With a step of forming an insulating sidewall spacer}
29/66598	{forming drain [D] and lightly doped drain [LDD] simultaneously, e.g. using implantation through the wings a T-shaped layer, or through a specially shaped layer}	29/66727	{with a step of recessing the source electrode}
29/66606	{with final source and drain contacts formation strictly before final or dummy gate formation, e.g. contact first technology (H01L 29/66621 takes precedence)}	29/66734	{with a step of recessing the gate electrode, e.g. to form a trench gate electrode}
29/66613	{with a gate recessing step, e.g. using local oxidation (making recessed gate LDMOS transistors H01L 29/66704)}	29/66742	{Thin film unipolar transistors}
29/66621	{using etching to form a recess at the gate location (etching of semiconductor bodies H01L 21/302)}	29/6675	{Amorphous silicon or polysilicon transistors}
29/66628	{recessing the gate by forming single crystalline semiconductor material at the source or drain location}	29/66757	{Lateral single gate single channel transistors with non-inverted structure, i.e. the channel layer is formed before the gate}
29/66636	{with source or drain recessed by etching or first recessed by etching and then refilled}	29/66765	{Lateral single gate single channel transistors with inverted structure, i.e. the channel layer is formed after the gate}
29/66643	{with source or drain regions formed by a Schottky barrier or a conductor-insulator-semiconductor structure}	29/66772	{Monocrystalline silicon transistors on insulating substrates, e.g. quartz substrates (H01L 29/66666 takes precedence; thin film FinFETs H01L 29/66795)}
29/66651	{with a single crystalline channel formed on the silicon substrate after insulating device isolation}	29/6678	{on sapphire substrates, e.g. SOS transistors}
29/66659	{with asymmetry in the channel direction, e.g. lateral high-voltage MISFETs with drain offset region, extended drain MISFETs}	29/66787	{with a gate at the side of the channel}
29/66666	{Vertical transistors (H01L 29/66712, H01L 29/66742 take precedence)}	29/66795	{with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}
29/66674	{DMOS transistors, i.e. MISFETs with a channel accommodating body or base region adjoining a drain drift region (making lateral high-voltage MISFETs with channel well and drain offset region H01L 29/66659)}	29/66803	{with a step of doping the vertical sidewall, e.g. using tilted or multi-angled implants}
29/66681	{Lateral DMOS transistors, i.e. LDMOS transistors}	29/6681	{using dummy structures having essentially the same shape as the semiconductor body, e.g. to provide stability}
29/66689	{with a step of forming an insulating sidewall spacer (forming insulating material on a substrate H01L 21/02107)}	29/66818	{the channel being thinned after patterning, e.g. sacrificial oxidation on fin}
29/66696	{with a step of recessing the source electrode}	29/66825	{with a floating gate (H01L 29/6684 takes precedence)}
29/66704	{with a step of recessing the gate electrode, e.g. to form a trench gate electrode}	29/66833	{with a charge trapping gate insulator, e.g. MNOS transistors}
29/66712	{Vertical DMOS transistors, i.e. VDMOS transistors}	29/6684	{with a ferroelectric gate insulator}
			29/66848	{with a Schottky gate, i.e. MESFET}
			29/66856	{with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence)}
			29/66863	{Lateral single gate transistors}
			29/66871	{Processes wherein the final gate is made after the formation of the source and drain regions in the active layer, e.g. dummy-gate processes}
			29/66878	{Processes wherein the final gate is made before the formation, e.g. activation anneal, of the source and drain regions in the active layer}
			29/66886	{Lateral transistors with two or more independent gates}
			29/66893	{with a PN junction gate, i.e. JFET}

29/66901	{ with a PN homojunction gate }	29/7325	{ having an emitter-base junction leaving at a main surface and a base-collector junction leaving at a peripheral surface of the body, e.g. mesa planar transistor }
29/66909	{ Vertical transistors, e.g. tecnetrans }			
29/66916	{ with a PN heterojunction gate }	29/7327	{ Inverse vertical transistors }
29/66924	{ with an active layer made of a group 13/15 material (H01L 29/66446 takes precedence) }	29/735	Lateral transistors
29/66931	{ BJT-like unipolar transistors, e.g. hot electron transistors [HET], metal base transistors [MBT], resonant tunneling transistor [RTT], bulk barrier transistor [BBT], planar doped barrier transistor [PDBT], charge injection transistor [CHINT] }	29/737	Hetero-junction transistors
			29/7371	{ Vertical transistors }
			29/7373	{ having a two-dimensional base, e.g. modulation-doped base, inversion layer base, delta-doped base }
29/66939	{ with an active layer made of a group 13/15 material }	29/7375	{ having an emitter comprising one or more non-monocrystalline elements of group IV, e.g. amorphous silicon, alloys comprising group IV elements }
29/66946	{ Charge transfer devices }			
29/66954	{ with an insulated gate }	29/7376	{ Resonant tunnelling transistors }
29/66962	{ with a Schottky gate }	29/7378	{ comprising lattice mismatched active layers, e.g. SiGe strained layer transistors }
29/66969	. . .	{ of devices having semiconductor bodies not comprising group 14 or group 13/15 materials (comprising selenium or tellurium in uncombined form other than as impurities in semiconductor bodies of other materials, comprising cuprous oxide or cuprous iodide H01L 21/02365) }	29/739	controlled by field-effect, {e.g. bipolar static induction transistors [BSIT] (unijunction transistors H01L 29/705) }
29/66977	. .	{ Quantum effect devices, e.g. using quantum reflection, diffraction or interference effects, i.e. Bragg- or Aharonov-Bohm effects }	29/7391	{ Gated diode structures }
			29/7392	{ with PN junction gate, e.g. field controlled thyristors (FCTh), static induction thyristors (SITH) }
29/66984	. .	{ Devices using spin polarized carriers }	29/7393	{ Insulated gate bipolar mode transistors, i.e. IGBT; IGT; COMFET }
29/66992	. .	{ controllable only by the variation of applied heat (controllable by IR radiation H01L 31/00; measuring quantity of heat G01K 17/00) }	29/7394	{ on an insulating layer or substrate, e.g. thin film device or device isolated from the bulk substrate (H01L 29/7398 takes precedence) }
29/68	. .	controllable by only the electric current supplied, or only the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched	29/7395	{ Vertical transistors, e.g. vertical IGBT }
29/685	. . .	{ Hi-Lo semiconductor devices, e.g. memory devices }			NOTE
29/70	. . .	Bipolar devices			The transistor is called vertical if the emitter and the collector are not on the same main surface or, if they are on the same main surface, at least a part of the main current has a component substantially not parallel to the main surface
29/705	{ Double base diodes }			
29/72	Transistor-type devices, i.e. able to continuously respond to applied control signals			
29/73	Bipolar junction transistors			
29/7302	{ structurally associated with other devices (assemblies of devices H01L 25/00; integrated circuits H01L 27/00; IGBT H01L 29/7393) }	29/7396	{ with a non planar surface, e.g. with a non planar gate or with a trench or recess or pillar in the surface of the emitter, base or collector region for improving current density or short circuiting the emitter and base regions (H01L 29/7398 takes precedence) }
29/7304	{ the device being a resistive element, e.g. ballasting resistor (transistors integrated with resistors H01L 27/075) }			
29/7306	{ Point contact transistors }	29/7397	{ and a gate structure lying on a slanted or vertical surface or formed in a groove, e.g. trench gate IGBT }
29/7308	{ Schottky transistors }	29/7398	{ with both emitter and collector contacts in the same substrate side }
29/7311	{ Tunnel transistors }			
29/7313	{ Avalanche transistors }	29/74	Thyristor-type devices, e.g. having four-zone regenerative action { (two-terminal thyristors H01L 29/87) }
29/7315	{ Transistors with hook collector }			
29/7317	{ Bipolar thin film transistors }			
29/732	Vertical transistors			
29/7322	{ having emitter-base and base-collector junctions leaving at the same surface of the body, e.g. planar transistor }			

29/7404	{structurally associated with at least one other device (assemblies H01L 25/00; integrated circuits H01L 27/00)}	29/778	with two-dimensional charge carrier gas channel, e.g. HEMT {; with two-dimensional charge-carrier layer formed at a heterojunction interface (H01L 29/803 takes precedence)}
29/7408	{the device being a capacitor or a resistor}	29/7781	{with inverted single heterostructure, i.e. with active layer formed on top of wide bandgap layer, e.g. IHEMT}
29/7412	{the device being a diode}	29/7782	{with confinement of carriers by at least two heterojunctions, e.g. DHHEMT, quantum well HEMT, DHMODFET}
29/7416	{the device being an antiparallel diode, e.g. RCT (shorted anode structures enabling reverse conduction H01L 29/0834)}	29/7783	{using III-V semiconductor material}
29/742	{the device being a field effect transistor (for turn-on or turn-off by field effect H01L 29/745, H01L 29/749)}	29/7784	{with delta or planar doped donor layer (H01L 29/7785 takes precedence)}
29/7424	{having a built-in localised breakdown/breakover region, e.g. self-protected against destructive spontaneous, e.g. voltage breakover, firing}	29/7785	{with more than one donor layer}
29/7428	{having an amplifying gate structure, e.g. cascade (Darlington) configuration}	29/7786	{with direct single heterostructure, i.e. with wide bandgap layer formed on top of active layer, e.g. direct single heterostructure MIS-like HEMT}
29/7432	{Asymmetrical thyristors (with a particular shorted anode structure H01L 29/0834)}	29/7787	{with wide bandgap charge-carrier supplying layer, e.g. direct single heterostructure MODFET}
29/7436	{Lateral thyristors}	29/7788	{Vertical transistors}
29/744	Gate-turn-off devices	29/7789	{the two-dimensional charge carrier gas being at least partially not parallel to a main surface of the semiconductor body}
29/745	with turn-off by field effect	29/78	with field effect produced by an insulated gate (H01L 29/7725, H01L 29/775, H01L 29/778 take precedence)}
29/7455	{produced by an insulated gate structure}	29/7801	{DMOS transistors, i.e. MISFETs with a channel accommodating body or base region adjoining a drain drift region (lateral high-voltage MISFETs with channel well and drain offset region H01L 29/7835)}
29/747	Bidirectional devices, e.g. triacs	29/7802	{Vertical DMOS transistors, i.e. VDMOS transistors}
29/749	with turn-on by field effect	29/7803	{structurally associated with at least one other device (assemblies H01L 25/00; integrated circuits H01L 27/00)}
29/76	Unipolar devices {, e.g. field effect transistors}	<u>WARNING</u> Groups H01L 29/7803 – H01L 29/7808 are incomplete pending reclassification of documents from group H01L 29/7802 . Groups H01L 29/7803 – H01L 29/7808 and H01L 29/7802 should be considered in order to perform a complete search.		
29/7606	{Transistor-like structures, e.g. hot electron transistor [HET]; metal base transistor [MBT]}			
29/7613	{Single electron transistors; Coulomb blockade devices (H01L 29/7888 takes precedence)}			
29/762	Charge transfer devices			
29/765	Charge-coupled devices ({ peripheral circuits for CCD storage devices G11C 19/285 })			
29/768	with field effect produced by an insulated gate			
29/76808	{Input structures}			
29/76816	{Output structures}			
29/76825	{Structures for regeneration, refreshing, leakage compensation or the like}			
29/76833	{Buried channel CCD}			
29/76841	{Two-Phase CCD}	29/7804	{the other device being a pn-junction diode}
29/7685	{Three-Phase CCD}	29/7805	{in antiparallel, e.g. freewheel diode}
29/76858	{Four-Phase CCD}	29/7806	{the other device being a Schottky barrier diode}
29/76866	{Surface Channel CCD}	29/7808	{the other device being a breakdown diode, e.g. Zener diode}
29/76875	{Two-Phase CCD}			
29/76883	{Three-Phase CCD}			
29/76891	{Four-Phase CCD}			
29/772	Field effect transistors			
29/7722	{using static field induced regions, e.g. SIT, PBT}			
29/7725	{with delta-doped channel (H01L 29/778 takes precedence)}			
29/7727	{Velocity modulation transistors, i.e. VMT}			
29/775	with one dimensional charge carrier gas channel, e.g. quantum wire FET			

29/7809	{having both source and drain contacts on the same surface, i.e. Up-Drain VDMOS transistors}	29/7826	{with voltage or current sensing structure, e.g. emulator section, overcurrent sensing cell}
29/781	{Inverted VDMOS transistors, i.e. Source-Down VDMOS transistors}	29/7827	{Vertical transistors (H01L 29/7802 , H01L 29/78642 take precedence)}
29/7811	{with an edge termination structure (guard regions per se H01L 29/0619 ; field plates per se H01L 29/402)}	29/7828	{without inversion channel, e.g. vertical ACCUFETs, normally-on vertical MISFETs}
<u>WARNING</u>			29/783	{comprising a gate to body connection, i.e. bulk dynamic threshold voltage MOSFET (for thin film transistors H01L 29/78612 , H01L 29/78696)}
Group H01L 29/7811 is incomplete pending reclassification of documents from group H01L 29/7802 .			29/7831	{with multiple gate structure (FinFETs or MuGFETs H01L 29/7855 , thin film transistors H01L 29/78645)}
Groups H01L 29/7811 and H01L 29/7802 should be considered in order to perform a complete search.			29/7832	{the structure comprising a MOS gate and at least one non-MOS gate, e.g. JFET or MESFET gate}
29/7812	{with a substrate comprising an insulating layer, e.g. SOI-VDMOS transistors}	29/7833	{with lightly doped drain or source extension, e.g. LDD MOSFET's; DDD MOSFET's (for thin film transistors H01L 29/78618)}
29/7813	{with trench gate electrode, e.g. UMOS transistors (trench gate electrodes per se H01L 29/4236)}	29/7834	{with a non-planar structure, e.g. the gate or the source or the drain being non-planar}
29/7815	{with voltage or current sensing structure, e.g. emulator section, overcurrent sensing cell}	<u>NOTE</u>		
<u>WARNING</u>			Field oxide sunken in the substrate and not filling a groove is not an element characterising a non-planar structure		
Group H01L 29/7815 is incomplete pending reclassification of documents from group H01L 29/7802 .			29/7835	{with asymmetrical source and drain regions, e.g. lateral high-voltage MISFETs with drain offset region, extended drain MISFETs}
Groups H01L 29/7815 and H01L 29/7802 should be considered in order to perform a complete search.			29/7836	{with a significant overlap between the lightly doped extension and the gate electrode (H01L 29/7834 , H01L 29/7835 take precedence)}
29/7816	{Lateral DMOS transistors, i.e. LDMOS transistors}	29/7838	{without inversion channel, e.g. buried channel lateral MISFETs, normally-on lateral MISFETs, depletion-mode lateral MISFETs}
29/7817	{structurally associated with at least one other device (assemblies H01L 25/00 ; integrated circuits H01L 27/00)}	29/7839	{with Schottky drain or source contact}
29/7818	{the other device being a pn-junction diode}	29/78391	{the gate comprising a layer which is used for its ferroelectric properties}
29/7819	{in antiparallel, e.g. freewheel diode}	29/7841	{with floating body, e.g. programmable transistors}
29/782	{the other device being a Schottky barrier diode}	29/7842	{means for exerting mechanical stress on the crystal lattice of the channel region, e.g. using a flexible substrate (variation of the composition of the channel H01L 29/1054)}
29/7821	{the other device being a breakdown diode, e.g. Zener diode}	29/7843	{the means being an applied insulating layer}
29/7823	{with an edge termination structure (guard regions per se H01L 29/0619 ; field plates per se H01L 29/402)}	29/7845	{the means being a conductive material, e.g. silicided S/D or Gate}
29/7824	{with a substrate comprising an insulating layer, e.g. SOI-LDMOS transistors}	29/7846	{the means being located in the lateral device isolation region, e.g. STI}
29/7825	{with trench gate electrode (trench gate electrodes per se H01L 29/4236)}	29/7847	{using a memorization technique, e.g. re-crystallization under strain, bonding on a substrate having a thermal expansion coefficient different from the one of the region}

29/7848	{the means being located in the source/drain region, e.g. SiGe source and drain}	29/78621	{with LDD structure or an extension or an offset region or characterised by the doping profile}
29/7849	{the means being provided under the channel}	29/78624	{the source and the drain regions being asymmetrical}
29/785	{having a channel with a horizontal current flow in a vertical sidewall of a semiconductor body, e.g. FinFET, MuGFET}	29/78627	{with a significant overlap between the lightly doped drain and the gate electrode, e.g. GOLDD}
29/7851	{with the body tied to the substrate}	2029/7863	{with an LDD consisting of more than one lightly doped zone or having a non-homogeneous dopant distribution, e.g. graded LDD}
29/7853	{the body having a non-rectangular crosssection}	29/78633	{with a light shield}
29/7854	{with rounded corners}	29/78636	{with supplementary region or layer for improving the flatness of the device}
29/7855	{with at least two independent gates}	29/78639	{with a drain or source connected to a bulk conducting substrate}
29/7856	{with an non-uniform gate, e.g. varying doping structure, shape or composition on different sides of the fin, or different gate insulator thickness or composition on opposing fin sides (H01L 29/7855 takes precedence)}	29/78642	{Vertical transistors}
2029/7857	{of the accumulation type}	29/78645	{with multiple gate}
2029/7858	{having contacts specially adapted to the FinFET geometry, e.g. wrap-around contacts}	29/78648	{arranged on opposing sides of the channel}
29/786	Thin film transistors, {i.e. transistors with a channel being at least partly a thin film (transistors having only the source or the drain region on an insulator layer H01L 29/0653; thin film FinFETs H01L 29/785)}	29/78651	{Silicon transistors (H01L 29/78606 - H01L 29/78645 take precedence)}
NOTE			29/78654	{Monocrystalline silicon transistors}
In groups H01L 29/78651 - H01L 29/78696 , the materials specified for the transistors are the material of the channel region			29/78657	{SOS transistors}
			29/7866	{Non-monocrystalline silicon transistors}
			29/78663	{Amorphous silicon transistors}
			29/78666	{with normal-type structure, e.g. with top gate}
			29/78669	{with inverted-type structure, e.g. with bottom gate}
29/78603	{characterised by the insulating substrate or support (H01L 29/78657 takes precedence)}	29/78672	{Polycrystalline or microcrystalline silicon transistor}
29/78606	{with supplementary region or layer in the thin film or in the insulated bulk substrate supporting it for controlling or increasing the safety of the device (H01L 29/78642, H01L 29/78645 take precedence)}	29/78675	{with normal-type structure, e.g. with top gate}
29/78609	{for preventing leakage current (H01L 29/78618 takes precedence)}	29/78678	{with inverted-type structure, e.g. with bottom gate}
29/78612	{for preventing the kink- or the snapback effect, e.g. discharging the minority carriers of the channel region for preventing bipolar effect}	29/78681	{having a semiconductor body comprising $A_{III}B_V$ or $A_{II}B_{VI}$ or $A_{IV}B_{VI}$ semiconductor materials, or Se or Te}
29/78615	{with a body contact}	29/78684	{having a semiconductor body comprising semiconductor materials of Group IV not being silicon, or alloys including an element of the group IV, e.g. Ge, SiN alloys, SiC alloys (H01L 29/7869 takes precedence)}
29/78618	{characterised by the drain or the source properties, e.g. the doping structure, the composition, the sectional shape or the contact structure (silicide contacts, electrodes in general H01L 29/458)}	29/78687	{with a multilayer structure or superlattice structure}
			29/7869	{having a semiconductor body comprising an oxide semiconductor material, e.g. zinc oxide, copper aluminium oxide, cadmium stannate}
			29/78693	{the semiconducting oxide being amorphous}

29/78696	{ characterised by the structure of the channel, e.g. multichannel, transverse or longitudinal shape, length or width, doping structure, or the overlap or alignment between the channel and the gate, the source or the drain, or the contacting structure of the channel (H01L 29/78612 takes precedence; transistors having a drain offset region or a lightly doped drain [LDD] H01L 29/78621)}	29/812	with a Schottky gate {(H01L 29/7725 , H01L 29/775 , H01L 29/778 , H01L 29/806 take precedence; with Schottky contact on top of heterojunction gate H01L 29/802)}
29/788	with floating gate {(H01L 29/78391 takes precedence)}	29/8122	{ Vertical transistors (SIT , PBT H01L 29/7722)}
29/7881	{ Programmable transistors with only two possible levels of programming (H01L 29/7888 takes precedence)}	29/8124	{ with multiple gate }
29/7882	{ charging by injection of carriers through a conductive insulator, e.g. Poole-Frankel conduction }	29/8126	{ Thin film MESFET's }
29/7883	{ charging by tunnelling of carriers, e.g. Fowler-Nordheim tunnelling }	29/8128	{ with recessed gate }
29/7884	{ charging by hot carrier injection }	29/82	. .	controllable by variation of the magnetic field applied to the device
29/7885	{ Hot carrier injection from the channel }	29/84	. .	controllable by variation of applied mechanical force, e.g. of pressure
29/7886	{ Hot carrier produced by avalanche breakdown of a PN junction, e.g. FAMOS }	29/86	. .	controllable only by variation of the electric current supplied, or only the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched
29/7887	{ Programmable transistors with more than two possible different levels of programming }	29/8605	. . .	Resistors with PN junctions
29/7888	{ Transistors programmable by two single electrons }	29/861	. . .	Diodes
29/7889	{ Vertical transistors, i.e. transistors having source and drain not in the same horizontal plane }	29/8611	{ Planar PN junction diodes }
29/792	with charge trapping gate insulator, e.g. MNOS-memory transistors	29/8613	{ Mesa PN junction diodes }
29/7923	{ Programmable transistors with more than two possible different levels of programming }	29/8615	{ Hi-lo semiconductor devices, e.g. memory devices }
29/7926	{ Vertical transistors, i.e. transistors having source and drain not in the same horizontal plane }	29/8616	{ Charge trapping diodes }
29/80	with field effect produced by a PN or other rectifying junction gate {, i.e. potential-jump barrier}	29/8618	{ Diodes with bulk potential barrier, e.g. Camel diodes, Planar Doped Barrier diodes, Graded bandgap diodes }
29/802	{ with heterojunction gate, e.g. transistors with semiconductor layer acting as gate insulating layer, MIS-like transistors (H01L 29/806 takes precedence; with one dimensional electron gas H01L 29/775 ; with dimensional electron gas H01L 29/778)}	29/862	Point contact diodes
29/803	{ Programmable transistors, e.g. with charge-trapping quantum well }	29/864	Transit-time diodes, e.g. IMPATT, TRAPATT diodes
29/806	{ with Schottky drain or source contact }	29/866	Zener diodes
29/808	with a PN junction gate {, e.g. PN homojunction gate (H01L 29/7725 , H01L 29/775 , H01L 29/778 , H01L 29/806 take precedence)}	29/868	PIN diodes
29/8083	{ Vertical transistors (SIT H01L 29/7722)}	29/87	Thyristor diodes, e.g. Shockley diodes, break-over diodes
29/8086	{ Thin film JFET's }	29/872	Schottky diodes
			29/8725	{ of the trench MOS barrier type [TMBS] }
			29/88	Tunnel-effect diodes
			29/882	{ Resonant tunneling diodes, i.e. RTD, RTBD }
			29/885	Esaki diodes
			29/92	. . .	Capacitors with potential-jump barrier or surface barrier
			29/93	Variable capacitance diodes, e.g. varactors
			29/94	Metal-insulator-semiconductors, e.g. MOS
			29/945	{ Trench capacitors }
			31/00		Semiconductor devices sensitive to infra-red radiation, light, electromagnetic radiation of shorter wavelength or corpuscular radiation and specially adapted either for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation; Processes or apparatus specially adapted for the manufacture or treatment thereof or of parts thereof; Details thereof (H01L 51/42 takes precedence; devices consisting of a plurality of solid state components formed in, or on, a common substrate, other than combinations of radiation-sensitive components with one or more electric light sources, H01L 27/00)
			31/02	. .	Details

- 31/02002 . . {Arrangements for conducting electric current to or from the device in operations}
- 31/02005 . . . {for device characterised by at least one potential jump barrier or surface barrier}
- 31/02008 {for solar cells or solar cell modules}
- 31/0201 {comprising specially adapted module bus-bar structures}
- 31/02013 {comprising output lead wires elements}
- 31/02016 . . {Circuit arrangements of general character for the devices}
- 31/02019 . . . {for devices characterised by at least one potential jump barrier or surface barrier}
- 31/02021 {for solar cells (electrical connection means, e.g. junction boxes, specially adapted for structural association with photovoltaic modules [H02S 40/34](#))}
- 31/02024 {Position sensitive and lateral effect photodetectors; Quadrant photodiodes}
- 31/02027 {for devices working in avalanche mode}
- 31/0203 . . Containers; Encapsulations {, e.g. encapsulation of photodiodes}(for photovoltaic devices [H01L 31/048](#); for organic photosensitive devices [H01L 51/44](#))
- 31/0216 . . Coatings ([H01L 31/041](#) takes precedence)
- 31/02161 . . . {for devices characterised by at least one potential jump barrier or surface barrier}
- 31/02162 {for filtering or shielding light, e.g. multicolour filters for photodetectors}
- 31/02164 {for shielding light, e.g. light blocking layers, cold shields for infra-red detectors}
- 31/02165 {using interference filters, e.g. multilayer dielectric filters ([interference filters G02B 5/28](#))}
- 31/02167 {for solar cells}
- 31/02168 {the coatings being antireflective or having enhancing optical properties for the solar cells}
- 31/0224 . . Electrodes
- 31/022408 . . . {for devices characterised by at least one potential jump barrier or surface barrier}
- 31/022416 {comprising ring electrodes}
- 31/022425 {for solar cells}
- 31/022433 {Particular geometry of the grid contacts}
- 31/022441 {Electrode arrangements specially adapted for back-contact solar cells}
- 31/02245 {for metallisation wrap-through [MWT] type solar cells}
- 31/022458 {for emitter wrap-through [EWT] type solar cells, e.g. interdigitated emitter-base back-contacts}
- 31/022466 . . . {made of transparent conductive layers, e.g. TCO, ITO layers}
- 31/022475 {composed of indium tin oxide [ITO]}
- 31/022483 {composed of zinc oxide [ZnO]}
- 31/022491 {composed of a thin transparent metal layer, e.g. gold}
- 31/0232 . . Optical elements or arrangements associated with the device ([H01L 31/0236](#) takes precedence; for photovoltaic cells [H01L 31/054](#); for photovoltaic modules [H02S 40/20](#))
- 31/02322 . . . {comprising luminescent members, e.g. fluorescent sheets upon the device}
- 31/02325 . . . {the optical elements not being integrated nor being directly associated with the device}
- 31/02327 {the optical elements being integrated or being directly associated to the device, e.g. back reflectors ([optical coatings H01L 31/0216](#))}
- 31/0236 . . Special surface textures
- 31/02363 . . . {of the semiconductor body itself, e.g. textured active layers}
- 31/02366 . . . {of the substrate or of a layer on the substrate, e.g. textured ITO/glass substrate or superstrate, textured polymer layer on glass substrate}
- 31/024 . . Arrangements for cooling, heating, ventilating or temperature compensation (for photovoltaic devices [H01L 31/052](#))
- 31/0248 . characterised by their semiconductor bodies
- 31/0256 . . characterised by the material
- 31/0264 . . . Inorganic materials
- 31/0272 Selenium or tellurium
- 31/02725 {characterised by the doping material}
- 31/028 including, apart from doping material or other impurities, only elements of Group IV of the Periodic System
- 31/0284 {comprising porous silicon as part of the active layer(s) (porous silicon as antireflective layer for photodiodes [H01L 31/0216](#); for solar cells [H01L 31/02168](#))}
- 31/0288 characterised by the doping material
- 31/0296 including, apart from doping material or other impurities, only $A_{II}B_{VI}$ compounds, e.g. CdS, ZnS, HgCdTe
- 31/02963 {characterised by the doping material}
- 31/02966 {including ternary compounds, e.g. HgCdTe}
- 31/0304 including, apart from doping materials or other impurities, only $A_{III}B_V$ compounds
- 31/03042 {characterised by the doping material}
- 31/03044 {comprising a nitride compounds, e.g. GaN}
- 31/03046 {including ternary or quaternary compounds, e.g. GaAlAs, InGaAs, InGaAsP}
- 31/03048 {comprising a nitride compounds, e.g. InGaN}
- 31/0312 including, apart from doping materials or other impurities, only $A_{IV}B_{IV}$ compounds, e.g. SiC
- 31/03125 {characterised by the doping material}
- 31/032 including, apart from doping materials or other impurities, only compounds not provided for in groups [H01L 31/0272](#) - [H01L 31/0312](#)
- 31/0321 {characterised by the doping material ([H01L 31/0323](#), [H01L 31/0325](#) take precedence)}
- 31/0322 {comprising only $A_I B_{III} C_{VI}$ chalcopyrite compounds, e.g. Cu In Se₂, Cu Ga Se₂, Cu In Ga Se₂}
- 31/0323 {characterised by the doping material}
- 31/0324 {comprising only $A_{IV} B_{VI}$ or $A_{II} B_{IV} C_{VI}$ chalcogenide compounds, e.g. Pb Sn Te}
- 31/0325 {characterised by the doping material}
- 31/0326 {comprising $A_I B_{II} C_{IV} D_{VI}$ kesterite compounds, e.g. Cu₂ZnSnSe₄, Cu₂ZnSnS₄}
- 31/0327 {characterised by the doping material}

- 31/0328 including, apart from doping materials or other impurities, semiconductor materials provided for in two or more of groups [H01L 31/0272](#) - [H01L 31/032](#)
- 31/0336 in different semiconductor regions, e.g. Cu₂X/CdX hetero-junctions, X being an element of Group VI of the Periodic System
- 31/03365 {comprising only Cu₂X / CdX heterojunctions, X being an element of Group VI of the Periodic System}
- 2031/0344 {Organic materials}
- 31/0352 . . characterised by their shape or by the shapes, relative sizes or disposition of the semiconductor regions
- 31/035209 {comprising a quantum structures}
- 31/035218 {the quantum structure being quantum dots}
- 31/035227 {the quantum structure being quantum wires, or nanorods ([carbon nanotubes H01L 51/0048](#))}
- 31/035236 {Superlattices; Multiple quantum well structures}
- 31/035245 {characterised by amorphous semiconductor layers}
- 31/035254 {including, apart from doping materials or other impurities, only elements of Group IV of the Periodic System, e.g. Si-SiGe superlattices}
- 31/035263 {Doping superlattices, e.g. nipi superlattices}
- 31/035272 {characterised by at least one potential jump barrier or surface barrier}
- 31/035281 {Shape of the body}
- 31/03529 {Shape of the potential jump barrier or surface barrier}
- 31/036 . . characterised by their crystalline structure or particular orientation of the crystalline planes
- 31/0368 . . . including polycrystalline semiconductors ([H01L 31/0392 takes precedence](#))
- 31/03682 {including only elements of Group IV of the Periodic System}
- 31/03685 {including microcrystalline silicon, uc-Si}
- 31/03687 {including microcrystalline A_{IV}B_{IV} alloys, e.g. uc-SiGe, uc-SiC}
- 31/0376 . . . including amorphous semiconductors ([H01L 31/0392 takes precedence](#))
- 31/03762 {including only elements of Group IV of the Periodic System}
- 31/03765 {including A_{IV}B_{IV} compounds or alloys, e.g. SiGe, SiC}
- 31/03767 {presenting light-induced characteristic variations, e.g. Staebler-Wronski effect}
- 31/0384 . . . including other non-monocrystalline materials, e.g. semiconductor particles embedded in an insulating material ([H01L 31/0392 takes precedence](#))
- 31/03845 {comprising semiconductor nanoparticles embedded in a semiconductor matrix ([in insulating matrix H01L 31/0384](#))}
- 31/0392 . . . including thin films deposited on metallic or insulating substrates {; characterised by specific substrate materials or substrate features or by the presence of intermediate layers, e.g. barrier layers, on the substrate ([textured substrates H01L 31/02366](#))}
- 31/03921 {including only elements of Group IV of the Periodic System}
- 31/03923 {including A_{IV}B_{III}C_{VI} compound materials, e.g. CIS, CIGS}
- 31/03925 {including A_{IV}B_{VI} compound materials, e.g. CdTe, CdS}
- 31/03926 {comprising a flexible substrate}
- 31/03928 {including A_{IV}B_{III}C_{VI} compound, e.g. CIS, CIGS deposited on metal or polymer foils}
- 31/04 . . adapted as photovoltaic [PV] conversion devices ([testing thereof during manufacture {H01L 22/00}](#); [testing thereof after manufacture H02S 50/10](#))
- 31/041 . . Provisions for preventing damage caused by corpuscular radiation, e.g. for space applications
- 31/042 . . PV modules or arrays of single PV cells ([supporting structures for PV modules H02S 20/00](#))
- 31/043 . . . Mechanically stacked PV cells
- 31/044 . . . including bypass diodes ([bypass diodes in the junction box H02S 40/34](#))
- 31/0443 comprising bypass diodes integrated or directly associated with the devices, e.g. bypass diodes integrated or formed in or on the same substrate as the photovoltaic cells
- 31/0445 . . . including thin film solar cells, e.g. single thin film a-Si, CIS or CdTe solar cells
- 31/046 PV modules composed of a plurality of thin film solar cells deposited on the same substrate
- 31/0463 characterised by special patterning methods to connect the PV cells in a module, e.g. laser cutting of the conductive or active layers
- 31/0465 comprising particular structures for the electrical interconnection of adjacent PV cells in the module ([H01L 31/0463 takes precedence](#))
- 31/0468 comprising specific means for obtaining partial light transmission through the module, e.g. partially transparent thin film solar modules for windows
- 31/047 . . . PV cell arrays including PV cells having multiple vertical junctions or multiple V-groove junctions formed in a semiconductor substrate
- 31/0475 . . . PV cell arrays made by cells in a planar, e.g. repetitive, configuration on a single semiconductor substrate; PV cell microarrays ([PV modules composed of a plurality of thin film solar cells deposited on the same substrate H01L 31/046](#))
- 31/048 . . . Encapsulation of modules
- 31/0481 {characterised by the composition of the encapsulation material}
- 31/0488 {Double glass encapsulation, e.g. photovoltaic cells arranged between front and rear glass sheets}
- 31/049 Protective back sheets

- 31/05 . . . Electrical interconnection means between PV cells inside the PV module, e.g. series connection of PV cells ([electrodes H01L 31/0224](#); electrical interconnection of thin film solar cells formed on a common substrate [H01L 31/046](#); particular structures for electrical interconnecting of adjacent thin film solar cells in the module [H01L 31/0465](#); electrical interconnection means specially adapted for electrically connecting two or more PV modules [H02S 40/36](#))
- 31/0504 {specially adapted for series or parallel connection of solar cells in a module}
- 31/0508 {the interconnection means having a particular shape}
- 31/0512 {made of a particular material or composition of materials}
- 31/0516 {specially adapted for interconnection of back-contact solar cells}
- 31/052 . . Cooling means directly associated or integrated with the PV cell, e.g. integrated Peltier elements for active cooling or heat sinks directly associated with the PV cells ([cooling means in combination with the PV module H02S 40/42](#))
- 31/0521 . . . {using a gaseous or a liquid coolant, e.g. air flow ventilation, water circulation}
- 31/0525 . . . including means to utilise heat energy directly associated with the PV cell, e.g. integrated Seebeck elements
- 31/053 . . Energy storage means directly associated or integrated with the PV cell, e.g. a capacitor integrated with a PV cell ([energy storage means associated with the PV module H02S 40/38](#))
- 31/054 . . Optical elements directly associated or integrated with the PV cell, e.g. light-reflecting means or light-concentrating means
- 31/0543 . . . {comprising light concentrating means of the refractive type, e.g. lenses}
- 31/0547 . . . {comprising light concentrating means of the reflecting type, e.g. parabolic mirrors, concentrators using total internal reflection}
- 31/0549 . . . {comprising spectrum splitting means, e.g. dichroic mirrors}
- 31/055 . . . where light is absorbed and re-emitted at a different wavelength by the optical element directly associated or integrated with the PV cell, e.g. by using luminescent material, fluorescent concentrators or up-conversion arrangements
- 31/056 . . . the light-reflecting means being of the back surface reflector [BSR] type
- 31/06 . . characterised by at least one potential-jump barrier or surface barrier
- 31/061 . . . the potential barriers being of the point-contact type ([H01L 31/07 takes precedence](#))
- 31/062 . . . the potential barriers being only of the metal-insulator-semiconductor type
- 31/065 . . . the potential barriers being only of the graded gap type
- 31/068 . . . the potential barriers being only of the PN homojunction type, e.g. bulk silicon PN homojunction solar cells or thin film polycrystalline silicon PN homojunction solar cells
- 31/0682 {back-junction, i.e. rearside emitter, solar cells, e.g. interdigitated base-emitter regions back-junction cells}
- 31/0684 {double emitter cells, e.g. bifacial solar cells}
- 31/0687 Multiple junction or tandem solar cells
- 31/06875 {inverted grown metamorphic [IMM] multiple junction solar cells, e.g. III-V compounds inverted metamorphic multi-junction cells}
- 31/0693 the devices including, apart from doping material or other impurities, only $A_{III}B_V$ compounds, e.g. GaAs or InP solar cells
- 31/07 . . . the potential barriers being only of the Schottky type
- 31/072 . . . the potential barriers being only of the PN heterojunction type
- 31/0725 Multiple junction or tandem solar cells
- 31/073 comprising only $A_{II}B_{VI}$ compound semiconductors, e.g. CdS/CdTe solar cells
- 31/0735 comprising only $A_{III}B_V$ compound semiconductors, e.g. GaAs/AlGaAs or InP/GaInAs solar cells
- 31/074 comprising a heterojunction with an element of Group IV of the Periodic System, e.g. ITO/Si, GaAs/Si or CdTe/Si solar cells
- 31/0745 comprising a $A_{IV}B_{IV}$ heterojunction, e.g. Si/Ge, SiGe/Si or Si/SiC solar cells
- 31/0747 comprising a heterojunction of crystalline and amorphous materials, e.g. heterojunction with intrinsic thin layer or HIT® solar cells; solar cells
- 31/0749 including a $A_{II}B_{III}C_{VI}$ compound, e.g. CdS/CuInSe₂ [CIS] heterojunction solar cells
- 31/075 . . . the potential barriers being only of the PIN type
- 31/076 Multiple junction or tandem solar cells
- 31/077 the devices comprising monocrystalline or polycrystalline materials
- 31/078 . . . including different types of potential barriers provided for in two or more of groups [H01L 31/062](#) - [H01L 31/075](#)
- 31/08 . . in which radiation controls flow of current through the device, e.g. photoresistors
- 31/085 . . . {the device being sensitive to very short wavelength, e.g. X-ray, Gamma-rays}
- 31/09 . . Devices sensitive to infra-red, visible or ultraviolet radiation ([H01L 31/101 takes precedence](#))
- 31/095 . . . {comprising amorphous semiconductors}
- 31/10 . . characterised by at least one potential-jump barrier or surface barrier, e.g. phototransistors
- 31/101 . . . Devices sensitive to infra-red, visible or ultraviolet radiation
- 31/1013 {devices sensitive to two or more wavelengths, e.g. multi-spectrum radiation detection devices}
- 31/1016 {comprising transparent or semitransparent devices}
- 31/102 characterised by only one potential barrier or surface barrier
- 31/1025 {the potential barrier being of the point contact type}
- 31/103 the potential barrier being of the PN homojunction type

- 31/1032 {the devices comprising active layers formed only by $A_{II}B_{VI}$ compounds, e.g. HgCdTe IR photodiodes}
- 31/1035 {the devices comprising active layers formed only by $A_{III}B_V$ compounds}
- 31/1037 {the devices comprising active layers formed only by $A_{IV}B_{VI}$ compounds}
- 31/105 the potential barrier being of the PIN type
- 31/1055 {the devices comprising amorphous materials of Group IV of the Periodic System}
- 31/107 the potential barrier working in avalanche mode, e.g. avalanche photodiode
- 31/1075 {in which the active layers, e.g. absorption or multiplication layers, form an heterostructure, e.g. SAM structure}
- 31/108 the potential barrier being of the Schottky type
- 31/1085 {the devices being of the Metal-Semiconductor-Metal [MSM] Schottky barrier type}
- 31/109 the potential barrier being of the PN heterojunction type
- 31/11 characterised by two potential barriers or surface barriers, e.g. bipolar phototransistor
- 31/1105 {the device being a bipolar phototransistor}
- 31/111 characterised by at least three potential barriers, e.g. photothyristor
- 31/1113 {the device being a photothyristor}
- 31/1116 {of the static induction type}
- 31/112 characterised by field-effect operation, e.g. junction field-effect phototransistor
- 31/1121 {Devices with Schottky gate}
- 31/1122 {the device being a CCD device}
- 31/1123 {the device being a photo MESFET}
- 31/1124 {Devices with PN homojunction gate}
- 31/1125 {the device being a CCD device}
- 31/1126 {the device being a field-effect phototransistor}
- 31/1127 {Devices with PN heterojunction gate}
- 31/1128 {the device being a CCD device}
- 31/1129 {the device being a field-effect phototransistor}
- 31/113 being of the conductor-insulator-semiconductor type, e.g. metal-insulator-semiconductor field-effect transistor
- 31/1133 {the device being a conductor-insulator-semiconductor diode or a CCD device}
- 31/1136 {the device being a metal-insulator-semiconductor field-effect transistor}
- 31/115 Devices sensitive to very short wavelength, e.g. X-rays, gamma-rays or corpuscular radiation
- 31/117 of the bulk effect radiation detector type, e.g. Ge-Li compensated PIN gamma-ray detectors
- 31/1175 {Li compensated PIN gamma-ray detectors}
- 31/118 of the surface barrier or shallow PN junction detector type, e.g. surface barrier alpha-particle detectors
- 31/1185 {of the shallow PN junction detector type}
- 31/119 characterised by field-effect operation, e.g. MIS type detectors
- 31/12 structurally associated with, e.g. formed in or on a common substrate with, one or more electric light sources, e.g. electroluminescent light sources, and electrically or optically coupled thereto (semiconductor devices with at least one potential barrier or surface barrier adapted for light emission [H01L 33/00](#); amplifiers using electroluminescent element and photocell [H03F 17/00](#); electroluminescent light sources [per se](#) [H05B 33/00](#))
- 31/125 {Composite devices with photosensitive elements and electroluminescent elements within one single body}
- 31/14 the light source or sources being controlled by the semiconductor device sensitive to radiation, e.g. image converters, image amplifiers or image storage devices
- 31/141 {the semiconductor device sensitive to radiation being without a potential-jump barrier or surface barrier}
- 31/143 {the light source being a semiconductor device with at least one potential-jump barrier or surface barrier, e.g. light emitting diode}
- 31/145 {the semiconductor device sensitive to radiation being characterised by at least one potential-jump barrier or surface barrier}
- 31/147 the light sources and the devices sensitive to radiation all being semiconductor devices characterised by at least one potential or surface barrier
- 31/153 formed in, or on, a common substrate
- 31/16 the semiconductor device sensitive to radiation being controlled by the light source or sources
- 31/161 {Semiconductor device sensitive to radiation without a potential-jump or surface barrier, e.g. photoresistors}
- 31/162 {the light source being a semiconductor device with at least one potential-jump barrier or surface barrier, e.g. a light emitting diode}
- 31/164 {Optical potentiometers}
- 31/165 {the semiconductor sensitive to radiation being characterised by at least one potential-jump or surface barrier}
- 31/167 the light sources and the devices sensitive to radiation all being semiconductor devices characterised by at least one potential or surface barrier
- 31/173 formed in, or on, a common substrate
- 31/18 Processes or apparatus specially adapted for the manufacture or treatment of these devices or of parts thereof
- 31/1804 {comprising only elements of Group IV of the Periodic System}
- 31/1808 {including only Ge}
- 31/1812 {including only $A_{IV}B_{IV}$ alloys, e.g. SiGe}
- 31/1816 {Special manufacturing methods for microcrystalline layers, e.g. uc-SiGe, uc-SiC}
- 31/182 {Special manufacturing methods for polycrystalline Si, e.g. Si ribbon, poly Si ingots, thin films of polycrystalline Si}
- 31/1824 {Special manufacturing methods for microcrystalline Si, uc-Si}

31/1828	. . {the active layers comprising only A _{II} B _{VI} compounds, e.g. CdS, ZnS, CdTe}	33/0025	. . . {comprising only A _{III} B _V compounds}
31/1832	. . . {comprising ternary compounds, e.g. Hg Cd Te}	33/0029	. . . {comprising only A _{II} B _{VI} compounds}
31/1836	. . . {comprising a growth substrate not being an A _{II} B _{VI} compound}	33/0033	. . {having Schottky barriers}
31/184	. . {the active layers comprising only A _{III} B _V compounds, e.g. GaAs, InP}	33/0037	. . {having a MIS barrier layer}
31/1844	. . . {comprising ternary or quaternary compounds, e.g. Ga Al As, In Ga As P}	33/0041	. . {characterised by field-effect operation}
31/1848 {comprising nitride compounds, e.g. InGaN, InGaAlN}	33/0045	. . {the devices being superluminescent diodes}
31/1852	. . . {comprising a growth substrate not being an A _{III} B _V compound}	33/005	. {Processes}
31/1856	. . . {comprising nitride compounds, e.g. GaN}	33/0054	. . {for devices with an active region comprising only group IV elements}
31/186	. . {Particular post-treatment for the devices, e.g. annealing, impurity gettering, short-circuit elimination, recrystallisation}	33/0058	. . . {comprising amorphous semiconductors}
31/1864	. . . {Annealing}	33/0062	. . {for devices with an active region comprising only III-V compounds}
31/1868	. . . {Passivation}	33/0066	. . . {with a substrate not being a III-V compound}
31/1872	. . . {Recrystallisation}	33/007 {comprising nitride compounds}
31/1876	. . {Particular processes or apparatus for batch treatment of the devices}	33/0075	. . . {comprising nitride compounds}
31/188	. . . {Apparatus specially adapted for automatic interconnection of solar cells in a module}	33/0083	. . {for devices with an active region comprising only II-VI compounds}
31/1884	. . {Manufacture of transparent electrodes, e.g. TCO, ITO}	33/0087	. . . {with a substrate not being a II-VI compound}
31/1888	. . . {methods for etching transparent electrodes}	33/0091	. . {for devices with an active region comprising only IV-VI compounds}
31/1892	. . {methods involving the use of temporary, removable substrates}	33/0093	. . {Wafer bonding; Removal of the growth substrate}
31/1896	. . . {for thin-film semiconductors}	33/0095	. . {Post-treatment of devices, e.g. annealing, recrystallisation or short-circuit elimination}
31/20	. . such devices or parts thereof comprising amorphous semiconductor materials	33/02	. characterised by the semiconductor bodies
31/202	. . . {including only elements of Group IV of the Periodic System}	33/025	. . {Physical imperfections, e.g. particular concentration or distribution of impurities}
31/204 {including A _{IV} B _{IV} alloys, e.g. SiGe, SiC}	33/04	. . with a quantum effect structure or superlattice, e.g. tunnel junction
31/206	. . . {Particular processes or apparatus for continuous treatment of the devices, e.g. roll-to-roll processes, multi-chamber deposition}	33/06	. . . within the light emitting region, e.g. quantum confinement structure or tunnel barrier
31/208	. . . {Particular post-treatment of the devices, e.g. annealing, short-circuit elimination}	33/08	. . with a plurality of light emitting regions, e.g. laterally discontinuous light emitting layer or photoluminescent region integrated within the semiconductor body (H01L 27/15 takes precedence)
33/00	Semiconductor devices with at least one potential-jump barrier or surface barrier specially adapted for light emission; Processes or apparatus specially adapted for the manufacture or treatment thereof or of parts thereof; Details thereof (H01L 51/50 takes precedence; devices consisting of a plurality of semiconductor components formed in or on a common substrate and including semiconductor components with at least one potential-jump barrier or surface barrier, specially adapted for light emission H01L 27/15; semiconductor lasers H01S 5/00)	33/10	. . with a light reflecting structure, e.g. semiconductor Bragg reflector
	NOTE	33/105	. . . {with a resonant cavity structure}
	This group covers light emitting diodes [LEDs] or superluminescent diodes [SLDs], including LEDs or SLDs emitting infra-red [IR] light or ultra-violet [UV] light.	33/12	. . with a stress relaxation structure, e.g. buffer layer
33/0004	. {Devices characterised by their operation}	33/14	. . with a carrier transport control structure, e.g. highly-doped semiconductor layer or current-blocking structure
33/0008	. . {having p-n or hi-lo junctions}	33/145	. . . {with a current-blocking structure}
33/0012	. . . {p-i-n devices}	33/16	. . with a particular crystal structure or orientation, e.g. polycrystalline, amorphous or porous
33/0016	. . . {having at least two p-n junctions}	33/18	. . . within the light emitting region
33/002	. . {having heterojunctions or graded gap}		NOTE
			When classifying in this group, classification is also made in group H01L 33/26 or one of its subgroups in order to identify the chemical composition of the light emitting region
		33/20	. . with a particular shape, e.g. curved or truncated substrate
		33/22	. . . Roughened surfaces, e.g. at the interface between epitaxial layers
		33/24	. . . of the light emitting region, e.g. non-planar junction
		33/26	. . Materials of the light emitting region
		33/28	. . . containing only elements of group II and group VI of the periodic system

- 33/285 {characterised by the doping materials}
- 33/30 . . . containing only elements of group III and group V of the periodic system
- 33/305 {characterised by the doping materials}
- 33/32 containing nitrogen
- 33/325 {characterised by the doping materials}
- 33/34 . . . containing only elements of group IV of the periodic system
- 33/343 {characterised by the doping materials}
- 33/346 {containing porous silicon}
- 33/36 . characterised by the electrodes
- 33/38 . . with a particular shape
- 33/382 . . . {the electrode extending partially in or entirely through the semiconductor body}
- 33/385 . . . {the electrode extending at least partially onto a side surface of the semiconductor body}
- 33/387 . . . {with a plurality of electrode regions in direct contact with the semiconductor body and being electrically interconnected by another electrode layer}
- 33/40 . . Materials therefor
- 33/405 . . . {Reflective materials}
- 33/42 . . . Transparent materials
- 33/44 . characterised by the coatings, e.g. passivation layer or anti-reflective coating
- 33/46 . . Reflective coating, e.g. dielectric Bragg reflector
- 33/465 . . . {with a resonant cavity structure}
- 33/48 . characterised by the semiconductor body packages
- NOTE**
This group covers elements in intimate contact with the semiconductor body or integrated with the package
- 33/483 . . {Containers}
- 33/486 . . . {adapted for surface mounting}
- 33/50 . . Wavelength conversion elements
- 33/501 . . . {characterised by the materials, e.g. binder}
- 33/502 {Wavelength conversion materials}
- 33/504 {Elements with two or more wavelength conversion materials}
- 33/505 . . . {characterised by the shape, e.g. plate or foil}
- 33/507 . . . {the elements being in intimate contact with parts other than the semiconductor body or integrated with parts other than the semiconductor body}
- 33/508 . . . {having a non-uniform spatial arrangement or non-uniform concentration, e.g. patterned wavelength conversion layer, wavelength conversion layer with a concentration gradient of the wavelength conversion material}
- 33/52 . . Encapsulations
- 33/54 . . . having a particular shape
- 33/56 . . . Materials, e.g. epoxy or silicone resin
- 33/58 . . Optical field-shaping elements
- 33/60 . . . Reflective elements
- 33/62 . . Arrangements for conducting electric current to or from the semiconductor body, e.g. lead-frames, wire-bonds or solder balls
- 33/64 . . Heat extraction or cooling elements
- 33/641 . . . {characterized by the materials}
- 33/642 . . . {characterized by the shape}
- 33/644 . . . {in intimate contact or integrated with parts of the device other than the semiconductor body}
- 33/645 . . . {the elements being electrically controlled, e.g. Peltier elements}
- 33/647 . . . {the elements conducting electric current to or from the semiconductor body}
- 33/648 . . . {the elements comprising fluids, e.g. heat-pipes}
- 35/00 Thermoelectric devices comprising a junction of dissimilar materials, i.e. exhibiting Seebeck or Peltier effect with or without other thermoelectric effects or thermomagnetic effects; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof; Details thereof (devices consisting of a plurality of solid state components formed in or on a common substrate H01L 27/00)**
- 35/02 . Details
- 35/04 . . Structural details of the junction; Connections of leads
- 35/06 . . . detachable, e.g. using a spring
- 35/08 . . . non-detachable, e.g. cemented, sintered, soldered {, e.g. thin films}
- 35/10 . . . Connections of leads
- 35/12 . Selection of the material for the legs of the junction
- 35/14 . . using inorganic compositions
- 35/16 . . . comprising tellurium or selenium or sulfur
- 35/18 . . . comprising arsenic or antimony or bismuth (H01L 35/16 takes precedence), {e.g. A_{III}B_V compounds}
- 35/20 . . . comprising metals only (H01L 35/16, H01L 35/18 take precedence)
- 35/22 . . . comprising compounds containing boron, carbon, oxygen or nitrogen {or germanium or silicon, e.g. superconductors}
- 35/225 {Superconducting materials}
- 35/24 . . using organic compositions
- 35/26 . . using compositions changing continuously or discontinuously inside the material
- 35/28 . operating with Peltier or Seebeck effect only
- 35/30 . . characterised by the heat-exchanging means at the junction
- 35/32 . . characterised by the structure or configuration of the cell or thermocouple forming the device {including details about housing, insulation, geometry or module}
- 35/325 . . . {Cascades of thermocouples}
- 35/34 . Processes or apparatus specially adapted for peculiar to the manufacture or treatment of these devices or of parts thereof
- 37/00 Thermoelectric devices without a junction of dissimilar materials; Thermomagnetic devices, e.g. using Nernst-Ettinghausen effect; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate H01L 27/00)**
- 37/02 . using thermal change of dielectric constant, e.g. working above and below Curie point {, e.g. pyroelectric devices}
- 37/025 . . {Selection of materials}
- 37/04 . using thermal change of magnetic permeability, e.g. working above and below the Curie point {, e.g. pyromagnetic devices}

- 39/00** **Devices using superconductivity; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof**
(devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#); {light detection [G01J](#), [G02F 2/00](#); application to memories [G11C 11/44](#), [G11C 15/00](#), [G11C 19/32](#)} ; superconducting conductors cables or transmission lines [H01B 12/00](#); {microwaves [H01P 7/00](#), [H01P 11/00](#)} ; superconductive coils or windings [H01F](#); amplifiers using superconductivity [H03F 19/00](#); {impulse generators and logic circuits [H03K 3/38](#), [H03K 17/92](#), [H03K 19/195](#); lasers [H01S 3/00](#), [H01S 5/00](#)})
- NOTE**
- In this group, in the absence of an indication to the contrary, an invention is classified in the last appropriate place
- 39/005 . {Alleged superconductivity}
 - 39/02 . Details
 - 39/025 . . {for Josephson devices}
 - 39/04 . . Containers; Mountings
 - 39/045 . . . {for Josephson devices}
 - 39/06 . . characterised by the current path
 - 39/08 . . characterised by the shape of the element
 - 39/10 . . characterised by the means for switching
{between superconductive and normal states}
 - 39/12 . . characterised by the material
 - 39/121 . . . {Organic materials}
 - 39/123 {Fullerene superconductors, e.g. soccerball-shaped allotrope of carbon, e.g. C₆₀, C₉₄
(fullerenes in general [C07C 13/00](#))}
 - 39/125 . . . {Ceramic materials}
 - 39/126 {comprising copper oxide}
 - 39/128 {Multi-layered structures, e.g. super lattices}
 - 39/14 . Permanent superconductor devices
 - 39/141 . . {comprising metal borides, e.g. MgB₂}
 - 39/143 . . {comprising high Tc ceramic materials}
 - 39/145 . . {Three or more electrode devices ([H01L 39/228](#) takes precedence)}
 - 39/146 . . . {Field effect devices}
 - 39/148 . . {Abrikosov vortex devices}
 - 39/16 . Devices switchable between superconductive and normal states {, e.g. switches, current limiters
(circuits for current limitation using superconductor elements [H02H 9/023](#))}
 - 39/18 . . Cryotrons
 - 39/20 . . . Power cryotrons
 - 39/22 . Devices comprising a junction of dissimilar materials, e.g. Josephson-effect devices
 - 39/221 . . {Single electron tunnelling devices}
 - 39/223 . . {Josephson-effect devices}
 - 39/225 . . . {comprising high Tc ceramic materials}
 - 39/226 . . . {comprising metal borides, e.g. MgB₂}
 - 39/228 . . {three or more electrode devices, e.g. transistor-like structures}
 - 39/24 . Processes or apparatus peculiar to the manufacture or treatment of devices provided for in [H01L 39/00](#) or of parts thereof

- 39/2403 . . {Processes peculiar to the manufacture or treatment of composite superconductor filaments
(comprising copper oxide [H01L 39/2419](#))}
- 39/2406 . . {of devices comprising Nb or an alloy of Nb with one or more of the elements of group 4, e.g. Ti, Zr, Hf}
- 39/2409 . . {of devices comprising an intermetallic compound of type A-15, e.g. Nb₃Sn}
- 39/2412 . . {of devices comprising molybdenum chalcogenides}
- 39/2416 . . {of devices comprising nitrides or carbonitrides}
- 39/2419 . . {the superconducting material comprising copper oxide}
- 39/2422 . . . {Processes for depositing or forming superconductor layers}
- 39/2425 {from a solution}
- 39/2429 {from a suspension or slurry, e.g. screen printing; doctor blade casting}
- 39/2432 {by evaporation independent of heat source, e.g. MBE}
- 39/2435 {by sputtering}
- 39/2438 {by chemical vapour deposition [CVD]}
- 39/2441 {by metalloorganic chemical vapour deposition [MOCVD]}
- 39/2445 {by thermal spraying, e.g. plasma deposition}
- 39/2448 {Pulsed laser deposition, e.g. laser sputtering; laser ablation}
- 39/2451 {Precursor deposition followed by after-treatment, e.g. oxidation}
- 39/2454 {characterised by the substrate}
- 39/2458 {Monocrystalline substrates, e.g. epitaxial growth}
- 39/2461 {Intermediate layers, e.g. for growth control}
- 39/2464 . . . {After-treatment, e.g. patterning}
- 39/2467 {Etching}
- 39/247 {Passivation}
- 39/2474 . . . {Manufacture or deposition of contacts or electrodes}
- 39/2477 . . . {Processes including the use of precursors}
- 39/248 . . . {Processes peculiar to the manufacture or treatment of filaments or composite wires}
- 39/2483 . . . {Introducing flux pinning centres}
- 39/2487 . . {of devices comprising metal borides, e.g. MgB₂}
- 39/249 . . {Treatment of superconductive layers by irradiation, e.g. ion-beam, electron-beam, laser beam, X-rays (irradiation devices [G21K](#), [H01J](#))}
- 39/2493 . . {for Josephson devices}
- 39/2496 . . . {comprising high Tc ceramic materials}

- 41/00** Piezo-electric devices in general; Electrostrictive devices in general; Magnetostrictive devices in general; Processes or apparatus specially adapted for the manufacture or treatment thereof or of parts thereof; Details thereof (devices consisting of a plurality of solid-state components formed in or on a common substrate [H01L 27/00](#))
- WARNING**
- Groups [H01L 41/23-H01L 41/47](#) are incomplete pending reclassification of documents from group [H01L 41/22](#).
- Groups [H01L 41/23-H01L 41/47](#) and [H01L 41/22](#) should be considered in order to perform a complete search.
- 41/02 . Details
 - 41/04 . . of piezo-electric or electrostrictive devices
 - 41/042 . . . {Drive or control circuitry or methods for piezo-electric or electrostrictive devices not otherwise provided for}
 - 41/044 {for piezoelectric transformers (conversion of DC or AC power [H02M](#); for operating discharge lamps [H05B 41/282](#))}
 - 41/047 . . . Electrodes {or electrical connection arrangements}
 - 41/0471 {Individual layer electrodes of multilayer piezo-electric or electrostrictive devices, e.g. internal electrodes}
 - 41/0472 {Connection electrodes of multilayer piezo-electric or electrostrictive devices, e.g. external electrodes}
 - 41/0474 {embedded within piezo-electric or electrostrictive material, e.g. via connections}
 - 41/0475 {Further connection or lead arrangements, e.g. flexible wiring boards, terminal pins}
 - 41/0477 {Conductive materials (in general [H01B 1/00](#))}
 - 41/0478 {the principal material being non-metallic, e.g. oxide or carbon based}
 - 41/053 . . . Mounts, supports, enclosures or casings
 - 41/0533 {Further insulation means against electrical, physical or chemical damage, e.g. protective coatings}
 - 41/0536 {Mechanical prestressing means, e.g. springs (in general [F16F 1/00](#))}
 - 41/06 . . of magnetostrictive devices
 - 41/08 . Piezo-electric or electrostrictive devices
 - 41/0805 . . {based on piezo-electric or electrostrictive films or coatings}
 - 41/081 . . . {characterised by the underlying base, e.g. substrates}
 - 41/0815 {Intermediate layers, e.g. barrier, adhesion or growth control buffer layers}
 - 41/082 . . {based on piezo-electric or electrostrictive fibres}
 - 41/0825 . . {with electrical and mechanical input and output, e.g. having combined actuator and sensor parts}
 - 41/083 . . having a stacked or multilayer structure
 - 41/0831 . . . {with non-rectangular cross-section in stacking direction, e.g. polygonal, trapezoidal}
 - 41/0833 . . . {with non-rectangular cross-section orthogonal to the stacking direction, e.g. polygonal, circular}
 - 41/0835 {Annular cross-section}
 - 41/0836 {of cylindrical shape with stacking in radial direction, e.g. coaxial or spiral type rolls}
 - 41/0838 {adapted for alleviating internal stress, e.g. cracking control layers ("Sollbruchstellen")}
 - 41/087 . . formed as coaxial cables
 - 41/09 . . with electrical input and mechanical output {, e.g. actuators, vibrators (in frequency selective networks [H03H 9/00](#))}
 - 41/0906 {using longitudinal or thickness displacement combined with bending, shear or torsion displacement}
 - 41/0913 {with polygonal or rectangular shape}
 - 41/092 {with cylindrical or annular shape}
 - 41/0926 {using bending displacement, e.g. unimorph, bimorph or multimorph cantilever or membrane benders}
 - 41/0933 {Beam type}
 - 41/094 {Cantilevers, i.e. having one fixed end}
 - 41/0946 {connected at their free ends, e.g. parallelogram type}
 - 41/0953 {with multiple segments mechanically connected in series, e.g. zig-zag type}
 - 41/096 {adapted for in-plane bending displacement}
 - 41/0966 {adapted for multi-directional bending displacement}
 - 41/0973 {Membrane type}
 - 41/098 {with non-planar shape}
 - 41/0986 . . . {using longitudinal or thickness displacement only, e.g. d33 or d31 type devices}
 - 41/0993 . . . {using shear or torsion displacement, e.g. d15 type devices}
 - 41/107 . . with electrical input and electrical output {, e.g. transformers}
 - 41/113 . . with mechanical input and electrical output {, e.g. generators, sensors}
 - 41/1132 . . . {Sensors}
 - 41/1134 . . . {Beam type}
 - 41/1136 {Cantilevers}
 - 41/1138 . . . {Membrane type}
 - 41/12 . Magnetostrictive devices
 - 41/125 . . {with mechanical input and electrical output, e.g. generators, sensors}
 - 41/16 . Selection of materials
 - 41/18 . . for piezo-electric or electrostrictive devices {, e.g. bulk piezo-electric crystals}
 - 41/183 . . . {Composite materials, e.g. having 1-3 or 2-2 type connectivity}
 - 41/187 . . . Ceramic compositions {, i.e. synthetic inorganic polycrystalline compounds incl. epitaxial, quasi-crystalline materials}
 - 41/1871 {Alkaline earth metal based oxides, e.g. barium titanates}
 - 41/1873 {Alkali metal based oxides, e.g. lithium, sodium or potassium niobates}
 - 41/1875 {Lead based oxides}
 - 41/1876 {Lead zirconate titanate based}
 - 41/1878 {Bismuth based oxides}
 - 41/193 . . . Macromolecular compositions {, e.g. piezo-electric polymers}
 - 41/20 . . for magnetostrictive devices

- 41/22 . . . Processes or apparatus specially adapted for the assembly, manufacture or treatment of piezo-electric or electrostrictive devices or of parts thereof
- 41/23 . . . Forming enclosures or casings
- 41/25 . . . Assembling devices that include piezo-electric or electrostrictive parts
- 41/253 . . . Treating devices or parts thereof to modify a piezo-electric or electrostrictive property, e.g. polarisation characteristics, vibration characteristics or mode tuning
- 41/257 . . . by polarising
- 41/27 . . . Manufacturing multilayered piezo-electric or electrostrictive devices or parts thereof, e.g. by stacking piezo-electric bodies and electrodes
- 41/273 . . . by integrally sintering piezo-electric or electrostrictive bodies and electrodes
- 41/277 . . . by stacking bulk piezo-electric or electrostrictive bodies and electrodes
- 41/29 . . . Forming electrodes, leads or terminal arrangements
- 41/293 . . . Connection electrodes of multilayered piezo-electric or electrostrictive parts

NOTE

Integral individual layer electrode and connection electrode are classified in both [H01L 41/293](#) and [H01L 41/297](#)

- 41/297 . . . Individual layer electrodes of multilayered piezo-electric or electrostrictive parts

NOTE

Integral individual layer electrode and connection electrode are classified in both [H01L 41/293](#) and [H01L 41/297](#)

- 41/31 . . . Applying piezo-electric or electrostrictive parts or bodies onto an electrical element or another base
- 41/311 . . . Mounting of piezo-electric or electrostrictive parts together with semiconductor elements, or other circuit elements, on a common substrate
- 41/312 . . . by laminating or bonding of piezo-electric or electrostrictive bodies
- 41/313 . . . by metal fusing or with adhesives
- 41/314 . . . by depositing piezo-electric or electrostrictive layers, e.g. aerosol or screen printing
- 41/316 . . . by vapour phase deposition
- 41/317 . . . by liquid phase deposition
- 41/318 . . . by sol-gel deposition
- 41/319 . . . using intermediate layers, e.g. for growth control
- 41/33 . . . Shaping or machining of piezo-electric or electrostrictive bodies
- 41/331 . . . by coating or depositing using masks, e.g. lift-off
- 41/332 . . . by etching, e.g. lithography
- 41/333 . . . by moulding or extrusion
- 41/335 . . . by machining
- 41/337 . . . by polishing or grinding
- 41/338 . . . by cutting or dicing
- 41/339 . . . by punching
- 41/35 . . . Forming piezo-electric or electrostrictive materials
- 41/37 . . . Composite materials
- 41/39 . . . Inorganic materials

- 41/41 . . . by melting
- 41/43 . . . by sintering
- 41/45 . . . Organic materials
- 41/47 . . . Processes or apparatus specially adapted for the assembly, manufacture or treatment of magnetostrictive devices or of parts thereof

43/00 Devices using galvano-magnetic or similar magnetic effects; Processes or apparatus specially adapted for the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#))

- 43/02 . . . Details
- 43/04 . . . of Hall-effect devices
- 43/06 . . . Hall-effect devices
- 43/065 . . . {Semiconductor Hall-effect devices}
- 43/08 . . . Magnetic-field-controlled resistors
- 43/10 . . . Selection of materials
- 43/12 . . . Processes or apparatus specially adapted for the manufacture or treatment of these devices or of parts thereof
- 43/14 . . . for Hall-effect devices

45/00 Solid state devices adapted for rectifying, amplifying, oscillating or switching without a potential-jump barrier or surface barrier, e.g. dielectric triodes; Ovshinsky-effect devices; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate [H01L 27/00](#); devices using superconductivity [H01L 39/00](#); piezo-electric devices [H01L 41/00](#); bulk negative resistance effect devices [H01L 47/00](#); {memories [G11C 11/34](#); [G11C 13/0002](#); amplifying circuits [H03F 11/00](#); pulse generation [H03K 3/02](#); electronic switching circuits [H03K 17/00](#); logic circuits [H03K 19/00](#)})

- 45/005 . . . {Charge density wave transport devices}
- 45/02 . . . Solid state travelling-wave devices
- 45/04 . . . {Bistable or multistable switching devices, e.g. for resistance switching non-volatile memory}
- 45/06 . . . {based on solid-state phase change, e.g. between amorphous and crystalline phases, Ovshinsky effect}
- 45/065 . . . {between different crystalline phases, e.g. cubic and hexagonal}
- 45/08 . . . {based on migration or redistribution of ionic species, e.g. anions, vacancies}
- 45/085 . . . {the species being metal cations, e.g. programmable metallization cells}
- 45/10 . . . {based on bulk electronic defects, e.g. trapping of electrons}
- 45/12 . . . {Details}
- 45/1206 . . . {Three or more terminal devices, e.g. transistor like devices}
- 45/1213 . . . {Radiation or particle beam assisted switching devices, e.g. optically controlled devices}
- 45/122 . . . {Device geometry}
- 45/1226 . . . {adapted for essentially horizontal current flow, e.g. bridge type devices}
- 45/1233 . . . {adapted for essentially vertical current flow, e.g. sandwich or pillar type devices}

45/124 {on sidewalls of dielectric structures, e.g. mesa or cup type devices}	49/00	Solid state devices not provided for in groups H01L 27/00 - H01L 47/00 and H01L 51/00 and not provided for in any other subclass; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof
45/1246 {Further means within the switching material region to limit current flow, e.g. constrictions}	49/003	. {Devices using Mott metal-insulator transition, e.g. field effect transistors}
45/1253	. . . {Electrodes}	49/006	. {Quantum devices, e.g. Quantum Interference Devices, Metal Single Electron Transistor (using semiconductors in the active part H01L 29/00)}
45/126 {adapted for resistive heating}	49/02	. Thin-film or thick-film devices
45/1266 {adapted for supplying ionic species}	51/00	Solid state devices using organic materials as the active part, or using a combination of organic materials with other materials as the active part; Processes or apparatus specially adapted for the manufacture or treatment of such devices, or of parts thereof (devices consisting of a plurality of components formed in or on a common substrate H01L 27/28; thermoelectric devices using organic material H01L 35/00, H01L 37/00; piezoelectric, electrostrictive or magnetostrictive elements using organic material H01L 41/00)
45/1273 {adapted for electric field or current focusing, e.g. tip shaped}	51/0001	. {Processes specially adapted for the manufacture or treatment of devices or of parts thereof (multistep processes H01L 51/0098 , H01L 51/05 , H01L 51/42 , H01L 51/50)}
45/128	. . . {Thermal details}	51/0002	. . {Deposition of organic semiconductor materials on a substrate}
45/1286 {Heating or cooling means other than resistive heating electrodes, e.g. heater in parallel}	51/0003	. . . {using liquid deposition, e.g. spin coating}
45/1293 {Thermal insulation means}	51/0004 {using printing techniques, e.g. ink-jet printing, screen printing}
45/14	. . {Selection of switching materials}	51/0005 {ink-jet printing}
45/141	. . . {Compounds of sulfur, selenium or tellurium, e.g. chalcogenides}	51/0006 {Electrolytic deposition using an external electrical current, e.g. in-situ electropolymerisation}
45/142 {Sulfides, e.g. CuS}	51/0007 {characterised by the solvent}
45/143 {Selenides, e.g. GeSe}	51/0008	. . . {using physical deposition, e.g. sublimation, sputtering}
45/144 {Tellurides, e.g. GeSbTe}	51/0009 {using laser ablation}
45/145	. . . {Oxides or nitrides}	51/001 {Vacuum deposition}
45/146 {Binary metal oxides, e.g. TaOx}	51/0011 {selective deposition, e.g. using a mask}
45/147 {Complex metal oxides, e.g. perovskites, spinels}	51/0012	. . . {special provisions for the orientation or alignment of the layer to be deposited}
45/148	. . . {Other compounds of groups 13-15, e.g. elemental or compound semiconductors}	51/0013	. . . {using non liquid printing techniques, e.g. thermal transfer printing from a donor sheet}
45/149 {Carbon or carbides}	51/0014	. . {for changing the shape of the device layer, e.g. patterning}
45/16	. . {Manufacturing}	51/0015	. . . {by selective transformation of an existing layer}
45/1608	. . . {Formation of the switching material, e.g. layer deposition}	51/0016	. . . {lift off techniques}
45/1616 {by chemical vapor deposition, e.g. MOCVD, ALD}	51/0017	. . . {etching of an existing layer}
45/1625 {by physical vapor deposition, e.g. sputtering}	51/0018 {using photolithographic techniques}
45/1633 {by conversion of electrode material, e.g. oxidation}	51/0019 {using printing techniques, e.g. applying the etch liquid using an ink jet printer}
45/1641	. . . {Modification of the switching material, e.g. post-treatment, doping}	51/002	. . {Making n- or p-doped regions}
45/165 {by implantation}	51/0021	. . {Formation of conductors}
45/1658 {by diffusion, e.g. photo-dissolution}	51/0022	. . . {using printing techniques, e.g. ink jet printing}
45/1666	. . . {Patterning of the switching material}	51/0023	. . . {Patterning of conductive layers}
45/1675 {by etching of pre-deposited switching material layers, e.g. lithography}	51/0024	. . {for forming devices by joining two substrates together, e.g. lamination technique}
45/1683 {by filling of openings, e.g. damascene method}	51/0025	. . {Purification process of the organic semiconductor material}
45/1691 {Patterning process specially adapted for achieving sub-lithographic dimensions, e.g. using spacers}		
47/00	Bulk negative resistance effect devices, e.g. Gunn-effect devices; Processes or apparatus peculiar to the manufacture or treatment thereof or of parts thereof (devices consisting of a plurality of solid state components formed in or on a common substrate H01L 27/00)		
47/005	. {Processes or apparatus peculiar to the manufacture or treatment of these devices or of parts thereof (not peculiar thereto H01L 21/00)}		
47/02	. Gunn-effect devices {or transferred electron devices}		
47/023	. . {controlled by electromagnetic radiation}		
47/026	. . {Gunn diodes (H01L 47/02 takes precedence)}		

- 51/0026 . . {Thermal treatment of the active layer, e.g. annealing}
- 51/0027 . . . {using coherent electromagnetic radiation, e.g. laser annealing}
- 51/0028 . . . {Thermal treatment in the presence of solvent vapors, e.g. solvent annealing}
- 51/0029 . . {Special provisions for controlling the atmosphere during processing ([H01L 51/0026 takes precedence](#))}
- 51/003 . . {using a temporary substrate}
- 51/0031 . . {Testing, e.g. accelerated lifetime tests of photoelectric devices}
- 51/0032 . {Selection of organic semiconducting materials, e.g. organic light sensitive or organic light emitting materials}
- NOTE**
- This group only covers the selection of organic materials for their electrical or other properties insofar as they are specific for their use in devices covered by the group [H01L 51/00](#). For the materials per se, see the relevant subclasses.
- Attention is drawn to the following places:
- organic materials in general [C07C](#), [C07D](#), [C07F](#), [C08L](#);
 - organic materials as electrical conductors [H01B 1/12](#);
 - organic materials as electrical insulators [H01B 3/18](#)
- 51/0034 . . {Organic polymers or oligomers ([organic macromolecular compounds or compositions per se C08](#))}
- 51/0035 . . . {comprising aromatic, heteroaromatic, or aryllic chains, e.g. polyaniline ([per se C08G 73/026](#)), polyphenylene ([per se C08G 61/10](#)), polyphenylene vinylene ([per se C08G 61/02](#))}
- 51/0036 {Heteroaromatic compounds comprising sulfur or selen, e.g. polythiophene ([per se C08G 61/126](#))}
- 51/0037 {Polyethylene dioxythiophene [PEDOT] and derivatives}
- 51/0038 {Poly-phenylenevinylene and derivatives ([per se C08G 61/10](#))}
- 51/0039 {Polyfluorene and derivatives}
- 51/004 . . . {comprising aliphatic or olefinic chains, e.g. poly N-vinylcarbazol, PVC, PTFE}
- 51/0041 {Poly acetylene ([per se C08G 61/04](#), [C08F 38/02](#), [C08F 138/02](#), [C08F 238/02](#)) or derivatives}
- 51/0042 {poly N-vinylcarbazol and derivatives}
- 51/0043 . . . {Copolymers}
- 51/0044 . . . {Ladder-type polymers}
- 51/0045 . . {Carbon containing materials, e.g. carbon nanotubes, fullerenes ([per se C01B 32/15](#))}
- 51/0046 . . . {Fullerenes, e.g. C₆₀, C₇₀}
- 51/0047 {comprising substituents, e.g. PCBM}
- 51/0048 . . . {Carbon nanotubes}
- 51/0049 {comprising substituents}
- 51/005 . . {Macromolecular systems with low molecular weight, e.g. cyanine dyes, coumarine dyes, tetrathiafulvalene ([H01L 51/0045](#), [H01L 51/0077](#), [H01L 51/0093](#), [H01L 51/0094 take precedence](#))}
- 51/0051 {Charge transfer complexes}
- 51/0052 {Polycyclic condensed aromatic hydrocarbons, e.g. anthracene}
- 51/0053 {Aromatic anhydride or imide compounds, e.g. perylene tetra-carboxylic dianhydride, perylene tetracarboxylic diimide}
- 51/0054 {containing four rings, e.g. pyrene}
- 51/0055 {containing five rings, e.g. pentacene}
- 51/0056 {containing six or more rings}
- 51/0057 {containing at least one aromatic ring having 7 or more carbon atoms, e.g. azulene}
- 51/0058 {containing more than one polycyclic condensed aromatic rings, e.g. bis-anthracene}
- 51/0059 {Amine compounds having at least two aryl rest on at least one amine-nitrogen atom, e.g. triphenylamine ([per se C07C 211/00](#))}
- 51/006 {comprising polycyclic condensed aromatic hydrocarbons as substituents on the nitrogen atom}
- 51/0061 {comprising heteroaromatic hydrocarbons as substituents on the nitrogen atom}
- 51/0062 {aromatic compounds comprising a hetero atom, e.g.: N,P,S}
- 51/0064 {Cyanine Dyes}
- 51/0065 {comprising only oxygen as heteroatom}
- 51/0067 {comprising only nitrogen as heteroatom ([H01L 51/0064 takes precedence](#))}
- 51/0068 {comprising only sulfur as heteroatom}
- 51/0069 {comprising two or more different heteroatoms per ring, e.g. S and N ([H01L 51/0064 takes precedence](#))}
- 51/007 {Oxadiazole compounds}
- 51/0071 {Polycyclic condensed heteroaromatic hydrocarbons}
- 51/0072 {comprising only nitrogen in the heteroaromatic polycondensed ringsystem, e.g. phenanthroline, carbazole}
- 51/0073 {comprising only oxygen in the heteroaromatic polycondensed ringsystem, e.g. coumarine dyes}
- 51/0074 {comprising only sulfur in the heteroaromatic polycondensed ringsystem, e.g. benzothiophene}
- 51/0075 . . {Langmuir Blodgett films ([per se B05D 1/202](#))}
- 51/0076 . . {Liquid crystalline materials ([per se C09K 19/00](#))}
- 51/0077 . . {Coordination compounds, e.g. porphyrin}
- 51/0078 . . . {Phthalocyanine ([per se C09B 47/04](#))}
- 51/0079 . . . {Metal complexes comprising a IIIB-metal (B, Al, Ga, In or Tl), e.g. Tris (8-hydroxyquinoline) gallium (Ga₃)}
- 51/008 {comprising boron}
- 51/0081 {comprising aluminium, e.g. Al₃}
- 51/0082 {comprising gallium}
- 51/0083 . . . {Metal complexes comprising an iron-series metal, e.g. Fe, Co, Ni}
- 51/0084 . . . {Transition metal complexes, e.g. Ru(II)polypyridine complexes}
- 51/0085 {comprising Iridium}
- 51/0086 {comprising Ruthenium}
- 51/0087 {comprising platinum}
- 51/0088 {comprising osmium}

- 51/0089 . . . {Metal complexes comprising Lanthanides or Actinides, e.g. Eu}
- 51/009 . . . {Polynuclear complexes, i.e. complexes having two or more metal centers}
- 51/0091 . . . {Metal complexes comprising a IB-metal (Cu, Ag, Au)}
- 51/0092 . . . {Metal complexes comprising a IIB-metal (Zn, Cd, Hg)}
- 51/0093 . . {Biomolecules or bio-macromolecules, e.g. proteins, ATP, chlorophyll, beta-carotene, lipids, enzymes}
- 51/0094 . . {Silicon-containing organic semiconductors}
- 51/0095 . . {Starburst compounds}
- 51/0096 . {Substrates}
- 51/0097 . . {flexible substrates}
- 51/0098 . {Molecular electronic devices ([molecular computers G06F 15/80](#); [molecular memories G11C 11/00](#), [G11C 13/02](#))}
- 51/05 . specially adapted for rectifying, amplifying, oscillating or switching, or capacitors or resistors with at least one potential- jump barrier or surface barrier {multistep processes for their manufacture}
- 51/0504 . . {the devices being controllable only by the electric current supplied or the electric potential applied, to an electrode which does not carry the current to be rectified, amplified or switched, e.g. three-terminal devices}
- 51/0508 . . . {Field-effect devices, e.g. TFTs}
- 51/0512 {insulated gate field effect transistors}
- 51/0516 {characterised by the gate dielectric}
- 51/052 {the gate dielectric comprising only organic materials}
- 51/0525 {the gate dielectric comprising only inorganic materials}
- 51/0529 {the gate dielectric having a multilayered structure}
- 51/0533 {Combinations of organic and inorganic layers}
- 51/0537 {the gate dielectric comprising composite materials, e.g. TiO₂ particles in a polymer matrix}
- 51/0541 {Lateral single gate single channel transistors with non inverted structure, i.e. the organic semiconductor layer is formed before the gate electrode}
- 51/0545 {Lateral single gate single channel transistors with inverted structure, i.e. the organic semiconductor layer is formed after the gate electrode}
- 51/055 {characterised by the gate conductor}
- 51/0554 {the transistor having two or more gate electrodes}
- 51/0558 {characterised by the channel of the transistor}
- 51/0562 {the channel comprising two or more active layers, e.g. forming pn - hetero junction}
- 51/0566 {the channel comprising a composite layer, e.g. a mixture of donor and acceptor moieties, forming pn - bulk hetero junction}
- 51/057 {having a vertical structure, e.g. vertical carbon nanotube field effect transistors [CNT-FETs]}
- 51/0575 . . {the devices being controllable only by variation of the electric current supplied or the electric potential applied, to one or more of the electrodes carrying the current to be rectified, amplified, oscillated or switched, e.g. two-terminal devices}
- 51/0579 . . . {Schottky diodes}
- 51/0583 . . . {comprising an organic/organic junction, e.g. hetero-junction}
- 51/0587 . . . {comprising an organic/inorganic hetero-junction, e.g. hetero-junction}
- 51/0591 . . . {Bi-stable switching devices}
- 51/0595 . . . {molecular electronic devices ([molecular computers G06F 15/80](#); [molecular memories G11C 11/00](#), [G11C 13/02](#))}
- 51/10 . . Details of devices
- 51/102 . . . {Electrodes}
- 51/105 {Ohmic contacts, e.g. source and drain electrodes}
- 51/107 . . . {Passivation, containers, encapsulations}
- 51/42 . specially adapted for sensing infra-red radiation, light, electro-magnetic radiation of shorter wavelength or corpuscular radiation and adapted for the conversion of the energy of such radiation into electrical energy or for the control of electrical energy by such radiation {using organic materials as the active part, or using a combination of organic materials with other material as the active part; Multistep processes for their manufacture}
- 51/4206 . . {Metal-organic semiconductor-metal devices}
- 51/4213 . . {Comprising organic semiconductor-inorganic semiconductor hetero-junctions ([H01L 51/4253 takes precedence](#))}
- 51/422 . . . {Majority carrier devices using sensitisation of widebandgap semiconductors, e.g. TiO₂ ([photoelectrochemical devices with a liquid or solid electrolyte H01G 9/20](#))}
- 51/4226 {the wideband gap semiconductor comprising titanium oxide, e.g. TiO₂}
- 51/4233 {the wideband gap semiconductor comprising zinc oxide, e.g. ZnO}
- 51/424 . . {comprising organic semiconductor-organic semiconductor hetero-junctions ([H01L 51/4253 takes precedence](#))}
- 51/4246 . . . {comprising multi-junctions, e.g. double hetero-junctions}
- 51/4253 . . {comprising bulk hetero-junctions, e.g. interpenetrating networks}
- 51/426 . . . {comprising inorganic nanostructures, e.g. CdSe nanoparticles}
- 51/4266 {the inorganic nanostructures being nanotubes or nanowires, e.g. CdTe nanotubes in P3HT}
- 51/4273 . . . {comprising blocking layers, e.g. exciton blocking layers}
- 51/428 . . {light sensitive field effect devices}
- 51/4286 . . {Devices having a m-i-s structure}
- 51/4293 . . {Devices having a p-i-n structure}
- 51/44 . . Details of devices
- 51/441 . . . {Electrodes}
- 51/442 {transparent electrodes, e.g. ITO, TCO}
- 51/444 {comprising carbon nanotubes}

- 51/445 {comprising arrangements for extracting the current from the cell, e.g. metal finger grid systems to reduce the serial resistance of transparent electrodes}
- 51/447 . . . {Light trapping means}
- 51/448 . . . {Passivation, containers, encapsulations}
- 51/50 . specially adapted for light emission, e.g. organic light emitting diodes [OLED] or polymer light emitting devices [PLED] ([organic semiconductor lasers H01S 5/36](#) ; circuit arrangements for OLED or PLED [H05B 45/60](#); control arrangements for organic electroluminescent displays [G09G 3/3208](#))
- 51/5004 . . {characterised by the interrelation between parameters of constituting active layers, e.g. HOMO-LUMO relation}
- 51/5008 . . {Intermediate layers comprising a mixture of materials of the adjoining active layers}
- 51/5012 . . {Electroluminescent [EL] layer}
- 51/5016 . . . {Triplet emission}
- 51/502 . . . {comprising active inorganic nanostructures, e.g. luminescent quantum dots}
- 51/5024 . . . {having a host comprising an emissive dopant and further additive materials, e.g. for improving the dispersability, for improving the stabilisation, for assisting energy transfer}
- 51/5028 {for assisting energy transfer, e.g. sensitization}
- 51/5032 . . . {Light emitting electrochemical cells [LEC], i.e. with mobile ions in the active layer}
- 51/5036 . . . {Multi-colour light emission, e.g. colour tuning, polymer blend, stack of electroluminescent layers}
- 51/504 {Stack of electroluminescent layers}
- 51/5044 {with spacer layers between the emissive layers}
- 51/5048 . . {Carrier transporting layer}
- 51/5052 . . . {Doped transporting layer}

(Frozen)

WARNING

Groups [H01L 51/5052](#) is no longer used for the classification of documents as of January 1, 2020.

The content of this group is being reclassified into groups [H01L 51/506](#) and [H01L 51/5076](#).

Groups [H01L 51/5052](#), [H01L 51/506](#) and [H01L 51/5076](#) should be considered in order to perform a complete search.

- 51/5056 . . . {Hole transporting layer}
- 51/506 {comprising a dopant}

WARNING

Group [H01L 51/506](#) is incomplete pending reclassification of documents from group [H01L 51/5052](#).

Groups [H01L 51/5052](#) and [H01L 51/506](#) should be considered in order to perform a complete search.

- 51/5064 {having a multilayered structure}
- 51/5068 {arranged between the light emitting layer and the cathode}
- 51/5072 . . . {Electron transporting layer}

- 51/5076 {comprising a dopant}

WARNING

Group [H01L 51/5076](#) is incomplete pending reclassification of documents from group [H01L 51/5052](#).

Groups [H01L 51/5052](#) and [H01L 51/5076](#) should be considered in order to perform a complete search.

- 51/508 {having a multilayered structure}
- 51/5084 {arranged between the light emitting layer and the anode}
- 51/5088 . . {Carrier injection layer}
- 51/5092 . . . {Electron injection layer}
- 51/5096 . . {Carrier blocking layer}
- 51/52 . . Details of devices
- 51/5203 . . . {Electrodes}
- 51/5206 {Anodes, i.e. with high work-function material}
- 51/5209 {characterised by the shape}
- 51/5212 {combined with auxiliary electrode, e.g. ITO layer combined with metal lines}
- 51/5215 {composed of transparent multilayers}
- 51/5218 {Reflective anodes, e.g. ITO combined with thick metallic layer}
- 51/5221 {Cathodes, i.e. with low work-function material}
- 51/5225 {characterised by the shape}
- 51/5228 {combined with auxiliary electrodes}
- 51/5231 {composed of opaque multilayers}
- 51/5234 {Transparent, e.g. including thin metal film}
- 51/5237 . . . {Passivation; Containers; Encapsulation, e.g. against humidity}
- 51/524 {Sealing arrangements having a self-supporting structure, e.g. containers}
- 51/5243 {the sealing arrangements being made of metallic material}
- 51/5246 {characterised by the peripheral sealing arrangements, e.g. adhesives, sealants}
- 51/525 {Vertical spacers, e.g. arranged between the sealing arrangement and the OLED}
- 51/5253 {Protective coatings}
- 51/5256 {having repetitive multilayer structures}
- 51/5259 {including getter material or desiccant}
- 51/5262 . . . {Arrangements for extracting light from the device}
- 51/5265 {comprising a resonant cavity structure, e.g. Bragg reflector pair}
- 51/5268 {Scattering means}
- 51/5271 {Reflective means}
- 51/5275 {Refractive means, e.g. lens}
- 51/5278 {comprising a repetitive electroluminescent unit between one set of electrodes}
- 51/5281 . . . {Arrangements for contrast improvement, e.g. preventing reflection of ambient light}
- 51/5284 {comprising a light absorbing layer, e.g. black layer}
- 51/5287 . . . {OLED having a fiber structure}
- 51/529 . . . {Arrangements for heating or cooling}
- 51/5293 . . . {Arrangements for polarized light emission ([H01L 51/5281](#) takes precedence)}
- 51/5296 . . . {Light emitting organic transistors}

51/56	. . Processes or apparatus specially adapted for the manufacture or treatment of such devices or of parts thereof	2221/68336 involving stretching of the auxiliary support post dicing
2221/00	Processes or apparatus adapted for the manufacture or treatment of semiconductor or solid state devices or of parts thereof covered by H01L 21/00	2221/6834 used to protect an active side of a device or wafer
2221/10	. Applying interconnections to be used for carrying current between separate components within a device	2221/68345 used as a support during the manufacture of self supporting substrates
2221/1005	. . Formation and after-treatment of dielectrics	2221/6835 used as a support during build up manufacturing of active devices
2221/101	. . . Forming openings in dielectrics	2221/68354 used to support diced chips prior to mounting
2221/1015 for dual damascene structures	2221/68359 used as a support during manufacture of interconnect decals or build up layers
2221/1021 Pre-forming the dual damascene structure in a resist layer	2221/68363 used in a transfer process involving transfer directly from an origin substrate to a target substrate without use of an intermediate handle substrate
2221/1026 the via being formed by burying a sacrificial pillar in the dielectric and removing the pillar	2221/68368 used in a transfer process involving at least two transfer steps, i.e. including an intermediate handle substrate
2221/1031 Dual damascene by forming vias in the via-level dielectric prior to deposition of the trench-level dielectric	2221/68372 used to support a device or wafer when forming electrical connections thereto (when forming bonding pads H01L 24/03 ; when forming bump connectors H01L 24/11 ; when forming layer connectors H01L 24/27)
2221/1036 Dual damascene with different via-level and trench-level dielectrics	2221/68377 with parts of the auxiliary support remaining in the finished device
2221/1042	. . . the dielectric comprising air gaps	2221/68381 Details of chemical or physical process used for separating the auxiliary support from a device or wafer
2221/1047 the air gaps being formed by pores in the dielectric	2221/68386 Separation by peeling
2221/1052	. . . Formation of thin functional dielectric layers	2221/6839 using peeling wedge or knife or bar
2221/1057 in via holes or trenches	2221/68395 using peeling wheel
2221/1063 Sacrificial or temporary thin dielectric films in openings in a dielectric	2223/00	Details relating to semiconductor or other solid state devices covered by the group H01L 23/00
2221/1068	. . Formation and after-treatment of conductors	2223/544	. Marks applied to semiconductor devices or parts
2221/1073	. . . Barrier, adhesion or liner layers	2223/54406	. . comprising alphanumeric information
2221/1078 Multiple stacked thin films not being formed in openings in dielectrics	2223/54413	. . comprising digital information, e.g. bar codes, data matrix
2221/1084 Layers specifically deposited to enhance or enable the nucleation of further layers, i.e. seed layers	2223/5442	. . comprising non digital, non alphanumeric information, e.g. symbols
2221/1089 Stacks of seed layers	2223/54426	. . for alignment
2221/1094	. . . Conducting structures comprising nanotubes or nanowires	2223/54433	. . containing identification or tracking information
2221/67	. Apparatus for handling semiconductor or electric solid state devices during manufacture or treatment thereof; Apparatus for handling wafers during manufacture or treatment of semiconductor or electric solid state devices or components; Apparatus not specifically provided for elsewhere	2223/5444	. . . for electrical read out
2221/683	. . for supporting or gripping	2223/54446 Wireless electrical read out
2221/68304	. . . using temporarily an auxiliary support	2223/54453	. . for use prior to dicing
2221/68309 Auxiliary support including alignment aids	2223/5446	. . . Located in scribe lines
2221/68313 Auxiliary support including a cavity for storing a finished device, e.g. IC package, or a partly finished device, e.g. die, during manufacturing or mounting	2223/54466	. . . Located in a dummy or reference die
2221/68318 Auxiliary support including means facilitating the separation of a device or wafer from the auxiliary support	2223/54473	. . for use after dicing
2221/68322 Auxiliary support including means facilitating the selective separation of some of a plurality of devices from the auxiliary support	2223/5448	. . . Located on chip prior to dicing and remaining on chip after dicing
2221/68327 used during dicing or grinding	2223/54486	. . . Located on package parts, e.g. encapsulation, leads, package substrate
2221/68331 of passive members, e.g. die mounting substrate	2223/54493	. . Peripheral marks on wafers, e.g. orientation flats, notches, lot number
		2223/58	. Structural electrical arrangements for semiconductor devices not otherwise provided for
		2223/64	. . Impedance arrangements
		2223/66	. . . High-frequency adaptations
		2223/6605 High-frequency electrical connections
		2223/6611 Wire connections
		2223/6616 Vertical connections, e.g. vias
		2223/6622 Coaxial feed-throughs in active or passive substrates

2223/6627	Waveguides, e.g. microstrip line, strip line, coplanar line	2224/0221	Shape of the protective coating
2223/6633	Transition between different waveguide types	2224/02215	Material of the protective coating
2223/6638	Differential pair signal lines	2224/02233	not in direct contact with the bonding area
2223/6644	Packaging aspects of high-frequency amplifiers (amplifiers per se H03F)	2224/02235	Reinforcing structures
2223/665	Bias feed arrangements	2224/0224	Alignment aids
2223/6655	Matching arrangements, e.g. arrangement of inductive and capacitive components	2224/02245	Flow barrier
2223/6661	for passive devices (passive components per se H01L 28/00)	2224/0225	Structure of the auxiliary member
2223/6666	for decoupling, e.g. bypass capacitors	2224/02251	Multilayer auxiliary member
2223/6672	for integrated passive components, e.g. semiconductor device with passive components only (integrated circuits with passive components only per se H01L 27/01)	2224/02255	Shape of the auxiliary member
2223/6677	for antenna, e.g. antenna included within housing of semiconductor device (antennas per se H01Q)	2224/0226	Material of the auxiliary member
2223/6683	for monolithic microwave integrated circuit [MMIC]	2224/023	. . .	Redistribution layers [RDL] for bonding areas
2223/6688	Mixed frequency adaptations, i.e. for operation at different frequencies	2224/0231	Manufacturing methods of the redistribution layers
2223/6694	Optical signal interface included within high-frequency semiconductor device housing	2224/02311	Additive methods
2224/00		Indexing scheme for arrangements for connecting or disconnecting semiconductor or solid-state bodies and methods related thereto as covered by H01L 24/00	2224/02313	Subtractive methods
2224/01	Means for bonding being attached to, or being formed on, the surface to be connected, e.g. chip-to-package, die-attach, "first-level" interconnects; Manufacturing methods related thereto	2224/02315	Self-assembly processes
2224/02	. . .	Bonding areas; Manufacturing methods related thereto	2224/02317	by local deposition
2224/0212	. . .	Auxiliary members for bonding areas, e.g. spacers	2224/02319	by using a preform
2224/02122	being formed on the semiconductor or solid-state body	2224/02321	Reworking
2224/02123	inside the bonding area	2224/0233	Structure of the redistribution layers
2224/02125	Reinforcing structures	2224/02331	Multilayer structure
2224/02126	Collar structures	2224/02333	being a bump
2224/0213	Alignment aids	2224/02335	Free-standing redistribution layers
2224/02135	Flow barrier	2224/0235	Shape of the redistribution layers
2224/0214	Structure of the auxiliary member	2224/02351	comprising interlocking features
2224/02141	Multilayer auxiliary member	2224/0236	Shape of the insulating layers therebetween
2224/02145	Shape of the auxiliary member	2224/0237	Disposition of the redistribution layers
2224/0215	Material of the auxiliary member	2224/02371	connecting the bonding area on a surface of the semiconductor or solid-state body with another surface of the semiconductor or solid-state body
2224/02163	on the bonding area	2224/02372	connecting to a via connection in the semiconductor or solid-state body
2224/02165	Reinforcing structures	2224/02373	Layout of the redistribution layers
2224/02166	Collar structures	2224/02375	Top view
2224/0217	Alignment aids	2224/02377	Fan-in arrangement
2224/02175	Flow barrier	2224/02379	Fan-out arrangement
2224/0218	Structure of the auxiliary member	2224/02381	Side view
2224/02181	Multilayer auxiliary member	2224/0239	Material of the redistribution layers
2224/02185	Shape of the auxiliary member	2224/024	Material of the insulating layers therebetween
2224/0219	Material of the auxiliary member	2224/03	. . .	Manufacturing methods
2224/022	Protective coating, i.e. protective bond-through coating	2224/03001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate
2224/02205	Structure of the protective coating	2224/03002	for supporting the semiconductor or solid-state body
2224/02206	Multilayer protective coating	2224/03003	for holding or transferring a preform
			2224/03005	for aligning the bonding area, e.g. marks, spacers
			2224/03009	for protecting parts during manufacture
			2224/03011	Involving a permanent auxiliary member, i.e. a member which is left at least partly in the finished device, e.g. coating, dummy feature
			2224/03013	for holding or confining the bonding area, e.g. solder flow barrier
			2224/03015	for aligning the bonding area, e.g. marks, spacers
			2224/03019	for protecting parts during the process
			2224/031	Manufacture and pre-treatment of the bonding area preform
			2224/0311	Shaping

2224/0312	Applying permanent coating	2224/03524	with special adaptation of the surface of the body to be connected or of an auxiliary substrate, e.g. surface shape specially adapted for the self-assembly process
2224/033	by local deposition of the material of the bonding area	2224/0355	Selective modification
2224/0331	in liquid form	2224/03552	using a laser or a focussed ion beam [FIB]
2224/03312	Continuous flow, e.g. using a microsyringe, a pump, a nozzle or extrusion	2224/03554	Stereolithography, i.e. solidification of a pattern defined by a laser trace in a photosensitive resin
2224/03318	by dispensing droplets	2224/036	by patterning a pre-deposited material (treatment of parts prior to assembly of the devices H01L 21/48)
2224/0332	Screen printing, i.e. using a stencil	2224/03602	Mechanical treatment, e.g. polishing, grinding
2224/0333	in solid form	2224/0361	Physical or chemical etching
2224/03332	using a powder	2224/03612	by physical means only
2224/03334	using a preform	2224/03614	by chemical means only
2224/034	by blanket deposition of the material of the bonding area	2224/03616	Chemical mechanical polishing [CMP]
2224/0341	in liquid form	2224/03618	with selective exposure, development and removal of a photosensitive material, e.g. of a photosensitive conductive resin
2224/03416	Spin coating	2224/0362	Photolithography
2224/03418	Spray coating	2224/03622	using masks
2224/0342	Curtain coating	2224/0363	using a laser or a focused ion beam [FIB]
2224/03422	by dipping, e.g. in a solder bath (hot-dipping C23C 2/00)	2224/03632	Ablation by means of a laser or focused ion beam [FIB]
2224/03424	Immersion coating, e.g. in a solder bath (immersion processes C23C 2/00)	2224/037	involving monitoring, e.g. feedback loop
2224/03426	Chemical solution deposition [CSD], i.e. using a liquid precursor	2224/038	Post-treatment of the bonding area
2224/03428	Wave coating	2224/0381	Cleaning, e.g. oxide removal step, desmearing
2224/0343	in solid form	2224/0382	Applying permanent coating, e.g. in-situ coating
2224/03436	Lamination of a preform, e.g. foil, sheet or layer	2224/03821	Spray coating
2224/03438	the preform being at least partly pre-patterned	2224/03822	by dipping, e.g. in a solder bath
2224/0344	by transfer printing	2224/03823	Immersion coating, e.g. in a solder bath
2224/03442	using a powder	2224/03824	Chemical solution deposition [CSD], i.e. using a liquid precursor
2224/03444	in gaseous form	2224/03825	Plating, e.g. electroplating, electroless plating
2224/0345	Physical vapour deposition [PVD], e.g. evaporation, or sputtering	2224/03826	Physical vapour deposition [PVD], e.g. evaporation, or sputtering
2224/03452	Chemical vapour deposition [CVD], e.g. laser CVD	2224/03827	Chemical vapour deposition [CVD], e.g. laser CVD
2224/0346	Plating	2224/03828	Applying flux
2224/03462	Electroplating	2224/03829	Applying a precursor material
2224/03464	Electroless plating	2224/0383	Reworking, e.g. shaping (reflowing H01L 2224/03849)
2224/03466	Conformal deposition, i.e. blanket deposition of a conformal layer on a patterned surface	2224/03831	involving a chemical process, e.g. etching the bonding area
2224/0347	using a lift-off mask	2224/0384	involving a mechanical process, e.g. planarising the bonding area
2224/03472	Profile of the lift-off mask	2224/03845	Chemical mechanical polishing [CMP]
2224/03474	Multilayer masks	2224/03848	Thermal treatments, e.g. annealing, controlled cooling
2224/0348	Permanent masks, i.e. masks left in the finished device, e.g. passivation layers	2224/03849	Reflowing
2224/035	by chemical or physical modification of a pre-existing or pre-deposited material	2224/039	Methods of manufacturing bonding areas involving a specific sequence of method steps
2224/03502	Pre-existing or pre-deposited material	2224/03901	with repetition of the same manufacturing step
2224/03505	Sintering	2224/03902	Multiple masking steps
2224/0351	Anodisation			
2224/03515	Curing and solidification, e.g. of a photosensitive material			
2224/0352	Self-assembly, e.g. self-agglomeration of the material in a fluid			
2224/03522	Auxiliary means therefor, e.g. for self-assembly activation			

2224/03903	using different masks	2224/05024	the internal layer being disposed on a redistribution layer on the semiconductor or solid-state body
2224/03906	with modification of the same mask	2224/05025	the internal layer being disposed on a via connection of the semiconductor or solid-state body
2224/0391	Forming a passivation layer after forming the bonding area	2224/05026	the internal layer being disposed in a recess of the surface
2224/03912	the bump being used as a mask for patterning the bonding area	2224/05027	the internal layer extending out of an opening
2224/03914	the bonding area, e.g. under bump metallisation [UBM], being used as a mask for patterning other parts	2224/05073	Single internal layer
2224/03916	a passivation layer being used as a mask for patterning the bonding area	2224/05075	Plural internal layers
2224/0392	specifically adapted to include a probing step	2224/05076	being mutually engaged together, e.g. through inserts
2224/03921	by repairing the bonding area damaged by the probing step	2224/05078	being disposed next to each other, e.g. side-to-side arrangements
2224/04	. . .	Structure, shape, material or disposition of the bonding areas prior to the connecting process	2224/0508	being stacked
2224/0401	Bonding areas specifically adapted for bump connectors, e.g. under bump metallisation [UBM]	2224/05082	Two-layer arrangements
2224/04026	Bonding areas specifically adapted for layer connectors	2224/05083	Three-layer arrangements
2224/04034	Bonding areas specifically adapted for strap connectors	2224/05084	Four-layer arrangements
2224/04042	Bonding areas specifically adapted for wire connectors, e.g. wirebond pads	2224/05085	with additional elements, e.g. vias arrays, interposed between the stacked layers
2224/0405	Bonding areas specifically adapted for tape automated bonding [TAB] connectors	2224/05086	Structure of the additional element
2224/04073	Bonding areas specifically adapted for connectors of different types	2224/05087	being a via with at least a lining layer
2224/04105	Bonding areas formed on an encapsulation of the semiconductor or solid-state body, e.g. bonding areas on chip-scale packages	2224/05088	Shape of the additional element
2224/05	of an individual bonding area	2224/05089	Disposition of the additional element
2224/05001	Internal layers	2224/0509	of a single via
2224/05005	Structure	2224/05091	at the center of the internal layers
2224/05006	Dual damascene structure	2224/05092	at the periphery of the internal layers
2224/05007	comprising a core and a coating	2224/05093	of a plurality of vias
2224/05008	Bonding area integrally formed with a redistribution layer on the semiconductor or solid-state body, e.g.	2224/05094	at the center of the internal layers
2224/05009	Bonding area integrally formed with a via connection of the semiconductor or solid-state body	2224/05095	at the periphery of the internal layers
2224/0501	Shape	2224/05096	Uniform arrangement, i.e. array
2224/05011	comprising apertures or cavities	2224/05097	Random arrangement
2224/05012	in top view	2224/05098	Material of the additional element
2224/05013	being rectangular	2224/05099	Material
2224/05014	being square	2224/051	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/05015	being circular or elliptic	2224/05101	the principal constituent melting at a temperature of less than 400°C
2224/05016	in side view	2224/05105	Gallium [Ga] as principal constituent
2224/05017	comprising protrusions or indentations	2224/05109	Indium [In] as principal constituent
2224/05018	being a conformal layer on a patterned surface	2224/05111	Tin [Sn] as principal constituent
2224/05019	being a non conformal layer on a patterned surface	2224/05113	Bismuth [Bi] as principal constituent
2224/0502	Disposition	2224/05114	Thallium [Tl] as principal constituent
2224/05022	the internal layer being at least partially embedded in the surface	2224/05116	Lead [Pb] as principal constituent
2224/05023	the whole internal layer protruding from the surface			

2224/05117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05188	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/05118	Zinc [Zn] as principal constituent	2224/0519	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/0512	Antimony [Sb] as principal constituent	2224/05191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05123	Magnesium [Mg] as principal constituent	2224/05193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/051 - H01L 2224/05191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/05124	Aluminium [Al] as principal constituent	2224/05194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/051 - H01L 2224/05191
2224/05138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/051 - H01L 2224/05191
2224/05139	Silver [Ag] as principal constituent	2224/05198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/05144	Gold [Au] as principal constituent	2224/05199	Material of the matrix
2224/05147	Copper [Cu] as principal constituent	2224/052	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/05149	Manganese [Mn] as principal constituent	2224/05201	the principal constituent melting at a temperature of less than 400°C
2224/05155	Nickel [Ni] as principal constituent	2224/05205	Gallium [Ga] as principal constituent
2224/05157	Cobalt [Co] as principal constituent	2224/05209	Indium [In] as principal constituent
2224/0516	Iron [Fe] as principal constituent	2224/05211	Tin [Sn] as principal constituent
2224/05163	the principal constituent melting at a temperature of greater than 1550°C	2224/05213	Bismuth [Bi] as principal constituent
2224/05164	Palladium [Pd] as principal constituent	2224/05214	Thallium [Tl] as principal constituent
2224/05166	Titanium [Ti] as principal constituent	2224/05216	Lead [Pb] as principal constituent
2224/05169	Platinum [Pt] as principal constituent	2224/05217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/0517	Zirconium [Zr] as principal constituent	2224/05218	Zinc [Zn] as principal constituent
2224/05171	Chromium [Cr] as principal constituent	2224/0522	Antimony [Sb] as principal constituent
2224/05172	Vanadium [V] as principal constituent	2224/05223	Magnesium [Mg] as principal constituent
2224/05173	Rhodium [Rh] as principal constituent	2224/05224	Aluminium [Al] as principal constituent
2224/05176	Ruthenium [Ru] as principal constituent		
2224/05178	Iridium [Ir] as principal constituent		
2224/05179	Niobium [Nb] as principal constituent		
2224/0518	Molybdenum [Mo] as principal constituent		
2224/05181	Tantalum [Ta] as principal constituent		
2224/05183	Rhenium [Re] as principal constituent		
2224/05184	Tungsten [W] as principal constituent		
2224/05186	with a principal constituent of the material being a non metallic, non metalloid inorganic material		
2224/05187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05188)		

2224/05238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05239	Silver [Ag] as principal constituent	2224/05293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/052 - H01L 2224/05291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/05244	Gold [Au] as principal constituent	2224/05294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/052 - H01L 2224/05291
2224/05247	Copper [Cu] as principal constituent	2224/05295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/052 - H01L 2224/05291
2224/05249	Manganese [Mn] as principal constituent	2224/05298	Fillers
2224/05255	Nickel [Ni] as principal constituent	2224/05299	Base material
2224/05257	Cobalt [Co] as principal constituent	2224/053	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/0526	Iron [Fe] as principal constituent	2224/05301	the principal constituent melting at a temperature of less than 400°C
2224/05263	the principal constituent melting at a temperature of greater than 1550°C	2224/05305	Gallium [Ga] as principal constituent
2224/05264	Palladium [Pd] as principal constituent	2224/05309	Indium [In] as principal constituent
2224/05266	Titanium [Ti] as principal constituent	2224/05311	Tin [Sn] as principal constituent
2224/05269	Platinum [Pt] as principal constituent	2224/05313	Bismuth [Bi] as principal constituent
2224/0527	Zirconium [Zr] as principal constituent	2224/05314	Thallium [Tl] as principal constituent
2224/05271	Chromium [Cr] as principal constituent	2224/05316	Lead [Pb] as principal constituent
2224/05272	Vanadium [V] as principal constituent	2224/05317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/05273	Rhodium [Rh] as principal constituent	2224/05318	Zinc [Zn] as principal constituent
2224/05276	Ruthenium [Ru] as principal constituent	2224/0532	Antimony [Sb] as principal constituent
2224/05278	Iridium [Ir] as principal constituent	2224/05323	Magnesium [Mg] as principal constituent
2224/05279	Niobium [Nb] as principal constituent	2224/05324	Aluminium [Al] as principal constituent
2224/0528	Molybdenum [Mo] as principal constituent	2224/05338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/05281	Tantalum [Ta] as principal constituent	2224/05339	Silver [Ag] as principal constituent
2224/05283	Rhenium [Re] as principal constituent	2224/05344	Gold [Au] as principal constituent
2224/05284	Tungsten [W] as principal constituent	2224/05347	Copper [Cu] as principal constituent
2224/05286	with a principal constituent of the material being a non metallic, non metalloid inorganic material		
2224/05287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05288)		
2224/05288	Glasses, e.g. amorphous oxides, nitrides or fluorides		
2224/0529	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy		

2224/05349	Manganese [Mn] as principal constituent	2224/05394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/053 - H01L 2224/05391
2224/05355	Nickel [Ni] as principal constituent	2224/05395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/053 - H01L 2224/05391
2224/05357	Cobalt [Co] as principal constituent	2224/05398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/0536	Iron [Fe] as principal constituent	2224/05399	Coating material
2224/05363	the principal constituent melting at a temperature of greater than 1550°C	2224/054	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/05364	Palladium [Pd] as principal constituent	2224/05401	the principal constituent melting at a temperature of less than 400°C
2224/05366	Titanium [Ti] as principal constituent	2224/05405	Gallium [Ga] as principal constituent
2224/05369	Platinum [Pt] as principal constituent	2224/05409	Indium [In] as principal constituent
2224/0537	Zirconium [Zr] as principal constituent	2224/05411	Tin [Sn] as principal constituent
2224/05371	Chromium [Cr] as principal constituent	2224/05413	Bismuth [Bi] as principal constituent
2224/05372	Vanadium [V] as principal constituent	2224/05414	Thallium [Tl] as principal constituent
2224/05373	Rhodium [Rh] as principal constituent	2224/05416	Lead [Pb] as principal constituent
2224/05376	Ruthenium [Ru] as principal constituent	2224/05417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/05378	Iridium [Ir] as principal constituent	2224/05418	Zinc [Zn] as principal constituent
2224/05379	Niobium [Nb] as principal constituent	2224/0542	Antimony [Sb] as principal constituent
2224/0538	Molybdenum [Mo] as principal constituent	2224/05423	Magnesium [Mg] as principal constituent
2224/05381	Tantalum [Ta] as principal constituent	2224/05424	Aluminium [Al] as principal constituent
2224/05383	Rhenium [Re] as principal constituent	2224/05438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/05384	Tungsten [W] as principal constituent	2224/05439	Silver [Ag] as principal constituent
2224/05386	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/05444	Gold [Au] as principal constituent
2224/05387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05388)	2224/05447	Copper [Cu] as principal constituent
2224/05388	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/05449	Manganese [Mn] as principal constituent
2224/0539	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/05455	Nickel [Ni] as principal constituent
2224/05391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene		
2224/05393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/053 - H01L 2224/05391 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond		

2224/05457	Cobalt [Co] as principal constituent	2224/05495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/054 - H01L 2224/05491
2224/0546	Iron [Fe] as principal constituent	2224/05498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/05463	the principal constituent melting at a temperature of greater than 1550°C	2224/05499	Shape or distribution of the fillers
2224/05464	Palladium [Pd] as principal constituent	2224/0554	External layer
2224/05466	Titanium [Ti] as principal constituent	2224/05541	Structure
2224/05469	Platinum [Pt] as principal constituent	2224/05546	Dual damascene structure
2224/0547	Zirconium [Zr] as principal constituent	2224/05547	comprising a core and a coating
2224/05471	Chromium [Cr] as principal constituent	2224/05548	Bonding area integrally formed with a redistribution layer on the semiconductor or solid-state body
2224/05472	Vanadium [V] as principal constituent	2224/0555	Shape
2224/05473	Rhodium [Rh] as principal constituent	2224/05551	comprising apertures or cavities
2224/05476	Ruthenium [Ru] as principal constituent	2224/05552	in top view
2224/05478	Iridium [Ir] as principal constituent	2224/05553	being rectangular
2224/05479	Niobium [Nb] as principal constituent	2224/05554	being square
2224/0548	Molybdenum [Mo] as principal constituent	2224/05555	being circular or elliptic
2224/05481	Tantalum [Ta] as principal constituent	2224/05556	in side view
2224/05483	Rhenium [Re] as principal constituent	2224/05557	comprising protrusions or indentations
2224/05484	Tungsten [W] as principal constituent	2224/05558	conformal layer on a patterned surface
2224/05486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/05559	non conformal layer on a patterned surface
2224/05487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05488)	2224/0556	Disposition
2224/05488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/05561	On the entire surface of the internal layer
2224/0549	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/05562	On the entire exposed surface of the internal layer
2224/05491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/05563	Only on parts of the surface of the internal layer
2224/05493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/054 - H01L 2224/05491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/05564	Only on the bonding interface of the bonding area
2224/05494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/054 - H01L 2224/05491	2224/05565	Only outside the bonding interface of the bonding area
		2224/05566	Both on and outside the bonding interface of the bonding area
		2224/05567	the external layer being at least partially embedded in the surface
		2224/05568	the whole external layer protruding from the surface
		2224/05569	the external layer being disposed on a redistribution layer on the semiconductor or solid-state body
		2224/0557	the external layer being disposed on a via connection of the semiconductor or solid-state body
		2224/05571	the external layer being disposed in a recess of the surface
		2224/05572	the external layer extending out of an opening
		2224/05573	Single external layer
		2224/05575	Plural external layers
		2224/05576	being mutually engaged together, e.g. through inserts

2224/05578	being disposed next to each other, e.g. side-to-side arrangements	2224/05671	Chromium [Cr] as principal constituent
2224/0558	being stacked	2224/05672	Vanadium [V] as principal constituent
2224/05582	Two-layer coating	2224/05673	Rhodium [Rh] as principal constituent
2224/05583	Three-layer coating	2224/05676	Ruthenium [Ru] as principal constituent
2224/05584	Four-layer coating	2224/05678	Iridium [Ir] as principal constituent
2224/05599	Material	2224/05679	Niobium [Nb] as principal constituent
2224/056	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/0568	Molybdenum [Mo] as principal constituent
2224/05601	the principal constituent melting at a temperature of less than 400°C	2224/05681	Tantalum [Ta] as principal constituent
2224/05605	Gallium [Ga] as principal constituent	2224/05683	Rhenium [Re] as principal constituent
2224/05609	Indium [In] as principal constituent	2224/05684	Tungsten [W] as principal constituent
2224/05611	Tin [Sn] as principal constituent	2224/05686	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/05613	Bismuth [Bi] as principal constituent	2224/05687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05688)
2224/05614	Thallium [Tl] as principal constituent	2224/05688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/05616	Lead [Pb] as principal constituent	2224/0569	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/05617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05618	Zinc [Zn] as principal constituent	2224/05693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/056 - H01L 2224/05691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/0562	Antimony [Sb] as principal constituent	2224/05694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/056 - H01L 2224/05691
2224/05623	Magnesium [Mg] as principal constituent	2224/05695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/056 - H01L 2224/05691
2224/05624	Aluminium [Al] as principal constituent	2224/05698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/05638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05699	Material of the matrix
2224/05639	Silver [Ag] as principal constituent	2224/057	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/05644	Gold [Au] as principal constituent		
2224/05647	Copper [Cu] as principal constituent		
2224/05649	Manganese [Mn] as principal constituent		
2224/05655	Nickel [Ni] as principal constituent		
2224/05657	Cobalt [Co] as principal constituent		
2224/0566	Iron [Fe] as principal constituent		
2224/05663	the principal constituent melting at a temperature of greater than 1550°C		
2224/05664	Palladium [Pd] as principal constituent		
2224/05666	Titanium [Ti] as principal constituent		
2224/05669	Platinum [Pt] as principal constituent		
2224/0567	Zirconium [Zr] as principal constituent		

2224/05701	the principal constituent melting at a temperature of less than 400°C	2224/05778	Iridium [Ir] as principal constituent
2224/05705	Gallium [Ga] as principal constituent	2224/05779	Niobium [Nb] as principal constituent
2224/05709	Indium [In] as principal constituent	2224/0578	Molybdenum [Mo] as principal constituent
2224/05711	Tin [Sn] as principal constituent	2224/05781	Tantalum [Ta] as principal constituent
2224/05713	Bismuth [Bi] as principal constituent	2224/05783	Rhenium [Re] as principal constituent
2224/05714	Thallium [Tl] as principal constituent	2224/05784	Tungsten [W] as principal constituent
2224/05716	Lead [Pb] as principal constituent	2224/05786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/05717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05788)
2224/05718	Zinc [Zn] as principal constituent	2224/05788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/0572	Antimony [Sb] as principal constituent	2224/0579	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/05723	Magnesium [Mg] as principal constituent	2224/05791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05724	Aluminium [Al] as principal constituent	2224/05793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/057 - H01L 2224/05791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/05738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/057 - H01L 2224/05791
2224/05739	Silver [Ag] as principal constituent	2224/05795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/057 - H01L 2224/05791
2224/05744	Gold [Au] as principal constituent	2224/05798	Fillers
2224/05747	Copper [Cu] as principal constituent	2224/05799	Base material
2224/05749	Manganese [Mn] as principal constituent	2224/058	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/05755	Nickel [Ni] as principal constituent	2224/05801	the principal constituent melting at a temperature of less than 400°C
2224/05757	Cobalt [Co] as principal constituent	2224/05805	Gallium [Ga] as principal constituent
2224/0576	Iron [Fe] as principal constituent	2224/05809	Indium [In] as principal constituent
2224/05763	the principal constituent melting at a temperature of greater than 1550°C	2224/05811	Tin [Sn] as principal constituent
2224/05764	Palladium [Pd] as principal constituent	2224/05813	Bismuth [Bi] as principal constituent
2224/05766	Titanium [Ti] as principal constituent	2224/05814	Thallium [Tl] as principal constituent
2224/05769	Platinum [Pt] as principal constituent		
2224/0577	Zirconium [Zr] as principal constituent		
2224/05771	Chromium [Cr] as principal constituent		
2224/05772	Vanadium [V] as principal constituent		
2224/05773	Rhodium [Rh] as principal constituent		
2224/05776	Ruthenium [Ru] as principal constituent		

2224/05816	Lead [Pb] as principal constituent	2224/05886	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/05817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05888)
2224/05818	Zinc [Zn] as principal constituent	2224/05888	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/0582	Antimony [Sb] as principal constituent	2224/0589	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/05823	Magnesium [Mg] as principal constituent	2224/05891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05824	Aluminium [Al] as principal constituent	2224/05893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/058 - H01L 2224/05891 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/05838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/058 - H01L 2224/05891
2224/05839	Silver [Ag] as principal constituent	2224/05895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/058 - H01L 2224/05891
2224/05844	Gold [Au] as principal constituent	2224/05898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/05847	Copper [Cu] as principal constituent	2224/05899	Coating material
2224/05849	Manganese [Mn] as principal constituent	2224/059	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/05855	Nickel [Ni] as principal constituent	2224/05901	the principal constituent melting at a temperature of less than 400°C
2224/05857	Cobalt [Co] as principal constituent	2224/05905	Gallium [Ga] as principal constituent
2224/0586	Iron [Fe] as principal constituent	2224/05909	Indium [In] as principal constituent
2224/05863	the principal constituent melting at a temperature of greater than 1550°C	2224/05911	Tin [Sn] as principal constituent
2224/05864	Palladium [Pd] as principal constituent	2224/05913	Bismuth [Bi] as principal constituent
2224/05866	Titanium [Ti] as principal constituent	2224/05914	Thallium [Tl] as principal constituent
2224/05869	Platinum [Pt] as principal constituent	2224/05916	Lead [Pb] as principal constituent
2224/0587	Zirconium [Zr] as principal constituent		
2224/05871	Chromium [Cr] as principal constituent		
2224/05872	Vanadium [V] as principal constituent		
2224/05873	Rhodium [Rh] as principal constituent		
2224/05876	Ruthenium [Ru] as principal constituent		
2224/05878	Iridium [Ir] as principal constituent		
2224/05879	Niobium [Nb] as principal constituent		
2224/0588	Molybdenum [Mo] as principal constituent		
2224/05881	Tantalum [Ta] as principal constituent		
2224/05883	Rhenium [Re] as principal constituent		
2224/05884	Tungsten [W] as principal constituent		

2224/05917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/05986	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/05918	Zinc [Zn] as principal constituent	2224/05987	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/05988)
2224/0592	Antimony [Sb] as principal constituent	2224/05988	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/05923	Magnesium [Mg] as principal constituent	2224/0599	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/05924	Aluminium [Al] as principal constituent	2224/05991	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/05938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/05993	with a principal constituent of the material being a solid not provided for in groups H01L 2224/059 - H01L 2224/05991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/05939	Silver [Ag] as principal constituent	2224/05994	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/059 - H01L 2224/05991
2224/05944	Gold [Au] as principal constituent	2224/05995	with a principal constituent of the material being a gas not provided for in groups H01L 2224/059 - H01L 2224/05991
2224/05947	Copper [Cu] as principal constituent	2224/05998	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/05949	Manganese [Mn] as principal constituent	2224/05999	Shape or distribution of the fillers
2224/05955	Nickel [Ni] as principal constituent	2224/06	of a plurality of bonding areas
2224/05957	Cobalt [Co] as principal constituent	2224/0601	Structure
2224/0596	Iron [Fe] as principal constituent	2224/0603	Bonding areas having different sizes, e.g. different heights or widths
2224/05963	the principal constituent melting at a temperature of greater than 1550°C	2224/0605	Shape
2224/05964	Palladium [Pd] as principal constituent	2224/06051	Bonding areas having different shapes
2224/05966	Titanium [Ti] as principal constituent	2224/061	Disposition
2224/05969	Platinum [Pt] as principal constituent	2224/06102	the bonding areas being at different heights
2224/0597	Zirconium [Zr] as principal constituent	2224/0612	Layout
2224/05971	Chromium [Cr] as principal constituent	2224/0613	Square or rectangular array
2224/05972	Vanadium [V] as principal constituent	2224/06131	being uniform, i.e. having a uniform pitch across the array
2224/05973	Rhodium [Rh] as principal constituent	2224/06132	being non uniform, i.e. having a non uniform pitch across the array
2224/05976	Ruthenium [Ru] as principal constituent	2224/06133	with a staggered arrangement, e.g. depopulated array
2224/05978	Iridium [Ir] as principal constituent	2224/06134	covering only portions of the surface to be connected
2224/05979	Niobium [Nb] as principal constituent	2224/06135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/0598	Molybdenum [Mo] as principal constituent	2224/06136	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/05981	Tantalum [Ta] as principal constituent		
2224/05983	Rhenium [Re] as principal constituent		
2224/05984	Tungsten [W] as principal constituent		

2224/06137	with specially adapted redistribution layers [RDL]	2224/06168	being disposed in a single wiring level, i.e. planar layout
2224/06138	being disposed in a single wiring level, i.e. planar layout	2224/06169	being disposed in different wiring levels, i.e. resurf layout
2224/06139	being disposed in different wiring levels, i.e. resurf layout	2224/06177	Combinations of arrays with different layouts
2224/0614	Circular array, i.e. array with radial symmetry	2224/06179	Corner adaptations, i.e. disposition of the bonding areas at the corners of the semiconductor or solid-state body
2224/06141	being uniform, i.e. having a uniform pitch across the array	2224/0618	being disposed on at least two different sides of the body, e.g. dual array
2224/06142	being non uniform, i.e. having a non uniform pitch across the array	2224/06181	On opposite sides of the body
2224/06143	with a staggered arrangement, e.g. depopulated array	2224/06182	with specially adapted redistribution layers [RDL]
2224/06144	covering only portions of the surface to be connected	2224/06183	On contiguous sides of the body
2224/06145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/06187	with specially adapted redistribution layers [RDL]
2224/06146	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/06188	being disposed in a single wiring level, i.e. planar layout
2224/06147	with specially adapted redistribution layers [RDL]	2224/06189	being disposed in different wiring levels, i.e. resurf layout
2224/06148	being disposed in a single wiring level, i.e. planar layout	2224/065	Material
2224/06149	being disposed in different wiring levels, i.e. resurf layout	2224/06505	Bonding areas having different materials
2224/0615	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry	2224/0651	Function
2224/06151	being uniform, i.e. having a uniform pitch across the array	2224/06515	Bonding areas having different functions
2224/06152	being non uniform, i.e. having a non uniform pitch across the array	2224/06517	including bonding areas providing primarily mechanical bonding
2224/06153	with a staggered arrangement, e.g. depopulated array	2224/06519	including bonding areas providing primarily thermal dissipation
2224/06154	covering only portions of the surface to be connected	2224/07	. . .	Structure, shape, material or disposition of the bonding areas after the connecting process
2224/06155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/08	of an individual bonding area
2224/06156	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/0801	Structure
2224/06157	with specially adapted redistribution layers [RDL]	2224/0805	Shape
2224/06158	being disposed in a single wiring level, i.e. planar layout	2224/08052	in top view
2224/06159	being disposed in different wiring levels, i.e. resurf layout	2224/08053	being non uniform along the bonding area
2224/0616	Random array, i.e. array with no symmetry	2224/08054	being rectangular
2224/06163	with a staggered arrangement	2224/08055	being square
2224/06164	covering only portions of the surface to be connected	2224/08056	being circular or elliptic
2224/06165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/08057	in side view
2224/06166	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/08058	being non uniform along the bonding area
2224/06167	with specially adapted redistribution layers [RDL]	2224/08059	comprising protrusions or indentations
			2224/0807	of bonding interfaces, e.g. interlocking features
			2224/081	Disposition
			2224/08111	the bonding area being disposed in a recess of the surface of the body
			2224/08112	the bonding area being at least partially embedded in the surface of the body
			2224/08113	the whole bonding area protruding from the surface of the body
			2224/0812	the bonding area connecting directly to another bonding area, i.e. connectorless bonding, e.g. bumpless bonding
			2224/08121	the connected bonding areas being not aligned with respect to each other
			2224/08123	the bonding area connecting directly to at least two bonding areas

2224/08135	the bonding area connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip	2224/08233	the bonding area connecting to a potential ring of the item
2224/08137	the bodies being arranged next to each other, e.g. on a common substrate	2224/08235	the bonding area connecting to a via metallisation of the item
2224/08145	the bodies being stacked	2224/08237	the bonding area connecting to a bonding area disposed in a recess of the surface of the item
2224/08146	the bonding area connecting to a via connection in the body	2224/08238	the bonding area connecting to a bonding area protruding from the surface of the item
2224/08147	the bonding area connecting to a bonding area disposed in a recess of the surface of the body	2224/08245	the item being metallic
2224/08148	the bonding area connecting to a bonding area protruding from the surface of the body	2224/08253	the bonding area connecting to a potential ring of the item
2224/08151	the bonding area connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive	2224/08257	the bonding area connecting to a bonding area disposed in a recess of the surface of the item
2224/08153	the body and the item being arranged next to each other, e.g. on a common substrate	2224/08258	the bonding area connecting to a bonding area protruding from the surface of the item
2224/08155	the item being non-metallic, e.g. being an insulating substrate with or without metallisation	2224/08265	the item being a discrete passive component
2224/0816	the bonding area connecting to a pin of the item	2224/08267	the bonding area connecting to a bonding area disposed in a recess of the surface of the item
2224/08163	the bonding area connecting to a potential ring of the item	2224/08268	the bonding area connecting to a bonding area protruding from the surface of the item
2224/08165	the bonding area connecting to a via metallisation of the item	2224/085	Material
2224/08167	the bonding area connecting to a bonding area disposed in a recess of the surface of the item	2224/08501	at the bonding interface
2224/08168	the bonding area connecting to a bonding area protruding from the surface of the item	2224/08502	comprising an eutectic alloy
2224/08175	the item being metallic	2224/08503	comprising an intermetallic compound
2224/08183	the bonding area connecting to a potential ring of the item	2224/08505	outside the bonding interface
2224/08187	the bonding area connecting to a bonding area disposed in a recess of the surface of the item	2224/08506	comprising an eutectic alloy
2224/08188	the bonding area connecting to a bonding area protruding from the surface of the item	2224/09	of a plurality of bonding areas
2224/08195	the item being a discrete passive component	2224/0901	Structure
2224/08197	the bonding area connecting to a bonding area disposed in a recess of the surface of the item	2224/0903	Bonding areas having different sizes, e.g. different diameters, heights or widths
2224/08198	the bonding area connecting to a bonding area protruding from the surface of the item	2224/0905	Shape
2224/08221	the body and the item being stacked	2224/09051	Bonding areas having different shapes
2224/08225	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/09055	of their bonding interfaces
2224/0823	the bonding area connecting to a pin of the item	2224/091	Disposition
		2224/09102	the bonding areas being at different heights
		2224/09103	on the semiconductor or solid-state body
		2224/09104	outside the semiconductor or solid-state body
		2224/0912	Layout (layout of bonding areas prior to the connecting process H01L 2224/0612)
		2224/0913	Square or rectangular array
		2224/09132	being non uniform, i.e. having a non uniform pitch across the array
		2224/09133	with a staggered arrangement, e.g. depopulated array
		2224/09134	covering only portions of the surface to be connected

2224/09135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/10135	Alignment aids
2224/0914	Circular array, i.e. array with radial symmetry	2224/10145	Flow barriers
2224/09142	being non uniform, i.e. having a non uniform pitch across the array	2224/10152	being formed on an item to be connected not being a semiconductor or solid-state body
2224/09143	with a staggered arrangement	2224/10155	Reinforcing structures
2224/09144	covering only portions of the surface to be connected	2224/10156	Bump collar
2224/09145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/10165	Alignment aids
2224/0915	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry	2224/10175	Flow barriers
2224/09151	being uniform, i.e. having a uniform pitch across the array	2224/11	Manufacturing methods
2224/09152	being non uniform, i.e. having a non uniform pitch across the array	2224/11001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate
2224/09153	with a staggered arrangement, e.g. depopulated array	2224/11002	for supporting the semiconductor or solid-state body
2224/09154	covering only portions of the surface to be connected	2224/11003	for holding or transferring the bump preform
2224/09155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/11005	for aligning the bump connector, e.g. marks, spacers
2224/09156	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/11009	for protecting parts during manufacture
2224/0916	Random array, i.e. array with no symmetry	2224/11011	Involving a permanent auxiliary member, i.e. a member which is left at least partly in the finished device, e.g. coating, dummy feature
2224/09163	with a staggered arrangement	2224/11013	for holding or confining the bump connector, e.g. solder flow barrier
2224/09164	covering only portions of the surface to be connected	2224/11015	for aligning the bump connector, e.g. marks, spacers
2224/09165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/11019	for protecting parts during the process
2224/09177	Combinations of arrays with different layouts	2224/111	Manufacture and pre-treatment of the bump connector preform
2224/09179	Corner adaptations, i.e. disposition of the bonding areas at the corners of the semiconductor or solid-state body	2224/1111	Shaping
2224/0918	being disposed on at least two different sides of the body, e.g. dual array	2224/1112	Applying permanent coating
2224/09181	On opposite sides of the body	2224/113	by local deposition of the material of the bump connector
2224/09183	On contiguous sides of the body	2224/1131	in liquid form
2224/095	Material	2224/11312	Continuous flow, e.g. using a microsyringe, a pump, a nozzle or extrusion
2224/09505	Bonding areas having different materials	2224/11318	by dispensing droplets
2224/0951	Function	2224/1132	Screen printing, i.e. using a stencil
2224/09515	Bonding areas having different functions	2224/1133	in solid form
2224/09517	including bonding areas providing primarily mechanical support	2224/11332	using a powder
2224/09519	including bonding areas providing primarily thermal dissipation	2224/11334	using preformed bumps
2224/10	Bump connectors; Manufacturing methods related thereto	2224/1134	Stud bumping, i.e. using a wire-bonding apparatus
2224/1012	Auxiliary members for bump connectors, e.g. spacers	2224/114	by blanket deposition of the material of the bump connector
2224/10122	being formed on the semiconductor or solid-state body to be connected	2224/1141	in liquid form
2224/10125	Reinforcing structures	2224/11416	Spin coating
2224/10126	Bump collar	2224/11418	Spray coating
			2224/1142	Curtain coating
			2224/11422	by dipping, e.g. in a solder bath (hot-dipping C23C 2/00)
			2224/11424	Immersion coating, e.g. in a solder bath (immersion processes C23C 2/00)
			2224/11426	Chemical solution deposition [CSD], i.e. using a liquid precursor
			2224/11428	Wave coating
			2224/1143	in solid form
			2224/11436	Lamination of a preform, e.g. foil, sheet or layer
			2224/11438	the preform being at least partly pre-patterned

2224/1144	by transfer printing	2224/1181	Cleaning, e.g. oxide removal step, desmearing
2224/11442	using a powder	2224/1182	Applying permanent coating, e.g. in-situ coating
2224/11444	in gaseous form	2224/11821	Spray coating
2224/1145	Physical vapour deposition [PVD], e.g. evaporation, or sputtering	2224/11822	by dipping, e.g. in a solder bath
2224/11452	Chemical vapour deposition [CVD], e.g. laser CVD	2224/11823	Immersion coating, e.g. in a solder bath
2224/1146	Plating	2224/11824	Chemical solution deposition [CSD], i.e. using a liquid precursor
2224/11462	Electroplating	2224/11825	Plating, e.g. electroplating, electroless plating
2224/11464	Electroless plating	2224/11826	Physical vapour deposition [PVD], e.g. evaporation, or sputtering
2224/11466	Conformal deposition, i.e. blanket deposition of a conformal layer on a patterned surface	2224/11827	Chemical vapour deposition [CVD], e.g. laser CVD
2224/1147	using a lift-off mask	2224/1183	Reworking, e.g. shaping (reflowing H01L 2224/11849)
2224/11472	Profile of the lift-off mask	2224/11831	involving a chemical process, e.g. etching the bump connector
2224/11474	Multilayer masks	2224/1184	involving a mechanical process, e.g. planarising the bump connector
2224/1148	Permanent masks, i.e. masks left in the finished device, e.g. passivation layers	2224/11845	Chemical mechanical polishing [CMP]
2224/115	by chemical or physical modification of a pre-existing or pre-deposited material	2224/11848	Thermal treatments, e.g. annealing, controlled cooling
2224/11502	Pre-existing or pre-deposited material	2224/11849	Reflowing
2224/11505	Sintering	2224/119	Methods of manufacturing bump connectors involving a specific sequence of method steps
2224/1151	Anodisation	2224/11901	with repetition of the same manufacturing step
2224/11515	Curing and solidification, e.g. of a photosensitive bump material	2224/11902	Multiple masking steps
2224/1152	Self-assembly, e.g. self-agglomeration of the bump material in a fluid	2224/11903	using different masks
2224/11522	Auxiliary means therefor, e.g. for self-assembly activation	2224/11906	with modification of the same mask
2224/11524	with special adaptation of the surface or of an auxiliary substrate, e.g. surface shape specially adapted for the self-assembly process	2224/1191	Forming a passivation layer after forming the bump connector
2224/11526	involving the material of the bonding area, e.g. bonding pad or under bump metallisation [UBM]	2224/11912	the bump being used as a mask for patterning other parts
2224/1155	Selective modification	2224/11914	the under bump metallisation [UBM] being used as a mask for patterning other parts
2224/11552	using a laser or a focussed ion beam [FIB]	2224/11916	a passivation layer being used as a mask for patterning other parts
2224/11554	Stereolithography, i.e. solidification of a pattern defined by a laser trace in a photosensitive resin	2224/12	Structure, shape, material or disposition of the bump connectors prior to the connecting process
2224/116	by patterning a pre-deposited material (treatment of parts prior to assembly of the devices H01L 21/48)	2224/12105	Bump connectors formed on an encapsulation of the semiconductor or solid-state body, e.g. bumps on chip-scale packages
2224/11602	Mechanical treatment, e.g. polishing, grinding	2224/13	of an individual bump connector
2224/1161	Physical or chemical etching	2224/13001	Core members of the bump connector
2224/11612	by physical means only	2224/13005	Structure
2224/11614	by chemical means only	2224/13006	Bump connector larger than the underlying bonding area, e.g. than the under bump metallisation [UBM]
2224/11616	Chemical mechanical polishing [CMP]	2224/13007	Bump connector smaller than the underlying bonding area, e.g. than the under bump metallisation [UBM]
2224/11618	with selective exposure, development and removal of a photosensitive bump material, e.g. of a photosensitive conductive resin	2224/13008	Bump connector integrally formed with a redistribution layer on the semiconductor or solid-state body
2224/1162	using masks	2224/13009	Bump connector integrally formed with a via connection of the semiconductor or solid-state body
2224/11622	Photolithography			
2224/1163	using a laser or a focused ion beam [FIB]			
2224/11632	Ablation by means of a laser or focused ion beam [FIB]			
2224/117	involving monitoring, e.g. feedback loop			
2224/118	Post-treatment of the bump connector			

2224/1301	Shape	2224/13114	Thallium [Tl] as principal constituent
2224/13011	comprising apertures or cavities, e.g. hollow bump	2224/13116	Lead [Pb] as principal constituent
2224/13012	in top view	2224/13117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13013	being rectangular or square	2224/13118	Zinc [Zn] as principal constituent
2224/13014	being circular or elliptic	2224/1312	Antimony [Sb] as principal constituent
2224/13015	comprising protrusions or indentations	2224/13123	Magnesium [Mg] as principal constituent
2224/13016	in side view	2224/13124	Aluminium [Al] as principal constituent
2224/13017	being non uniform along the bump connector	2224/13138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13018	comprising protrusions or indentations	2224/13139	Silver [Ag] as principal constituent
2224/13019	at the bonding interface of the bump connector, i.e. on the surface of the bump connector	2224/13144	Gold [Au] as principal constituent
2224/1302	Disposition	2224/13147	Copper [Cu] as principal constituent
2224/13021	the bump connector being disposed in a recess of the surface	2224/13149	Manganese [Mn] as principal constituent
2224/13022	the bump connector being at least partially embedded in the surface	2224/13155	Nickel [Ni] as principal constituent
2224/13023	the whole bump connector protruding from the surface	2224/13157	Cobalt [Co] as principal constituent
2224/13024	the bump connector being disposed on a redistribution layer on the semiconductor or solid-state body	2224/1316	Iron [Fe] as principal constituent
2224/13025	the bump connector being disposed on a via connection of the semiconductor or solid-state body	2224/13163	the principal constituent melting at a temperature of greater than 1550°C
2224/13026	relative to the bonding area, e.g. bond pad, of the semiconductor or solid-state body	2224/13164	Palladium [Pd] as principal constituent
2224/13027	the bump connector being offset with respect to the bonding area, e.g. bond pad	2224/13166	Titanium [Ti] as principal constituent
2224/13028	the bump connector being disposed on at least two separate bonding areas, e.g. bond pads	2224/13169	Platinum [Pt] as principal constituent
2224/13075	Plural core members	2224/1317	Zirconium [Zr] as principal constituent
2224/13076	being mutually engaged together, e.g. through inserts	2224/13171	Chromium [Cr] as principal constituent
2224/13078	being disposed next to each other, e.g. side-to-side arrangements	2224/13172	Vanadium [V] as principal constituent
2224/1308	being stacked	2224/13173	Rhodium [Rh] as principal constituent
2224/13082	Two-layer arrangements	2224/13176	Ruthenium [Ru] as principal constituent
2224/13083	Three-layer arrangements	2224/13178	Iridium [Ir] as principal constituent
2224/13084	Four-layer arrangements	2224/13179	Niobium [Nb] as principal constituent
2224/13099	Material	2224/1318	Molybdenum [Mo] as principal constituent
2224/131	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/13181	Tantalum [Ta] as principal constituent
2224/13101	the principal constituent melting at a temperature of less than 400°C	2224/13183	Rhenium [Re] as principal constituent
2224/13105	Gallium [Ga] as principal constituent	2224/13184	Tungsten [W] as principal constituent
2224/13109	Indium [In] as principal constituent	2224/13186	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/13111	Tin [Sn] as principal constituent		
2224/13113	Bismuth [Bi] as principal constituent		

2224/13187 Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13188)	2224/13224 Aluminium [Al] as principal constituent
2224/13188 Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13238 the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/1319 with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/13239 Silver [Ag] as principal constituent
2224/13191 The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13244 Gold [Au] as principal constituent
2224/13193 with a principal constituent of the material being a solid not provided for in groups H01L 2224/131 - H01L 2224/13191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/13247 Copper [Cu] as principal constituent
2224/13194 with a principal constituent of the material being a liquid not provided for in groups H01L 2224/131 - H01L 2224/13191	2224/13249 Manganese [Mn] as principal constituent
2224/13195 with a principal constituent of the material being a gas not provided for in groups H01L 2224/131 - H01L 2224/13191	2224/13255 Nickel [Ni] as principal constituent
2224/13198 with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/13257 Cobalt [Co] as principal constituent
2224/13199 Material of the matrix	2224/1326 Iron [Fe] as principal constituent
2224/132 with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/13263 the principal constituent melting at a temperature of greater than 1550°C
2224/13201 the principal constituent melting at a temperature of less than 400°C	2224/13264 Palladium [Pd] as principal constituent
2224/13205 Gallium [Ga] as principal constituent	2224/13266 Titanium [Ti] as principal constituent
2224/13209 Indium [In] as principal constituent	2224/13269 Platinum [Pt] as principal constituent
2224/13211 Tin [Sn] as principal constituent	2224/1327 Zirconium [Zr] as principal constituent
2224/13213 Bismuth [Bi] as principal constituent	2224/13271 Chromium [Cr] as principal constituent
2224/13214 Thallium [Tl] as principal constituent	2224/13272 Vanadium [V] as principal constituent
2224/13216 Lead [Pb] as principal constituent	2224/13273 Rhodium [Rh] as principal constituent
2224/13217 the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/13276 Ruthenium [Ru] as principal constituent
2224/13218 Zinc [Zn] as principal constituent	2224/13278 Iridium [Ir] as principal constituent
2224/1322 Antimony [Sb] as principal constituent	2224/13279 Niobium [Nb] as principal constituent
2224/13223 Magnesium [Mg] as principal constituent	2224/1328 Molybdenum [Mo] as principal constituent
		2224/13281 Tantalum [Ta] as principal constituent
		2224/13283 Rhenium [Re] as principal constituent
		2224/13284 Tungsten [W] as principal constituent
		2224/13286 with a principal constituent of the material being a non metallic, non metalloid inorganic material
		2224/13287 Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13288)
		2224/13288 Glasses, e.g. amorphous oxides, nitrides or fluorides
		2224/1329 with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy

2224/13291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13349	Manganese [Mn] as principal constituent
2224/13293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/132 - H01L 2224/13291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/13355	Nickel [Ni] as principal constituent
2224/13294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/132 - H01L 2224/13291	2224/13357	Cobalt [Co] as principal constituent
2224/13295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/132 - H01L 2224/13291	2224/1336	Iron [Fe] as principal constituent
2224/13298	Fillers	2224/13363	the principal constituent melting at a temperature of greater than 1550°C
2224/13299	Base material	2224/13364	Palladium [Pd] as principal constituent
2224/133	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/13366	Titanium [Ti] as principal constituent
2224/13301	the principal constituent melting at a temperature of less than 400°C	2224/13369	Platinum [Pt] as principal constituent
2224/13305	Gallium [Ga] as principal constituent	2224/1337	Zirconium [Zr] as principal constituent
2224/13309	Indium [In] as principal constituent	2224/13371	Chromium [Cr] as principal constituent
2224/13311	Tin [Sn] as principal constituent	2224/13372	Vanadium [V] as principal constituent
2224/13313	Bismuth [Bi] as principal constituent	2224/13373	Rhodium [Rh] as principal constituent
2224/13314	Thallium [Tl] as principal constituent	2224/13376	Ruthenium [Ru] as principal constituent
2224/13316	Lead [Pb] as principal constituent	2224/13378	Iridium [Ir] as principal constituent
2224/13317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/13379	Niobium [Nb] as principal constituent
2224/13318	Zinc [Zn] as principal constituent	2224/1338	Molybdenum [Mo] as principal constituent
2224/1332	Antimony [Sb] as principal constituent	2224/13381	Tantalum [Ta] as principal constituent
2224/13323	Magnesium [Mg] as principal constituent	2224/13383	Rhenium [Re] as principal constituent
2224/13324	Aluminium [Al] as principal constituent	2224/13384	Tungsten [W] as principal constituent
2224/13338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/13386	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/13339	Silver [Ag] as principal constituent	2224/13387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13388)
2224/13344	Gold [Au] as principal constituent	2224/13388	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/13347	Copper [Cu] as principal constituent	2224/1339	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
		2224/13391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
		2224/13393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/133 - H01L 2224/13391 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond

2224/13394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/133 - H01L 2224/13391	2224/13457	Cobalt [Co] as principal constituent
2224/13395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/133 - H01L 2224/13391	2224/1346	Iron [Fe] as principal constituent
2224/13398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/13463	the principal constituent melting at a temperature of greater than 1550°C
2224/13399	Coating material	2224/13464	Palladium [Pd] as principal constituent
2224/134	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/13466	Titanium [Ti] as principal constituent
2224/13401	the principal constituent melting at a temperature of less than 400°C	2224/13469	Platinum [Pt] as principal constituent
2224/13405	Gallium [Ga] as principal constituent	2224/1347	Zirconium [Zr] as principal constituent
2224/13409	Indium [In] as principal constituent	2224/13471	Chromium [Cr] as principal constituent
2224/13411	Tin [Sn] as principal constituent	2224/13472	Vanadium [V] as principal constituent
2224/13413	Bismuth [Bi] as principal constituent	2224/13473	Rhodium [Rh] as principal constituent
2224/13414	Thallium [Tl] as principal constituent	2224/13476	Ruthenium [Ru] as principal constituent
2224/13416	Lead [Pb] as principal constituent	2224/13478	Iridium [Ir] as principal constituent
2224/13417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/13479	Niobium [Nb] as principal constituent
2224/13418	Zinc [Zn] as principal constituent	2224/1348	Molybdenum [Mo] as principal constituent
2224/1342	Antimony [Sb] as principal constituent	2224/13481	Tantalum [Ta] as principal constituent
2224/13423	Magnesium [Mg] as principal constituent	2224/13483	Rhenium [Re] as principal constituent
2224/13424	Aluminium [Al] as principal constituent	2224/13484	Tungsten [W] as principal constituent
2224/13438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/13486	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/13439	Silver [Ag] as principal constituent	2224/13487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13488)
2224/13444	Gold [Au] as principal constituent	2224/13488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/13447	Copper [Cu] as principal constituent	2224/1349	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/13449	Manganese [Mn] as principal constituent	2224/13491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/13455	Nickel [Ni] as principal constituent	2224/13493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/134 - H01L 2224/13491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
		2224/13494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/134 - H01L 2224/13491

2224/13495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/134 - H01L 2224/13491	2224/13617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/13498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/13618	Zinc [Zn] as principal constituent
2224/13499	Shape or distribution of the fillers	2224/1362	Antimony [Sb] as principal constituent
2224/1354	Coating	2224/13623	Magnesium [Mg] as principal constituent
2224/13541	Structure	2224/13624	Aluminium [Al] as principal constituent
2224/1355	Shape	2224/13638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/13551	being non uniform	2224/13639	Silver [Ag] as principal constituent
2224/13552	comprising protrusions or indentations	2224/13644	Gold [Au] as principal constituent
2224/13553	at the bonding interface of the bump connector, i.e. on the surface of the bump connector	2224/13647	Copper [Cu] as principal constituent
2224/1356	Disposition	2224/13649	Manganese [Mn] as principal constituent
2224/13561	On the entire surface of the core, i.e. integral coating	2224/13655	Nickel [Ni] as principal constituent
2224/13562	On the entire exposed surface of the core	2224/13657	Cobalt [Co] as principal constituent
2224/13563	Only on parts of the surface of the core, i.e. partial coating	2224/1366	Iron [Fe] as principal constituent
2224/13564	Only on the bonding interface of the bump connector	2224/13663	the principal constituent melting at a temperature of greater than 1550°C
2224/13565	Only outside the bonding interface of the bump connector	2224/13664	Palladium [Pd] as principal constituent
2224/13566	Both on and outside the bonding interface of the bump connector	2224/13666	Titanium [Ti] as principal constituent
2224/1357	Single coating layer	2224/13669	Platinum [Pt] as principal constituent
2224/13575	Plural coating layers	2224/1367	Zirconium [Zr] as principal constituent
2224/13576	being mutually engaged together, e.g. through inserts	2224/13671	Chromium [Cr] as principal constituent
2224/13578	being disposed next to each other, e.g. side-to-side arrangements	2224/13672	Vanadium [V] as principal constituent
2224/1358	being stacked	2224/13673	Rhodium [Rh] as principal constituent
2224/13582	Two-layer coating	2224/13676	Ruthenium [Ru] as principal constituent
2224/13583	Three-layer coating	2224/13678	Iridium [Ir] as principal constituent
2224/13584	Four-layer coating	2224/13679	Niobium [Nb] as principal constituent
2224/13599	Material	2224/1368	Molybdenum [Mo] as principal constituent
2224/136	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/13681	Tantalum [Ta] as principal constituent
2224/13601	the principal constituent melting at a temperature of less than 400°C	2224/13683	Rhenium [Re] as principal constituent
2224/13605	Gallium [Ga] as principal constituent	2224/13684	Tungsten [W] as principal constituent
2224/13609	Indium [In] as principal constituent	2224/13686	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/13611	Tin [Sn] as principal constituent	2224/13687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13688)
2224/13613	Bismuth [Bi] as principal constituent		
2224/13614	Thallium [Tl] as principal constituent		
2224/13616	Lead [Pb] as principal constituent		

2224/13688	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/13738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/1369	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/13739	Silver [Ag] as principal constituent
2224/13691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13744	Gold [Au] as principal constituent
2224/13693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/136 - H01L 2224/13691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/13747	Copper [Cu] as principal constituent
2224/13694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/136 - H01L 2224/13691	2224/13749	Manganese [Mn] as principal constituent
2224/13695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/136 - H01L 2224/13691	2224/13755	Nickel [Ni] as principal constituent
2224/13698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/13757	Cobalt [Co] as principal constituent
2224/13699	Material of the matrix	2224/1376	Iron [Fe] as principal constituent
2224/137	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/13763	the principal constituent melting at a temperature of greater than 1550°C
2224/13701	the principal constituent melting at a temperature of less than 400°C	2224/13764	Palladium [Pd] as principal constituent
2224/13705	Gallium [Ga] as principal constituent	2224/13766	Titanium [Ti] as principal constituent
2224/13709	Indium [In] as principal constituent	2224/13769	Platinum [Pt] as principal constituent
2224/13711	Tin [Sn] as principal constituent	2224/1377	Zirconium [Zr] as principal constituent
2224/13713	Bismuth [Bi] as principal constituent	2224/13771	Chromium [Cr] as principal constituent
2224/13714	Thallium [Tl] as principal constituent	2224/13772	Vanadium [V] as principal constituent
2224/13716	Lead [Pb] as principal constituent	2224/13773	Rhodium [Rh] as principal constituent
2224/13717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/13776	Ruthenium [Ru] as principal constituent
2224/13718	Zinc [Zn] as principal constituent	2224/13778	Iridium [Ir] as principal constituent
2224/1372	Antimony [Sb] as principal constituent	2224/13779	Niobium [Nb] as principal constituent
2224/13723	Magnesium [Mg] as principal constituent	2224/1378	Molybdenum [Mo] as principal constituent
2224/13724	Aluminium [Al] as principal constituent	2224/13781	Tantalum [Ta] as principal constituent
			2224/13783	Rhenium [Re] as principal constituent
			2224/13784	Tungsten [W] as principal constituent
			2224/13786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
			2224/13787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13788)
			2224/13788	Glasses, e.g. amorphous oxides, nitrides or fluorides
			2224/1379	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy

2224/13791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/13849	Manganese [Mn] as principal constituent
2224/13793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/137 - H01L 2224/13791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/13855	Nickel [Ni] as principal constituent
2224/13794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/137 - H01L 2224/13791	2224/13857	Cobalt [Co] as principal constituent
2224/13795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/137 - H01L 2224/13791	2224/1386	Iron [Fe] as principal constituent
2224/13798	Fillers	2224/13863	the principal constituent melting at a temperature of greater than 1550°C
2224/13799	Base material	2224/13864	Palladium [Pd] as principal constituent
2224/138	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/13866	Titanium [Ti] as principal constituent
2224/13801	the principal constituent melting at a temperature of less than 400°C	2224/13869	Platinum [Pt] as principal constituent
2224/13805	Gallium [Ga] as principal constituent	2224/1387	Zirconium [Zr] as principal constituent
2224/13809	Indium [In] as principal constituent	2224/13871	Chromium [Cr] as principal constituent
2224/13811	Tin [Sn] as principal constituent	2224/13872	Vanadium [V] as principal constituent
2224/13813	Bismuth [Bi] as principal constituent	2224/13873	Rhodium [Rh] as principal constituent
2224/13814	Thallium [Tl] as principal constituent	2224/13876	Ruthenium [Ru] as principal constituent
2224/13816	Lead [Pb] as principal constituent	2224/13878	Iridium [Ir] as principal constituent
2224/13817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/13879	Niobium [Nb] as principal constituent
2224/13818	Zinc [Zn] as principal constituent	2224/1388	Molybdenum [Mo] as principal constituent
2224/1382	Antimony [Sb] as principal constituent	2224/13881	Tantalum [Ta] as principal constituent
2224/13823	Magnesium [Mg] as principal constituent	2224/13883	Rhenium [Re] as principal constituent
2224/13824	Aluminium [Al] as principal constituent	2224/13884	Tungsten [W] as principal constituent
2224/13838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/13886	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/13839	Silver [Ag] as principal constituent	2224/13887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13888)
2224/13844	Gold [Au] as principal constituent	2224/13888	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/13847	Copper [Cu] as principal constituent	2224/1389	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
		2224/13891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
		2224/13893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/138 - H01L 2224/13891 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond

2224/13894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/138 - H01L 2224/13891	2224/13957	Cobalt [Co] as principal constituent
2224/13895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/138 - H01L 2224/13891	2224/1396	Iron [Fe] as principal constituent
2224/13898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/13963	the principal constituent melting at a temperature of greater than 1550°C
2224/13899	Coating material	2224/13964	Palladium [Pd] as principal constituent
2224/139	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/13966	Titanium [Ti] as principal constituent
2224/13901	the principal constituent melting at a temperature of less than 400°C	2224/13969	Platinum [Pt] as principal constituent
2224/13905	Gallium [Ga] as principal constituent	2224/1397	Zirconium [Zr] as principal constituent
2224/13909	Indium [In] as principal constituent	2224/13971	Chromium [Cr] as principal constituent
2224/13911	Tin [Sn] as principal constituent	2224/13972	Vanadium [V] as principal constituent
2224/13913	Bismuth [Bi] as principal constituent	2224/13973	Rhodium [Rh] as principal constituent
2224/13914	Thallium [Tl] as principal constituent	2224/13976	Ruthenium [Ru] as principal constituent
2224/13916	Lead [Pb] as principal constituent	2224/13978	Iridium [Ir] as principal constituent
2224/13917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/13979	Niobium [Nb] as principal constituent
2224/13918	Zinc [Zn] as principal constituent	2224/1398	Molybdenum [Mo] as principal constituent
2224/1392	Antimony [Sb] as principal constituent	2224/13981	Tantalum [Ta] as principal constituent
2224/13923	Magnesium [Mg] as principal constituent	2224/13983	Rhenium [Re] as principal constituent
2224/13924	Aluminium [Al] as principal constituent	2224/13984	Tungsten [W] as principal constituent
2224/13938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/13986	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/13939	Silver [Ag] as principal constituent	2224/13987	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/13988)
2224/13944	Gold [Au] as principal constituent	2224/13988	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/13947	Copper [Cu] as principal constituent	2224/1399	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/13949	Manganese [Mn] as principal constituent	2224/13991	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/13955	Nickel [Ni] as principal constituent	2224/13993	with a principal constituent of the material being a solid not provided for in groups H01L 2224/139 - H01L 2224/13991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
		2224/13994	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/139 - H01L 2224/13991

2224/13995	with a principal constituent of the material being a gas not provided for in groups H01L 2224/139 - H01L 2224/13991	2224/14152	being non uniform, i.e. having a non uniform pitch across the array
2224/13998	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/14153	with a staggered arrangement, e.g. depopulated array
2224/13999	Shape or distribution of the fillers	2224/14154	covering only portions of the surface to be connected
2224/14	of a plurality of bump connectors	2224/14155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/1401	Structure	2224/14156	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/1403	Bump connectors having different sizes, e.g. different diameters, heights or widths	2224/1416	Random layout, i.e. layout with no symmetry
2224/1405	Shape	2224/14163	with a staggered arrangement
2224/14051	Bump connectors having different shapes	2224/14164	covering only portions of the surface to be connected
2224/141	Disposition	2224/14165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/14104	relative to the bonding areas, e.g. bond pads, of the semiconductor or solid-state body	2224/14166	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/1411	the bump connectors being bonded to at least one common bonding area	2224/14177	Combinations of arrays with different layouts
2224/1412	Layout	2224/14179	Corner adaptations, i.e. disposition of the bump connectors at the corners of the semiconductor or solid-state body
2224/1413	Square or rectangular array	2224/1418	being disposed on at least two different sides of the body, e.g. dual array
2224/14131	being uniform, i.e. having a uniform pitch across the array	2224/14181	On opposite sides of the body
2224/14132	being non uniform, i.e. having a non uniform pitch across the array	2224/14183	On contiguous sides of the body
2224/14133	with a staggered arrangement, e.g. depopulated array	2224/145	Material
2224/14134	covering only portions of the surface to be connected	2224/14505	Bump connectors having different materials
2224/14135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/1451	Function
2224/14136	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/14515	Bump connectors having different functions
2224/1414	Circular array, i.e. array with radial symmetry	2224/14517	including bump connectors providing primarily mechanical bonding
2224/14141	being uniform, i.e. having a uniform pitch across the array	2224/14519	including bump connectors providing primarily thermal dissipation
2224/14142	being non uniform, i.e. having a non uniform pitch across the array	2224/15	Structure, shape, material or disposition of the bump connectors after the connecting process
2224/14143	with a staggered arrangement, e.g. depopulated array	2224/16	of an individual bump connector
2224/14144	covering only portions of the surface to be connected	2224/1601	Structure
2224/14145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/16012	relative to the bonding area, e.g. bond pad
2224/14146	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/16013	the bump connector being larger than the bonding area, e.g. bond pad
2224/1415	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry	2224/16014	the bump connector being smaller than the bonding area, e.g. bond pad
2224/14151	being uniform, i.e. having a uniform pitch across the array	2224/1605	Shape
		2224/16052	in top view
		2224/16054	being rectangular or square
		2224/16055	being circular or elliptic
		2224/16056	comprising protrusions or indentations
		2224/16057	in side view
		2224/16058	being non uniform along the bump connector
		2224/16059	comprising protrusions or indentations

2224/1607	of bonding interfaces, e.g. interlocking features	2224/16168	the bump connector connecting to a bonding area protruding from the surface of the item
2224/161	Disposition	2224/16175	the item being metallic
2224/16104	relative to the bonding area, e.g. bond pad	2224/16183	the bump connector connecting to a potential ring of the item
2224/16105	the bump connector connecting bonding areas being not aligned with respect to each other	2224/16187	the bump connector connecting to a bonding area disposed in a recess of the surface of the item
2224/16106	the bump connector connecting one bonding area to at least two respective bonding areas	2224/16188	the bump connector connecting to a bonding area protruding from the surface of the item
2224/16108	the bump connector not being orthogonal to the surface	2224/16195	the item being a discrete passive component
2224/16111	the bump connector being disposed in a recess of the surface	2224/16197	the bump connector connecting to a bonding area disposed in a recess of the surface of the item
2224/16112	the bump connector being at least partially embedded in the surface	2224/16198	the bump connector connecting to a bonding area protruding from the surface of the item
2224/16113	the whole bump connector protruding from the surface	2224/16221	the body and the item being stacked
2224/1613	the bump connector connecting within a semiconductor or solid-state body, i.e. connecting two bonding areas on the same semiconductor or solid-state body	2224/16225	the item being non-metallic, e.g. insulating substrate with or without metallisation
2224/16135	the bump connector connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip	2224/16227	the bump connector connecting to a bond pad of the item
2224/16137	the bodies being arranged next to each other, e.g. on a common substrate	2224/1623	the bump connector connecting to a pin of the item
2224/16141	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements	2224/16233	the bump connector connecting to a potential ring of the item
2224/16145	the bodies being stacked	2224/16235	the bump connector connecting to a via metallisation of the item
2224/16146	the bump connector connecting to a via connection in the semiconductor or solid-state body	2224/16237	the bump connector connecting to a bonding area disposed in a recess of the surface of the item
2224/16147	the bump connector connecting to a bonding area disposed in a recess of the surface	2224/16238	the bump connector connecting to a bonding area protruding from the surface of the item
2224/16148	the bump connector connecting to a bonding area protruding from the surface	2224/1624	the bump connector connecting between the body and an opposite side of the item with respect to the body
2224/16151	the bump connector connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive	2224/16245	the item being metallic
2224/16153	the body and the item being arranged next to each other, e.g. on a common substrate	2224/16253	the bump connector connecting to a potential ring of the item
2224/16155	the item being non-metallic, e.g. being an insulating substrate with or without metallisation	2224/16257	the bump connector connecting to a bonding area disposed in a recess of the surface of the item
2224/16157	the bump connector connecting to a bond pad of the item	2224/16258	the bump connector connecting to a bonding area protruding from the surface of the item
2224/1616	the bump connector connecting to a pin of the item	2224/1626	the bump connector connecting between the body and an opposite side of the item with respect to the body
2224/16163	the bump connector connecting to a potential ring of the item	2224/16265	the item being a discrete passive component
2224/16165	the bump connector connecting to a via metallisation of the item	2224/16267	the bump connector connecting to a bonding area disposed in a recess of the surface of the item
2224/16167	the bump connector connecting to a bonding area disposed in a recess of the surface of the item	2224/16268	the bump connector connecting to a bonding area protruding from the surface of the item
			2224/165	Material

2224/16501	at the bonding interface	2224/17154	covering only portions of the surface to be connected
2224/16502	comprising an eutectic alloy	2224/17155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/16503	comprising an intermetallic compound	2224/17156	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/16505	outside the bonding interface, e.g. in the bulk of the bump connector	2224/1716	Random layout, i.e. layout with no symmetry
2224/16506	comprising an eutectic alloy	2224/17163	with a staggered arrangement
2224/16507	comprising an intermetallic compound	2224/17164	covering only portions of the surface to be connected
2224/17	of a plurality of bump connectors	2224/17165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/1701	Structure	2224/17166	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/1703	Bump connectors having different sizes, e.g. different diameters, heights or widths	2224/17177	Combinations of arrays with different layouts
2224/1705	Shape	2224/17179	Corner adaptations, i.e. disposition of the bump connectors at the corners of the semiconductor or solid-state body
2224/17051	Bump connectors having different shapes	2224/1718	being disposed on at least two different sides of the body, e.g. dual array
2224/17055	of their bonding interfaces	2224/17181	On opposite sides of the body
2224/171	Disposition	2224/17183	On contiguous sides of the body
2224/17104	relative to the bonding areas, e.g. bond pads	2224/175	Material
2224/17106	the bump connectors being bonded to at least one common bonding area	2224/17505	Bump connectors having different materials
2224/17107	the bump connectors connecting two common bonding areas	2224/1751	Function
2224/1712	Layout (layout of bump connectors prior to the connecting process H01L 2224/1412)	2224/17515	Bump connectors having different functions
2224/1713	Square or rectangular array	2224/17517	including bump connectors providing primarily mechanical support
2224/17132	being non uniform, i.e. having a non uniform pitch across the array	2224/17519	including bump connectors providing primarily thermal dissipation
2224/17133	with a staggered arrangement, e.g. depopulated array	2224/18	High density interconnect [HDI] connectors; Manufacturing methods related thereto
2224/17134	covering only portions of the surface to be connected	2224/19	Manufacturing methods of high density interconnect preforms
2224/17135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/20	Structure, shape, material or disposition of high density interconnect preforms
2224/17136	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/21	of an individual HDI interconnect
2224/1714	Circular array, i.e. array with radial symmetry	2224/2101	Structure
2224/17142	being non uniform, i.e. having a non uniform pitch across the array	2224/2105	Shape
2224/17143	with a staggered arrangement	2224/211	Disposition
2224/17144	covering only portions of the surface to be connected	2224/214	Connecting portions
2224/17145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/215	Material
2224/17146	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/22	of a plurality of HDI interconnects
2224/1715	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry	2224/2201	Structure
2224/17151	being uniform, i.e. having a uniform pitch across the array	2224/2205	Shape
2224/17152	being non uniform, i.e. having a non uniform pitch across the array	2224/221	Disposition
2224/17153	with a staggered arrangement, e.g. depopulated array	2224/224	Connecting portions
			2224/225	Material
			2224/22505	HDI interconnects having different materials
			2224/23	Structure, shape, material or disposition of the high density interconnect connectors after the connecting process
			2224/24	of an individual high density interconnect connector

2224/2401	Structure	2224/24227	the HDI interconnect not connecting to the same level of the item at which the semiconductor or solid-state body is mounted, e.g. the semiconductor or solid-state body being mounted in a cavity or on a protrusion of the item
2224/24011	Deposited, e.g. MCM-D type	2224/24245	the item being metallic
2224/2402	Laminated, e.g. MCM-L type	2224/24246	the HDI interconnect connecting to the same level of the item at which the semiconductor or solid-state body is mounted, e.g. the item being planar
2224/2405	Shape	2224/24247	the HDI interconnect not connecting to the same level of the item at which the semiconductor or solid-state body is mounted, e.g. the semiconductor or solid-state body being mounted in a cavity or on a protrusion of the item
2224/24051	Conformal with the semiconductor or solid-state device	2224/24265	the item being a discrete passive component
2224/241	Disposition	2224/244	Connecting portions
2224/24101	Connecting bonding areas at the same height	2224/245	Material
2224/24105	Connecting bonding areas at different heights	2224/2499	Auxiliary members for HDI interconnects, e.g. spacers, alignment aids
2224/2413	Connecting within a semiconductor or solid-state body	2224/24991	being formed on the semiconductor or solid-state body to be connected
2224/24135	Connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip	2224/24992	Flow barrier
2224/24137	the bodies being arranged next to each other, e.g. on a common substrate	2224/24996	being formed on an item to be connected not being a semiconductor or solid-state body
2224/24141	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements	2224/24997	Flow barrier
2224/24145	the bodies being stacked	2224/24998	Reinforcing structures, e.g. ramp-like support
2224/24146	the HDI interconnect connecting to the same level of the lower semiconductor or solid-state body at which the upper semiconductor or solid-state body is mounted	2224/25	of a plurality of high density interconnect connectors
2224/24147	the HDI interconnect not connecting to the same level of the lower semiconductor or solid-state body at which the upper semiconductor or solid-state body is mounted, e.g. the upper semiconductor or solid-state body being mounted in a cavity or on a protrusion of the lower semiconductor or solid-state body	2224/2501	Structure
2224/24151	Connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive	2224/2505	Shape
2224/24153	the body and the item being arranged next to each other, e.g. on a common substrate	2224/251	Disposition
2224/24155	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/25105	Connecting at different heights
2224/24175	the item being metallic	2224/2511	the connectors being bonded to at least one common bonding area
2224/24195	the item being a discrete passive component	2224/25111	the connectors connecting two common bonding areas
2224/24221	the body and the item being stacked	2224/25112	the connectors connecting a common bonding area on the semiconductor or solid-state body to different bonding areas outside the body
2224/24225	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/25113	the connectors connecting different bonding areas on the semiconductor or solid-state body to a common bonding area outside the body
2224/24226	the HDI interconnect connecting to the same level of the item at which the semiconductor or solid-state body is mounted, e.g. the item being planar	2224/2512	Layout
			2224/25171	Fan-out arrangements
			2224/25174	Stacked arrangements
			2224/25175	Parallel arrangements
			2224/25177	Combinations of a plurality of arrangements
			2224/2518	being disposed on at least two different sides of the body, e.g. dual array
			2224/254	Connecting portions

2224/2541	the connecting portions being stacked	2224/27426	Chemical solution deposition [CSD], i.e. using a liquid precursor
2224/2543	the connecting portions being staggered	2224/27428	Wave coating
2224/255	Material	2224/2743	in solid form
2224/26	. .	Layer connectors, e.g. plate connectors, solder or adhesive layers; Manufacturing methods related thereto	2224/27436	Lamination of a preform, e.g. foil, sheet or layer
2224/2612	. . .	Auxiliary members for layer connectors, e.g. spacers	2224/27438	the preform being at least partly pre-patterned
2224/26122	being formed on the semiconductor or solid-state body to be connected	2224/2744	by transfer printing
2224/26125	Reinforcing structures	2224/27442	using a powder
2224/26135	Alignment aids	2224/27444	in gaseous form
2224/26145	Flow barriers	2224/2745	Physical vapour deposition [PVD], e.g. evaporation, or sputtering
2224/26152	being formed on an item to be connected not being a semiconductor or solid-state body	2224/27452	Chemical vapour deposition [CVD], e.g. laser CVD
2224/26155	Reinforcing structures	2224/2746	Plating
2224/26165	Alignment aids	2224/27462	Electroplating
2224/26175	Flow barriers	2224/27464	Electroless plating
2224/27	. . .	Manufacturing methods	2224/27466	Conformal deposition, i.e. blanket deposition of a conformal layer on a patterned surface
2224/27001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate	2224/2747	using a lift-off mask
2224/27002	for supporting the semiconductor or solid-state body	2224/27472	Profile of the lift-off mask
2224/27003	for holding or transferring the layer preform	2224/27474	Multilayer masks
2224/27005	for aligning the layer connector, e.g. marks, spacers	2224/2748	Permanent masks, i.e. masks left in the finished device, e.g. passivation layers
2224/27009	for protecting parts during manufacture	2224/275	by chemical or physical modification of a pre-existing or pre-deposited material
2224/27011	Involving a permanent auxiliary member, i.e. a member which is left at least partly in the finished device, e.g. coating, dummy feature	2224/27502	Pre-existing or pre-deposited material
2224/27013	for holding or confining the layer connector, e.g. solder flow barrier	2224/27505	Sintering
2224/27015	for aligning the layer connector, e.g. marks, spacers	2224/2751	Anodisation
2224/27019	for protecting parts during the process	2224/27515	Curing and solidification, e.g. of a photosensitive layer material
2224/271	Manufacture and pre-treatment of the layer connector preform	2224/2752	Self-assembly, e.g. self-agglomeration of the layer material in a fluid
2224/2711	Shaping	2224/27522	Auxiliary means therefor, e.g. for self-assembly activation
2224/2712	Applying permanent coating	2224/27524	with special adaptation of the surface or of an auxiliary substrate, e.g. surface shape specially adapted for the self-assembly process
2224/273	by local deposition of the material of the layer connector	2224/27526	involving the material of the bonding area, e.g. bonding pad
2224/2731	in liquid form	2224/2755	Selective modification
2224/27312	Continuous flow, e.g. using a microsyringe, a pump, a nozzle or extrusion	2224/27552	using a laser or a focussed ion beam [FIB]
2224/27318	by dispensing droplets	2224/27554	Stereolithography, i.e. solidification of a pattern defined by a laser trace in a photosensitive resin
2224/2732	Screen printing, i.e. using a stencil	2224/276	by patterning a pre-deposited material (treatment of parts prior to assembly of the devices H01L 21/48)
2224/2733	in solid form	2224/27602	Mechanical treatment, e.g. polishing, grinding
2224/27332	using a powder	2224/2761	Physical or chemical etching
2224/27334	using preformed layer	2224/27612	by physical means only
2224/274	by blanket deposition of the material of the layer connector	2224/27614	by chemical means only
2224/2741	in liquid form	2224/27616	Chemical mechanical polishing [CMP]
2224/27416	Spin coating	2224/27618	with selective exposure, development and removal of a photosensitive layer material, e.g. of a photosensitive conductive resin
2224/27418	Spray coating	2224/2762	using masks
2224/2742	Curtain coating	2224/27622	Photolithography
2224/27422	by dipping, e.g. in a solder bath (hot-dipping C23C 2/00)			
2224/27424	Immersion coating, e.g. in a solder bath (immersion processes C23C 2/00)			

2224/2763	using a laser or a focused ion beam [FIB]	2224/29011	comprising apertures or cavities
2224/27632	Ablation by means of a laser or focused ion beam [FIB]	2224/29012	in top view
2224/277	involving monitoring, e.g. feedback loop	2224/29013	being rectangular or square
2224/278	Post-treatment of the layer connector	2224/29014	being circular or elliptic
2224/2781	Cleaning, e.g. oxide removal step, desmearing	2224/29015	comprising protrusions or indentations
2224/2782	Applying permanent coating, e.g. in-situ coating	2224/29016	in side view
2224/27821	Spray coating	2224/29017	being non uniform along the layer connector
2224/27822	by dipping, e.g. in a solder bath	2224/29018	comprising protrusions or indentations
2224/27823	Immersion coating, e.g. in a solder bath	2224/29019	at the bonding interface of the layer connector, i.e. on the surface of the layer connector
2224/27824	Chemical solution deposition [CSD], i.e. using a liquid precursor	2224/2902	Disposition
2224/27825	Plating, e.g. electroplating, electroless plating	2224/29021	the layer connector being disposed in a recess of the surface (embedded layer connector H01L 2224/29022)
2224/27826	Physical vapour deposition [PVD], e.g. evaporation, or sputtering	2224/29022	the layer connector being at least partially embedded in the surface
2224/27827	Chemical vapour deposition [CVD], e.g. laser CVD	2224/29023	the whole layer connector protruding from the surface
2224/2783	Reworking, e.g. shaping (reflowing H01L 2224/27849)	2224/29024	the layer connector being disposed on a redistribution layer on the semiconductor or solid-state body
2224/27831	involving a chemical process, e.g. etching the layer connector	2224/29025	the layer connector being disposed on a via connection of the semiconductor or solid-state body
2224/2784	involving a mechanical process, e.g. planarising the layer connector	2224/29026	relative to the bonding area, e.g. bond pad, of the semiconductor or solid-state body
2224/27845	Chemical mechanical polishing [CMP]	2224/29027	the layer connector being offset with respect to the bonding area, e.g. bond pad
2224/27848	Thermal treatments, e.g. annealing, controlled cooling	2224/29028	the layer connector being disposed on at least two separate bonding areas, e.g. bond pads
2224/27849	Reflowing	2224/29034	the layer connector covering only portions of the surface to be connected
2224/279	Methods of manufacturing layer connectors involving a specific sequence of method steps	2224/29035	covering only the peripheral area of the surface to be connected
2224/27901	with repetition of the same manufacturing step	2224/29036	covering only the central area of the surface to be connected
2224/27902	Multiple masking steps	2224/29075	Plural core members
2224/27903	using different masks	2224/29076	being mutually engaged together, e.g. through inserts
2224/27906	with modification of the same mask	2224/29078	being disposed next to each other, e.g. side-to-side arrangements
2224/2791	Forming a passivation layer after forming the layer connector	2224/2908	being stacked
2224/27912	the layer being used as a mask for patterning other parts	2224/29082	Two-layer arrangements
2224/27916	a passivation layer being used as a mask for patterning other parts	2224/29083	Three-layer arrangements
2224/28	Structure, shape, material or disposition of the layer connectors prior to the connecting process	2224/29084	Four-layer arrangements
2224/28105	Layer connectors formed on an encapsulation of the semiconductor or solid-state body, e.g. layer connectors on chip-scale packages	2224/29099	Material
2224/29	of an individual layer connector	2224/291	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/29001	Core members of the layer connector	2224/29101	the principal constituent melting at a temperature of less than 400°C
2224/29005	Structure	2224/29105	Gallium [Ga] as principal constituent
2224/29006	Layer connector larger than the underlying bonding area			
2224/29007	Layer connector smaller than the underlying bonding area			
2224/29008	Layer connector integrally formed with a redistribution layer on the semiconductor or solid-state body			
2224/29009	Layer connector integrally formed with a via connection of the semiconductor or solid-state body			
2224/2901	Shape			

2224/29109	Indium [In] as principal constituent	2224/29184	Tungsten [W] as principal constituent
2224/29111	Tin [Sn] as principal constituent	2224/29186	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/29113	Bismuth [Bi] as principal constituent	2224/29187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29188)
2224/29114	Thallium [Tl] as principal constituent	2224/29188	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/29116	Lead [Pb] as principal constituent	2224/2919	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/29191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/29118	Zinc [Zn] as principal constituent	2224/29193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/291 - H01L 2224/29191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/2912	Antimony [Sb] as principal constituent	2224/29194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/291 - H01L 2224/29191
2224/29123	Magnesium [Mg] as principal constituent	2224/29195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/291 - H01L 2224/29191
2224/29124	Aluminium [Al] as principal constituent	2224/29198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/29138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29199	Material of the matrix
2224/29139	Silver [Ag] as principal constituent	2224/292	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/29144	Gold [Au] as principal constituent	2224/29201	the principal constituent melting at a temperature of less than 400°C
2224/29147	Copper [Cu] as principal constituent	2224/29205	Gallium [Ga] as principal constituent
2224/29149	Manganese [Mn] as principal constituent	2224/29209	Indium [In] as principal constituent
2224/29155	Nickel [Ni] as principal constituent	2224/29211	Tin [Sn] as principal constituent
2224/29157	Cobalt [Co] as principal constituent	2224/29213	Bismuth [Bi] as principal constituent
2224/2916	Iron [Fe] as principal constituent	2224/29214	Thallium [Tl] as principal constituent
2224/29163	the principal constituent melting at a temperature of greater than 1550°C	2224/29216	Lead [Pb] as principal constituent
2224/29164	Palladium [Pd] as principal constituent	2224/29217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/29166	Titanium [Ti] as principal constituent		
2224/29169	Platinum [Pt] as principal constituent		
2224/2917	Zirconium [Zr] as principal constituent		
2224/29171	Chromium [Cr] as principal constituent		
2224/29172	Vanadium [V] as principal constituent		
2224/29173	Rhodium [Rh] as principal constituent		
2224/29176	Ruthenium [Ru] as principal constituent		
2224/29178	Iridium [Ir] as principal constituent		
2224/29179	Niobium [Nb] as principal constituent		
2224/2918	Molybdenum [Mo] as principal constituent		
2224/29181	Tantalum [Ta] as principal constituent		
2224/29183	Rhenium [Re] as principal constituent		

2224/29218	Zinc [Zn] as principal constituent	2224/29288	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/2922	Antimony [Sb] as principal constituent	2224/2929	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29223	Magnesium [Mg] as principal constituent	2224/29291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/29224	Aluminium [Al] as principal constituent	2224/29293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/292 - H01L 2224/29291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/29238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/292 - H01L 2224/29291
2224/29239	Silver [Ag] as principal constituent	2224/29295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/292 - H01L 2224/29291
2224/29244	Gold [Au] as principal constituent	2224/29298	Fillers
2224/29247	Copper [Cu] as principal constituent	2224/29299	Base material
2224/29249	Manganese [Mn] as principal constituent	2224/293	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/29255	Nickel [Ni] as principal constituent	2224/29301	the principal constituent melting at a temperature of less than 400°C
2224/29257	Cobalt [Co] as principal constituent	2224/29305	Gallium [Ga] as principal constituent
2224/2926	Iron [Fe] as principal constituent	2224/29309	Indium [In] as principal constituent
2224/29263	the principal constituent melting at a temperature of greater than 1550°C	2224/29311	Tin [Sn] as principal constituent
2224/29264	Palladium [Pd] as principal constituent	2224/29313	Bismuth [Bi] as principal constituent
2224/29266	Titanium [Ti] as principal constituent	2224/29314	Thallium [Tl] as principal constituent
2224/29269	Platinum [Pt] as principal constituent	2224/29316	Lead [Pb] as principal constituent
2224/2927	Zirconium [Zr] as principal constituent	2224/29317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/29271	Chromium [Cr] as principal constituent	2224/29318	Zinc [Zn] as principal constituent
2224/29272	Vanadium [V] as principal constituent	2224/2932	Antimony [Sb] as principal constituent
2224/29273	Rhodium [Rh] as principal constituent	2224/29323	Magnesium [Mg] as principal constituent
2224/29276	Ruthenium [Ru] as principal constituent	2224/29324	Aluminium [Al] as principal constituent
2224/29278	Iridium [Ir] as principal constituent	2224/29338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/29279	Niobium [Nb] as principal constituent			
2224/2928	Molybdenum [Mo] as principal constituent			
2224/29281	Tantalum [Ta] as principal constituent			
2224/29283	Rhenium [Re] as principal constituent			
2224/29284	Tungsten [W] as principal constituent			
2224/29286	with a principal constituent of the material being a non metallic, non metalloid inorganic material			
2224/29287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29288)			

2224/29339	Silver [Ag] as principal constituent	2224/29393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/293 - H01L 2224/29391 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/29344	Gold [Au] as principal constituent	2224/29394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/293 - H01L 2224/29391
2224/29347	Copper [Cu] as principal constituent	2224/29395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/293 - H01L 2224/29391
2224/29349	Manganese [Mn] as principal constituent	2224/29398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/29355	Nickel [Ni] as principal constituent	2224/29399	Coating material
2224/29357	Cobalt [Co] as principal constituent	2224/294	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/2936	Iron [Fe] as principal constituent	2224/29401	the principal constituent melting at a temperature of less than 400°C
2224/29363	the principal constituent melting at a temperature of greater than 1550°C	2224/29405	Gallium [Ga] as principal constituent
2224/29364	Palladium [Pd] as principal constituent	2224/29409	Indium [In] as principal constituent
2224/29366	Titanium [Ti] as principal constituent	2224/29411	Tin [Sn] as principal constituent
2224/29369	Platinum [Pt] as principal constituent	2224/29413	Bismuth [Bi] as principal constituent
2224/2937	Zirconium [Zr] as principal constituent	2224/29414	Thallium [Tl] as principal constituent
2224/29371	Chromium [Cr] as principal constituent	2224/29416	Lead [Pb] as principal constituent
2224/29372	Vanadium [V] as principal constituent	2224/29417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/29373	Rhodium [Rh] as principal constituent	2224/29418	Zinc [Zn] as principal constituent
2224/29376	Ruthenium [Ru] as principal constituent	2224/2942	Antimony [Sb] as principal constituent
2224/29378	Iridium [Ir] as principal constituent	2224/29423	Magnesium [Mg] as principal constituent
2224/29379	Niobium [Nb] as principal constituent	2224/29424	Aluminium [Al] as principal constituent
2224/2938	Molybdenum [Mo] as principal constituent	2224/29438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/29381	Tantalum [Ta] as principal constituent	2224/29439	Silver [Ag] as principal constituent
2224/29383	Rhenium [Re] as principal constituent	2224/29444	Gold [Au] as principal constituent
2224/29384	Tungsten [W] as principal constituent		
2224/29386	with a principal constituent of the material being a non metallic, non metalloid inorganic material		
2224/29387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29388)		
2224/29388	Glasses, e.g. amorphous oxides, nitrides or fluorides		
2224/2939	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy		
2224/29391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene		

2224/29447	Copper [Cu] as principal constituent	2224/29494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/294 - H01L 2224/29491
2224/29449	Manganese [Mn] as principal constituent	2224/29495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/294 - H01L 2224/29491
2224/29455	Nickel [Ni] as principal constituent	2224/29498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/29457	Cobalt [Co] as principal constituent	2224/29499	Shape or distribution of the fillers
2224/2946	Iron [Fe] as principal constituent	2224/2954	Coating
2224/29463	the principal constituent melting at a temperature of greater than 1550°C	2224/29541	Structure
2224/29464	Palladium [Pd] as principal constituent	2224/2955	Shape
2224/29466	Titanium [Ti] as principal constituent	2224/29551	being non uniform
2224/29469	Platinum [Pt] as principal constituent	2224/29552	comprising protrusions or indentations
2224/2947	Zirconium [Zr] as principal constituent	2224/29553	at the bonding interface of the layer connector, i.e. on the surface of the layer connector
2224/29471	Chromium [Cr] as principal constituent	2224/2956	Disposition
2224/29472	Vanadium [V] as principal constituent	2224/29561	On the entire surface of the core, i.e. integral coating
2224/29473	Rhodium [Rh] as principal constituent	2224/29562	On the entire exposed surface of the core
2224/29476	Ruthenium [Ru] as principal constituent	2224/29563	Only on parts of the surface of the core, i.e. partial coating
2224/29478	Iridium [Ir] as principal constituent	2224/29564	Only on the bonding interface of the layer connector
2224/29479	Niobium [Nb] as principal constituent	2224/29565	Only outside the bonding interface of the layer connector
2224/2948	Molybdenum [Mo] as principal constituent	2224/29566	Both on and outside the bonding interface of the layer connector
2224/29481	Tantalum [Ta] as principal constituent	2224/2957	Single coating layer
2224/29483	Rhenium [Re] as principal constituent	2224/29575	Plural coating layers
2224/29484	Tungsten [W] as principal constituent	2224/29576	being mutually engaged together, e.g. through inserts
2224/29486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/29578	being disposed next to each other, e.g. side-to-side arrangements
2224/29487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29488)	2224/2958	being stacked
2224/29488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/29582	Two-layer coating
2224/2949	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/29583	Three-layer coating
2224/29491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/29584	Four-layer coating
2224/29493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/294 - H01L 2224/29491 e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/29599	Material
		2224/296	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
		2224/29601	the principal constituent melting at a temperature of less than 400°C
		2224/29605	Gallium [Ga] as principal constituent
		2224/29609	Indium [In] as principal constituent
		2224/29611	Tin [Sn] as principal constituent
		2224/29613	Bismuth [Bi] as principal constituent

2224/29614	Thallium [Tl] as principal constituent	2224/29687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29688)
2224/29616	Lead [Pb] as principal constituent	2224/29688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/29617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/2969	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/29618	Zinc [Zn] as principal constituent	2224/29691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/2962	Antimony [Sb] as principal constituent	2224/29693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/296 - H01L 2224/29691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/29623	Magnesium [Mg] as principal constituent	2224/29694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/296 - H01L 2224/29691
2224/29624	Aluminium [Al] as principal constituent	2224/29695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/296 - H01L 2224/29691
2224/29638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/29639	Silver [Ag] as principal constituent	2224/29699	Material of the matrix
2224/29644	Gold [Au] as principal constituent	2224/297	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/29647	Copper [Cu] as principal constituent	2224/29701	the principal constituent melting at a temperature of less than 400°C
2224/29649	Manganese [Mn] as principal constituent	2224/29705	Gallium [Ga] as principal constituent
2224/29655	Nickel [Ni] as principal constituent	2224/29709	Indium [In] as principal constituent
2224/29657	Cobalt [Co] as principal constituent	2224/29711	Tin [Sn] as principal constituent
2224/2966	Iron [Fe] as principal constituent	2224/29713	Bismuth [Bi] as principal constituent
2224/29663	the principal constituent melting at a temperature of greater than 1550°C	2224/29714	Thallium [Tl] as principal constituent
2224/29664	Palladium [Pd] as principal constituent	2224/29716	Lead [Pb] as principal constituent
2224/29666	Titanium [Ti] as principal constituent	2224/29717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/29669	Platinum [Pt] as principal constituent	2224/29718	Zinc [Zn] as principal constituent
2224/2967	Zirconium [Zr] as principal constituent	2224/2972	Antimony [Sb] as principal constituent
2224/29671	Chromium [Cr] as principal constituent	2224/29723	Magnesium [Mg] as principal constituent
2224/29672	Vanadium [V] as principal constituent		
2224/29673	Rhodium [Rh] as principal constituent		
2224/29676	Ruthenium [Ru] as principal constituent		
2224/29678	Iridium [Ir] as principal constituent		
2224/29679	Niobium [Nb] as principal constituent		
2224/2968	Molybdenum [Mo] as principal constituent		
2224/29681	Tantalum [Ta] as principal constituent		
2224/29683	Rhenium [Re] as principal constituent		
2224/29684	Tungsten [W] as principal constituent		
2224/29686	with a principal constituent of the material being a non metallic, non metalloid inorganic material		

2224/29724	Aluminium [Al] as principal constituent	2224/29791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/29738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/29793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/297 - H01L 2224/29791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/29739	Silver [Ag] as principal constituent	2224/29794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/297 - H01L 2224/29791
2224/29744	Gold [Au] as principal constituent	2224/29795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/297 - H01L 2224/29791
2224/29747	Copper [Cu] as principal constituent	2224/29798	Fillers
2224/29749	Manganese [Mn] as principal constituent	2224/29799	Base material
2224/29755	Nickel [Ni] as principal constituent	2224/298	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/29757	Cobalt [Co] as principal constituent	2224/29801	the principal constituent melting at a temperature of less than 400°C
2224/2976	Iron [Fe] as principal constituent	2224/29805	Gallium [Ga] as principal constituent
2224/29763	the principal constituent melting at a temperature of greater than 1550°C	2224/29809	Indium [In] as principal constituent
2224/29764	Palladium [Pd] as principal constituent	2224/29811	Tin [Sn] as principal constituent
2224/29766	Titanium [Ti] as principal constituent	2224/29813	Bismuth [Bi] as principal constituent
2224/29769	Platinum [Pt] as principal constituent	2224/29814	Thallium [Tl] as principal constituent
2224/2977	Zirconium [Zr] as principal constituent	2224/29816	Lead [Pb] as principal constituent
2224/29771	Chromium [Cr] as principal constituent	2224/29817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/29772	Vanadium [V] as principal constituent	2224/29818	Zinc [Zn] as principal constituent
2224/29773	Rhodium [Rh] as principal constituent	2224/2982	Antimony [Sb] as principal constituent
2224/29776	Ruthenium [Ru] as principal constituent	2224/29823	Magnesium [Mg] as principal constituent
2224/29778	Iridium [Ir] as principal constituent	2224/29824	Aluminium [Al] as principal constituent
2224/29779	Niobium [Nb] as principal constituent	2224/29838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/2978	Molybdenum [Mo] as principal constituent	2224/29839	Silver [Ag] as principal constituent
2224/29781	Tantalum [Ta] as principal constituent	2224/29844	Gold [Au] as principal constituent
2224/29783	Rhenium [Re] as principal constituent	2224/29847	Copper [Cu] as principal constituent
2224/29784	Tungsten [W] as principal constituent		
2224/29786	with a principal constituent of the material being a non metallic, non metalloid inorganic material		
2224/29787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29788)		
2224/29788	Glasses, e.g. amorphous oxides, nitrides or fluorides		
2224/2979	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy		

2224/29849	Manganese [Mn] as principal constituent	2224/29894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/298 - H01L 2224/29891
2224/29855	Nickel [Ni] as principal constituent	2224/29895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/298 - H01L 2224/29891
2224/29857	Cobalt [Co] as principal constituent	2224/29898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/2986	Iron [Fe] as principal constituent	2224/29899	Coating material
2224/29863	the principal constituent melting at a temperature of greater than 1550°C	2224/299	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/29864	Palladium [Pd] as principal constituent	2224/29901	the principal constituent melting at a temperature of less than 400°C
2224/29866	Titanium [Ti] as principal constituent	2224/29905	Gallium [Ga] as principal constituent
2224/29869	Platinum [Pt] as principal constituent	2224/29909	Indium [In] as principal constituent
2224/2987	Zirconium [Zr] as principal constituent	2224/29911	Tin [Sn] as principal constituent
2224/29871	Chromium [Cr] as principal constituent	2224/29913	Bismuth [Bi] as principal constituent
2224/29872	Vanadium [V] as principal constituent	2224/29914	Thallium [Tl] as principal constituent
2224/29873	Rhodium [Rh] as principal constituent	2224/29916	Lead [Pb] as principal constituent
2224/29876	Ruthenium [Ru] as principal constituent	2224/29917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/29878	Iridium [Ir] as principal constituent	2224/29918	Zinc [Zn] as principal constituent
2224/29879	Niobium [Nb] as principal constituent	2224/2992	Antimony [Sb] as principal constituent
2224/2988	Molybdenum [Mo] as principal constituent	2224/29923	Magnesium [Mg] as principal constituent
2224/29881	Tantalum [Ta] as principal constituent	2224/29924	Aluminium [Al] as principal constituent
2224/29883	Rhenium [Re] as principal constituent	2224/29938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/29884	Tungsten [W] as principal constituent	2224/29939	Silver [Ag] as principal constituent
2224/29886	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/29944	Gold [Au] as principal constituent
2224/29887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29888)	2224/29947	Copper [Cu] as principal constituent
2224/29888	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/29949	Manganese [Mn] as principal constituent
2224/2989	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/29955	Nickel [Ni] as principal constituent
2224/29891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene		
2224/29893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/298 - H01L 2224/29891 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond		

2224/29957	Cobalt [Co] as principal constituent	2224/29995	with a principal constituent of the material being a gas not provided for in groups H01L 2224/299 - H01L 2224/29991
2224/2996	Iron [Fe] as principal constituent	2224/29998	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/29963	the principal constituent melting at a temperature of greater than 1550°C	2224/29999	Shape or distribution of the fillers
2224/29964	Palladium [Pd] as principal constituent	2224/30	of a plurality of layer connectors
2224/29966	Titanium [Ti] as principal constituent	2224/3001	Structure
2224/29969	Platinum [Pt] as principal constituent	2224/3003	Layer connectors having different sizes, e.g. different heights or widths
2224/2997	Zirconium [Zr] as principal constituent	2224/3005	Shape
2224/29971	Chromium [Cr] as principal constituent	2224/30051	Layer connectors having different shapes
2224/29972	Vanadium [V] as principal constituent	2224/301	Disposition
2224/29973	Rhodium [Rh] as principal constituent	2224/30104	relative to the bonding areas, e.g. bond pads, of the semiconductor or solid-state body
2224/29976	Ruthenium [Ru] as principal constituent	2224/3011	the layer connectors being bonded to at least one common bonding area
2224/29978	Iridium [Ir] as principal constituent	2224/3012	Layout
2224/29979	Niobium [Nb] as principal constituent	2224/3013	Square or rectangular array
2224/2998	Molybdenum [Mo] as principal constituent	2224/30131	being uniform, i.e. having a uniform pitch across the array
2224/29981	Tantalum [Ta] as principal constituent	2224/30132	being non uniform, i.e. having a non uniform pitch across the array
2224/29983	Rhenium [Re] as principal constituent	2224/30133	with a staggered arrangement, e.g. depopulated array
2224/29984	Tungsten [W] as principal constituent	2224/30134	covering only portions of the surface to be connected
2224/29986	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/30135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/29987	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/29988)	2224/30136	Covering only the central area of the surface to be connected, i.e. central arrangements
2224/29988	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/3014	Circular array, i.e. array with radial symmetry
2224/2999	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/30141	being uniform, i.e. having a uniform pitch across the array
2224/29991	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/30142	being non uniform, i.e. having a non uniform pitch across the array
2224/29993	with a principal constituent of the material being a solid not provided for in groups H01L 2224/299 - H01L 2224/29991 e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/30143	covering only portions of the surface to be connected
2224/29994	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/299 - H01L 2224/29991	2224/30145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
		2224/30146	Covering only the central area of the surface to be connected, i.e. central arrangements
		2224/3015	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry
		2224/30151	being uniform, i.e. having a uniform pitch across the array
		2224/30152	being non uniform, i.e. having a non uniform pitch across the array
		2224/30153	with a staggered arrangement, e.g. depopulated array

2224/30154	covering only portions of the surface to be connected	2224/32104	relative to the bonding area, e.g. bond pad
2224/30155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/32105	the layer connector connecting bonding areas being not aligned with respect to each other
2224/30156	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/32106	the layer connector connecting one bonding area to at least two respective bonding areas
2224/3016	Random layout, i.e. layout with no symmetry	2224/32111	the layer connector being disposed in a recess of the surface
2224/30163	with a staggered arrangement	2224/32112	the layer connector being at least partially embedded in the surface
2224/30164	covering only portions of the surface to be connected	2224/32113	the whole layer connector protruding from the surface
2224/30165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/3213	the layer connector connecting within a semiconductor or solid-state body, i.e. connecting two bonding areas on the same semiconductor or solid-state body
2224/30166	Covering only the central area of the surface to be connected, i.e. central arrangements	2224/32135	the layer connector connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip
2224/30177	Combinations of arrays with different layouts	2224/32137	the bodies being arranged next to each other, e.g. on a common substrate
2224/30179	Corner adaptations, i.e. disposition of the layer connectors at the corners of the semiconductor or solid-state body	2224/32141	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements
2224/3018	being disposed on at least two different sides of the body, e.g. dual array	2224/32145	the bodies being stacked
2224/30181	On opposite sides of the body	2224/32146	the layer connector connecting to a via connection in the semiconductor or solid-state body
2224/30183	On contiguous sides of the body	2224/32147	the layer connector connecting to a bonding area disposed in a recess of the surface
2224/305	Material	2224/32148	the layer connector connecting to a bonding area protruding from the surface
2224/30505	Layer connectors having different materials	2224/32151	the layer connector connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive
2224/3051	Function	2224/32153	the body and the item being arranged next to each other, e.g. on a common substrate
2224/30515	Layer connectors having different functions	2224/32155	the item being non-metallic, e.g. being an insulating substrate with or without metallisation
2224/30517	including layer connectors providing primarily mechanical bonding	2224/32157	the layer connector connecting to a bond pad of the item
2224/30519	including layer connectors providing primarily thermal dissipation	2224/3216	the layer connector connecting to a pin of the item
2224/31	Structure, shape, material or disposition of the layer connectors after the connecting process	2224/32163	the layer connector connecting to a potential ring of the item
2224/32	of an individual layer connector	2224/32165	the layer connector connecting to a via metallisation of the item
2224/3201	Structure	2224/32167	the layer connector connecting to a bonding area disposed in a recess of the surface of the item
2224/32012	relative to the bonding area, e.g. bond pad	2224/32168	the layer connector connecting to a bonding area protruding from the surface of the item
2224/32013	the layer connector being larger than the bonding area, e.g. bond pad	2224/32175	the item being metallic
2224/32014	the layer connector being smaller than the bonding area, e.g. bond pad	2224/32183	the layer connector connecting to a potential ring of the item
2224/3205	Shape		
2224/32052	in top view		
2224/32053	being non uniform along the layer connector		
2224/32054	being rectangular or square		
2224/32055	being circular or elliptic		
2224/32056	comprising protrusions or indentations		
2224/32057	in side view		
2224/32058	being non uniform along the layer connector		
2224/32059	comprising protrusions or indentations		
2224/3207	of bonding interfaces, e.g. interlocking features		
2224/321	Disposition		

2224/32187	the layer connector connecting to a bonding area disposed in a recess of the surface of the item	2224/32506	comprising an eutectic alloy
2224/32188	the layer connector connecting to a bonding area protruding from the surface of the item	2224/32507	comprising an intermetallic compound
2224/32195	the item being a discrete passive component	2224/33	of a plurality of layer connectors
2224/32197	the layer connector connecting to a bonding area disposed in a recess of the surface of the item	2224/3301	Structure
2224/32198	the layer connector connecting to a bonding area protruding from the surface of the item	2224/3303	Layer connectors having different sizes, e.g. different heights or widths
2224/32221	the body and the item being stacked	2224/3305	Shape
2224/32225	the item being non-metallic, e.g. insulating substrate with or without metallisation	2224/33051	Layer connectors having different shapes
2224/32227	the layer connector connecting to a bond pad of the item	2224/33055	of their bonding interfaces
2224/3223	the layer connector connecting to a pin of the item	2224/331	Disposition
2224/32233	the layer connector connecting to a potential ring of the item	2224/33104	relative to the bonding areas, e.g. bond pads
2224/32235	the layer connector connecting to a via metallisation of the item	2224/33106	the layer connectors being bonded to at least one common bonding area
2224/32237	the layer connector connecting to a bonding area disposed in a recess of the surface of the item	2224/33107	the layer connectors connecting two common bonding areas
2224/32238	the layer connector connecting to a bonding area protruding from the surface of the item	2224/3312	Layout (layout of layer connectors prior to the connecting process H01L 2224/3012)
2224/3224	the layer connector connecting between the body and an opposite side of the item with respect to the body	2224/3313	Square or rectangular array
2224/32245	the item being metallic	2224/33132	being non uniform, i.e. having a non uniform pitch across the array
2224/32253	the layer connector connecting to a potential ring of the item	2224/33133	with a staggered arrangement, e.g. depopulated array
2224/32257	the layer connector connecting to a bonding area disposed in a recess of the surface of the item	2224/33134	covering only portions of the surface to be connected
2224/32258	the layer connector connecting to a bonding area protruding from the surface of the item	2224/33135	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/3226	the layer connector connecting between the body and an opposite side of the item with respect to the body	2224/3314	Circular array, i.e. array with radial symmetry
2224/32265	the item being a discrete passive component	2224/33142	being non uniform, i.e. having a non uniform pitch across the array
2224/32267	the layer connector connecting to a bonding area disposed in a recess of the surface of the item	2224/33143	with a staggered arrangement
2224/32268	the layer connector connecting to a bonding area protruding from the surface of the item	2224/33144	covering only portions of the surface to be connected
2224/325	Material	2224/33145	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
2224/32501	at the bonding interface	2224/3315	Mirror array, i.e. array having only a reflection symmetry, i.e. bilateral symmetry
2224/32502	comprising an eutectic alloy	2224/33151	being uniform, i.e. having a uniform pitch across the array
2224/32503	comprising an intermetallic compound	2224/33152	being non uniform, i.e. having a non uniform pitch across the array
2224/32505	outside the bonding interface, e.g. in the bulk of the layer connector	2224/33153	with a staggered arrangement, e.g. depopulated array
			2224/33154	covering only portions of the surface to be connected
			2224/33155	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements
			2224/33156	Covering only the central area of the surface to be connected, i.e. central arrangements
			2224/3316	Random layout, i.e. layout with no symmetry
			2224/33163	with a staggered arrangement
			2224/33164	covering only portions of the surface to be connected

2224/33165	Covering only the peripheral area of the surface to be connected, i.e. peripheral arrangements	2224/35848	Thermal treatments, e.g. annealing, controlled cooling
2224/33177	Combinations of arrays with different layouts	2224/35985	Methods of manufacturing strap connectors involving a specific sequence of method steps
2224/33179	Corner adaptations, i.e. disposition of the layer connectors at the corners of the semiconductor or solid-state body	2224/35986	with repetition of the same manufacturing step
2224/3318	being disposed on at least two different sides of the body, e.g. dual array	2224/36	Structure, shape, material or disposition of the strap connectors prior to the connecting process
2224/33181	On opposite sides of the body	2224/37	of an individual strap connector
2224/33183	On contiguous sides of the body	2224/37001	Core members of the connector
2224/335	Material	2224/37005	Structure
2224/33505	Layer connectors having different materials	2224/3701	Shape
2224/3351	Function	2224/37011	comprising apertures or cavities
2224/33515	Layer connectors having different functions	2224/37012	Cross-sectional shape
2224/33517	including layer connectors providing primarily mechanical support	2224/37013	being non uniform along the connector
2224/33519	including layer connectors providing primarily thermal dissipation	2224/3702	Disposition
2224/34	Strap connectors, e.g. copper straps for grounding power devices; Manufacturing methods related thereto	2224/37025	Plural core members
2224/35	Manufacturing methods	2224/37026	being mutually engaged together, e.g. through inserts
2224/35001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate	2224/37028	Side-to-side arrangements
2224/351	Pre-treatment of the preform connector	2224/3703	Stacked arrangements
2224/3512	Applying permanent coating, e.g. in-situ coating	2224/37032	Two-layer arrangements
2224/35125	Plating, e.g. electroplating, electroless plating	2224/37033	Three-layer arrangements
2224/352	Mechanical processes	2224/37034	Four-layer arrangements
2224/3521	Pulling	2224/37099	Material
2224/355	Modification of a pre-existing material	2224/371	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/3551	Sintering	2224/37101	the principal constituent melting at a temperature of less than 400°C
2224/3552	Anodisation	2224/37105	Gallium [Ga] as principal constituent
2224/357	Involving monitoring, e.g. feedback loop	2224/37109	Indium [In] as principal constituent
2224/358	Post-treatment of the connector	2224/37111	Tin [Sn] as principal constituent
2224/3581	Cleaning, e.g. oxide removal step, desmearing	2224/37113	Bismuth [Bi] as principal constituent
2224/3582	Applying permanent coating, e.g. in-situ coating	2224/37114	Thallium [Tl] as principal constituent
2224/35821	Spray coating	2224/37116	Lead [Pb] as principal constituent
2224/35822	Dip coating	2224/37117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/35823	Immersion coating, e.g. solder bath	2224/37118	Zinc [Zn] as principal constituent
2224/35824	Chemical solution deposition [CSD], i.e. using a liquid precursor	2224/3712	Antimony [Sb] as principal constituent
2224/35825	Plating, e.g. electroplating, electroless plating	2224/37123	Magnesium [Mg] as principal constituent
2224/35826	Physical vapour deposition [PVD], e.g. evaporation, sputtering	2224/37124	Aluminium [Al] as principal constituent
2224/35827	Chemical vapour deposition [CVD], e.g. laser CVD	2224/37138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/3583	Reworking	2224/37139	Silver [Ag] as principal constituent
2224/35831	with a chemical process, e.g. with etching of the connector	2224/37144	Gold [Au] as principal constituent
2224/35847	with a mechanical process, e.g. with flattening of the connector			

2224/37147	Copper [Cu] as principal constituent	2224/37194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/371 - H01L 2224/37191
2224/37149	Manganese [Mn] as principal constituent	2224/37195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/371 - H01L 2224/37191
2224/37155	Nickel [Ni] as principal constituent	2224/37198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/37157	Cobalt [Co] as principal constituent	2224/37199	Material of the matrix
2224/3716	Iron [Fe] as principal constituent	2224/372	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37163	the principal constituent melting at a temperature of greater than 1550°C	2224/37201	the principal constituent melting at a temperature of less than 400°C
2224/37164	Palladium [Pd] as principal constituent	2224/37205	Gallium [Ga] as principal constituent
2224/37166	Titanium [Ti] as principal constituent	2224/37209	Indium [In] as principal constituent
2224/37169	Platinum [Pt] as principal constituent	2224/37211	Tin [Sn] as principal constituent
2224/3717	Zirconium [Zr] as principal constituent	2224/37213	Bismuth [Bi] as principal constituent
2224/37171	Chromium [Cr] as principal constituent	2224/37214	Thallium [Tl] as principal constituent
2224/37172	Vanadium [V] as principal constituent	2224/37216	Lead [Pb] as principal constituent
2224/37173	Rhodium [Rh] as principal constituent	2224/37217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/37176	Ruthenium [Ru] as principal constituent	2224/37218	Zinc [Zn] as principal constituent
2224/37178	Iridium [Ir] as principal constituent	2224/3722	Antimony [Sb] as principal constituent
2224/37179	Niobium [Nb] as principal constituent	2224/37223	Magnesium [Mg] as principal constituent
2224/3718	Molybdenum [Mo] as principal constituent	2224/37224	Aluminium [Al] as principal constituent
2224/37181	Tantalum [Ta] as principal constituent	2224/37238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/37183	Rhenium [Re] as principal constituent	2224/37239	Silver [Ag] as principal constituent
2224/37184	Tungsten [W] as principal constituent	2224/37244	Gold [Au] as principal constituent
2224/37186	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/37247	Copper [Cu] as principal constituent
2224/37187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37188)	2224/37249	Manganese [Mn] as principal constituent
2224/37188	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/37255	Nickel [Ni] as principal constituent
2224/3719	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/37257	Cobalt [Co] as principal constituent
2224/37191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene		
2224/37193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/371 - H01L 2224/37191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond		

2224/3726	Iron [Fe] as principal constituent	2224/37299	Base material
2224/37263	the principal constituent melting at a temperature of greater than 1550°C	2224/373	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37264	Palladium [Pd] as principal constituent	2224/37301	the principal constituent melting at a temperature of less than 400°C
2224/37266	Titanium [Ti] as principal constituent	2224/37305	Gallium [Ga] as principal constituent
2224/37269	Platinum [Pt] as principal constituent	2224/37309	Indium [In] as principal constituent
2224/3727	Zirconium [Zr] as principal constituent	2224/37311	Tin [Sn] as principal constituent
2224/37271	Chromium [Cr] as principal constituent	2224/37313	Bismuth [Bi] as principal constituent
2224/37272	Vanadium [V] as principal constituent	2224/37314	Thallium [Tl] as principal constituent
2224/37273	Rhodium [Rh] as principal constituent	2224/37316	Lead [Pb] as principal constituent
2224/37276	Ruthenium [Ru] as principal constituent	2224/37317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/37278	Iridium [Ir] as principal constituent	2224/37318	Zinc [Zn] as principal constituent
2224/37279	Niobium [Nb] as principal constituent	2224/3732	Antimony [Sb] as principal constituent
2224/3728	Molybdenum [Mo] as principal constituent	2224/37323	Magnesium [Mg] as principal constituent
2224/37281	Tantalum [Ta] as principal constituent	2224/37324	Aluminium [Al] as principal constituent
2224/37283	Rhenium [Re] as principal constituent	2224/37338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/37284	Tungsten [W] as principal constituent	2224/37339	Silver [Ag] as principal constituent
2224/37286	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/37344	Gold [Au] as principal constituent
2224/37287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37288)	2224/37347	Copper [Cu] as principal constituent
2224/37288	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/37349	Manganese [Mn] as principal constituent
2224/3729	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/37355	Nickel [Ni] as principal constituent
2224/37291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/37357	Cobalt [Co] as principal constituent
2224/37293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/372 - H01L 2224/37291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/3736	Iron [Fe] as principal constituent
2224/37294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/372 - H01L 2224/37291	2224/37363	the principal constituent melting at a temperature of greater than 1550°C
2224/37295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/372 - H01L 2224/37291	2224/37364	Palladium [Pd] as principal constituent
2224/37298	Fillers	2224/37366	Titanium [Ti] as principal constituent
		2224/37369	Platinum [Pt] as principal constituent
		2224/3737	Zirconium [Zr] as principal constituent

2224/37371	Chromium [Cr] as principal constituent	2224/374	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37372	Vanadium [V] as principal constituent	2224/37401	the principal constituent melting at a temperature of less than 400°C
2224/37373	Rhodium [Rh] as principal constituent	2224/37405	Gallium [Ga] as principal constituent
2224/37376	Ruthenium [Ru] as principal constituent	2224/37409	Indium [In] as principal constituent
2224/37378	Iridium [Ir] as principal constituent	2224/37411	Tin [Sn] as principal constituent
2224/37379	Niobium [Nb] as principal constituent	2224/37413	Bismuth [Bi] as principal constituent
2224/3738	Molybdenum [Mo] as principal constituent	2224/37414	Thallium [Tl] as principal constituent
2224/37381	Tantalum [Ta] as principal constituent	2224/37416	Lead [Pb] as principal constituent
2224/37383	Rhenium [Re] as principal constituent	2224/37417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/37384	Tungsten [W] as principal constituent	2224/37418	Zinc [Zn] as principal constituent
2224/37386	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/3742	Antimony [Sb] as principal constituent
2224/37387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37388)	2224/37423	Magnesium [Mg] as principal constituent
2224/37388	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/37424	Aluminium [Al] as principal constituent
2224/3739	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/37438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/37391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/37439	Silver [Ag] as principal constituent
2224/37393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/373 - H01L 2224/37391	2224/37444	Gold [Au] as principal constituent
2224/37394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/373 - H01L 2224/37391	2224/37447	Copper [Cu] as principal constituent
2224/37395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/373 - H01L 2224/37391	2224/37449	Manganese [Mn] as principal constituent
2224/37398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/37455	Nickel [Ni] as principal constituent
2224/37399	Coating material	2224/37457	Cobalt [Co] as principal constituent
		2224/3746	Iron [Fe] as principal constituent
		2224/37463	the principal constituent melting at a temperature of greater than 1550°C
		2224/37464	Palladium [Pd] as principal constituent
		2224/37466	Titanium [Ti] as principal constituent
		2224/37469	Platinum [Pt] as principal constituent
		2224/3747	Zirconium [Zr] as principal constituent

2224/37471	Chromium [Cr] as principal constituent	2224/37565	Single coating layer
2224/37472	Vanadium [V] as principal constituent	2224/3757	Plural coating layers
2224/37473	Rhodium [Rh] as principal constituent	2224/37572	Two-layer stack coating
2224/37476	Ruthenium [Ru] as principal constituent	2224/37573	Three-layer stack coating
2224/37478	Iridium [Ir] as principal constituent	2224/37574	Four-layer stack coating
2224/37479	Niobium [Nb] as principal constituent	2224/37576	being mutually engaged together, e.g. through inserts
2224/3748	Molybdenum [Mo] as principal constituent	2224/37578	being disposed next to each other, e.g. side-to-side arrangements
2224/37481	Tantalum [Ta] as principal constituent	2224/37599	Material
2224/37483	Rhenium [Re] as principal constituent	2224/376	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/37484	Tungsten [W] as principal constituent	2224/37601	the principal constituent melting at a temperature of less than 400°C
2224/37486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/37605	Gallium [Ga] as principal constituent
2224/37487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37488)	2224/37609	Indium [In] as principal constituent
2224/37488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/37611	Tin [Sn] as principal constituent
2224/3749	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/37613	Bismuth [Bi] as principal constituent
2224/37491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/37614	Thallium [Tl] as principal constituent
2224/37493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/374 - H01L 2224/37491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/37616	Lead [Pb] as principal constituent
2224/37494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/374 - H01L 2224/37491	2224/37617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/37495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/374 - H01L 2224/37491	2224/37618	Zinc [Zn] as principal constituent
2224/37498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/3762	Antimony [Sb] as principal constituent
2224/37499	Shape or distribution of the fillers	2224/37623	Magnesium [Mg] as principal constituent
2224/3754	Coating	2224/37624	Aluminium [Al] as principal constituent
2224/37541	Structure	2224/37638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/3755	Shape	2224/37639	Silver [Ag] as principal constituent
2224/3756	Disposition, e.g. coating on a part of the core	2224/37644	Gold [Au] as principal constituent
		2224/37647	Copper [Cu] as principal constituent
		2224/37649	Manganese [Mn] as principal constituent
		2224/37655	Nickel [Ni] as principal constituent
		2224/37657	Cobalt [Co] as principal constituent
		2224/3766	Iron [Fe] as principal constituent
		2224/37663	the principal constituent melting at a temperature of greater than 1550°C
		2224/37664	Palladium [Pd] as principal constituent
		2224/37666	Titanium [Ti] as principal constituent
		2224/37669	Platinum [Pt] as principal constituent

2224/3767	Zirconium [Zr] as principal constituent	2224/37701	the principal constituent melting at a temperature of less than 400°C
2224/37671	Chromium [Cr] as principal constituent	2224/37705	Gallium [Ga] as principal constituent
2224/37672	Vanadium [V] as principal constituent	2224/37709	Indium [In] as principal constituent
2224/37673	Rhodium [Rh] as principal constituent	2224/37711	Tin [Sn] as principal constituent
2224/37676	Ruthenium [Ru] as principal constituent	2224/37713	Bismuth [Bi] as principal constituent
2224/37678	Iridium [Ir] as principal constituent	2224/37714	Thallium [Tl] as principal constituent
2224/37679	Niobium [Nb] as principal constituent	2224/37716	Lead [Pb] as principal constituent
2224/3768	Molybdenum [Mo] as principal constituent	2224/37717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/37681	Tantalum [Ta] as principal constituent	2224/37718	Zinc [Zn] as principal constituent
2224/37683	Rhenium [Re] as principal constituent	2224/3772	Antimony [Sb] as principal constituent
2224/37684	Tungsten [W] as principal constituent	2224/37723	Magnesium [Mg] as principal constituent
2224/37686	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/37724	Aluminium [Al] as principal constituent
2224/37687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37688)	2224/37738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/37688	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/37739	Silver [Ag] as principal constituent
2224/3769	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/37744	Gold [Au] as principal constituent
2224/37691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/37747	Copper [Cu] as principal constituent
2224/37693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/376 - H01L 2224/37691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/37749	Manganese [Mn] as principal constituent
2224/37694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/376 - H01L 2224/37691	2224/37755	Nickel [Ni] as principal constituent
2224/37695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/376 - H01L 2224/37691	2224/37757	Cobalt [Co] as principal constituent
2224/37698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/3776	Iron [Fe] as principal constituent
2224/37699	Material of the matrix	2224/37763	the principal constituent melting at a temperature of greater than 1550°C
2224/377	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/37764	Palladium [Pd] as principal constituent
			2224/37766	Titanium [Ti] as principal constituent
			2224/37769	Platinum [Pt] as principal constituent
			2224/3777	Zirconium [Zr] as principal constituent
			2224/37771	Chromium [Cr] as principal constituent
			2224/37772	Vanadium [V] as principal constituent
			2224/37773	Rhodium [Rh] as principal constituent
			2224/37776	Ruthenium [Ru] as principal constituent

2224/37778	Iridium [Ir] as principal constituent	2224/37816	Lead [Pb] as principal constituent
2224/37779	Niobium [Nb] as principal constituent	2224/37817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/3778	Molybdenum [Mo] as principal constituent	2224/37818	Zinc [Zn] as principal constituent
2224/37781	Tantalum [Ta] as principal constituent	2224/3782	Antimony [Sb] as principal constituent
2224/37783	Rhenium [Re] as principal constituent	2224/37823	Magnesium [Mg] as principal constituent
2224/37784	Tungsten [W] as principal constituent	2224/37824	Aluminium [Al] as principal constituent
2224/37786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/37838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/37787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37788)	2224/37839	Silver [Ag] as principal constituent
2224/37788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/37844	Gold [Au] as principal constituent
2224/3779	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/37847	Copper [Cu] as principal constituent
2224/37791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/37849	Manganese [Mn] as principal constituent
2224/37793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/377 - H01L 2224/37791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/37855	Nickel [Ni] as principal constituent
2224/37794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/377 - H01L 2224/37791	2224/37857	Cobalt [Co] as principal constituent
2224/37795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/377 - H01L 2224/37791	2224/3786	Iron [Fe] as principal constituent
2224/37798	Fillers	2224/37863	the principal constituent melting at a temperature of greater than 1550°C
2224/37799	Base material	2224/37864	Palladium [Pd] as principal constituent
2224/378	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/37866	Titanium [Ti] as principal constituent
2224/37801	the principal constituent melting at a temperature of less than 400°C	2224/37869	Platinum [Pt] as principal constituent
2224/37805	Gallium [Ga] as principal constituent	2224/3787	Zirconium [Zr] as principal constituent
2224/37809	Indium [In] as principal constituent	2224/37871	Chromium [Cr] as principal constituent
2224/37811	Tin [Sn] as principal constituent	2224/37872	Vanadium [V] as principal constituent
2224/37813	Bismuth [Bi] as principal constituent	2224/37873	Rhodium [Rh] as principal constituent
2224/37814	Thallium [Tl] as principal constituent	2224/37876	Ruthenium [Ru] as principal constituent
		2224/37878	Iridium [Ir] as principal constituent
		2224/37879	Niobium [Nb] as principal constituent
		2224/3788	Molybdenum [Mo] as principal constituent
		2224/37881	Tantalum [Ta] as principal constituent
		2224/37883	Rhenium [Re] as principal constituent
		2224/37884	Tungsten [W] as principal constituent

2224/37886	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/37917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/37887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37888)	2224/37918	Zinc [Zn] as principal constituent
2224/37888	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/3792	Antimony [Sb] as principal constituent
2224/3789	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/37923	Magnesium [Mg] as principal constituent
2224/37891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/37924	Aluminium [Al] as principal constituent
2224/37893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/378 - H01L 2224/37891 e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/37938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/37894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/378 - H01L 2224/37891	2224/37939	Silver [Ag] as principal constituent
2224/37895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/378 - H01L 2224/37891	2224/37944	Gold [Au] as principal constituent
2224/37898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/37947	Copper [Cu] as principal constituent
2224/37899	Coating material	2224/37949	Manganese [Mn] as principal constituent
2224/379	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/37955	Nickel [Ni] as principal constituent
2224/37901	the principal constituent melting at a temperature of less than 400°C	2224/37957	Cobalt [Co] as principal constituent
2224/37905	Gallium [Ga] as principal constituent	2224/3796	Iron [Fe] as principal constituent
2224/37909	Indium [In] as principal constituent	2224/37963	the principal constituent melting at a temperature of greater than 1550°C
2224/37911	Tin [Sn] as principal constituent	2224/37964	Palladium [Pd] as principal constituent
2224/37913	Bismuth [Bi] as principal constituent	2224/37966	Titanium [Ti] as principal constituent
2224/37914	Thallium [Tl] as principal constituent	2224/37969	Platinum [Pt] as principal constituent
2224/37916	Lead [Pb] as principal constituent	2224/3797	Zirconium [Zr] as principal constituent
		2224/37971	Chromium [Cr] as principal constituent
		2224/37972	Vanadium [V] as principal constituent
		2224/37973	Rhodium [Rh] as principal constituent
		2224/37976	Ruthenium [Ru] as principal constituent
		2224/37978	Iridium [Ir] as principal constituent
		2224/37979	Niobium [Nb] as principal constituent
		2224/3798	Molybdenum [Mo] as principal constituent
		2224/37981	Tantalum [Ta] as principal constituent
		2224/37983	Rhenium [Re] as principal constituent
		2224/37984	Tungsten [W] as principal constituent

2224/37986	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/40111	the strap connector extending above another semiconductor or solid-state body
2224/37987	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/37988)	2224/4013	Connecting within a semiconductor or solid-state body, i.e. fly strap, bridge strap
2224/37988	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/40132	with an intermediate bond, e.g. continuous strap daisy chain
2224/3799	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/40135	Connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip
2224/37991	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/40137	the bodies being arranged next to each other, e.g. on a common substrate
2224/37993	with a principal constituent of the material being a solid not provided for in groups H01L 2224/379 - H01L 2224/37991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/40139	with an intermediate bond, e.g. continuous strap daisy chain
2224/37994	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/379 - H01L 2224/37991	2224/40141	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements
2224/37995	with a principal constituent of the material being a gas not provided for in groups H01L 2224/379 - H01L 2224/37991	2224/40145	the bodies being stacked
2224/37998	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/40147	with an intermediate bond, e.g. continuous strap daisy chain
2224/37999	Shape or distribution of the fillers	2224/40151	Connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive
2224/38	of a plurality of strap connectors	2224/40153	the body and the item being arranged next to each other, e.g. on a common substrate
2224/39	Structure, shape, material or disposition of the strap connectors after the connecting process	2224/40155	the item being non-metallic, e.g. insulating substrate with or without metallisation
2224/40	of an individual strap connector	2224/40157	Connecting the strap to a bond pad of the item
2224/4001	Structure	2224/40158	the bond pad being disposed in a recess of the surface of the item
2224/4005	Shape	2224/40159	the bond pad protruding from the surface of the item
2224/4007	of bonding interfaces, e.g. interlocking features	2224/4016	Connecting the strap to a pin of the item
2224/4009	Loop shape	2224/40163	Connecting the strap to a potential ring of the item
2224/40091	Arched	2224/40165	Connecting the strap to a via metallisation of the item
2224/40095	Kinked	2224/40175	the item being metallic
2224/401	Disposition	2224/40177	Connecting the strap to a bond pad of the item
2224/40101	Connecting bonding areas at the same height, e.g. horizontal bond	2224/40178	the bond pad being disposed in a recess of the surface of the item
2224/40105	Connecting bonding areas at different heights	2224/40179	the bond pad protruding from the surface of the item
2224/40106	the connector being orthogonal to a side surface of the semiconductor or solid-state body, e.g. parallel layout	2224/40183	Connecting the strap to a potential ring of the item
2224/40108	the connector not being orthogonal to a side surface of the semiconductor or solid-state body, e.g. fanned-out connectors, radial layout	2224/40195	the item being a discrete passive component
		2224/40221	the body and the item being stacked
		2224/40225	the item being non-metallic, e.g. insulating substrate with or without metallisation
		2224/40227	Connecting the strap to a bond pad of the item

2224/40228	the bond pad being disposed in a recess of the surface of the item	2224/4052	Bonding interface between the connecting portion and the bonding area
2224/40229	the bond pad protruding from the surface of the item	2224/4099	Auxiliary members for strap connectors, e.g. flow-barriers, spacers
2224/4023	Connecting the strap to a pin of the item	2224/40991	being formed on the semiconductor or solid-state body to be connected
2224/40233	Connecting the strap to a potential ring of the item	2224/40992	Reinforcing structures
2224/40235	Connecting the strap to a via metallisation of the item	2224/40993	Alignment aids
2224/40237	Connecting the strap to a die pad of the item	2224/40996	being formed on an item to be connected not being a semiconductor or solid-state body
2224/4024	Connecting between the body and an opposite side of the item with respect to the body	2224/40997	Reinforcing structures
2224/40245	the item being metallic	2224/40998	Alignment aids
2224/40247	Connecting the strap to a bond pad of the item	2224/41	of a plurality of strap connectors
2224/40248	the bond pad being disposed in a recess of the surface of the item	2224/4101	Structure
2224/40249	the bond pad protruding from the surface of the item	2224/4103	Connectors having different sizes
2224/40253	Connecting the strap to a potential ring of the item	2224/4105	Shape
2224/40257	Connecting the strap to a die pad of the item	2224/41051	Connectors having different shapes
2224/4026	Connecting between the body and an opposite side of the item with respect to the body	2224/41052	Different loop heights
2224/40265	the item being a discrete passive component	2224/411	Disposition
2224/404	Connecting portions	2224/41105	Connecting at different heights
2224/4046	with multiple bonds on the same bonding area	2224/41107	on the semiconductor or solid-state body being
2224/40475	connected to auxiliary connecting means on the bonding areas	2224/41109	outside the semiconductor or solid-state body
2224/40477	being a pre-ball (i.e. a ball formed by capillary bonding)	2224/4111	the connectors being bonded to at least one common bonding area, e.g. daisy chain
2224/40479	on the semiconductor or solid-state body	2224/41111	the connectors connecting two common bonding areas
2224/4048	outside the semiconductor or solid-state body	2224/41112	the connectors connecting a common bonding area on the semiconductor or solid-state body to different bonding areas outside the body, e.g. diverging straps
2224/40484	being a plurality of pre-balls disposed side-to-side	2224/41113	the connectors connecting different bonding areas on the semiconductor or solid-state body to a common bonding area outside the body, e.g. converging straps
2224/40486	on the semiconductor or solid-state body	2224/4112	Layout
2224/40487	outside the semiconductor or solid-state body	2224/4117	Crossed straps
2224/40491	being an additional member attached to the bonding area through an adhesive or solder, e.g. buffer pad	2224/41171	Fan-out arrangements
2224/40496	not being interposed between the connector and the bonding area	2224/41173	Radial fan-out arrangements
2224/40499	Material of the auxiliary connecting means	2224/41174	Stacked arrangements
2224/405	Material	2224/41175	Parallel arrangements
2224/40505	at the bonding interface	2224/41176	Strap connectors having the same loop shape and height
2224/40506	comprising an eutectic alloy	2224/41177	Combinations of different arrangements
2224/40507	comprising an intermetallic compound	2224/41179	Corner adaptations, i.e. disposition of the strap connectors at the corners of the semiconductor or solid-state body
2224/4051	Morphology of the connecting portion, e.g. grain size distribution	2224/4118	being disposed on at least two different sides of the body, e.g. dual array
			2224/414	Connecting portions
			2224/4141	the connecting portions being stacked
			2224/41421	on the semiconductor or solid-state body
			2224/41422	outside the semiconductor or solid-state body
			2224/4143	the connecting portions being staggered

2224/415	Material	2224/45026	being mutually engaged together, e.g. through inserts
2224/41505	Connectors having different materials	2224/45028	Side-to-side arrangements
2224/42	. .	Wire connectors; Manufacturing methods related thereto	2224/4503	Stacked arrangements
2224/43	. . .	Manufacturing methods	2224/45032	Two-layer arrangements
2224/43001	Involving a temporary auxiliary member not forming part of the manufacturing apparatus, e.g. removable or sacrificial coating, film or substrate	2224/45033	Three-layer arrangements
2224/431	Pre-treatment of the preform connector	2224/45034	Four-layer arrangements
2224/4312	Applying permanent coating, e.g. in-situ coating	2224/45099	Material
2224/43125	Plating, e.g. electroplating, electroless plating	2224/451	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/432	Mechanical processes	2224/45101	the principal constituent melting at a temperature of less than 400°C
2224/4321	Pulling	2224/45105	Gallium (Ga) as principal constituent
2224/435	Modification of a pre-existing material	2224/45109	Indium (In) as principal constituent
2224/4351	Sintering	2224/45111	Tin (Sn) as principal constituent
2224/4352	Anodisation	2224/45113	Bismuth (Bi) as principal constituent
2224/437	Involving monitoring, e.g. feedback loop	2224/45114	Thallium (Tl) as principal constituent
2224/438	Post-treatment of the connector	2224/45116	Lead (Pb) as principal constituent
2224/4381	Cleaning, e.g. oxide removal step, desmearing	2224/45117	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/4382	Applying permanent coating, e.g. in-situ coating	2224/45118	Zinc (Zn) as principal constituent
2224/43821	Spray coating	2224/4512	Antimony (Sb) as principal constituent
2224/43822	Dip coating	2224/45123	Magnesium (Mg) as principal constituent
2224/43823	Immersion coating, e.g. solder bath	2224/45124	Aluminium (Al) as principal constituent
2224/43824	Chemical solution deposition [CSD], i.e. using a liquid precursor	2224/45138	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/43825	Plating, e.g. electroplating, electroless plating	2224/45139	Silver (Ag) as principal constituent
2224/43826	Physical vapour deposition [PVD], e.g. evaporation, sputtering	2224/45144	Gold (Au) as principal constituent
2224/43827	Chemical vapour deposition [CVD], e.g. laser CVD	2224/45147	Copper (Cu) as principal constituent
2224/4383	Reworking	2224/45149	Manganese (Mn) as principal constituent
2224/43831	with a chemical process, e.g. with etching of the connector	2224/45155	Nickel (Ni) as principal constituent
2224/43847	with a mechanical process, e.g. with flattening of the connector	2224/45157	Cobalt (Co) as principal constituent
2224/43848	Thermal treatments, e.g. annealing, controlled cooling	2224/4516	Iron (Fe) as principal constituent
2224/43985	Methods of manufacturing wire connectors involving a specific sequence of method steps	2224/45163	the principal constituent melting at a temperature of greater than 1550°C
2224/43986	with repetition of the same manufacturing step	2224/45164	Palladium (Pd) as principal constituent
2224/44	. . .	Structure, shape, material or disposition of the wire connectors prior to the connecting process	2224/45166	Titanium (Ti) as principal constituent
2224/45	of an individual wire connector	2224/45169	Platinum (Pt) as principal constituent
2224/45001	Core members of the connector	2224/4517	Zirconium (Zr) as principal constituent
2224/45005	Structure			
2224/4501	Shape			
2224/45012	Cross-sectional shape			
2224/45013	being non uniform along the connector			
2224/45014	Ribbon connectors, e.g. rectangular cross-section			
2224/45015	being circular			
2224/45016	being elliptic			
2224/4502	Disposition			
2224/45025	Plural core members			

2224/45171	Chromium (Cr) as principal constituent	2224/45201	the principal constituent melting at a temperature of less than 400°C
2224/45172	Vanadium (V) as principal constituent	2224/45205	Gallium (Ga) as principal constituent
2224/45173	Rhodium (Rh) as principal constituent	2224/45209	Indium (In) as principal constituent
2224/45176	Ruthenium (Ru) as principal constituent	2224/45211	Tin (Sn) as principal constituent
2224/45178	Iridium (Ir) as principal constituent	2224/45213	Bismuth (Bi) as principal constituent
2224/45179	Niobium (Nb) as principal constituent	2224/45214	Thallium (Tl) as principal constituent
2224/4518	Molybdenum (Mo) as principal constituent	2224/45216	Lead (Pb) as principal constituent
2224/45181	Tantalum (Ta) as principal constituent	2224/45217	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45183	Rhenium (Re) as principal constituent	2224/45218	Zinc (Zn) as principal constituent
2224/45184	Tungsten (W) as principal constituent	2224/4522	Antimony (Sb) as principal constituent
2224/45186	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/45223	Magnesium (Mg) as principal constituent
2224/45187	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45188)	2224/45224	Aluminium (Al) as principal constituent
2224/45188	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/45238	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/4519	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45239	Silver (Ag) as principal constituent
2224/45191	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45244	Gold (Au) as principal constituent
2224/45193	with a principal constituent of the material being a solid not provided for in groups H01L 2224/451 - H01L 2224/45191 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45247	Copper (Cu) as principal constituent
2224/45194	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/451 - H01L 2224/45191	2224/45249	Manganese (Mn) as principal constituent
2224/45195	with a principal constituent of the material being a gas not provided for in groups H01L 2224/451 - H01L 2224/45191	2224/45255	Nickel (Ni) as principal constituent
2224/45198	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/45257	Cobalt (Co) as principal constituent
2224/45199	Material of the matrix	2224/4526	Iron (Fe) as principal constituent
2224/452	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/45263	the principal constituent melting at a temperature of greater than 1550°C
		2224/45264	Palladium (Pd) as principal constituent
		2224/45266	Titanium (Ti) as principal constituent
		2224/45269	Platinum (Pt) as principal constituent
		2224/4527	Zirconium (Zr) as principal constituent
		2224/45271	Chromium (Cr) as principal constituent
		2224/45272	Vanadium (V) as principal constituent
		2224/45273	Rhodium (Rh) as principal constituent
		2224/45276	Ruthenium (Ru) as principal constituent

2224/45278	Iridium (Ir) as principal constituent	2224/45316	Lead (Pb) as principal constituent
2224/45279	Niobium (Nb) as principal constituent	2224/45317	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/4528	Molybdenum (Mo) as principal constituent	2224/45318	Zinc (Zn) as principal constituent
2224/45281	Tantalum (Ta) as principal constituent	2224/4532	Antimony (Sb) as principal constituent
2224/45283	Rhenium (Re) as principal constituent	2224/45323	Magnesium (Mg) as principal constituent
2224/45284	Tungsten (W) as principal constituent	2224/45324	Aluminium (Al) as principal constituent
2224/45286	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/45338	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45287	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45288)	2224/45339	Silver (Ag) as principal constituent
2224/45288	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/45344	Gold (Au) as principal constituent
2224/4529	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45347	Copper (Cu) as principal constituent
2224/45291	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45349	Manganese (Mn) as principal constituent
2224/45293	with a principal constituent of the material being a solid not provided for in groups H01L 2224/452 - H01L 2224/45291 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45355	Nickel (Ni) as principal constituent
2224/45294	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/452 - H01L 2224/45291	2224/45357	Cobalt (Co) as principal constituent
2224/45295	with a principal constituent of the material being a gas not provided for in groups H01L 2224/452 - H01L 2224/45291	2224/4536	Iron (Fe) as principal constituent
2224/45298	Fillers	2224/45363	the principal constituent melting at a temperature of greater than 1550°C
2224/45299	Base material	2224/45364	Palladium (Pd) as principal constituent
2224/453	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/45366	Titanium (Ti) as principal constituent
2224/45301	the principal constituent melting at a temperature of less than 400°C	2224/45369	Platinum (Pt) as principal constituent
2224/45305	Gallium (Ga) as principal constituent	2224/4537	Zirconium (Zr) as principal constituent
2224/45309	Indium (In) as principal constituent	2224/45371	Chromium (Cr) as principal constituent
2224/45311	Tin (Sn) as principal constituent	2224/45372	Vanadium (V) as principal constituent
2224/45313	Bismuth (Bi) as principal constituent	2224/45373	Rhodium (Rh) as principal constituent
2224/45314	Thallium (Tl) as principal constituent	2224/45376	Ruthenium (Ru) as principal constituent
		2224/45378	Iridium (Ir) as principal constituent
		2224/45379	Niobium (Nb) as principal constituent
		2224/4538	Molybdenum (Mo) as principal constituent
		2224/45381	Tantalum (Ta) as principal constituent
		2224/45383	Rhenium (Re) as principal constituent
		2224/45384	Tungsten (W) as principal constituent

2224/45386	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/45417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45387	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45388)	2224/45418	Zinc (Zn) as principal constituent
2224/45388	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/4542	Antimony (Sb) as principal constituent
2224/4539	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45423	Magnesium (Mg) as principal constituent
2224/45391	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45424	Aluminium (Al) as principal constituent
2224/45393	with a principal constituent of the material being a solid not provided for in groups H01L 2224/453 - H01L 2224/45391 e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45394	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/453 - H01L 2224/45391	2224/45439	Silver (Ag) as principal constituent
2224/45395	with a principal constituent of the material being a gas not provided for in groups H01L 2224/453 - H01L 2224/45391	2224/45444	Gold (Au) as principal constituent
2224/45398	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/45447	Copper (Cu) as principal constituent
2224/45399	Coating material	2224/45449	Manganese (Mn) as principal constituent
2224/454	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/45455	Nickel (Ni) as principal constituent
2224/45401	the principal constituent melting at a temperature of less than 400°C	2224/45457	Cobalt (Co) as principal constituent
2224/45405	Gallium (Ga) as principal constituent	2224/4546	Iron (Fe) as principal constituent
2224/45409	Indium (In) as principal constituent	2224/45463	the principal constituent melting at a temperature of greater than 1550°C
2224/45411	Tin (Sn) as principal constituent	2224/45464	Palladium (Pd) as principal constituent
2224/45413	Bismuth (Bi) as principal constituent	2224/45466	Titanium (Ti) as principal constituent
2224/45414	Thallium (Tl) as principal constituent	2224/45469	Platinum (Pt) as principal constituent
2224/45416	Lead (Pb) as principal constituent	2224/4547	Zirconium (Zr) as principal constituent
		2224/45471	Chromium (Cr) as principal constituent
		2224/45472	Vanadium (V) as principal constituent
		2224/45473	Rhodium (Rh) as principal constituent
		2224/45476	Ruthenium (Ru) as principal constituent
		2224/45478	Iridium (Ir) as principal constituent
		2224/45479	Niobium (Nb) as principal constituent
		2224/4548	Molybdenum (Mo) as principal constituent
		2224/45481	Tantalum (Ta) as principal constituent
		2224/45483	Rhenium (Re) as principal constituent
		2224/45484	Tungsten (W) as principal constituent

2224/45486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/45609	Indium (In) as principal constituent
2224/45487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45488)	2224/45611	Tin (Sn) as principal constituent
2224/45488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/45613	Bismuth (Bi) as principal constituent
2224/4549	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45614	Thallium (Tl) as principal constituent
2224/45491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45616	Lead (Pb) as principal constituent
2224/45493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/454 - H01L 2224/45491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/45494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/454 - H01L 2224/45491	2224/45618	Zinc (Zn) as principal constituent
2224/45495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/454 - H01L 2224/45491	2224/4562	Antimony (Sb) as principal constituent
2224/45498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/45623	Magnesium (Mg) as principal constituent
2224/45499	Shape or distribution of the fillers	2224/45624	Aluminium (Al) as principal constituent
2224/4554	Coating	2224/45638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45541	Structure	2224/45639	Silver (Ag) as principal constituent
2224/4555	Shape	2224/45644	Gold (Au) as principal constituent
2224/4556	Disposition, e.g. coating on a part of the core	2224/45647	Copper (Cu) as principal constituent
2224/45565	Single coating layer	2224/45649	Manganese (Mn) as principal constituent
2224/4557	Plural coating layers	2224/45655	Nickel (Ni) as principal constituent
2224/45572	Two-layer stack coating	2224/45657	Cobalt (Co) as principal constituent
2224/45573	Three-layer stack coating	2224/4566	Iron (Fe) as principal constituent
2224/45574	Four-layer stack coating	2224/45663	the principal constituent melting at a temperature of greater than 1550°C
2224/45576	being mutually engaged together, e.g. through inserts	2224/45664	Palladium (Pd) as principal constituent
2224/45578	being disposed next to each other, e.g. side-to-side arrangements	2224/45666	Titanium (Ti) as principal constituent
2224/45599	Material	2224/45669	Platinum (Pt) as principal constituent
2224/456	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/4567	Zirconium (Zr) as principal constituent
2224/45601	the principal constituent melting at a temperature of less than 400°C	2224/45671	Chromium (Cr) as principal constituent
2224/45605	Gallium (Ga) as principal constituent	2224/45672	Vanadium (V) as principal constituent
		2224/45673	Rhodium (Rh) as principal constituent
		2224/45676	Ruthenium (Ru) as principal constituent
		2224/45678	Iridium (Ir) as principal constituent
		2224/45679	Niobium (Nb) as principal constituent
		2224/4568	Molybdenum (Mo) as principal constituent
		2224/45681	Tantalum (Ta) as principal constituent
		2224/45683	Rhenium (Re) as principal constituent

2224/45684	• • • • • Tungsten (W) as principal constituent	2224/45718	• • • • • Zinc (Zn) as principal constituent
2224/45686	• • • • • with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/4572	• • • • • Antimony (Sb) as principal constituent
2224/45687	• • • • • Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45688)	2224/45723	• • • • • Magnesium (Mg) as principal constituent
2224/45688	• • • • • Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/45724	• • • • • Aluminium (Al) as principal constituent
2224/4569	• • • • • with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45738	• • • • • the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/45691	• • • • • The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45739	• • • • • Silver (Ag) as principal constituent
2224/45693	• • • • • with a principal constituent of the material being a solid not provided for in groups H01L 2224/456 - H01L 2224/45691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45744	• • • • • Gold (Au) as principal constituent
2224/45694	• • • • • with a principal constituent of the material being a liquid not provided for in groups H01L 2224/456 - H01L 2224/45691	2224/45747	• • • • • Copper (Cu) as principal constituent
2224/45695	• • • • • with a principal constituent of the material being a gas not provided for in groups H01L 2224/456 - H01L 2224/45691	2224/45749	• • • • • Manganese (Mn) as principal constituent
2224/45698	• • • • • with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/45755	• • • • • Nickel (Ni) as principal constituent
2224/45699	• • • • • Material of the matrix	2224/45757	• • • • • Cobalt (Co) as principal constituent
2224/457	• • • • • with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/4576	• • • • • Iron (Fe) as principal constituent
2224/45701	• • • • • the principal constituent melting at a temperature of less than 400°C	2224/45763	• • • • • the principal constituent melting at a temperature of greater than 1550°C
2224/45705	• • • • • Gallium (Ga) as principal constituent	2224/45764	• • • • • Palladium (Pd) as principal constituent
2224/45709	• • • • • Indium (In) as principal constituent	2224/45766	• • • • • Titanium (Ti) as principal constituent
2224/45711	• • • • • Tin (Sn) as principal constituent	2224/45769	• • • • • Platinum (Pt) as principal constituent
2224/45713	• • • • • Bismuth (Bi) as principal constituent	2224/4577	• • • • • Zirconium (Zr) as principal constituent
2224/45714	• • • • • Thallium (Tl) as principal constituent	2224/45771	• • • • • Chromium (Cr) as principal constituent
2224/45716	• • • • • Lead (Pb) as principal constituent	2224/45772	• • • • • Vanadium (V) as principal constituent
2224/45717	• • • • • the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/45773	• • • • • Rhodium (Rh) as principal constituent
		2224/45776	• • • • • Ruthenium (Ru) as principal constituent
		2224/45778	• • • • • Iridium (Ir) as principal constituent
		2224/45779	• • • • • Niobium (Nb) as principal constituent
		2224/4578	• • • • • Molybdenum (Mo) as principal constituent
		2224/45781	• • • • • Tantalum (Ta) as principal constituent
		2224/45783	• • • • • Rhenium (Re) as principal constituent
		2224/45784	• • • • • Tungsten (W) as principal constituent
		2224/45786	• • • • • with a principal constituent of the material being a non metallic, non metalloid inorganic material
		2224/45787	• • • • • Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45788)

2224/45788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/45839	Silver (Ag) as principal constituent
2224/4579	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/45844	Gold (Au) as principal constituent
2224/45791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/45847	Copper (Cu) as principal constituent
2224/45793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/457 - H01L 2224/45791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45849	Manganese (Mn) as principal constituent
2224/45794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/457 - H01L 2224/45791	2224/45855	Nickel (Ni) as principal constituent
2224/45795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/457 - H01L 2224/45791	2224/45857	Cobalt (Co) as principal constituent
2224/45798	Fillers	2224/4586	Iron (Fe) as principal constituent
2224/45799	Base material	2224/45863	the principal constituent melting at a temperature of greater than 1550°C
2224/458	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/45864	Palladium (Pd) as principal constituent
2224/45801	the principal constituent melting at a temperature of less than 400°C	2224/45866	Titanium (Ti) as principal constituent
2224/45805	Gallium (Ga) as principal constituent	2224/45869	Platinum (Pt) as principal constituent
2224/45809	Indium (In) as principal constituent	2224/4587	Zirconium (Zr) as principal constituent
2224/45811	Tin (Sn) as principal constituent	2224/45871	Chromium (Cr) as principal constituent
2224/45813	Bismuth (Bi) as principal constituent	2224/45872	Vanadium (V) as principal constituent
2224/45814	Thallium (Tl) as principal constituent	2224/45873	Rhodium (Rh) as principal constituent
2224/45816	Lead (Pb) as principal constituent	2224/45876	Ruthenium (Ru) as principal constituent
2224/45817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/45878	Iridium (Ir) as principal constituent
2224/45818	Zinc (Zn) as principal constituent	2224/45879	Niobium (Nb) as principal constituent
2224/4582	Antimony (Sb) as principal constituent	2224/4588	Molybdenum (Mo) as principal constituent
2224/45823	Magnesium (Mg) as principal constituent	2224/45881	Tantalum (Ta) as principal constituent
2224/45824	Aluminium (Al) as principal constituent	2224/45883	Rhenium (Re) as principal constituent
2224/45838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/45884	Tungsten (W) as principal constituent
		2224/45886	with a principal constituent of the material being a non metallic, non metalloid inorganic material
		2224/45887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45888)
		2224/45888	Glasses, e.g. amorphous oxides, nitrides or fluorides
		2224/4589	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
		2224/45891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene

2224/45893	with a principal constituent of the material being a solid not provided for in groups H01L 2224/458 - H01L 2224/45891 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/45947	Copper (Cu) as principal constituent
2224/45894	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/458 - H01L 2224/45891	2224/45949	Manganese (Mn) as principal constituent
2224/45895	with a principal constituent of the material being a gas not provided for in groups H01L 2224/458 - H01L 2224/45891	2224/45955	Nickel (Ni) as principal constituent
2224/45898	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/45957	Cobalt (Co) as principal constituent
2224/45899	Coating material	2224/4596	Iron (Fe) as principal constituent
2224/459	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/45963	the principal constituent melting at a temperature of greater than 1550°C
2224/45901	the principal constituent melting at a temperature of less than 400°C	2224/45964	Palladium (Pd) as principal constituent
2224/45905	Gallium (Ga) as principal constituent	2224/45966	Titanium (Ti) as principal constituent
2224/45909	Indium (In) as principal constituent	2224/45969	Platinum (Pt) as principal constituent
2224/45911	Tin (Sn) as principal constituent	2224/4597	Zirconium (Zr) as principal constituent
2224/45913	Bismuth (Bi) as principal constituent	2224/45971	Chromium (Cr) as principal constituent
2224/45914	Thallium (Tl) as principal constituent	2224/45972	Vanadium (V) as principal constituent
2224/45916	Lead (Pb) as principal constituent	2224/45973	Rhodium (Rh) as principal constituent
2224/45917	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/45976	Ruthenium (Ru) as principal constituent
2224/45918	Zinc (Zn) as principal constituent	2224/45978	Iridium (Ir) as principal constituent
2224/4592	Antimony (Sb) as principal constituent	2224/45979	Niobium (Nb) as principal constituent
2224/45923	Magnesium (Mg) as principal constituent	2224/4598	Molybdenum (Mo) as principal constituent
2224/45924	Aluminium (Al) as principal constituent	2224/45981	Tantalum (Ta) as principal constituent
2224/45938	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/45983	Rhenium (Re) as principal constituent
2224/45939	Silver (Ag) as principal constituent	2224/45984	Tungsten (W) as principal constituent
2224/45944	Gold (Au) as principal constituent	2224/45986	with a principal constituent of the material being a non metallic, non metalloid inorganic material
		2224/45987	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/45988)
		2224/45988	Glasses, e.g. amorphous oxides, nitrides or fluorides
		2224/4599	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
		2224/45991	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
		2224/45993	with a principal constituent of the material being a solid not provided for in groups H01L 2224/459 - H01L 2224/45991 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond

2224/45994	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/459 - H01L 2224/45991	2224/48137	the bodies being arranged next to each other, e.g. on a common substrate
2224/45995	with a principal constituent of the material being a gas not provided for in groups H01L 2224/459 - H01L 2224/45991	2224/48138	the wire connector connecting to a bonding area disposed in a recess of the surface
2224/45998	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/48139	with an intermediate bond, e.g. continuous wire daisy chain
2224/45999	Shape or distribution of the fillers	2224/4814	the wire connector connecting to a bonding area protruding from the surface
2224/46	of a plurality of wire connectors	2224/48141	the bodies being arranged on opposite sides of a substrate, e.g. mirror arrangements
2224/47	Structure, shape, material or disposition of the wire connectors after the connecting process	2224/48145	the bodies being stacked
2224/48	of an individual wire connector	2224/48147	with an intermediate bond, e.g. continuous wire daisy chain
2224/4801	Structure	2224/48148	the wire connector connecting to a bonding area disposed in a recess of the surface
2224/48011	Length	2224/48149	the wire connector connecting to a bonding area protruding from the surface
2224/4805	Shape	2224/48151	Connecting between a semiconductor or solid-state body and an item not being a semiconductor or solid-state body, e.g. chip-to-substrate, chip-to-passive
2224/4807	of bonding interfaces, e.g. interlocking features	2224/48153	the body and the item being arranged next to each other, e.g. on a common substrate
2224/4809	Loop shape	2224/48155	the item being non-metallic, e.g. insulating substrate with or without metallisation
2224/48091	Arched	2224/48157	connecting the wire to a bond pad of the item
2224/48092	Helix	2224/48158	the bond pad being disposed in a recess of the surface of the item
2224/48095	Kinked	2224/48159	the bond pad protruding from the surface of the item
2224/48096	the kinked part being in proximity to the bonding area on the semiconductor or solid-state body	2224/4816	connecting the wire to a pin of the item
2224/48097	the kinked part being in proximity to the bonding area outside the semiconductor or solid-state body	2224/48163	connecting the wire to a potential ring of the item
2224/481	Disposition	2224/48165	connecting the wire to a via metallisation of the item
2224/48101	Connecting bonding areas at the same height, e.g. horizontal bond	2224/48175	the item being metallic
2224/48105	Connecting bonding areas at different heights	2224/48177	connecting the wire to a bond pad of the item
2224/48106	the connector being orthogonal to a side surface of the semiconductor or solid-state body, e.g. parallel layout	2224/48178	the bond pad being disposed in a recess of the surface of the item
2224/48108	the connector not being orthogonal to a side surface of the semiconductor or solid-state body, e.g. fanned-out connectors, radial layout	2224/48179	the bond pad protruding from the surface of the item
2224/4811	Connecting to a bonding area of the semiconductor or solid-state body located at the far end of the body with respect to the bonding area outside the semiconductor or solid-state body	2224/48183	connecting the wire to a potential ring of the item
2224/48111	the wire connector extending above another semiconductor or solid-state body	2224/48195	the item being a discrete passive component
2224/4813	Connecting within a semiconductor or solid-state body, i.e. fly wire, bridge wire	2224/48221	the body and the item being stacked
2224/48132	with an intermediate bond, e.g. continuous wire daisy chain	2224/48225	the item being non-metallic, e.g. insulating substrate with or without metallisation
2224/48135	Connecting between different semiconductor or solid-state bodies, i.e. chip-to-chip	2224/48227	connecting the wire to a bond pad of the item

2224/48228	the bond pad being disposed in a recess of the surface of the item	2224/48475	connected to auxiliary connecting means on the bonding areas, e.g. pre-ball, wedge-on-ball, ball-on-ball
2224/48229	the bond pad protruding from the surface of the item	2224/48476	between the wire connector and the bonding area
2224/4823	connecting the wire to a pin of the item	2224/48477	being a pre-ball (i.e. a ball formed by capillary bonding)
2224/48233	connecting the wire to a potential ring of the item	2224/48478	the connecting portion being a wedge bond, i.e. wedge on pre-ball
2224/48235	connecting the wire to a via metallisation of the item	2224/48479	on the semiconductor or solid-state body
2224/48237	connecting the wire to a die pad of the item	2224/4848	outside the semiconductor or solid-state body
2224/4824	Connecting between the body and an opposite side of the item with respect to the body	2224/48481	the connecting portion being a ball bond, i.e. ball on pre-ball
2224/48245	the item being metallic	2224/48482	on the semiconductor or solid-state body
2224/48247	connecting the wire to a bond pad of the item	2224/48483	outside the semiconductor or solid-state body
2224/48248	the bond pad being disposed in a recess of the surface of the item	2224/48484	being a plurality of pre-balls disposed side-to-side
2224/48249	the bond pad protruding from the surface of the item	2224/48485	the connecting portion being a wedge bond, i.e. wedge on pre-ball
2224/48253	connecting the wire to a potential ring of the item	2224/48486	on the semiconductor or solid-state body
2224/48257	connecting the wire to a die pad of the item	2224/48487	outside the semiconductor or solid-state body
2224/4826	Connecting between the body and an opposite side of the item with respect to the body	2224/48488	the connecting portion being a ball bond, i.e. ball on pre-ball
2224/48265	the item being a discrete passive component	2224/48489	on the semiconductor or solid-state body
2224/484	Connecting portions	2224/4849	outside the semiconductor or solid-state body
2224/4845	Details of ball bonds	2224/48491	being an additional member attached to the bonding area through an adhesive or solder, e.g. buffer pad
2224/48451	Shape	2224/48496	not being interposed between the wire connector and the bonding area
2224/48453	of the interface with the bonding area	2224/48499	Material of the auxiliary connecting means
2224/48455	Details of wedge bonds	2224/485	Material
2224/48456	Shape	2224/48505	at the bonding interface
2224/48458	of the interface with the bonding area	2224/48506	comprising an eutectic alloy
2224/4846	with multiple bonds on the same bonding area	2224/48507	comprising an intermetallic compound
2224/48463	the connecting portion on the bonding area of the semiconductor or solid-state body being a ball bond	2224/4851	Morphology of the connecting portion, e.g. grain size distribution
2224/48464	the other connecting portion not on the bonding area also being a ball bond, i.e. ball-to-ball	2224/48511	Heat affected zone [HAZ]
2224/48465	the other connecting portion not on the bonding area being a wedge bond, i.e. ball-to-wedge, regular stitch	2224/4852	Bonding interface between the connecting portion and the bonding area
2224/4847	the connecting portion on the bonding area of the semiconductor or solid-state body being a wedge bond	2224/48599	Principal constituent of the connecting portion of the wire connector being Gold (Au)
2224/48471	the other connecting portion not on the bonding area being a ball bond, i.e. wedge-to-ball, reverse stitch	2224/486	with a principal constituent of the bonding area being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/48472	the other connecting portion not on the bonding area also being a wedge bond, i.e. wedge-to-wedge			

2224/48601	the principal constituent melting at a temperature of less than 400°C	2224/48679	Niobium (Nb) as principal constituent
2224/48605	Gallium (Ga) as principal constituent	2224/4868	Molybdenum (Mo) as principal constituent
2224/48609	Indium (In) as principal constituent	2224/48681	Tantalum (Ta) as principal constituent
2224/48611	Tin (Sn) as principal constituent	2224/48683	Rhenium (Re) as principal constituent
2224/48613	Bismuth (Bi) as principal constituent	2224/48684	Tungsten (W) as principal constituent
2224/48614	Thallium (Tl) as principal constituent	2224/48686	with a principal constituent of the bonding area being a non metallic, non metalloid inorganic material
2224/48616	Lead (Pb) as principal constituent	2224/48687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/48688)
2224/48617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950 °C	2224/48688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/48618	Zinc (Zn) as principal constituent	2224/4869	with a principal constituent of the bonding area being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/4862	Antimony (Sb) as principal constituent	2224/48691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/48623	Magnesium (Mg) as principal constituent	2224/48693	with a principal constituent of the bonding area being a solid not provided for in groups H01L 2224/486 - H01L 2224/4869 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/48624	Aluminium (Al) as principal constituent	2224/48694	with a principal constituent of the bonding area being a liquid not provided for in groups H01L 2224/486 - H01L 2224/4869
2224/48638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/48698	with a principal constituent of the bonding area being a combination of two or more material regions, i.e. being a hybrid material, e.g. segmented structures, island patterns
2224/48639	Silver (Ag) as principal constituent	2224/48699	Principal constituent of the connecting portion of the wire connector being Aluminium (Al)
2224/48644	Gold (Au) as principal constituent	2224/487	with a principal constituent of the bonding area being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/48647	Copper (Cu) as principal constituent	2224/48701	the principal constituent melting at a temperature of less than 400°C
2224/48649	Manganese (Mn) as principal constituent	2224/48705	Gallium (Ga) as principal constituent
2224/48655	Nickel (Ni) as principal constituent	2224/48709	Indium (In) as principal constituent
2224/48657	Cobalt (Co) as principal constituent	2224/48711	Tin (Sn) as principal constituent
2224/4866	Iron (Fe) as principal constituent	2224/48713	Bismuth (Bi) as principal constituent
2224/48663	the principal constituent melting at a temperature of greater than 1550°C	2224/48714	Thallium (Tl) as principal constituent
2224/48664	Palladium (Pd) as principal constituent		
2224/48666	Titanium (Ti) as principal constituent		
2224/48669	Platinum (Pt) as principal constituent		
2224/4867	Zirconium (Zr) as principal constituent		
2224/48671	Chromium (Cr) as principal constituent		
2224/48672	Vanadium (V) as principal constituent		
2224/48673	Rhodium (Rh) as principal constituent		
2224/48678	Iridium (Ir) as principal constituent		

2224/48716	Lead (Pb) as principal constituent	2224/48787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/48788)
2224/48717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950 °C	2224/48788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/48718	Zinc (Zn) as principal constituent	2224/4879	with a principal constituent of the bonding area being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/4872	Antimony (Sb) as principal constituent	2224/48791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/48723	Magnesium (Mg) as principal constituent	2224/48793	with a principal constituent of the bonding area being a solid not provided for in groups H01L 2224/487 - H01L 2224/4879 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/48724	Aluminium (Al) as principal constituent	2224/48794	with a principal constituent of the bonding area being a liquid not provided for in groups H01L 2224/487 - H01L 2224/4879
2224/48738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/48798	with a principal constituent of the bonding area being a combination of two or more material regions, i.e. being a hybrid material, e.g. segmented structures, island patterns
2224/48739	Silver (Ag) as principal constituent	2224/48799	Principal constituent of the connecting portion of the wire connector being Copper (Cu)
2224/48744	Gold (Au) as principal constituent	2224/488	with a principal constituent of the bonding area being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/48747	Copper (Cu) as principal constituent	2224/48801	the principal constituent melting at a temperature of less than 400°C
2224/48749	Manganese (Mn) as principal constituent	2224/48805	Gallium (Ga) as principal constituent
2224/48755	Nickel (Ni) as principal constituent	2224/48809	Indium (In) as principal constituent
2224/48757	Cobalt (Co) as principal constituent	2224/48811	Tin (Sn) as principal constituent
2224/4876	Iron (Fe) as principal constituent	2224/48813	Bismuth (Bi) as principal constituent
2224/48763	the principal constituent melting at a temperature of greater than 1550°C	2224/48814	Thallium (Tl) as principal constituent
2224/48764	Palladium (Pd) as principal constituent	2224/48816	Lead (Pb) as principal constituent
2224/48766	Titanium (Ti) as principal constituent	2224/48817	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950 °C
2224/48769	Platinum (Pt) as principal constituent	2224/48818	Zinc (Zn) as principal constituent
2224/4877	Zirconium (Zr) as principal constituent	2224/4882	Antimony (Sb) as principal constituent
2224/48771	Chromium (Cr) as principal constituent	2224/48823	Magnesium (Mg) as principal constituent
2224/48772	Vanadium (V) as principal constituent	2224/48824	Aluminium (Al) as principal constituent
2224/48773	Rhodium (Rh) as principal constituent		
2224/48778	Iridium (Ir) as principal constituent		
2224/48779	Niobium (Nb) as principal constituent		
2224/4878	Molybdenum (Mo) as principal constituent		
2224/48781	Tantalum (Ta) as principal constituent		
2224/48783	Rhenium (Re) as principal constituent		
2224/48784	Tungsten (W) as principal constituent		
2224/48786	with a principal constituent of the bonding area being a non metallic, non metalloid inorganic material		

2224/48838	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/48893	with a principal constituent of the bonding area being a solid not provided for in groups H01L 2224/488 - H01L 2224/4889 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/48839	Silver (Ag) as principal constituent	2224/48894	with a principal constituent of the bonding area being a liquid not provided for in groups H01L 2224/488 - H01L 2224/4889
2224/48844	Gold (Au) as principal constituent	2224/48898	with a principal constituent of the bonding area being a combination of two or more material regions, i.e. being a hybrid material, e.g. segmented structures, island patterns
2224/48847	Copper (Cu) as principal constituent	2224/4899	Auxiliary members for wire connectors, e.g. flow-barriers, reinforcing structures, spacers, alignment aids
2224/48849	Manganese (Mn) as principal constituent	2224/48991	being formed on the semiconductor or solid-state body to be connected
2224/48855	Nickel (Ni) as principal constituent	2224/48992	Reinforcing structures
2224/48857	Cobalt (Co) as principal constituent	2224/48993	Alignment aids
2224/4886	Iron (Fe) as principal constituent	2224/48996	being formed on an item to be connected not being a semiconductor or solid-state body
2224/48863	the principal constituent melting at a temperature of greater than 1550°C	2224/48997	Reinforcing structures
2224/48864	Palladium (Pd) as principal constituent	2224/48998	Alignment aids
2224/48866	Titanium (Ti) as principal constituent	2224/49	of a plurality of wire connectors
2224/48869	Platinum (Pt) as principal constituent	2224/4901	Structure
2224/4887	Zirconium (Zr) as principal constituent	2224/4903	Connectors having different sizes, e.g. different diameters
2224/48871	Chromium (Cr) as principal constituent	2224/4905	Shape
2224/48872	Vanadium (V) as principal constituent	2224/49051	Connectors having different shapes
2224/48873	Rhodium (Rh) as principal constituent	2224/49052	Different loop heights
2224/48878	Iridium (Ir) as principal constituent	2224/4909	Loop shape arrangement
2224/48879	Niobium (Nb) as principal constituent	2224/49095	parallel in plane
2224/4888	Molybdenum (Mo) as principal constituent	2224/49096	horizontal
2224/48881	Tantalum (Ta) as principal constituent	2224/49097	vertical
2224/48883	Rhenium (Re) as principal constituent	2224/491	Disposition
2224/48884	Tungsten (W) as principal constituent	2224/49105	Connecting at different heights
2224/48886	with a principal constituent of the bonding area being a non metallic, non metalloid inorganic material	2224/49107	on the semiconductor or solid-state body
2224/48887	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/48888)	2224/49109	outside the semiconductor or solid-state body
2224/48888	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/4911	the connectors being bonded to at least one common bonding area, e.g. daisy chain
2224/4889	with a principal constituent of the bonding area being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/49111	the connectors connecting two common bonding areas, e.g. Litz or braid wires
2224/48891	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/49112	the connectors connecting a common bonding area on the semiconductor or solid-state body to different bonding areas outside the body, e.g. diverging wires
		2224/49113	the connectors connecting different bonding areas on the semiconductor or solid-state body to a common bonding area outside the body, e.g. converging wires
		2224/4912	Layout
		2224/4917	Crossed wires

- 2224/49171 Fan-out arrangements
- 2224/49173 Radial fan-out arrangements
- 2224/49174 Stacked arrangements
- 2224/49175 Parallel arrangements
- 2224/49176 Wire connectors having the same loop shape and height
- 2224/49177 Combinations of different arrangements
- 2224/49179 Corner adaptations, i.e. disposition of the wire connectors at the corners of the semiconductor or solid-state body
- 2224/4918 being disposed on at least two different sides of the body, e.g. dual array
- 2224/494 Connecting portions
- 2224/4941 the connecting portions being stacked
- 2224/4942 Ball bonds
- 2224/49421 on the semiconductor or solid-state body
- 2224/49422 outside the semiconductor or solid-state body
- 2224/49425 Wedge bonds
- 2224/49426 on the semiconductor or solid-state body
- 2224/49427 outside the semiconductor or solid-state body
- 2224/49429 Wedge and ball bonds
- 2224/4943 the connecting portions being staggered
- 2224/49431 on the semiconductor or solid-state body
- 2224/49433 outside the semiconductor or solid-state body
- 2224/4945 Wire connectors having connecting portions of different types on the semiconductor or solid-state body, e.g. regular and reverse stitches
- 2224/495 Material
- 2224/49505 Connectors having different materials
- 2224/50 Tape automated bonding [TAB] connectors, i.e. film carriers; Manufacturing methods related thereto
- 2224/63 Connectors not provided for in any of the groups [H01L 2224/10](#) - [H01L 2224/50](#) and subgroups; Manufacturing methods related thereto
- 2224/64 Manufacturing methods
- 2224/65 Structure, shape, material or disposition of the connectors prior to the connecting process
- 2224/66 of an individual connector
- 2224/67 of a plurality of connectors
- 2224/68 Structure, shape, material or disposition of the connectors after the connecting process
- 2224/69 of an individual connector
- 2224/70 of a plurality of connectors
- 2224/71 Means for bonding not being attached to, or not being formed on, the surface to be connected
- 2224/72 Detachable connecting means consisting of mechanical auxiliary parts connecting the device, e.g. pressure contacts using springs or clips
- 2224/73 Means for bonding being of different types provided for in two or more of groups [H01L 2224/10](#), [H01L 2224/18](#), [H01L 2224/26](#), [H01L 2224/34](#), [H01L 2224/42](#), [H01L 2224/50](#), [H01L 2224/63](#), [H01L 2224/71](#)
- 2224/731 Location prior to the connecting process
- 2224/73101 on the same surface
- 2224/73103 Bump and layer connectors
- 2224/73104 the bump connector being embedded into the layer connector
- 2224/73151 on different surfaces
- 2224/73153 Bump and layer connectors
- 2224/732 Location after the connecting process
- 2224/73201 on the same surface
- 2224/73203 Bump and layer connectors
- 2224/73204 the bump connector being embedded into the layer connector
- 2224/73205 Bump and strap connectors
- 2224/73207 Bump and wire connectors
- 2224/73209 Bump and HDI connectors
- 2224/73211 Bump and TAB connectors
- 2224/73213 Layer and strap connectors
- 2224/73215 Layer and wire connectors
- 2224/73217 Layer and HDI connectors
- 2224/73219 Layer and TAB connectors
- 2224/73221 Strap and wire connectors
- 2224/73223 Strap and HDI connectors
- 2224/73225 Strap and TAB connectors
- 2224/73227 Wire and HDI connectors
- 2224/73229 Wire and TAB connectors
- 2224/73231 HDI and TAB connectors
- 2224/73251 on different surfaces
- 2224/73253 Bump and layer connectors
- 2224/73255 Bump and strap connectors
- 2224/73257 Bump and wire connectors
- 2224/73259 Bump and HDI connectors
- 2224/73261 Bump and TAB connectors
- 2224/73263 Layer and strap connectors
- 2224/73265 Layer and wire connectors
- 2224/73267 Layer and HDI connectors
- 2224/73269 Layer and TAB connectors
- 2224/73271 Strap and wire connectors
- 2224/73273 Strap and HDI connectors
- 2224/73275 Strap and TAB connectors
- 2224/73277 Wire and HDI connectors
- 2224/73279 Wire and TAB connectors
- 2224/73281 HDI and TAB connectors
- 2224/74 Apparatus for manufacturing arrangements for connecting or disconnecting semiconductor or solid-state bodies and for methods related thereto
- 2224/741 Apparatus for manufacturing means for bonding, e.g. connectors
- 2224/742 Apparatus for manufacturing bump connectors
- 2224/743 Apparatus for manufacturing layer connectors
- 2224/744 Apparatus for manufacturing strap connectors
- 2224/745 Apparatus for manufacturing wire connectors
- 2224/749 Tools for reworking, e.g. for shaping
- 2224/75 Apparatus for connecting with bump connectors or layer connectors
- 2224/75001 Calibration means
- 2224/7501 Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma
- 2224/751 Means for controlling the bonding environment, e.g. valves, vacuum pumps
- 2224/75101 Chamber
- 2224/75102 Vacuum chamber

2224/7511	High pressure chamber	2224/7531	of other parts
2224/7515	. . .	Means for applying permanent coating, e.g. in-situ coating	2224/75312	Material
2224/75151	Means for direct writing	2224/75313	Removable bonding head
2224/75152	Syringe	2224/75314	Auxiliary members on the pressing surface
2224/75153	integrated into the bonding head	2224/75315	Elastomer inlay
2224/75155	Jetting means, e.g. ink jet	2224/75316	with retaining mechanisms
2224/75158	including a laser	2224/75317	Removable auxiliary member
2224/75161	Means for screen printing, e.g. roller, squeegee, screen stencil	2224/75318	Shape of the auxiliary member
2224/7517	Means for applying a preform, e.g. laminator	2224/7532	Material of the auxiliary member
2224/75171	including a vacuum-bag	2224/75343	by ultrasonic vibrations
2224/7518	Means for blanket deposition	2224/75344	Eccentric cams
2224/75181	for spin coating, i.e. spin coater	2224/75345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75182	for curtain coating	2224/75346	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/75183	for immersion coating, i.e. bath	2224/75347	Piezoelectric transducers
2224/75184	for spray coating, i.e. nozzle	2224/75348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75185	Means for physical vapour deposition [PVD], e.g. evaporation, sputtering	2224/75349	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/75186	Means for sputtering, e.g. target	2224/7535	Stable and mobile yokes
2224/75187	Means for evaporation	2224/75351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75188	Means for chemical vapour deposition [CVD], e.g. for laser CVD	2224/75352	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/75189	Means for plating, e.g. for electroplating, electroless plating	2224/75353	Ultrasonic horns
2224/752	. . .	Protection means against electrical discharge	2224/75354	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/7525	. . .	Means for applying energy, e.g. heating means	2224/75355	Design, e.g. of the wave guide
2224/75251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/755	. . .	Cooling means
2224/75252	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75253	adapted for localised heating	2224/75502	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/7526	Polychromatic heating lamp	2224/7555	. . .	Mechanical means, e.g. for planarising, pressing, stamping
2224/75261	Laser	2224/756	. . .	Means for supplying the connector to be connected in the bonding apparatus
2224/75262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/75601	Storing means
2224/75263	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75611	Feeding means
2224/75264	by induction heating, i.e. coils	2224/75621	Holding means
2224/75265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/7565	. . .	Means for transporting the components to be connected
2224/75266	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75651	Belt conveyor
2224/75267	Flame torch, e.g. hydrogen torch	2224/75652	Chain conveyor
2224/75268	Discharge electrode	2224/75653	Vibrating conveyor
2224/75269	Shape of the discharge electrode	2224/75654	Pneumatic conveyor
2224/7527	Material of the discharge electrode	2224/75655	in a fluid
2224/75271	Circuitry of the discharge electrode	2224/757	. . .	Means for aligning
2224/75272	Oven	2224/75701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/7528	Resistance welding electrodes, i.e. for ohmic heating	2224/75702	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/75281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/75703	Mechanical holding means
2224/75282	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/75704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75283	by infrared heating, e.g. infrared heating lamp	2224/75705	in the upper part of the bonding apparatus, e.g. in the bonding head
2224/753	by means of pressure	2224/75723	Electrostatic holding means
2224/75301	Bonding head	2224/75724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75302	Shape			
2224/75303	of the pressing surface			
2224/75304	being curved			
2224/75305	comprising protrusions			

2224/75725	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/76155	Jetting means, e.g. ink jet
2224/75733	Magnetic holding means	2224/76158	including a laser
2224/75734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76161	Means for screen printing, e.g. roller, squeegee, screen stencil
2224/75735	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/7617	Means for applying a preform, e.g. laminator
2224/75743	Suction holding means	2224/76171	including a vacuum-bag
2224/75744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/7618	Means for blanket deposition
2224/75745	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/76181	for spin coating, i.e. spin coater
2224/75753	Means for optical alignment, e.g. sensors	2224/76182	for curtain coating
2224/75754	Guiding structures	2224/76183	for immersion coating, i.e. bath
2224/75755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76184	for spray coating, i.e. nozzle
2224/75756	in the upper part of the bonding apparatus, e.g. in the bonding head	2224/76185	Means for physical vapour deposition [PVD]
2224/758	Means for moving parts	2224/76186	Means for sputtering, e.g. target
2224/75801	Lower part of the bonding apparatus, e.g. XY table	2224/76187	Means for evaporation
2224/75802	Rotational mechanism	2224/76188	Means for chemical vapour deposition [CVD], e.g. for laser CVD
2224/75803	Pivoting mechanism	2224/76189	Means for plating, e.g. for electroplating, electroless plating
2224/75804	Translational mechanism	2224/762	Protection means against electrical discharge
2224/75821	Upper part of the bonding apparatus, i.e. bonding head	2224/7625	Means for applying energy, e.g. heating means
2224/75822	Rotational mechanism	2224/76251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75823	Pivoting mechanism	2224/76252	in the upper part of the bonding apparatus
2224/75824	Translational mechanism	2224/76253	adapted for localised heating
2224/75841	of the bonding head	2224/7626	Polychromatic heating lamp
2224/75842	Rotational mechanism	2224/76261	Laser
2224/75843	Pivoting mechanism	2224/76262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/759	Means for monitoring the connection process	2224/76263	in the upper part of the bonding apparatus
2224/75901	using a computer, e.g. fully- or semi-automatic bonding	2224/76264	by induction heating, i.e. coils
2224/7592	Load or pressure adjusting means, e.g. sensors	2224/76265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75925	Vibration adjusting means, e.g. sensors	2224/76266	in the upper part of the bonding apparatus
2224/7595	Means for forming additional members	2224/76267	Flame torch, e.g. hydrogen torch
2224/7598	specially adapted for batch processes	2224/76268	Discharge electrode
2224/75981	Apparatus chuck	2224/76269	Shape of the discharge electrode
2224/75982	Shape	2224/7627	Material of the discharge electrode
2224/75983	of the mounting surface	2224/76271	Circuitry of the discharge electrode
2224/75984	of other portions	2224/76272	Oven
2224/75985	Material	2224/7628	Resistance welding electrodes, i.e. for ohmic heating
2224/75986	Auxiliary members on the pressing surface	2224/76281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/75987	Shape of the auxiliary member	2224/76282	in the upper part of the bonding apparatus
2224/75988	Material of the auxiliary member	2224/76283	by infrared heating, e.g. infrared heating lamp
2224/76	Apparatus for connecting with build-up interconnects	2224/763	by means of pressure
2224/76001	Calibration means	2224/76301	Pressing head
2224/7601	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma	2224/76302	Shape
2224/761	Means for controlling the bonding environment, e.g. valves, vacuum pumps	2224/76303	of the pressing surface
2224/76101	Chamber	2224/76304	being curved
2224/76102	Vacuum chamber	2224/76305	comprising protrusions
2224/7611	High pressure chamber	2224/7631	of other parts
2224/7615	Means for depositing	2224/76312	Material
2224/76151	Means for direct writing	2224/76313	Removable pressing head
2224/76152	Syringe	2224/76314	Auxiliary members on the pressing surface
			2224/76315	Elastomer inlay
			2224/76316	with retaining mechanisms
			2224/76317	Removable auxiliary member
			2224/76318	Shape of the auxiliary member

2224/7632	Material of the auxiliary member	2224/76754	Guiding structures
2224/76343	by ultrasonic vibrations	2224/76755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/76344	Eccentric cams	2224/76756	in the upper part of the bonding apparatus
2224/76345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/768	. . .	Means for moving parts
2224/76346	in the upper part of the bonding apparatus	2224/76801	Lower part of the bonding apparatus, e.g. XY table
2224/76347	Piezoelectric transducers	2224/76802	Rotational mechanism
2224/76348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76803	Pivoting mechanism
2224/76349	in the upper part of the bonding apparatus	2224/76804	Translational mechanism
2224/7635	Stable and mobile yokes	2224/76821	Upper part of the bonding apparatus, i.e. bonding head
2224/76351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76822	Rotational mechanism
2224/76352	in the upper part of the bonding apparatus	2224/76823	Pivoting mechanism
2224/76353	Ultrasonic horns	2224/76824	Translational mechanism
2224/76354	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/76841	of the bonding head
2224/76355	Design, e.g. of the wave guide	2224/76842	Rotational mechanism
2224/765	. . .	Cooling means	2224/76843	Pivoting mechanism
2224/76501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/769	. . .	Means for monitoring the connection process
2224/76502	in the upper part of the bonding apparatus	2224/76901	using a computer, e.g. fully- or semi-automatic bonding
2224/7655	. . .	Mechanical means, e.g. for planarising, pressing, stamping	2224/7692	Load or pressure adjusting means, e.g. sensors
2224/76552	for drilling	2224/76925	Vibration adjusting means, e.g. sensors
2224/76554	for abrasive blasting, e.g. sand blasting, wet blasting, hydro-blasting, dry ice blasting	2224/7695	. . .	Means for forming additional members
2224/766	. . .	Means for supplying the material of the interconnect	2224/7698	. . .	specially adapted for batch processes
2224/76601	Storing means	2224/76981	. . .	Apparatus chuck
2224/76611	Feeding means	2224/76982	Shape
2224/76621	Holding means	2224/76983	of the mounting surface
2224/7665	. . .	Means for transporting the components to be connected	2224/76984	of other portions
2224/76651	Belt conveyor	2224/76985	Material
2224/76652	Chain conveyor	2224/76986	Auxiliary members on the pressing surface
2224/76653	Vibrating conveyor	2224/76987	Shape of the auxiliary member
2224/76654	Pneumatic conveyor	2224/76988	Material of the auxiliary member
2224/76655	in a fluid	2224/77	. .	Apparatus for connecting with strap connectors
2224/767	. . .	Means for aligning	2224/77001	. . .	Calibration means
2224/76701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/7701	. . .	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma
2224/76702	in the upper part of the bonding apparatus	2224/771	. . .	Means for controlling the bonding environment, e.g. valves, vacuum pumps
2224/76703	Mechanical holding means	2224/77101	Chamber
2224/76704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/77102	Vacuum chamber
2224/76705	in the upper part of the bonding apparatus	2224/7711	High pressure chamber
2224/76723	Electrostatic holding means	2224/7715	. . .	Means for applying permanent coating, e.g. in-situ coating
2224/76724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/77151	Means for direct writing
2224/76725	in the upper part of the bonding apparatus	2224/77152	Syringe
2224/76733	Magnetic holding means	2224/77153	integrated into the capillary or wedge
2224/76734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/77155	Jetting means, e.g. ink jet
2224/76735	in the upper part of the bonding apparatus	2224/77158	including a laser
2224/76743	Suction holding means	2224/77161	Means for screen printing, e.g. roller, squeegee, screen stencil
2224/76744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/7717	Means for applying a preform, e.g. laminator
2224/76745	in the upper part of the bonding apparatus	2224/77171	including a vacuum-bag
2224/76753	Means for optical alignment, e.g. sensors	2224/7718	Means for blanket deposition
			2224/77181	for spin coating, i.e. spin coater
			2224/77182	for curtain coating
			2224/77183	for immersion coating, i.e. bath
			2224/77184	for spray coating, i.e. nozzle

2224/77185	Means for physical vapour deposition [PVD], e.g. evaporation, sputtering	2224/77348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77186	Means for sputtering, e.g. target	2224/77349	in the upper part of the bonding apparatus, e.g. in the wedge
2224/77187	Means for evaporation	2224/7735	Stable and mobile yokes
2224/77188	Means for chemical vapour deposition [CVD], e.g. for laser CVD	2224/77351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77189	Means for plating, e.g. for electroplating, electroless plating	2224/77352	in the upper part of the bonding apparatus, e.g. in the wedge
2224/772	Protection means against electrical discharge	2224/77353	Ultrasonic horns
2224/7725	Means for applying energy, e.g. heating means	2224/77354	in the lower part of the bonding apparatus, e.g. in the mounting chuck
2224/77251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/77355	Design, e.g. of the wave guide
2224/77252	in the upper part of the bonding apparatus, e.g. in the wedge	2224/775	Cooling means
2224/77253	adapted for localised heating	2224/77501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/7726	Polychromatic heating lamp	2224/77502	in the upper part of the bonding apparatus, e.g. in the wedge
2224/77261	Laser	2224/7755	Mechanical means, e.g. for severing, pressing, stamping
2224/77262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/776	Means for supplying the connector to be connected in the bonding apparatus
2224/77263	in the upper part of the bonding apparatus, e.g. in the wedge	2224/77601	Storing means
2224/77264	by induction heating, i.e. coils	2224/77611	Feeding means
2224/77265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/77621	Holding means, e.g. wire clampers
2224/77266	in the upper part of the bonding apparatus, e.g. in the wedge	2224/77631	Means for wire tension adjustments
2224/77267	Flame torch, e.g. hydrogen torch	2224/7765	Means for transporting the components to be connected
2224/77268	Discharge electrode	2224/77651	Belt conveyor
2224/77269	Shape of the discharge electrode	2224/77652	Chain conveyor
2224/7727	Material of the discharge electrode	2224/77653	Vibrating conveyor
2224/77271	Circuitry of the discharge electrode	2224/77654	Pneumatic conveyor
2224/77272	Oven	2224/77655	in a fluid
2224/7728	Resistance welding electrodes, i.e. for ohmic heating	2224/777	Means for aligning
2224/77281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/77701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77282	in the upper part of the bonding apparatus, e.g. in the wedge	2224/77702	in the upper part of the bonding apparatus, e.g. in the wedge
2224/77283	by infrared heating, e.g. infrared heating lamp	2224/77703	Mechanical holding means
2224/773	by means of pressure	2224/77704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77313	Wedge	2224/77705	in the upper part of the bonding apparatus, e.g. in the wedge
2224/77314	Shape	2224/77723	Electrostatic holding means
2224/77315	of the pressing surface, e.g. tip or head	2224/77724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77316	comprising protrusions	2224/77725	in the upper part of the bonding apparatus, e.g. in the wedge
2224/77317	of other portions	2224/77733	Magnetic holding means
2224/77318	inside the capillary	2224/77734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77319	outside the capillary	2224/77735	in the upper part of the bonding apparatus, e.g. in the wedge
2224/7732	Removable wedge	2224/77743	Suction holding means
2224/77321	Material	2224/77744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77325	Auxiliary members on the pressing surface	2224/77745	in the upper part of the bonding apparatus, e.g. in the wedge
2224/77326	Removable auxiliary member	2224/77753	Means for optical alignment, e.g. sensors
2224/77327	Shape of the auxiliary member	2224/77754	Guiding structures
2224/77328	Material of the auxiliary member	2224/77755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77343	by ultrasonic vibrations			
2224/77344	Eccentric cams			
2224/77345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck			
2224/77346	in the upper part of the bonding apparatus, e.g. in the wedge			
2224/77347	Piezoelectric transducers			

2224/77756	in the upper part of the bonding apparatus, e.g. in the wedge	2224/78267	Flame torch, e.g. hydrogen torch
2224/778	. . .	Means for moving parts	2224/78268	Discharge electrode
2224/77801	Lower part of the bonding apparatus, e.g. XY table	2224/78269	Shape of the discharge electrode
2224/77802	Rotational mechanism	2224/7827	Material of the discharge electrode
2224/77803	Pivoting mechanism	2224/78271	Circuitry of the discharge electrode
2224/77804	Translational mechanism	2224/78272	Oven
2224/77821	Upper part of the bonding apparatus, i.e. bonding head, e.g. capillary or wedge	2224/7828	Resistance welding electrodes, i.e. for ohmic heating
2224/77822	Rotational mechanism	2224/78281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/77823	Pivoting mechanism	2224/78282	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/77824	Translational mechanism	2224/78283	by infrared heating, e.g. infrared heating lamp
2224/77841	of the pressing portion, e.g. tip or head	2224/783	by means of pressure
2224/77842	Rotational mechanism	2224/78301	Capillary
2224/77843	Pivoting mechanism	2224/78302	Shape
2224/779	. . .	Means for monitoring the connection process	2224/78303	of the pressing surface, e.g. tip or head
2224/77901	using a computer, e.g. fully- or semi-automatic bonding	2224/78304	comprising protrusions
2224/7792	Load or pressure adjusting means, e.g. sensors	2224/78305	of other portions
2224/77925	Vibration adjusting means, e.g. sensors	2224/78306	inside the capillary
2224/7795	. . .	Means for forming additional members	2224/78307	outside the capillary
2224/7798	. . .	specially adapted for batch processes	2224/78308	Removable capillary
2224/77981	. . .	Apparatus chuck	2224/78309	Material
2224/77982	Shape	2224/7831	Auxiliary members on the pressing surface
2224/77983	of the mounting surface	2224/78311	Removable auxiliary member
2224/77984	of other portions	2224/78312	Shape of the auxiliary member
2224/77985	Material	2224/78313	Wedge
2224/77986	Auxiliary members on the pressing surface	2224/78314	Shape
2224/77987	Shape of the auxiliary member	2224/78315	of the pressing surface, e.g. tip or head
2224/77988	Material of the auxiliary member	2224/78316	comprising protrusions
2224/78	. .	Apparatus for connecting with wire connectors	2224/78317	of other portions
2224/78001	. . .	Calibration means	2224/78318	inside the capillary
2224/7801	. . .	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma	2224/78319	outside the capillary
2224/781	. . .	Means for controlling the bonding environment, e.g. valves, vacuum pumps	2224/7832	Removable wedge
2224/78101	Chamber	2224/78321	Material
2224/78102	Vacuum chamber	2224/78325	Auxiliary members on the pressing surface
2224/7811	High pressure chamber	2224/78326	Removable auxiliary member
2224/7815	. . .	Means for applying permanent coating, e.g. in-situ coating	2224/78327	Shape of the auxiliary member
2224/782	. . .	Protection means against electrical discharge	2224/78328	Material of the auxiliary member
2224/7825	. . .	Means for applying energy, e.g. heating means	2224/78343	by ultrasonic vibrations
2224/78251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78344	Eccentric cams
2224/78252	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/78345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78253	adapted for localised heating	2224/78346	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/7826	Polychromatic heating lamp	2224/78347	Piezoelectric transducers
2224/78261	Laser	2224/78348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78349	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78263	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/7835	Stable and mobile yokes
2224/78264	by induction heating, i.e. coils	2224/78351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/78265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78352	in the upper part of the bonding apparatus, e.g. in the capillary or wedge
2224/78266	in the upper part of the bonding apparatus, e.g. in the capillary or wedge			

2224/78353	Ultrasonic horns	2224/78822	Rotational mechanism
2224/78354	in the lower part of the bonding apparatus, e.g. in the mounting chuck	2224/78823	Pivoting mechanism
2224/78355	Design, e.g. of the wave guide	2224/78824	Translational mechanism
2224/785	. . .	Cooling means	2224/78841	of the pressing portion, e.g. tip or head
2224/78501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78842	Rotational mechanism
2224/78502	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/78843	Pivoting mechanism
2224/7855	. . .	Mechanical means, e.g. for severing, pressing, stamping	2224/789	. . .	Means for monitoring the connection process
2224/786	. . .	Means for supplying the connector to be connected in the bonding apparatus	2224/78901	using a computer, e.g. fully- or semi-automatic bonding
2224/78601	Storing means	2224/7892	Load or pressure adjusting means, e.g. sensors
2224/78611	Feeding means	2224/78925	Vibration adjusting means, e.g. sensors
2224/78621	Holding means, e.g. wire claspers	2224/7895	. . .	Means for forming additional members
2224/78631	Means for wire tension adjustments	2224/7898	. . .	specially adapted for batch processes
2224/7865	. . .	Means for transporting the components to be connected	2224/78981	. . .	Apparatus chuck
2224/78651	Belt conveyor	2224/78982	Shape
2224/78652	Chain conveyor	2224/78983	of the mounting surface
2224/78653	Vibrating conveyor	2224/78984	of other portions
2224/78654	Pneumatic conveyor	2224/78985	Material
2224/78655	in a fluid	2224/78986	Auxiliary members on the pressing surface
2224/787	. . .	Means for aligning	2224/78987	Shape of the auxiliary member
2224/78701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/78988	Material of the auxiliary member
2224/78702	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/79	. .	Apparatus for Tape Automated Bonding [TAB]
2224/78703	Mechanical holding means	2224/79001	. . .	Calibration means
2224/78704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/7901	. . .	Means for cleaning, e.g. brushes, for hydro blasting, for ultrasonic cleaning, for dry ice blasting, using gas-flow, by etching, by applying flux or plasma
2224/78705	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/791	. . .	Means for controlling the bonding environment, e.g. valves, vacuum pumps
2224/78723	Electrostatic holding means	2224/79101	Chamber
2224/78724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79102	Vacuum chamber
2224/78725	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/7911	High pressure chamber
2224/78733	Magnetic holding means	2224/7915	. . .	Means for applying permanent coating
2224/78734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79151	Means for direct writing
2224/78735	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/79152	Syringe
2224/78743	Suction holding means	2224/79153	integrated into the pressing head
2224/78744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79155	Jetting means, e.g. ink jet
2224/78745	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/79158	including a laser
2224/78753	Means for optical alignment, e.g. sensors	2224/79161	Means for screen printing, e.g. roller, squeegee, screen stencil
2224/78754	Guiding structures	2224/7917	Means for applying a preform, e.g. laminator
2224/78755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79171	including a vacuum-bag
2224/78756	in the upper part of the bonding apparatus, e.g. in the capillary or wedge	2224/7918	Means for blanket deposition
2224/788	. . .	Means for moving parts	2224/79181	for spin coating, i.e. spin coater
2224/78801	Lower part of the bonding apparatus, e.g. XY table	2224/79182	for curtain coating
2224/78802	Rotational mechanism	2224/79183	for immersion coating, i.e. bath
2224/78803	Pivoting mechanism	2224/79184	for spray coating, i.e. nozzle
2224/78804	Translational mechanism	2224/79185	Means for physical vapour deposition [PVD], e.g. evaporation, sputtering
2224/78821	Upper part of the bonding apparatus, i.e. bonding head, e.g. capillary or wedge	2224/79186	Means for sputtering, e.g. target
			2224/79187	Means for evaporation
			2224/79188	Means for chemical vapour deposition [CVD], e.g. for laser CVD
			2224/79189	Means for plating, e.g. for electroplating, electroless plating
			2224/792	. . .	Protection means against electrical discharge
			2224/7925	. . .	Means for applying energy, e.g. heating means
			2224/79251	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
			2224/79252	in the upper part of the bonding apparatus, e.g. in the pressing head

2224/79253	adapted for localised heating	2224/79501	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/7926	Polychromatic heating lamp	2224/79502	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79261	Laser	2224/7955	Mechanical means, e.g. for pressing, stamping
2224/79262	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/796	Means for supplying the connector to be connected in the bonding apparatus
2224/79263	in the upper part of the bonding apparatus, e.g. in the pressing head	2224/79601	Storing means
2224/79264	by induction heating, i.e. coils	2224/79611	Feeding means
2224/79265	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79621	Holding means
2224/79266	in the upper part of the bonding apparatus, e.g. in the pressing head	2224/7965	Means for transporting the components to be connected
2224/79267	Flame torch, e.g. hydrogen torch	2224/79651	Belt conveyor
2224/79268	Discharge electrode	2224/79652	Chain conveyor
2224/79269	Shape of the discharge electrode	2224/79653	Vibrating conveyor
2224/7927	Material of the discharge electrode	2224/79654	Pneumatic conveyor
2224/79271	Circuitry of the discharge electrode	2224/79655	in a fluid
2224/79272	Oven	2224/797	Means for aligning
2224/7928	Resistance welding electrodes, i.e. for ohmic heating	2224/79701	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/79281	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79702	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79282	in the upper part of the bonding apparatus, e.g. in the pressing head	2224/79703	Mechanical holding means
2224/79283	by infrared heating, e.g. infrared heating lamp	2224/79704	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/793	by means of pressure	2224/79705	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79301	Pressing head	2224/79723	Electrostatic holding means
2224/79302	Shape	2224/79724	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/79303	of the pressing surface	2224/79725	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79304	being curved	2224/79733	Magnetic holding means
2224/79305	comprising protrusions	2224/79734	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/7931	of other parts	2224/79735	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79312	Material	2224/79743	Suction holding means
2224/79313	Removable pressing head	2224/79744	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/79314	Auxiliary members on the pressing surface	2224/79745	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/79315	Elastomer inlay	2224/79753	Means for optical alignment, e.g. sensors
2224/79316	with retaining mechanisms	2224/79754	Guiding structures
2224/79317	Removable auxiliary member	2224/79755	in the lower part of the bonding apparatus, e.g. in the apparatus chuck
2224/79318	Shape of the auxiliary member	2224/79756	in the upper part of the bonding apparatus, e.g. in the pressing head
2224/7932	Material of the auxiliary member	2224/798	Means for moving parts
2224/79343	by ultrasonic vibrations	2224/79801	Lower part of the bonding apparatus, e.g. XY table
2224/79344	Eccentric cams	2224/79802	Rotational mechanism
2224/79345	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79803	Pivoting mechanism
2224/79346	in the upper part of the bonding apparatus, e.g. in the pressing head	2224/79804	Translational mechanism
2224/79347	Piezoelectric transducers	2224/79821	Upper part of the bonding apparatus, i.e. pressing head
2224/79348	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79822	Rotational mechanism
2224/79349	in the upper part of the bonding apparatus, e.g. in the pressing head	2224/79823	Pivoting mechanism
2224/7935	Stable and mobile yokes	2224/79824	Translational mechanism
2224/79351	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/79841	of the pressing head
2224/79352	in the upper part of the bonding apparatus, e.g. in the pressing head	2224/79842	Rotational mechanism
2224/79353	Ultrasonic horns	2224/79843	Pivoting mechanism
2224/79354	in the lower part of the bonding apparatus, e.g. in the apparatus chuck	2224/799	Means for monitoring the connection process
2224/79355	Design, e.g. of the wave guide			
2224/795	Cooling means			

2224/79901	using a computer, e.g. fully- or semi-automatic bonding	2224/80052	Detaching bonding areas, e.g. after testing (unsoldering in general B23K 1/018)
2224/7992	Load or pressure adjusting means, e.g. sensors	2224/80053	Bonding environment
2224/79925	Vibration adjusting means, e.g. sensors	2224/80054	Composition of the atmosphere
2224/7995	Means for forming additional members	2224/80055	being oxidating
2224/7998	specially adapted for batch processes	2224/80065	being reducing
2224/79981	Apparatus chuck	2224/80075	being inert
2224/79982	Shape	2224/80085	being a liquid, e.g. for fluidic self-assembly
2224/79983	of the mounting surface	2224/8009	Vacuum
2224/79984	of other portions	2224/80091	Under pressure
2224/79985	Material	2224/80092	Atmospheric pressure
2224/79986	Auxiliary members on the pressing surface	2224/80093	Transient conditions, e.g. gas-flow
2224/79987	Shape of the auxiliary member	2224/80095	Temperature settings
2224/79988	Material of the auxiliary member	2224/80096	Transient conditions
2224/7999	. .	for disconnecting	2224/80097	Heating
2224/80	. .	Methods for connecting semiconductor or other solid state bodies using means for bonding being attached to, or being formed on, the surface to be connected	2224/80098	Cooling
2224/80001	. .	by connecting a bonding area directly to another bonding area, i.e. connectorless bonding, e.g. bumpless bonding	2224/80099	Ambient temperature
2224/80003	. . .	involving a temporary auxiliary member not forming part of the bonding apparatus	2224/8011	involving protection against electrical discharge, e.g. removing electrostatic charge
2224/80004	being a removable or sacrificial coating	2224/8012	Aligning
2224/80006	being a temporary or sacrificial substrate	2224/80121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
2224/80007	. . .	involving a permanent auxiliary member being left in the finished device, e.g. aids for protecting the bonding area during or after the bonding process	2224/80122	by detecting inherent features of, or outside, the semiconductor or solid-state body
2224/80009	. . .	Pre-treatment of the bonding area	2224/80123	Shape or position of the body
2224/8001	Cleaning the bonding area, e.g. oxide removal step, desmearing	2224/80125	Bonding areas on the body
2224/80011	Chemical cleaning, e.g. etching, flux	2224/80127	Bonding areas outside the body
2224/80012	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow	2224/80129	Shape or position of the other item
2224/80013	Plasma cleaning	2224/8013	using marks formed on the semiconductor or solid-state body
2224/80014	Thermal cleaning, e.g. decomposition, sublimation	2224/80132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"
2224/80019	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8001 - H01L 2224/80014	2224/80136	involving guiding structures, e.g. spacers or supporting members
2224/8002	Applying permanent coating to the bonding area in the bonding apparatus, e.g. in-situ coating	2224/80138	the guiding structures being at least partially left in the finished device
2224/80024	Applying flux to the bonding area in the bonding apparatus	2224/80139	Guiding structures on the body
2224/8003	Reshaping the bonding area in the bonding apparatus, e.g. flattening the bonding area	2224/8014	Guiding structures outside the body
2224/80031	by chemical means, e.g. etching, anodisation	2224/80141	Guiding structures both on and outside the body
2224/80035	by heating means	2224/80143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
2224/80037	using a polychromatic heating lamp	2224/80148	involving movement of a part of the bonding apparatus
2224/80039	using a laser	2224/80149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
2224/80041	Induction heating, i.e. eddy currents	2224/8015	Rotational movements
2224/80047	by mechanical means, e.g. severing, pressing, stamping	2224/8016	Translational movements
2224/80048	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling	2224/80169	being the upper part of the bonding apparatus, i.e. bonding head
2224/80051	Forming additional members	2224/8017	Rotational movements
			2224/8018	Translational movements
			2224/8019	Arrangement of the bonding areas prior to mounting
			2224/80194	Lateral distribution of the bonding areas
			2224/802	Applying energy for connecting
			2224/80201	Compression bonding

2224/80203	Thermocompression bonding, e.g. diffusion bonding, pressure joining, thermocompression welding or solid-state welding	2224/80418	Zinc [Zn] as principal constituent
2224/80204	with a graded temperature profile	2224/8042	Antimony [Sb] as principal constituent
2224/80205	Ultrasonic bonding	2224/80423	Magnesium [Mg] as principal constituent
2224/80206	Direction of oscillation	2224/80424	Aluminium [Al] as principal constituent
2224/80207	Thermosonic bonding	2224/80438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/80209	applying unidirectional static pressure	2224/80439	Silver [Ag] as principal constituent
2224/80211	applying isostatic pressure, e.g. degassing using vacuum or a pressurised liquid	2224/80444	Gold [Au] as principal constituent
2224/80213	using a reflow oven	2224/80447	Copper [Cu] as principal constituent
2224/80215	with a graded temperature profile	2224/80449	Manganese [Mn] as principal constituent
2224/8022	with energy being in the form of electromagnetic radiation	2224/80455	Nickel [Ni] as principal constituent
2224/80222	Induction heating, i.e. eddy currents	2224/80457	Cobalt [Co] as principal constituent
2224/80224	using a laser	2224/8046	Iron [Fe] as principal constituent
2224/8023	Polychromatic or infrared lamp heating	2224/80463	the principal constituent melting at a temperature of greater than 1550°C
2224/80232	using an autocatalytic reaction, e.g. exothermic brazing	2224/80464	Palladium [Pd] as principal constituent
2224/80234	using means for applying energy being within the device, e.g. integrated heater	2224/80466	Titanium [Ti] as principal constituent
2224/80236	using electro-static corona discharge	2224/80469	Platinum [Pt] as principal constituent
2224/80237	using an electron beam (electron beam welding in general B23K 15/00)	2224/8047	Zirconium [Zr] as principal constituent
2224/80238	using electric resistance welding, i.e. ohmic heating	2224/80471	Chromium [Cr] as principal constituent
2224/8034	Bonding interfaces of the bonding area	2224/80472	Vanadium [V] as principal constituent
2224/80345	Shape, e.g. interlocking features	2224/80473	Rhodium [Rh] as principal constituent
2224/80355	having an external coating, e.g. protective bond-through coating	2224/80476	Ruthenium [Ru] as principal constituent
2224/80357	being flush with the surface	2224/80478	Iridium [Ir] as principal constituent
2224/80359	Material	2224/80479	Niobium [Nb] as principal constituent
2224/8036	Bonding interfaces of the semiconductor or solid state body	2224/8048	Molybdenum [Mo] as principal constituent
2224/80365	Shape, e.g. interlocking features	2224/80481	Tantalum [Ta] as principal constituent
2224/80375	having an external coating, e.g. protective bond-through coating	2224/80483	Rhenium [Re] as principal constituent
2224/80379	Material (material of the bonding area prior to the connecting process H01L 2224/05099 and H01L 2224/05599)	2224/80484	Tungsten [W] as principal constituent
2224/8038	Bonding interfaces outside the semiconductor or solid-state body	2224/80486	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/80385	Shape, e.g. interlocking features	2224/80487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/80488)
2224/80395	having an external coating, e.g. protective bond-through coating	2224/80488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/80399	Material	2224/8049	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/804	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/80491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/80401	the principal constituent melting at a temperature of less than 400°C	2224/80493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/804 - H01L 2224/80491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/80405	Gallium [Ga] as principal constituent	2224/80494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/804 - H01L 2224/80491
2224/80409	Indium [In] as principal constituent	2224/80495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/804 - H01L 2224/80491
2224/80411	Tin [Sn] as principal constituent			
2224/80413	Bismuth [Bi] as principal constituent			
2224/80414	Thallium [Tl] as principal constituent			
2224/80416	Lead [Pb] as principal constituent			
2224/80417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C			

2224/80498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/80572	Vanadium [V] as principal constituent
2224/80499	Material of the matrix	2224/80573	Rhodium [Rh] as principal constituent
2224/805	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/80576	Ruthenium [Ru] as principal constituent
2224/80501	the principal constituent melting at a temperature of less than 400°C	2224/80578	Iridium [Ir] as principal constituent
2224/80505	Gallium [Ga] as principal constituent	2224/80579	Niobium [Nb] as principal constituent
2224/80509	Indium [In] as principal constituent	2224/8058	Molybdenum [Mo] as principal constituent
2224/80511	Tin [Sn] as principal constituent	2224/80581	Tantalum [Ta] as principal constituent
2224/80513	Bismuth [Bi] as principal constituent	2224/80583	Rhenium [Re] as principal constituent
2224/80514	Thallium [Tl] as principal constituent	2224/80584	Tungsten [W] as principal constituent
2224/80516	Lead [Pb] as principal constituent	2224/80586	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/80517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/80587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/80588)
2224/80518	Zinc [Zn] as principal constituent	2224/80588	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/8052	Antimony [Sb] as principal constituent	2224/8059	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/80523	Magnesium [Mg] as principal constituent	2224/80591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/80524	Aluminium [Al] as principal constituent	2224/80593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/805 - H01L 2224/80591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/80538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/80594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/805 - H01L 2224/80591
2224/80539	Silver [Ag] as principal constituent	2224/80595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/805 - H01L 2224/80591
2224/80544	Gold [Au] as principal constituent	2224/80598	Fillers
2224/80547	Copper [Cu] as principal constituent	2224/80599	Base material
2224/80549	Manganese [Mn] as principal constituent	2224/806	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/80555	Nickel [Ni] as principal constituent	2224/80601	the principal constituent melting at a temperature of less than 400°C
2224/80557	Cobalt [Co] as principal constituent	2224/80605	Gallium [Ga] as principal constituent
2224/8056	Iron [Fe] as principal constituent	2224/80609	Indium [In] as principal constituent
2224/80563	the principal constituent melting at a temperature of greater than 1550°C	2224/80611	Tin [Sn] as principal constituent
2224/80564	Palladium [Pd] as principal constituent			
2224/80566	Titanium [Ti] as principal constituent			
2224/80569	Platinum [Pt] as principal constituent			
2224/8057	Zirconium [Zr] as principal constituent			
2224/80571	Chromium [Cr] as principal constituent			

2224/80613	Bismuth [Bi] as principal constituent	2224/80683	Rhenium [Re] as principal constituent
2224/80614	Thallium [Tl] as principal constituent	2224/80684	Tungsten [W] as principal constituent
2224/80616	Lead [Pb] as principal constituent	2224/80686	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/80617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/80687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/80688)
2224/80618	Zinc [Zn] as principal constituent	2224/80688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/8062	Antimony [Sb] as principal constituent	2224/8069	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/80623	Magnesium [Mg] as principal constituent	2224/80691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/80624	Aluminium [Al] as principal constituent	2224/80693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/806 - H01L 2224/80691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/80638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/80694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/806 - H01L 2224/80691
2224/80639	Silver [Ag] as principal constituent	2224/80695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/806 - H01L 2224/80691
2224/80644	Gold [Au] as principal constituent	2224/80698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/80647	Copper [Cu] as principal constituent	2224/80699	Coating material
2224/80649	Manganese [Mn] as principal constituent	2224/807	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/80655	Nickel [Ni] as principal constituent	2224/80701	the principal constituent melting at a temperature of less than 400°C
2224/80657	Cobalt [Co] as principal constituent	2224/80705	Gallium [Ga] as principal constituent
2224/8066	Iron [Fe] as principal constituent	2224/80709	Indium [In] as principal constituent
2224/80663	the principal constituent melting at a temperature of greater than 1550°C	2224/80711	Tin [Sn] as principal constituent
2224/80664	Palladium [Pd] as principal constituent	2224/80713	Bismuth [Bi] as principal constituent
2224/80666	Titanium [Ti] as principal constituent	2224/80714	Thallium [Tl] as principal constituent
2224/80669	Platinum [Pt] as principal constituent	2224/80716	Lead [Pb] as principal constituent
2224/8067	Zirconium [Zr] as principal constituent		
2224/80671	Chromium [Cr] as principal constituent		
2224/80672	Vanadium [V] as principal constituent		
2224/80673	Rhodium [Rh] as principal constituent		
2224/80676	Ruthenium [Ru] as principal constituent		
2224/80678	Iridium [Ir] as principal constituent		
2224/80679	Niobium [Nb] as principal constituent		
2224/8068	Molybdenum [Mo] as principal constituent		
2224/80681	Tantalum [Ta] as principal constituent		

2224/80717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/80787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/80788)
2224/80718	Zinc [Zn] as principal constituent	2224/80788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/8072	Antimony [Sb] as principal constituent	2224/8079	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/80723	Magnesium [Mg] as principal constituent	2224/80791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/80724	Aluminium [Al] as principal constituent	2224/80793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/807 - H01L 2224/80791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/80738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/80794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/807 - H01L 2224/80791
2224/80739	Silver [Ag] as principal constituent	2224/80795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/807 - H01L 2224/80791
2224/80744	Gold [Au] as principal constituent	2224/80798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/80747	Copper [Cu] as principal constituent	2224/80799	Shape or distribution of the fillers
2224/80749	Manganese [Mn] as principal constituent	2224/808	Bonding techniques
2224/80755	Nickel [Ni] as principal constituent	2224/80801	Soldering or alloying
2224/80757	Cobalt [Co] as principal constituent	2224/80805	involving forming a eutectic alloy at the bonding interface
2224/8076	Iron [Fe] as principal constituent	2224/8081	involving forming an intermetallic compound at the bonding interface
2224/80763	the principal constituent melting at a temperature of greater than 1550°C	2224/80815	Reflow soldering
2224/80764	Palladium [Pd] as principal constituent	2224/8082	Diffusion bonding
2224/80766	Titanium [Ti] as principal constituent	2224/80825	Solid-liquid interdiffusion
2224/80769	Platinum [Pt] as principal constituent	2224/8083	Solid-solid interdiffusion
2224/8077	Zirconium [Zr] as principal constituent	2224/8084	Sintering
2224/80771	Chromium [Cr] as principal constituent	2224/8085	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
2224/80772	Vanadium [V] as principal constituent	2224/80855	Hardening the adhesive by curing, i.e. thermosetting
2224/80773	Rhodium [Rh] as principal constituent	2224/80856	Pre-cured adhesive, i.e. B-stage adhesive
2224/80776	Ruthenium [Ru] as principal constituent	2224/80859	Localised curing of parts of the bonding area
2224/80778	Iridium [Ir] as principal constituent	2224/80862	Heat curing
2224/80779	Niobium [Nb] as principal constituent	2224/80865	Microwave curing
2224/8078	Molybdenum [Mo] as principal constituent	2224/80868	Infrared [IR] curing
2224/80781	Tantalum [Ta] as principal constituent	2224/80871	Visible light curing
2224/80783	Rhenium [Re] as principal constituent	2224/80874	Ultraviolet [UV] curing
2224/80784	Tungsten [W] as principal constituent	2224/80877	Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
2224/80786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/8088	Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives

- 2224/80885 Combinations of two or more hardening methods provided for in at least two different groups from [H01L 2224/80855](#) - [H01L 2224/8088](#), e.g. for hybrid thermoplastic-thermosetting adhesives
- 2224/8089 using an inorganic non metallic glass type adhesive, e.g. solder glass
- 2224/80893 Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
- 2224/80894 Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
- 2224/80895 between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
- 2224/80896 between electrically insulating surfaces, e.g. oxide or nitride layers
- 2224/80897 Mechanical interlocking, e.g. anchoring, hook and loop-type fastening or the like
- 2224/80898 Press-fitting, i.e. pushing the parts together and fastening by friction, e.g. by compression of one part against the other
- 2224/80899 using resilient parts in the bonding area
- 2224/809 with the bonding area not providing any mechanical bonding
- 2224/80901 Pressing a bonding area against another bonding area by means of a further bonding area or connector ([detachable pressure contact H01L 2224/72](#))
- 2224/80902 by means of a further bonding area
- 2224/80903 by means of a bump or layer connector
- 2224/80904 by means of an encapsulation layer or foil
- 2224/80905 Combinations of bonding methods provided for in at least two different groups from [H01L 2224/808](#) - [H01L 2224/80904](#)
- 2224/80906 Specific sequence of method steps
- 2224/80907 Intermediate bonding, i.e. intermediate bonding step for temporarily bonding the semiconductor or solid-state body, followed by at least a further bonding step
- 2224/80908 involving monitoring, e.g. feedback loop
- 2224/80909 Post-treatment of the bonding area
- 2224/8091 Cleaning, e.g. oxide removal step, desmearing
- 2224/80911 Chemical cleaning, e.g. etching, flux
- 2224/80912 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/80913 Plasma cleaning
- 2224/80914 Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge
- 2224/80919 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8091](#) - [H01L 2224/80914](#)
- 2224/8092 Applying permanent coating, e.g. protective coating
- 2224/8093 Reshaping
- 2224/80931 by chemical means, e.g. etching
- 2224/80935 by heating means, e.g. reflowing
- 2224/80937 using a polychromatic heating lamp
- 2224/80939 using a laser
- 2224/80941 Induction heating, i.e. eddy currents
- 2224/80943 using a flame torch, e.g. hydrogen torch
- 2224/80945 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/80947 by mechanical means, e.g. ?pull-and-cut?, pressing, stamping
- 2224/80948 Thermal treatments, e.g. annealing, controlled cooling
- 2224/80951 Forming additional members, e.g. for reinforcing
- 2224/80986 Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
- 2224/81 using a bump connector
- 2224/81001 involving a temporary auxiliary member not forming part of the bonding apparatus
- 2224/81002 being a removable or sacrificial coating
- 2224/81005 being a temporary or sacrificial substrate
- 2224/81007 involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the bump connector during or after the bonding process
- 2224/81009 Pre-treatment of the bump connector or the bonding area
- 2224/8101 Cleaning the bump connector, e.g. oxide removal step, desmearing
- 2224/81011 Chemical cleaning, e.g. etching, flux
- 2224/81012 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/81013 Plasma cleaning
- 2224/81014 Thermal cleaning, e.g. decomposition, sublimation
- 2224/81019 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8101](#) - [H01L 2224/81014](#)
- 2224/8102 Applying permanent coating to the bump connector in the bonding apparatus, e.g. in-situ coating
- 2224/81022 Cleaning the bonding area, e.g. oxide removal step, desmearing
- 2224/81024 Applying flux to the bonding area
- 2224/81026 Applying a precursor material to the bonding area
- 2224/8103 Reshaping the bump connector in the bonding apparatus, e.g. flattening the bump connector
- 2224/81031 by chemical means, e.g. etching, anodisation
- 2224/81035 by heating means
- 2224/81037 using a polychromatic heating lamp
- 2224/81039 using a laser
- 2224/81041 Induction heating, i.e. eddy currents
- 2224/81047 by mechanical means, e.g. severing, pressing, stamping
- 2224/81048 Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
- 2224/81051 Forming additional members
- 2224/81052 Detaching bump connectors, e.g. after testing ([unsoldering in general B23K 1/018](#))
- 2224/81053 Bonding environment
- 2224/81054 Composition of the atmosphere

2224/81055	being oxidating	2224/81192	wherein the bump connectors are disposed only on another item or body to be connected to the semiconductor or solid-state body
2224/81065	being reducing	2224/81193	wherein the bump connectors are disposed on both the semiconductor or solid-state body and another item or body to be connected to the semiconductor or solid-state body
2224/81075	being inert	2224/81194	Lateral distribution of the bump connectors
2224/81085	being a liquid, e.g. for fluidic self-assembly	2224/812	Applying energy for connecting
2224/8109	Vacuum	2224/81201	Compression bonding
2224/81091	Under pressure	2224/81203	Thermocompression bonding, e.g. diffusion bonding, pressure joining, thermocompression welding or solid-state welding
2224/81092	Atmospheric pressure	2224/81204	with a graded temperature profile
2224/81093	Transient conditions, e.g. gas-flow	2224/81205	Ultrasonic bonding
2224/81095	Temperature settings	2224/81206	Direction of oscillation
2224/81096	Transient conditions	2224/81207	Thermosonic bonding
2224/81097	Heating	2224/81208	applying unidirectional static pressure
2224/81098	Cooling	2224/81209	applying isostatic pressure, e.g. degassing using vacuum or a pressurised liquid
2224/81099	Ambient temperature	2224/8121	using a reflow oven
2224/811	the bump connector being supplied to the parts to be connected in the bonding apparatus	2224/81211	with a graded temperature profile
2224/81101	as prepeg comprising a bump connector, e.g. provided in an insulating plate member	2224/8122	with energy being in the form of electromagnetic radiation
2224/8111	involving protection against electrical discharge, e.g. removing electrostatic charge	2224/81222	Induction heating, i.e. eddy currents
2224/8112	Aligning	2224/81224	using a laser
2224/81121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors	2224/8123	Polychromatic or infrared lamp heating
2224/81122	by detecting inherent features of, or outside, the semiconductor or solid-state body	2224/81232	using an autocatalytic reaction, e.g. exothermic brazing
2224/81123	Shape or position of the body	2224/81234	using means for applying energy being within the device, e.g. integrated heater
2224/81125	Bonding areas on the body	2224/81236	using electro-static corona discharge
2224/81127	Bonding areas outside the body	2224/81237	using an electron beam (electron beam welding in general B23K 15/00)
2224/81129	Shape or position of the other item	2224/81238	using electric resistance welding, i.e. ohmic heating
2224/8113	using marks formed on the semiconductor or solid-state body	2224/8134	Bonding interfaces of the bump connector
2224/81132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"	2224/81345	Shape, e.g. interlocking features
2224/81136	involving guiding structures, e.g. spacers or supporting members	2224/81355	having an external coating, e.g. protective bond-through coating
2224/81138	the guiding structures being at least partially left in the finished device	2224/81359	Material
2224/81139	Guiding structures on the body	2224/8136	Bonding interfaces of the semiconductor or solid state body
2224/8114	Guiding structures outside the body	2224/81365	Shape, e.g. interlocking features
2224/81141	Guiding structures both on and outside the body	2224/81375	having an external coating, e.g. protective bond-through coating
2224/81143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium	2224/81379	Material (material of the bump connector prior to the connecting process H01L 2224/13099 and H01L 2224/13599, and subgroups)
2224/81148	involving movement of a part of the bonding apparatus	2224/8138	Bonding interfaces outside the semiconductor or solid-state body
2224/81149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table	2224/81385	Shape, e.g. interlocking features
2224/8115	Rotational movements	2224/81395	having an external coating, e.g. protective bond-through coating
2224/8116	Translational movements	2224/81399	Material
2224/81169	being the upper part of the bonding apparatus, i.e. bonding head	2224/814	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/8117	Rotational movements			
2224/8118	Translational movements			
2224/8119	Arrangement of the bump connectors prior to mounting			
2224/81191	wherein the bump connectors are disposed only on the semiconductor or solid-state body			

2224/81401	the principal constituent melting at a temperature of less than 400°C	2224/81491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/81405	Gallium [Ga] as principal constituent	2224/81493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/814 - H01L 2224/81491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/81409	Indium [In] as principal constituent	2224/81494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/814 - H01L 2224/81491
2224/81411	Tin [Sn] as principal constituent	2224/81495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/814 - H01L 2224/81491
2224/81413	Bismuth [Bi] as principal constituent	2224/81498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/81414	Thallium [Tl] as principal constituent	2224/81499	Material of the matrix
2224/81416	Lead [Pb] as principal constituent	2224/815	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/81417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/81501	the principal constituent melting at a temperature of less than 400°C
2224/81418	Zinc [Zn] as principal constituent	2224/81505	Gallium [Ga] as principal constituent
2224/8142	Antimony [Sb] as principal constituent	2224/81509	Indium [In] as principal constituent
2224/81423	Magnesium [Mg] as principal constituent	2224/81511	Tin [Sn] as principal constituent
2224/81424	Aluminium [Al] as principal constituent	2224/81513	Bismuth [Bi] as principal constituent
2224/81438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/81514	Thallium [Tl] as principal constituent
2224/81439	Silver [Ag] as principal constituent	2224/81516	Lead [Pb] as principal constituent
2224/81444	Gold [Au] as principal constituent	2224/81517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/81447	Copper [Cu] as principal constituent	2224/81518	Zinc [Zn] as principal constituent
2224/81449	Manganese [Mn] as principal constituent	2224/8152	Antimony [Sb] as principal constituent
2224/81455	Nickel [Ni] as principal constituent	2224/81523	Magnesium [Mg] as principal constituent
2224/81457	Cobalt [Co] as principal constituent	2224/81524	Aluminium [Al] as principal constituent
2224/8146	Iron [Fe] as principal constituent	2224/81538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/81463	the principal constituent melting at a temperature of greater than 1550°C	2224/81539	Silver [Ag] as principal constituent
2224/81464	Palladium [Pd] as principal constituent	2224/81544	Gold [Au] as principal constituent
2224/81466	Titanium [Ti] as principal constituent	2224/81547	Copper [Cu] as principal constituent
2224/81469	Platinum [Pt] as principal constituent	2224/81549	Manganese [Mn] as principal constituent
2224/8147	Zirconium [Zr] as principal constituent	2224/81555	Nickel [Ni] as principal constituent
2224/81471	Chromium [Cr] as principal constituent	2224/81557	Cobalt [Co] as principal constituent
2224/81472	Vanadium [V] as principal constituent			
2224/81473	Rhodium [Rh] as principal constituent			
2224/81476	Ruthenium [Ru] as principal constituent			
2224/81478	Iridium [Ir] as principal constituent			
2224/81479	Niobium [Nb] as principal constituent			
2224/8148	Molybdenum [Mo] as principal constituent			
2224/81481	Tantalum [Ta] as principal constituent			
2224/81483	Rhenium [Re] as principal constituent			
2224/81484	Tungsten [W] as principal constituent			
2224/81486	with a principal constituent of the material being a non metallic, non metalloid inorganic material			
2224/81487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/81488)			
2224/81488	Glasses, e.g. amorphous oxides, nitrides or fluorides			
2224/8149	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy			

2224/8156	Iron [Fe] as principal constituent	2224/816	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/81563	the principal constituent melting at a temperature of greater than 1550°C	2224/81601	the principal constituent melting at a temperature of less than 400°C
2224/81564	Palladium [Pd] as principal constituent	2224/81605	Gallium [Ga] as principal constituent
2224/81566	Titanium [Ti] as principal constituent	2224/81609	Indium [In] as principal constituent
2224/81569	Platinum [Pt] as principal constituent	2224/81611	Tin [Sn] as principal constituent
2224/8157	Zirconium [Zr] as principal constituent	2224/81613	Bismuth [Bi] as principal constituent
2224/81571	Chromium [Cr] as principal constituent	2224/81614	Thallium [Tl] as principal constituent
2224/81572	Vanadium [V] as principal constituent	2224/81616	Lead [Pb] as principal constituent
2224/81573	Rhodium [Rh] as principal constituent	2224/81617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/81576	Ruthenium [Ru] as principal constituent	2224/81618	Zinc [Zn] as principal constituent
2224/81578	Iridium [Ir] as principal constituent	2224/8162	Antimony [Sb] as principal constituent
2224/81579	Niobium [Nb] as principal constituent	2224/81623	Magnesium [Mg] as principal constituent
2224/8158	Molybdenum [Mo] as principal constituent	2224/81624	Aluminium [Al] as principal constituent
2224/81581	Tantalum [Ta] as principal constituent	2224/81638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/81583	Rhenium [Re] as principal constituent	2224/81639	Silver [Ag] as principal constituent
2224/81584	Tungsten [W] as principal constituent	2224/81644	Gold [Au] as principal constituent
2224/81586	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/81647	Copper [Cu] as principal constituent
2224/81587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/81588)	2224/81649	Manganese [Mn] as principal constituent
2224/81588	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/81655	Nickel [Ni] as principal constituent
2224/8159	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/81657	Cobalt [Co] as principal constituent
2224/81591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/8166	Iron [Fe] as principal constituent
2224/81593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/815 - H01L 2224/81591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/81663	the principal constituent melting at a temperature of greater than 1550°C
2224/81594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/815 - H01L 2224/81591	2224/81664	Palladium [Pd] as principal constituent
2224/81595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/815 - H01L 2224/81591	2224/81666	Titanium [Ti] as principal constituent
2224/81598	Fillers	2224/81669	Platinum [Pt] as principal constituent
2224/81599	Base material	2224/8167	Zirconium [Zr] as principal constituent
		2224/81671	Chromium [Cr] as principal constituent

2224/81672	Vanadium [V] as principal constituent	2224/81705	Gallium [Ga] as principal constituent
2224/81673	Rhodium [Rh] as principal constituent	2224/81709	Indium [In] as principal constituent
2224/81676	Ruthenium [Ru] as principal constituent	2224/81711	Tin [Sn] as principal constituent
2224/81678	Iridium [Ir] as principal constituent	2224/81713	Bismuth [Bi] as principal constituent
2224/81679	Niobium [Nb] as principal constituent	2224/81714	Thallium [Tl] as principal constituent
2224/8168	Molybdenum [Mo] as principal constituent	2224/81716	Lead [Pb] as principal constituent
2224/81681	Tantalum [Ta] as principal constituent	2224/81717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/81683	Rhenium [Re] as principal constituent	2224/81718	Zinc [Zn] as principal constituent
2224/81684	Tungsten [W] as principal constituent	2224/8172	Antimony [Sb] as principal constituent
2224/81686	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/81723	Magnesium [Mg] as principal constituent
2224/81687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/81688)	2224/81724	Aluminium [Al] as principal constituent
2224/81688	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/81738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/8169	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/81739	Silver [Ag] as principal constituent
2224/81691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/81744	Gold [Au] as principal constituent
2224/81693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/816 - H01L 2224/81691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/81747	Copper [Cu] as principal constituent
2224/81694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/816 - H01L 2224/81691	2224/81749	Manganese [Mn] as principal constituent
2224/81695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/816 - H01L 2224/81691	2224/81755	Nickel [Ni] as principal constituent
2224/81698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/81757	Cobalt [Co] as principal constituent
2224/81699	Coating material	2224/8176	Iron [Fe] as principal constituent
2224/817	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/81763	the principal constituent melting at a temperature of greater than 1550°C
2224/81701	the principal constituent melting at a temperature of less than 400°C	2224/81764	Palladium [Pd] as principal constituent
		2224/81766	Titanium [Ti] as principal constituent
		2224/81769	Platinum [Pt] as principal constituent
		2224/8177	Zirconium [Zr] as principal constituent
		2224/81771	Chromium [Cr] as principal constituent
		2224/81772	Vanadium [V] as principal constituent
		2224/81773	Rhodium [Rh] as principal constituent
		2224/81776	Ruthenium [Ru] as principal constituent
		2224/81778	Iridium [Ir] as principal constituent

2224/81779	Niobium [Nb] as principal constituent	2224/81856	Pre-cured adhesive, i.e. B-stage adhesive
2224/8178	Molybdenum [Mo] as principal constituent	2224/81859	Localised curing of parts of the bump connector
2224/81781	Tantalum [Ta] as principal constituent	2224/81862	Heat curing
2224/81783	Rhenium [Re] as principal constituent	2224/81865	Microwave curing
2224/81784	Tungsten [W] as principal constituent	2224/81868	Infrared [IR] curing
2224/81786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/81871	Visible light curing
2224/81787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/81788)	2224/81874	Ultraviolet [UV] curing
2224/81788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/81877	Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
2224/8179	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/8188	Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
2224/81791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/81885	Combinations of two or more hardening methods provided for in at least two different groups from H01L 2224/81855 - H01L 2224/8188 , e.g. for hybrid thermoplastic-thermosetting adhesives
2224/81793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/817 - H01L 2224/81791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/8189	using an inorganic non metallic glass type adhesive, e.g. solder glass
2224/81794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/817 - H01L 2224/81791	2224/81893	Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
2224/81795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/817 - H01L 2224/81791	2224/81894	Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
2224/81798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/81895	between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
2224/81799	Shape or distribution of the fillers	2224/81896	between electrically insulating surfaces, e.g. oxide or nitride layers
2224/818	Bonding techniques	2224/81897	Mechanical interlocking, e.g. anchoring, hook and loop-type fastening or the like
2224/81801	Soldering or alloying	2224/81898	Press-fitting, i.e. pushing the parts together and fastening by friction, e.g. by compression of one part against the other
2224/81805	involving forming a eutectic alloy at the bonding interface	2224/81899	using resilient parts in the bump connector or in the bonding area
2224/8181	involving forming an intermetallic compound at the bonding interface	2224/819	with the bump connector not providing any mechanical bonding
2224/81815	Reflow soldering	2224/81901	Pressing the bump connector against the bonding areas by means of another connector (detachable pressure contact H01L 2224/72)
2224/8182	Diffusion bonding	2224/81902	by means of another bump connector
2224/81825	Solid-liquid interdiffusion	2224/81903	by means of a layer connector
2224/8183	Solid-solid interdiffusion	2224/81904	by means of an encapsulation layer or foil
2224/8184	Sintering	2224/81905	Combinations of bonding methods provided for in at least two different groups from H01L 2224/818 - H01L 2224/81904
2224/8185	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester	2224/81906	Specific sequence of method steps
2224/81855	Hardening the adhesive by curing, i.e. thermosetting	2224/81907	Intermediate bonding, i.e. intermediate bonding step for temporarily bonding the semiconductor or solid-state body, followed by at least a further bonding step
			2224/81908	involving monitoring, e.g. feedback loop
			2224/81909	Post-treatment of the bump connector or bonding area
			2224/8191	Cleaning, e.g. oxide removal step, desmearing
			2224/81911	Chemical cleaning, e.g. etching, flux

2224/81912	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow	2224/82098	Cooling
2224/81913	Plasma cleaning	2224/82099	Ambient temperature
2224/81914	Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge	2224/821	. . .	Forming a build-up interconnect
2224/81919	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8191 - H01L 2224/81914	2224/82101	by additive methods, e.g. direct writing
2224/8192	Applying permanent coating, e.g. protective coating	2224/82102	using jetting, e.g. ink jet
2224/8193	Reshaping	2224/82103	using laser direct writing
2224/81931	by chemical means, e.g. etching	2224/82104	using screen printing
2224/81935	by heating means, e.g. reflowing	2224/82105	by using a preform
2224/81937	using a polychromatic heating lamp	2224/82106	by subtractive methods
2224/81939	using a laser	2224/82108	by self-assembly processes
2224/81941	Induction heating, i.e. eddy currents	2224/8211	. . .	involving protection against electrical discharge, e.g. removing electrostatic charge
2224/81943	using a flame torch, e.g. hydrogen torch	2224/8212	. . .	Aligning
2224/81945	using a corona discharge, e.g. electronic flame off [EFO]	2224/82121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
2224/81947	by mechanical means, e.g. "pull-and-cut", pressing, stamping	2224/82122	by detecting inherent features of, or outside, the semiconductor or solid-state body
2224/81948	Thermal treatments, e.g. annealing, controlled cooling	2224/8213	using marks formed on the semiconductor or solid-state body
2224/81951	Forming additional members, e.g. for reinforcing	2224/82132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"
2224/81986	. . .	Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence	2224/82136	involving guiding structures, e.g. spacers or supporting members
2224/82	. .	by forming build-up interconnects at chip-level, e.g. for high density interconnects [HDI]	2224/82138	the guiding structures being at least partially left in the finished device
2224/82001	. . .	involving a temporary auxiliary member not forming part of the bonding apparatus	2224/82143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
2224/82002	being a removable or sacrificial coating	2224/82148	involving movement of a part of the bonding apparatus
2224/82005	being a temporary or sacrificial substrate	2224/82149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
2224/82007	. . .	involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting a build-up interconnect during or after the bonding process	2224/8215	Rotational movements
2224/82009	. . .	Pre-treatment of the connector or the bonding area	2224/8216	Translational movements
2224/8201	Cleaning, e.g. oxide removal step, desmearing	2224/82169	being the upper part of the bonding apparatus, e.g. nozzle
2224/8203	Reshaping, e.g. forming vias	2224/8217	Rotational movement
2224/82031	by chemical means, e.g. etching, anodisation	2224/8218	Translational movements
2224/82035	by heating means	2224/82181	connecting first on the semiconductor or solid-state body, i.e. on-chip,
2224/82039	using a laser	2224/82186	connecting first outside the semiconductor or solid-state body, i.e. off-chip
2224/82045	using a corona discharge, e.g. electronic flame off [EFO]	2224/82191	connecting first both on and outside the semiconductor or solid-state body
2224/82047	by mechanical means, e.g. severing, pressing, stamping	2224/822	. . .	Applying energy for connecting
2224/82048	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling	2224/82201	Compression bonding
2224/82051	Forming additional members	2224/82203	Thermocompression bonding
2224/82053	. . .	Bonding environment	2224/82205	Ultrasonic bonding
2224/82054	Composition of the atmosphere	2224/82207	Thermosonic bonding
2224/82085	being a liquid, e.g. for fluidic self-assembly	2224/8221	with energy being in the form of electromagnetic radiation
2224/8209	Vacuum	2224/82212	Induction heating, i.e. eddy currents
2224/82091	Under pressure	2224/82214	using a laser
2224/82095	Temperature settings	2224/8223	Polychromatic or infrared lamp heating
2224/82096	Transient conditions	2224/82232	using an autocatalytic reaction, e.g. exothermic brazing
2224/82097	Heating	2224/82234	using means for applying energy being within the device, e.g. integrated heater
			2224/82236	using electro-static corona discharge

- 2224/82237 using electron beam, ([electron beam in general B23K 15/00](#))
- 2224/82238 using electric resistance welding, i.e. ohmic heating
- 2224/8234 Bonding interfaces of the connector
- 2224/82345 Shape, e.g. interlocking features
- 2224/82355 having an external coating, e.g. protective bond-through coating
- 2224/82359 Material
- 2224/8236 Bonding interfaces of the semiconductor or solid state body
- 2224/82365 Shape, e.g. interlocking features
- 2224/82375 having an external coating, e.g. protective bond-through coating
- 2224/82379 Material
- 2224/8238 Bonding interfaces outside the semiconductor or solid-state body
- 2224/82385 Shape, e.g. interlocking features
- 2224/82395 having an external coating, e.g. protective bond-through coating
- 2224/82399 Material
- 2224/828 Bonding techniques
- 2224/82801 Soldering or alloying
- 2224/82805 involving forming a eutectic alloy at the bonding interface
- 2224/8281 involving forming an intermetallic compound at the bonding interface
- 2224/82815 Reflow soldering
- 2224/8282 Diffusion bonding
- 2224/82825 Solid-liquid interdiffusion
- 2224/8283 Solid-solid interdiffusion
- 2224/8284 Sintering
- 2224/8285 using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
- 2224/82855 Hardening the adhesive by curing, i.e. thermosetting
- 2224/82856 Pre-cured adhesive, i.e. B-stage adhesive
- 2224/82859 Localised curing of parts of the connector
- 2224/82862 Heat curing
- 2224/82865 Microwave curing
- 2224/82868 Infrared [IR] curing
- 2224/82871 Visible light curing
- 2224/82874 Ultraviolet [UV] curing
- 2224/82877 Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
- 2224/8288 Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
- 2224/82885 Combinations of two or more hardening methods provided for in at least two different groups from [H01L 2224/82855](#) - [H01L 2224/8288](#), e.g. for hybrid thermoplastic-thermosetting adhesives
- 2224/8289 using an inorganic non metallic glass type adhesive, e.g. solder glass
- 2224/82893 Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
- 2224/82895 Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
- 2224/82896 between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
- 2224/82897 between electrically insulating surfaces, e.g. oxide or nitride layers
- 2224/82899 Combinations of bonding methods provided for in at least two different groups from [H01L 2224/828](#) - [H01L 2224/82897](#)
- 2224/829 involving monitoring, e.g. feedback loop
- 2224/82909 Post-treatment of the connector or the bonding area
- 2224/8291 Cleaning, e.g. oxide removal step, desmearing
- 2224/8293 Reshaping
- 2224/82931 by chemical means, e.g. etching, anodisation
- 2224/82935 by heating means
- 2224/82939 using a laser
- 2224/82945 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/82947 by mechanical means, e.g. severing, pressing, stamping
- 2224/82948 Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
- 2224/82951 Forming additional members
- 2224/82986 Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
- 2224/83 using a layer connector
- 2224/83001 involving a temporary auxiliary member not forming part of the bonding apparatus
- 2224/83002 being a removable or sacrificial coating
- 2224/83005 being a temporary or sacrificial substrate
- 2224/83007 involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the layer connector during or after the bonding process
- 2224/83009 Pre-treatment of the layer connector or the bonding area
- 2224/8301 Cleaning the layer connector, e.g. oxide removal step, desmearing
- 2224/83011 Chemical cleaning, e.g. etching, flux
- 2224/83012 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/83013 Plasma cleaning
- 2224/83014 Thermal cleaning, e.g. decomposition, sublimation
- 2224/83019 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8301](#) - [H01L 2224/83014](#)
- 2224/8302 Applying permanent coating to the layer connector in the bonding apparatus, e.g. in-situ coating
- 2224/83022 Cleaning the bonding area, e.g. oxide removal step, desmearing
- 2224/83024 Applying flux to the bonding area
- 2224/83026 Applying a precursor material to the bonding area

2224/8303	Reshaping the layer connector in the bonding apparatus, e.g. flattening the layer connector	2224/83143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
2224/83031	by chemical means, e.g. etching, anodisation	2224/83148	involving movement of a part of the bonding apparatus
2224/83035	by heating means	2224/83149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table
2224/83037	using a polychromatic heating lamp	2224/8315	Rotational movements
2224/83039	using a laser	2224/8316	Translational movements
2224/83041	Induction heating, i.e. eddy currents	2224/83169	being the upper part of the bonding apparatus, i.e. bonding head
2224/83047	by mechanical means, e.g. severing, pressing, stamping	2224/8317	Rotational movements
2224/83048	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling	2224/8318	Translational movements
2224/83051	Forming additional members, e.g. dam structures	2224/8319	Arrangement of the layer connectors prior to mounting
2224/83052	Detaching layer connectors, e.g. after testing (unsoldering in general B23K 1/018)	2224/83191	wherein the layer connectors are disposed only on the semiconductor or solid-state body
2224/83053	Bonding environment	2224/83192	wherein the layer connectors are disposed only on another item or body to be connected to the semiconductor or solid-state body
2224/83054	Composition of the atmosphere	2224/83193	wherein the layer connectors are disposed on both the semiconductor or solid-state body and another item or body to be connected to the semiconductor or solid-state body
2224/83055	being oxidating	2224/83194	Lateral distribution of the layer connectors
2224/83065	being reducing	2224/832	Applying energy for connecting
2224/83075	being inert	2224/83201	Compression bonding
2224/83085	being a liquid, e.g. for fluidic self-assembly	2224/83203	Thermocompression bonding, e.g. diffusion bonding, pressure joining, thermocompression welding or solid-state welding
2224/8309	Vacuum	2224/83204	with a graded temperature profile
2224/83091	Under pressure	2224/83205	Ultrasonic bonding
2224/83092	Atmospheric pressure	2224/83206	Direction of oscillation
2224/83093	Transient conditions, e.g. gas-flow	2224/83207	Thermosonic bonding
2224/83095	Temperature settings	2224/83208	applying unidirectional static pressure
2224/83096	Transient conditions	2224/83209	applying isostatic pressure, e.g. degassing using vacuum or a pressurised liquid
2224/83097	Heating	2224/8321	using a reflow oven
2224/83098	Cooling	2224/83211	with a graded temperature profile
2224/83099	Ambient temperature	2224/8322	with energy being in the form of electromagnetic radiation
2224/831	the layer connector being supplied to the parts to be connected in the bonding apparatus	2224/83222	Induction heating, i.e. eddy currents
2224/83101	as prepeg comprising a layer connector, e.g. provided in an insulating plate member	2224/83224	using a laser
2224/83102	using surface energy, e.g. capillary forces	2224/8323	Polychromatic or infrared lamp heating
2224/83104	by applying pressure, e.g. by injection	2224/83232	using an autocatalytic reaction, e.g. exothermic brazing
2224/8311	involving protection against electrical discharge, e.g. removing electrostatic charge	2224/83234	using means for applying energy being within the device, e.g. integrated heater
2224/8312	Aligning	2224/83236	using electro-static corona discharge
2224/83121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors	2224/83237	using an electron beam (electron beam welding in general B23K 15/00)
2224/83122	by detecting inherent features of, or outside, the semiconductor or solid-state body	2224/83238	using electric resistance welding, i.e. ohmic heating
2224/83123	Shape or position of the body	2224/8334	Bonding interfaces of the layer connector
2224/83125	Bonding areas on the body	2224/83345	Shape, e.g. interlocking features
2224/83127	Bonding areas outside the body	2224/83355	having an external coating, e.g. protective bond-through coating
2224/83129	Shape or position of the other item	2224/83359	Material
2224/8313	using marks formed on the semiconductor or solid-state body	2224/8336	Bonding interfaces of the semiconductor or solid state body
2224/83132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"			
2224/83136	involving guiding structures, e.g. spacers or supporting members			
2224/83138	the guiding structures being at least partially left in the finished device			
2224/83139	Guiding structures on the body			
2224/8314	Guiding structures outside the body			
2224/83141	Guiding structures both on and outside the body			

2224/83365	Shape, e.g. interlocking features	2224/8348	Molybdenum [Mo] as principal constituent
2224/83375	having an external coating, e.g. protective bond-through coating	2224/83481	Tantalum [Ta] as principal constituent
2224/83379	Material (material of the layer connector prior to the connecting process H01L 2224/29099 and H01L 2224/29599 , and subgroups)	2224/83483	Rhenium [Re] as principal constituent
2224/8338	. . .	Bonding interfaces outside the semiconductor or solid-state body	2224/83484	Tungsten [W] as principal constituent
2224/83385	Shape, e.g. interlocking features	2224/83486	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/83395	having an external coating, e.g. protective bond-through coating	2224/83487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/83488)
2224/83399	Material	2224/83488	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/834	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/8349	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/83401	the principal constituent melting at a temperature of less than 400°C	2224/83491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/83405	Gallium [Ga] as principal constituent	2224/83493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/834 - H01L 2224/83491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/83409	Indium [In] as principal constituent	2224/83494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/834 - H01L 2224/83491
2224/83411	Tin [Sn] as principal constituent	2224/83495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/834 - H01L 2224/83491
2224/83413	Bismuth [Bi] as principal constituent	2224/83498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/83414	Thallium [Tl] as principal constituent	2224/83499	Material of the matrix
2224/83416	Lead [Pb] as principal constituent	2224/835	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/83417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/83501	the principal constituent melting at a temperature of less than 400°C
2224/83418	Zinc [Zn] as principal constituent	2224/83505	Gallium [Ga] as principal constituent
2224/8342	Antimony [Sb] as principal constituent	2224/83509	Indium [In] as principal constituent
2224/83423	Magnesium [Mg] as principal constituent	2224/83511	Tin [Sn] as principal constituent
2224/83424	Aluminium [Al] as principal constituent	2224/83513	Bismuth [Bi] as principal constituent
2224/83438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/83514	Thallium [Tl] as principal constituent
2224/83439	Silver [Ag] as principal constituent	2224/83516	Lead [Pb] as principal constituent
2224/83444	Gold [Au] as principal constituent	2224/83517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/83447	Copper [Cu] as principal constituent	2224/83518	Zinc [Zn] as principal constituent
2224/83449	Manganese [Mn] as principal constituent	2224/8352	Antimony [Sb] as principal constituent
2224/83455	Nickel [Ni] as principal constituent	2224/83523	Magnesium [Mg] as principal constituent
2224/83457	Cobalt [Co] as principal constituent	2224/83524	Aluminium [Al] as principal constituent
2224/8346	Iron [Fe] as principal constituent			
2224/83463	the principal constituent melting at a temperature of greater than 1550°C			
2224/83464	Palladium [Pd] as principal constituent			
2224/83466	Titanium [Ti] as principal constituent			
2224/83469	Platinum [Pt] as principal constituent			
2224/8347	Zirconium [Zr] as principal constituent			
2224/83471	Chromium [Cr] as principal constituent			
2224/83472	Vanadium [V] as principal constituent			
2224/83473	Rhodium [Rh] as principal constituent			
2224/83476	Ruthenium [Ru] as principal constituent			
2224/83478	Iridium [Ir] as principal constituent			
2224/83479	Niobium [Nb] as principal constituent			

2224/83538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/83593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/835 - H01L 2224/83591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/83539	Silver [Ag] as principal constituent	2224/83594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/835 - H01L 2224/83591
2224/83544	Gold [Au] as principal constituent	2224/83595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/835 - H01L 2224/83591
2224/83547	Copper [Cu] as principal constituent	2224/83598	Fillers
2224/83549	Manganese [Mn] as principal constituent	2224/83599	Base material
2224/83555	Nickel [Ni] as principal constituent	2224/836	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/83557	Cobalt [Co] as principal constituent	2224/83601	the principal constituent melting at a temperature of less than 400°C
2224/8356	Iron [Fe] as principal constituent	2224/83605	Gallium [Ga] as principal constituent
2224/83563	the principal constituent melting at a temperature of greater than 1550°C	2224/83609	Indium [In] as principal constituent
2224/83564	Palladium [Pd] as principal constituent	2224/83611	Tin [Sn] as principal constituent
2224/83566	Titanium [Ti] as principal constituent	2224/83613	Bismuth [Bi] as principal constituent
2224/83569	Platinum [Pt] as principal constituent	2224/83614	Thallium [Tl] as principal constituent
2224/8357	Zirconium [Zr] as principal constituent	2224/83616	Lead [Pb] as principal constituent
2224/83571	Chromium [Cr] as principal constituent	2224/83617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/83572	Vanadium [V] as principal constituent	2224/83618	Zinc [Zn] as principal constituent
2224/83573	Rhodium [Rh] as principal constituent	2224/8362	Antimony [Sb] as principal constituent
2224/83576	Ruthenium [Ru] as principal constituent	2224/83623	Magnesium [Mg] as principal constituent
2224/83578	Iridium [Ir] as principal constituent	2224/83624	Aluminium [Al] as principal constituent
2224/83579	Niobium [Nb] as principal constituent	2224/83638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/8358	Molybdenum [Mo] as principal constituent	2224/83639	Silver [Ag] as principal constituent
2224/83581	Tantalum [Ta] as principal constituent	2224/83644	Gold [Au] as principal constituent
2224/83583	Rhenium [Re] as principal constituent	2224/83647	Copper [Cu] as principal constituent
2224/83584	Tungsten [W] as principal constituent	2224/83649	Manganese [Mn] as principal constituent
2224/83586	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/83655	Nickel [Ni] as principal constituent
2224/83587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/83588)	2224/83657	Cobalt [Co] as principal constituent
2224/83588	Glasses, e.g. amorphous oxides, nitrides or fluorides		
2224/8359	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy		
2224/83591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene		

2224/8366	Iron [Fe] as principal constituent	2224/83698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/83663	the principal constituent melting at a temperature of greater than 1550°C	2224/83699	Coating material
2224/83664	Palladium [Pd] as principal constituent	2224/837	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/83666	Titanium [Ti] as principal constituent	2224/83701	the principal constituent melting at a temperature of less than 400°C
2224/83669	Platinum [Pt] as principal constituent	2224/83705	Gallium [Ga] as principal constituent
2224/8367	Zirconium [Zr] as principal constituent	2224/83709	Indium [In] as principal constituent
2224/83671	Chromium [Cr] as principal constituent	2224/83711	Tin [Sn] as principal constituent
2224/83672	Vanadium [V] as principal constituent	2224/83713	Bismuth [Bi] as principal constituent
2224/83673	Rhodium [Rh] as principal constituent	2224/83714	Thallium [Tl] as principal constituent
2224/83676	Ruthenium [Ru] as principal constituent	2224/83716	Lead [Pb] as principal constituent
2224/83678	Iridium [Ir] as principal constituent	2224/83717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/83679	Niobium [Nb] as principal constituent	2224/83718	Zinc [Zn] as principal constituent
2224/8368	Molybdenum [Mo] as principal constituent	2224/8372	Antimony [Sb] as principal constituent
2224/83681	Tantalum [Ta] as principal constituent	2224/83723	Magnesium [Mg] as principal constituent
2224/83683	Rhenium [Re] as principal constituent	2224/83724	Aluminium [Al] as principal constituent
2224/83684	Tungsten [W] as principal constituent	2224/83738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/83686	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/83739	Silver [Ag] as principal constituent
2224/83687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/83688)	2224/83744	Gold [Au] as principal constituent
2224/83688	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/83747	Copper [Cu] as principal constituent
2224/8369	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/83749	Manganese [Mn] as principal constituent
2224/83691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/83755	Nickel [Ni] as principal constituent
2224/83693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/836 - H01L 2224/83691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/83757	Cobalt [Co] as principal constituent
2224/83694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/836 - H01L 2224/83691	2224/8376	Iron [Fe] as principal constituent
2224/83695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/836 - H01L 2224/83691	2224/83763	the principal constituent melting at a temperature of greater than 1550°C
		2224/83764	Palladium [Pd] as principal constituent
		2224/83766	Titanium [Ti] as principal constituent

2224/83769	Platinum [Pt] as principal constituent	2224/8381	involving forming an intermetallic compound at the bonding interface
2224/8377	Zirconium [Zr] as principal constituent	2224/83815	Reflow soldering
2224/83771	Chromium [Cr] as principal constituent	2224/8382	Diffusion bonding
2224/83772	Vanadium [V] as principal constituent	2224/83825	Solid-liquid interdiffusion
2224/83773	Rhodium [Rh] as principal constituent	2224/8383	Solid-solid interdiffusion
2224/83776	Ruthenium [Ru] as principal constituent	2224/8384	Sintering
2224/83778	Iridium [Ir] as principal constituent	2224/8385	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
2224/83779	Niobium [Nb] as principal constituent	2224/83851	being an anisotropic conductive adhesive
2224/8378	Molybdenum [Mo] as principal constituent	2224/83855	Hardening the adhesive by curing, i.e. thermosetting
2224/83781	Tantalum [Ta] as principal constituent	2224/83856	Pre-cured adhesive, i.e. B-stage adhesive
2224/83783	Rhenium [Re] as principal constituent	2224/83859	Localised curing of parts of the layer connector
2224/83784	Tungsten [W] as principal constituent	2224/83862	Heat curing
2224/83786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/83865	Microwave curing
2224/83787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/83788)	2224/83868	Infrared [IR] curing
2224/83788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/83871	Visible light curing
2224/8379	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/83874	Ultraviolet [UV] curing
2224/83791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/83877	Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
2224/83793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/837 - H01L 2224/83791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/8388	Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
2224/83794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/837 - H01L 2224/83791	2224/83885	Combinations of two or more hardening methods provided for in at least two different groups from H01L 2224/83855 - H01L 2224/8388 , e.g. for hybrid thermoplastic-thermosetting adhesives
2224/83795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/837 - H01L 2224/83791	2224/83886	Involving a self-assembly process, e.g. self-agglomeration of a material dispersed in a fluid
2224/83798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/83887	Auxiliary means therefor, e.g. for self-assembly activation
2224/83799	Shape or distribution of the fillers	2224/83888	with special adaptation of the surface of the body to be connected, e.g. surface shape specially adapted for the self-assembly process
2224/838	Bonding techniques	2224/83889	involving the material of the bonding area, e.g. bonding pad
2224/83801	Soldering or alloying	2224/8389	using an inorganic non metallic glass type adhesive, e.g. solder glass
2224/83805	involving forming a eutectic alloy at the bonding interface	2224/83893	Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
		2224/83894	Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
		2224/83895	between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
		2224/83896	between electrically insulating surfaces, e.g. oxide or nitride layers
		2224/83897	Mechanical interlocking, e.g. anchoring, hook and loop-type fastening or the like
		2224/83898	Press-fitting, i.e. pushing the parts together and fastening by friction, e.g. by compression of one part against the other

2224/83899	using resilient parts in the layer connector or in the bonding area	2224/8401	Cleaning, e.g. oxide removal step, desmearing
2224/839	. . .	with the layer connector not providing any mechanical bonding	2224/84011	Chemical cleaning, e.g. etching, flux
2224/83901	Pressing the layer connector against the bonding areas by means of another connector	2224/84012	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
2224/83902	by means of another layer connector	2224/84013	Plasma cleaning
2224/83903	by means of a bump connector	2224/84014	Thermal cleaning, e.g. decomposition, sublimation
2224/83904	by means of an encapsulation layer or foil	2224/84019	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8401 - H01L 2224/84014
2224/83905	. . .	Combinations of bonding methods provided for in at least two different groups from H01L 2224/838 - H01L 2224/83904	2224/8402	Applying permanent coating, e.g. in-situ coating
2224/83906	Specific sequence of method steps	2224/8403	Reshaping
2224/83907	Intermediate bonding, i.e. intermediate bonding step for temporarily bonding the semiconductor or solid-state body, followed by at least a further bonding step	2224/84031	by chemical means, e.g. etching, anodisation
2224/83908	. . .	involving monitoring, e.g. feedback loop	2224/84035	by heating means, e.g. "free-air-ball"
2224/83909	. . .	Post-treatment of the layer connector or bonding area	2224/84037	using a polychromatic heating lamp
2224/8391	Cleaning, e.g. oxide removal step, desmearing	2224/84039	using a laser
2224/83911	Chemical cleaning, e.g. etching, flux	2224/84041	Induction heating, i.e. eddy currents
2224/83912	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow	2224/84043	using a flame torch, e.g. hydrogen torch
2224/83913	Plasma cleaning	2224/84045	using a corona discharge, e.g. electronic flame off [EFO]
2224/83914	Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge	2224/84047	by mechanical means, e.g. severing, pressing, stamping
2224/83919	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8391 - H01L 2224/83914	2224/84048	Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
2224/8392	Applying permanent coating, e.g. protective coating	2224/84051	Forming additional members
2224/8393	Reshaping	2224/84053	. . .	Bonding environment
2224/83931	by chemical means, e.g. etching	2224/84054	Composition of the atmosphere
2224/83935	by heating means, e.g. reflowing	2224/84055	being oxidating
2224/83937	using a polychromatic heating lamp	2224/84065	being reducing
2224/83939	using a laser	2224/84075	being inert
2224/83941	Induction heating, i.e. eddy currents	2224/84085	being a liquid (e.g. for fluidic self-assembly)
2224/83943	using a flame torch, e.g. hydrogen torch	2224/8409	Vacuum
2224/83945	using a corona discharge, e.g. electronic flame off [EFO]	2224/84091	Under pressure
2224/83947	by mechanical means, e.g. "pull-and-cut", pressing, stamping	2224/84092	Atmospheric pressure
2224/83948	Thermal treatments, e.g. annealing, controlled cooling	2224/84093	Transient conditions, e.g. gas-flow
2224/83951	Forming additional members, e.g. for reinforcing, fillet sealant	2224/84095	Temperature settings
2224/83986	. . .	Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence	2224/84096	Transient conditions
2224/84	. . .	using a strap connector	2224/84097	Heating
2224/84001	. . .	involving a temporary auxiliary member not forming part of the bonding apparatus	2224/84098	Cooling
2224/84002	being a removable or sacrificial coating	2224/84099	Ambient temperature
2224/84005	being a temporary substrate	2224/841	. . .	the connector being supplied to the parts to be connected in the bonding apparatus
2224/84007	. . .	involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the strap connector during or after the bonding process	2224/8411	. . .	involving protection against electrical discharge, e.g. removing electrostatic charge
2224/84009	. . .	Pre-treatment of the connector and/or the bonding area	2224/8412	. . .	Aligning
			2224/84121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors
			2224/84122	by detecting inherent features of, or outside, the semiconductor or solid-state body
			2224/84123	Shape or position of the body
			2224/84125	Bonding areas on the body
			2224/84127	Bonding areas outside the body
			2224/84129	Shape or position of the other item
			2224/8413	using marks formed on the semiconductor or solid-state body

2224/84132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"	2224/84379	Material
2224/84136	involving guiding structures, e.g. spacers or supporting members	2224/8438	Bonding interfaces outside the semiconductor or solid-state body
2224/84138	the guiding structures being at least partially left in the finished device	2224/84385	Shape, e.g. interlocking features
2224/84143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium	2224/84395	having an external coating, e.g. protective bond-through coating
2224/84148	involving movement of a part of the bonding apparatus	2224/84399	Material
2224/84149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table	2224/844	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2224/8415	Rotational movements	2224/84401	the principal constituent melting at a temperature of less than 400°C
2224/8416	Translational movements	2224/84405	Gallium [Ga] as principal constituent
2224/84169	being the upper part of the bonding apparatus, i.e. bonding head,	2224/84409	Indium [In] as principal constituent
2224/8417	Rotational movements	2224/84411	Tin [Sn] as principal constituent
2224/8418	Translational movements	2224/84413	Bismuth [Bi] as principal constituent
2224/84181	connecting first on the semiconductor or solid-state body, i.e. on-chip, regular stitch	2224/84414	Thallium [Tl] as principal constituent
2224/84186	connecting first outside the semiconductor or solid-state body, i.e. off-chip, reverse stitch	2224/84416	Lead [Pb] as principal constituent
2224/84191	connecting first both on and outside the semiconductor or solid-state body, i.e. regular and reverse stitches	2224/84417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/84196	involving intermediate connecting steps before cutting the strap connector	2224/84418	Zinc [Zn] as principal constituent
2224/842	Applying energy for connecting	2224/8442	Antimony [Sb] as principal constituent
2224/84201	Compression bonding	2224/84423	Magnesium [Mg] as principal constituent
2224/84203	Thermocompression bonding	2224/84424	Aluminium [Al] as principal constituent
2224/84205	Ultrasonic bonding	2224/84438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/84206	Direction of oscillation	2224/84439	Silver [Ag] as principal constituent
2224/84207	Thermosonic bonding	2224/84444	Gold [Au] as principal constituent
2224/8421	with energy being in the form of electromagnetic radiation	2224/84447	Copper [Cu] as principal constituent
2224/84212	Induction heating, i.e. eddy currents	2224/84449	Manganese [Mn] as principal constituent
2224/84214	using a laser	2224/84455	Nickel [Ni] as principal constituent
2224/8423	Polychromatic or infrared lamp heating	2224/84457	Cobalt [Co] as principal constituent
2224/84232	using an autocatalytic reaction, e.g. exothermic brazing	2224/8446	Iron [Fe] as principal constituent
2224/84234	using means for applying energy being within the device, e.g. integrated heater	2224/84463	the principal constituent melting at a temperature of greater than 1550°C
2224/84236	using electro-static corona discharge	2224/84464	Palladium [Pd] as principal constituent
2224/84237	using an electron beam (electron beam welding in general B23K 15/00)	2224/84466	Titanium [Ti] as principal constituent
2224/84238	using electric resistance welding, i.e. ohmic heating	2224/84469	Platinum [Pt] as principal constituent
2224/8434	Bonding interfaces of the connector	2224/8447	Zirconium [Zr] as principal constituent
2224/84345	Shape, e.g. interlocking features	2224/84471	Chromium [Cr] as principal constituent
2224/84355	having an external coating, e.g. protective bond-through coating	2224/84472	Vanadium [V] as principal constituent
2224/84359	Material	2224/84473	Rhodium [Rh] as principal constituent
2224/8436	Bonding interfaces of the semiconductor or solid state body	2224/84476	Ruthenium [Ru] as principal constituent
2224/84365	Shape, e.g. interlocking features	2224/84478	Iridium [Ir] as principal constituent
2224/84375	having an external coating, e.g. protective bond-through coating	2224/84479	Niobium [Nb] as principal constituent
			2224/8448	Molybdenum [Mo] as principal constituent
			2224/84481	Tantalum [Ta] as principal constituent
			2224/84483	Rhenium [Re] as principal constituent
			2224/84484	Tungsten [W] as principal constituent

2224/84486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/84544	Gold [Au] as principal constituent
2224/84487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/84488)	2224/84547	Copper [Cu] as principal constituent
2224/84488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/84549	Manganese [Mn] as principal constituent
2224/8449	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/84555	Nickel [Ni] as principal constituent
2224/84491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/84557	Cobalt [Co] as principal constituent
2224/84493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/844 - H01L 2224/84491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/8456	Iron [Fe] as principal constituent
2224/84494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/844 - H01L 2224/84491	2224/84563	the principal constituent melting at a temperature of greater than 1550°C
2224/84495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/844 - H01L 2224/84491	2224/84564	Palladium [Pd] as principal constituent
2224/84498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/84566	Titanium [Ti] as principal constituent
2224/84499	Material of the matrix	2224/84569	Platinum [Pt] as principal constituent
2224/845	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/8457	Zirconium [Zr] as principal constituent
2224/84501	the principal constituent melting at a temperature of less than 400°C	2224/84571	Chromium [Cr] as principal constituent
2224/84505	Gallium [Ga] as principal constituent	2224/84572	Vanadium [V] as principal constituent
2224/84509	Indium [In] as principal constituent	2224/84573	Rhodium [Rh] as principal constituent
2224/84511	Tin [Sn] as principal constituent	2224/84576	Ruthenium [Ru] as principal constituent
2224/84513	Bismuth [Bi] as principal constituent	2224/84578	Iridium [Ir] as principal constituent
2224/84514	Thallium [Tl] as principal constituent	2224/84579	Niobium [Nb] as principal constituent
2224/84516	Lead [Pb] as principal constituent	2224/8458	Molybdenum [Mo] as principal constituent
2224/84517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/84581	Tantalum [Ta] as principal constituent
2224/84518	Zinc [Zn] as principal constituent	2224/84583	Rhenium [Re] as principal constituent
2224/8452	Antimony [Sb] as principal constituent	2224/84584	Tungsten [W] as principal constituent
2224/84523	Magnesium [Mg] as principal constituent	2224/84586	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/84524	Aluminium [Al] as principal constituent	2224/84587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/84588)
2224/84538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/84588	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/84539	Silver [Ag] as principal constituent	2224/8459	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
			2224/84591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
			2224/84593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/845 - H01L 2224/84591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond

2224/84594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/845 - H01L 2224/84591	2224/84664	Palladium [Pd] as principal constituent
2224/84595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/845 - H01L 2224/84591	2224/84666	Titanium [Ti] as principal constituent
2224/84598	Fillers	2224/84669	Platinum [Pt] as principal constituent
2224/84599	Base material	2224/8467	Zirconium [Zr] as principal constituent
2224/846	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/84671	Chromium [Cr] as principal constituent
2224/84601	the principal constituent melting at a temperature of less than 400°C	2224/84672	Vanadium [V] as principal constituent
2224/84605	Gallium [Ga] as principal constituent	2224/84673	Rhodium [Rh] as principal constituent
2224/84609	Indium [In] as principal constituent	2224/84676	Ruthenium [Ru] as principal constituent
2224/84611	Tin [Sn] as principal constituent	2224/84678	Iridium [Ir] as principal constituent
2224/84613	Bismuth [Bi] as principal constituent	2224/84679	Niobium [Nb] as principal constituent
2224/84614	Thallium [Tl] as principal constituent	2224/8468	Molybdenum [Mo] as principal constituent
2224/84616	Lead [Pb] as principal constituent	2224/84681	Tantalum [Ta] as principal constituent
2224/84617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/84683	Rhenium [Re] as principal constituent
2224/84618	Zinc [Zn] as principal constituent	2224/84684	Tungsten [W] as principal constituent
2224/8462	Antimony [Sb] as principal constituent	2224/84686	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/84623	Magnesium [Mg] as principal constituent	2224/84687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/84688)
2224/84624	Aluminium [Al] as principal constituent	2224/84688	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/84638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/8469	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/84639	Silver [Ag] as principal constituent	2224/84691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/84644	Gold [Au] as principal constituent	2224/84693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/846 - H01L 2224/84691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/84647	Copper [Cu] as principal constituent	2224/84694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/846 - H01L 2224/84691
2224/84649	Manganese [Mn] as principal constituent	2224/84695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/846 - H01L 2224/84691
2224/84655	Nickel [Ni] as principal constituent	2224/84698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/84657	Cobalt [Co] as principal constituent	2224/84699	Coating material
2224/8466	Iron [Fe] as principal constituent		
2224/84663	the principal constituent melting at a temperature of greater than 1550°C		

2224/847	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2224/84772	Vanadium [V] as principal constituent
2224/84701	the principal constituent melting at a temperature of less than 400°C	2224/84773	Rhodium [Rh] as principal constituent
2224/84705	Gallium [Ga] as principal constituent	2224/84776	Ruthenium [Ru] as principal constituent
2224/84709	Indium [In] as principal constituent	2224/84778	Iridium [Ir] as principal constituent
2224/84711	Tin [Sn] as principal constituent	2224/84779	Niobium [Nb] as principal constituent
2224/84713	Bismuth [Bi] as principal constituent	2224/8478	Molybdenum [Mo] as principal constituent
2224/84714	Thallium [Tl] as principal constituent	2224/84781	Tantalum [Ta] as principal constituent
2224/84716	Lead [Pb] as principal constituent	2224/84783	Rhenium [Re] as principal constituent
2224/84717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/84784	Tungsten [W] as principal constituent
2224/84718	Zinc [Zn] as principal constituent	2224/84786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2224/8472	Antimony [Sb] as principal constituent	2224/84787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/84788)
2224/84723	Magnesium [Mg] as principal constituent	2224/84788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2224/84724	Aluminium [Al] as principal constituent	2224/8479	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2224/84738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/84791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2224/84739	Silver [Ag] as principal constituent	2224/84793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/847 - H01L 2224/84791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2224/84744	Gold [Au] as principal constituent	2224/84794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/847 - H01L 2224/84791
2224/84747	Copper [Cu] as principal constituent	2224/84795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/847 - H01L 2224/84791
2224/84749	Manganese [Mn] as principal constituent	2224/84798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2224/84755	Nickel [Ni] as principal constituent	2224/84799	Shape or distribution of the fillers
2224/84757	Cobalt [Co] as principal constituent	2224/848	Bonding techniques
2224/8476	Iron [Fe] as principal constituent	2224/84801	Soldering or alloying
2224/84763	the principal constituent melting at a temperature of greater than 1550°C	2224/84805	involving forming a eutectic alloy at the bonding interface
2224/84764	Palladium [Pd] as principal constituent	2224/8481	involving forming an intermetallic compound at the bonding interface
2224/84766	Titanium [Ti] as principal constituent	2224/84815	Reflow soldering
2224/84769	Platinum [Pt] as principal constituent	2224/8482	Diffusion bonding
2224/8477	Zirconium [Zr] as principal constituent	2224/84825	Solid-liquid interdiffusion
2224/84771	Chromium [Cr] as principal constituent		

- 2224/8483 Solid-solid interdiffusion
- 2224/8484 Sintering
- 2224/8485 using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
- 2224/84855 Hardening the adhesive by curing, i.e. thermosetting
- 2224/84856 Pre-cured adhesive, i.e. B-stage adhesive
- 2224/84859 Localised curing of parts of the connector
- 2224/84862 Heat curing
- 2224/84865 Microwave curing
- 2224/84868 Infrared [IR] curing
- 2224/84871 Visible light curing
- 2224/84874 Ultraviolet [UV] curing
- 2224/84877 Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
- 2224/8488 Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
- 2224/84885 Combinations of two or more hardening methods provided for in at least two different groups from [H01L 2224/84855](#) - [H01L 2224/8488](#), e.g. for hybrid thermoplastic-thermosetting adhesives
- 2224/8489 using an inorganic non metallic glass type adhesive, e.g. solder glass
- 2224/84893 Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
- 2224/84895 Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
- 2224/84897 between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
- 2224/84898 between electrically insulating surfaces, e.g. oxide or nitride layersg
- 2224/84899 Combinations of bonding methods provided for in at least two different groups from [H01L 2224/848](#) - [H01L 2224/84898](#)
- 2224/849 involving monitoring, e.g. feedback loop
- 2224/84909 Post-treatment of the connector or bonding area
- 2224/8491 Cleaning, e.g. oxide removal step, desmearing
- 2224/84911 Chemical cleaning, e.g. etching, flux
- 2224/84912 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/84913 Plasma cleaning
- 2224/84914 Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge
- 2224/84919 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8491](#) - [H01L 2224/84914](#)
- 2224/8492 Applying permanent coating, e.g. protective coating
- 2224/8493 Reshaping, e.g. for severing the strap, modifying the loop shape
- 2224/84931 by chemical means, e.g. etching
- 2224/84935 by heating means, e.g. reflowing
- 2224/84937 using a polychromatic heating lamp
- 2224/84939 using a laser
- 2224/84941 Induction heating, i.e. eddy currents
- 2224/84943 using a flame torch, e.g. hydrogen torch
- 2224/84945 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/84947 by mechanical means, e.g. pressing, stamping
- 2224/84948 Thermal treatments, e.g. annealing, controlled cooling
- 2224/84951 Forming additional members, e.g. for reinforcing
- 2224/84986 Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
- 2224/85 using a wire connector
- 2224/85001 involving a temporary auxiliary member not forming part of the bonding apparatus, e.g. removable or sacrificial coating, film or substrate
- 2224/85002 being a removable or sacrificial coating
- 2224/85005 being a temporary or sacrificial substrate
- 2224/85007 involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the wire connector during or after the bonding process
- 2224/85009 Pre-treatment of the connector or the bonding area
- 2224/8501 Cleaning, e.g. oxide removal step, desmearing
- 2224/85011 Chemical cleaning, e.g. etching, flux
- 2224/85012 Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
- 2224/85013 Plasma cleaning
- 2224/85014 Thermal cleaning, e.g. decomposition, sublimation
- 2224/85016 using a laser
- 2224/85017 Electron beam cleaning
- 2224/85019 Combinations of two or more cleaning methods provided for in at least two different groups from [H01L 2224/8501](#) - [H01L 2224/85014](#)
- 2224/8502 Applying permanent coating, e.g. in-situ coating
- 2224/8503 Reshaping, e.g. forming the ball or the wedge of the wire connector
- 2224/85031 by chemical means, e.g. etching, anodisation
- 2224/85035 by heating means, e.g. "free-air-ball"
- 2224/85037 using a polychromatic heating lamp
- 2224/85039 using a laser
- 2224/85041 Induction heating, i.e. eddy currents
- 2224/85043 using a flame torch, e.g. hydrogen torch
- 2224/85045 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/85047 by mechanical means, e.g. severing, pressing, stamping
- 2224/85048 Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
- 2224/85051 Forming additional members, e.g. for "wedge-on-ball", "ball-on-wedge", "ball-on-ball" connections

2224/85053	. . .	Bonding environment	2224/85196	involving intermediate connecting steps before cutting the wire connector
2224/85054	Composition of the atmosphere	2224/852	. . .	Applying energy for connecting
2224/85055	being oxidating	2224/85201	Compression bonding
2224/85065	being reducing	2224/85203	Thermocompression bonding
2224/85075	being inert	2224/85205	Ultrasonic bonding
2224/85085	being a liquid, e.g. for fluidic self-assembly	2224/85206	Direction of oscillation
2224/8509	Vacuum	2224/85207	Thermosonic bonding
2224/85091	Under pressure	2224/8521	with energy being in the form of electromagnetic radiation
2224/85092	Atmospheric pressure	2224/85212	Induction heating, i.e. eddy currents
2224/85093	Transient conditions, e.g. gas-flow	2224/85214	using a laser
2224/85095	Temperature settings	2224/8523	Polychromatic or infrared lamp heating
2224/85096	Transient conditions	2224/85232	using an autocatalytic reaction, e.g. exothermic brazing
2224/85097	Heating	2224/85234	using means for applying energy being within the device, e.g. integrated heater
2224/85098	Cooling	2224/85236	using electro-static corona discharge
2224/85099	Ambient temperature	2224/85237	using electron beam (using electron beam in general B23K 15/00)
2224/851	. . .	the connector being supplied to the parts to be connected in the bonding apparatus	2224/85238	using electric resistance welding, i.e. ohmic heating
2224/8511	. . .	involving protection against electrical discharge, e.g. removing electrostatic charge	2224/8534	. . .	Bonding interfaces of the connector
2224/8512	. . .	Aligning	2224/85345	Shape, e.g. interlocking features
2224/85121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors	2224/85355	having an external coating, e.g. protective bond-through coating
2224/85122	by detecting inherent features of, or outside, the semiconductor or solid-state body	2224/85359	Material
2224/85123	Shape or position of the body	2224/8536	. . .	Bonding interfaces of the semiconductor or solid state body
2224/85125	Bonding areas on the body	2224/85365	Shape, e.g. interlocking features
2224/85127	Bonding areas outside the body	2224/85375	having an external coating, e.g. protective bond-through coating
2224/85129	Shape or position of the other item	2224/85379	Material
2224/8513	using marks formed on the semiconductor or solid-state body	2224/8538	. . .	Bonding interfaces outside the semiconductor or solid-state body
2224/85132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"	2224/85385	Shape, e.g. interlocking features
2224/85136	involving guiding structures, e.g. spacers or supporting members	2224/85395	having an external coating, e.g. protective bond-through coating
2224/85138	the guiding structures being at least partially left in the finished device	2224/85399	Material
2224/85143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium	2224/854	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/85148	involving movement of a part of the bonding apparatus	2224/85401	the principal constituent melting at a temperature of less than 400°C
2224/85149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table	2224/85405	Gallium (Ga) as principal constituent
2224/8515	Rotational movements	2224/85409	Indium (In) as principal constituent
2224/8516	Translational movements	2224/85411	Tin (Sn) as principal constituent
2224/85169	being the upper part of the bonding apparatus, i.e. bonding head, e.g. capillary or wedge	2224/85413	Bismuth (Bi) as principal constituent
2224/8517	Rotational movements	2224/85414	Thallium (Tl) as principal constituent
2224/8518	Translational movements	2224/85416	Lead (Pb) as principal constituent
2224/85181	connecting first on the semiconductor or solid-state body, i.e. on-chip, regular stitch	2224/85417	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/85186	connecting first outside the semiconductor or solid-state body, i.e. off-chip, reverse stitch	2224/85418	Zinc (Zn) as principal constituent
2224/85191	connecting first both on and outside the semiconductor or solid-state body, i.e. regular and reverse stitches	2224/8542	Antimony (Sb) as principal constituent
			2224/85423	Magnesium (Mg) as principal constituent
			2224/85424	Aluminium (Al) as principal constituent

2224/85438	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C	2224/855	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof
2224/85439	Silver (Ag) as principal constituent	2224/85501	the principal constituent melting at a temperature of less than 400°C
2224/85444	Gold (Au) as principal constituent	2224/85505	Gallium (Ga) as principal constituent
2224/85447	Copper (Cu) as principal constituent	2224/85509	Indium (In) as principal constituent
2224/85449	Manganese (Mn) as principal constituent	2224/85511	Tin (Sn) as principal constituent
2224/85455	Nickel (Ni) as principal constituent	2224/85513	Bismuth (Bi) as principal constituent
2224/85457	Cobalt (Co) as principal constituent	2224/85514	Thallium (Tl) as principal constituent
2224/8546	Iron (Fe) as principal constituent	2224/85516	Lead (Pb) as principal constituent
2224/85463	the principal constituent melting at a temperature of greater than 1550°C	2224/85517	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/85464	Palladium (Pd) as principal constituent	2224/85518	Zinc (Zn) as principal constituent
2224/85466	Titanium (Ti) as principal constituent	2224/8552	Antimony (Sb) as principal constituent
2224/85469	Platinum (Pt) as principal constituent	2224/85523	Magnesium (Mg) as principal constituent
2224/8547	Zirconium (Zr) as principal constituent	2224/85524	Aluminium (Al) as principal constituent
2224/85471	Chromium (Cr) as principal constituent	2224/85538	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/85472	Vanadium (V) as principal constituent	2224/85539	Silver (Ag) as principal constituent
2224/85473	Rhodium (Rh) as principal constituent	2224/85544	Gold (Au) as principal constituent
2224/85476	Ruthenium (Ru) as principal constituent	2224/85547	Copper (Cu) as principal constituent
2224/85478	Iridium (Ir) as principal constituent	2224/85549	Manganese (Mn) as principal constituent
2224/85479	Niobium (Nb) as principal constituent	2224/85555	Nickel (Ni) as principal constituent
2224/8548	Molybdenum (Mo) as principal constituent	2224/85557	Cobalt (Co) as principal constituent
2224/85481	Tantalum (Ta) as principal constituent	2224/8556	Iron (Fe) as principal constituent
2224/85483	Rhenium (Re) as principal constituent	2224/85563	the principal constituent melting at a temperature of greater than 1550°C
2224/85484	Tungsten (W) as principal constituent	2224/85564	Palladium (Pd) as principal constituent
2224/85486	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/85566	Titanium (Ti) as principal constituent
2224/85487	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/85488)	2224/85569	Platinum (Pt) as principal constituent
2224/85488	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/8557	Zirconium (Zr) as principal constituent
2224/8549	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/85571	Chromium (Cr) as principal constituent
2224/85491	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/85572	Vanadium (V) as principal constituent
2224/85493	with a principal constituent of the material being a solid not provided for in groups H01L 2224/854 - H01L 2224/85491 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/85573	Rhodium (Rh) as principal constituent
2224/85494	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/854 - H01L 2224/85491	2224/85576	Ruthenium (Ru) as principal constituent
2224/85495	with a principal constituent of the material being a gas not provided for in groups H01L 2224/854 - H01L 2224/85491			
2224/85498	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams			
2224/85499	Material of the matrix			

2224/85578	Iridium (Ir) as principal constituent	2224/85617	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C
2224/85579	Niobium (Nb) as principal constituent	2224/85618	Zinc (Zn) as principal constituent
2224/8558	Molybdenum (Mo) as principal constituent	2224/8562	Antimony (Sb) as principal constituent
2224/85581	Tantalum (Ta) as principal constituent	2224/85623	Magnesium (Mg) as principal constituent
2224/85583	Rhenium (Re) as principal constituent	2224/85624	Aluminium (Al) as principal constituent
2224/85584	Tungsten (W) as principal constituent	2224/85638	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/85586	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2224/85639	Silver (Ag) as principal constituent
2224/85587	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/85588)	2224/85644	Gold (Au) as principal constituent
2224/85588	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/85647	Copper (Cu) as principal constituent
2224/8559	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/85649	Manganese (Mn) as principal constituent
2224/85591	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/85655	Nickel (Ni) as principal constituent
2224/85593	with a principal constituent of the material being a solid not provided for in groups H01L 2224/855 - H01L 2224/85591 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/85657	Cobalt (Co) as principal constituent
2224/85594	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/855 - H01L 2224/85591	2224/8566	Iron (Fe) as principal constituent
2224/85595	with a principal constituent of the material being a gas not provided for in groups H01L 2224/855 - H01L 2224/85591	2224/85663	the principal constituent melting at a temperature of greater than 1550°C
2224/85598	Fillers	2224/85664	Palladium (Pd) as principal constituent
2224/85599	Base material	2224/85666	Titanium (Ti) as principal constituent
2224/856	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/85669	Platinum (Pt) as principal constituent
2224/85601	the principal constituent melting at a temperature of less than 400°C	2224/8567	Zirconium (Zr) as principal constituent
2224/85605	Gallium (Ga) as principal constituent	2224/85671	Chromium (Cr) as principal constituent
2224/85609	Indium (In) as principal constituent	2224/85672	Vanadium (V) as principal constituent
2224/85611	Tin (Sn) as principal constituent	2224/85673	Rhodium (Rh) as principal constituent
2224/85613	Bismuth (Bi) as principal constituent	2224/85676	Ruthenium (Ru) as principal constituent
2224/85614	Thallium (Tl) as principal constituent	2224/85678	Iridium (Ir) as principal constituent
2224/85616	Lead (Pb) as principal constituent	2224/85679	Niobium (Nb) as principal constituent
		2224/8568	Molybdenum (Mo) as principal constituent
		2224/85681	Tantalum (Ta) as principal constituent
		2224/85683	Rhenium (Re) as principal constituent
		2224/85684	Tungsten (W) as principal constituent
		2224/85686	with a principal constituent of the material being a non metallic, non metalloid inorganic material

2224/85687	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/85688)	2224/85724	Aluminium (Al) as principal constituent
2224/85688	Glasses, e.g. amorphous oxides, nitrides or fluorides	2224/85738	the principal constituent melting at a temperature of greater than or equal to 950°C and less than 1550°C
2224/8569	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2224/85739	Silver (Ag) as principal constituent
2224/85691	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/85744	Gold (Au) as principal constituent
2224/85693	with a principal constituent of the material being a solid not provided for in groups H01L 2224/856 - H01L 2224/85691 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/85747	Copper (Cu) as principal constituent
2224/85694	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/856 - H01L 2224/85691	2224/85749	Manganese (Mn) as principal constituent
2224/85695	with a principal constituent of the material being a gas not provided for in groups H01L 2224/856 - H01L 2224/85691	2224/85755	Nickel (Ni) as principal constituent
2224/85698	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/85757	Cobalt (Co) as principal constituent
2224/85699	Coating material	2224/8576	Iron (Fe) as principal constituent
2224/857	with a principal constituent of the material being a metal or a metalloid, e.g. boron (B), silicon (Si), germanium (Ge), arsenic (As), antimony (Sb), tellurium (Te) and polonium (Po), and alloys thereof	2224/85763	the principal constituent melting at a temperature of greater than 1550°C
2224/85701	the principal constituent melting at a temperature of less than 400°C	2224/85764	Palladium (Pd) as principal constituent
2224/85705	Gallium (Ga) as principal constituent	2224/85766	Titanium (Ti) as principal constituent
2224/85709	Indium (In) as principal constituent	2224/85769	Platinum (Pt) as principal constituent
2224/85711	Tin (Sn) as principal constituent	2224/8577	Zirconium (Zr) as principal constituent
2224/85713	Bismuth (Bi) as principal constituent	2224/85771	Chromium (Cr) as principal constituent
2224/85714	Thallium (Tl) as principal constituent	2224/85772	Vanadium (V) as principal constituent
2224/85716	Lead (Pb) as principal constituent	2224/85773	Rhodium (Rh) as principal constituent
2224/85717	the principal constituent melting at a temperature of greater than or equal to 400°C and less than 950°C	2224/85776	Ruthenium (Ru) as principal constituent
2224/85718	Zinc (Zn) as principal constituent	2224/85778	Iridium (Ir) as principal constituent
2224/8572	Antimony (Sb) as principal constituent	2224/85779	Niobium (Nb) as principal constituent
2224/85723	Magnesium (Mg) as principal constituent	2224/8578	Molybdenum (Mo) as principal constituent
			2224/85781	Tantalum (Ta) as principal constituent
			2224/85783	Rhenium (Re) as principal constituent
			2224/85784	Tungsten (W) as principal constituent
			2224/85786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
			2224/85787	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/85788)
			2224/85788	Glasses, e.g. amorphous oxides, nitrides or fluorides
			2224/8579	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy

2224/85791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2224/85893	Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
2224/85793	with a principal constituent of the material being a solid not provided for in groups H01L 2224/857 - H01L 2224/85791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2224/85895	Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
2224/85794	with a principal constituent of the material being a liquid not provided for in groups H01L 2224/857 - H01L 2224/85791	2224/85897	between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
2224/85795	with a principal constituent of the material being a gas not provided for in groups H01L 2224/857 - H01L 2224/85791	2224/85898	between electrically insulating surfaces, e.g. oxide or nitride layers
2224/85798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2224/85899	Combinations of bonding methods provided for in at least two different groups from H01L 2224/858 - H01L 2224/85898
2224/85799	Shape or distribution of the fillers	2224/859	. . .	involving monitoring, e.g. feedback loop
2224/858	. . .	Bonding techniques	2224/85909	. . .	Post-treatment of the connector or wire bonding area
2224/85801	Soldering or alloying	2224/8591	Cleaning, e.g. oxide removal step, desmearing
2224/85805	involving forming a eutectic alloy at the bonding interface	2224/85911	Chemical cleaning, e.g. etching, flux
2224/8581	involving forming an intermetallic compound at the bonding interface	2224/85912	Mechanical cleaning, e.g. abrasion using hydro blasting, brushes, ultrasonic cleaning, dry ice blasting, gas-flow
2224/85815	Reflow soldering	2224/85913	Plasma cleaning
2224/8582	Diffusion bonding	2224/85914	Thermal cleaning, e.g. using laser ablation or by electrostatic corona discharge
2224/85825	Solid-liquid interdiffusion	2224/85916	using a laser
2224/8583	Solid-solid interdiffusion, e.g. "direct bonding"	2224/85917	Electron beam cleaning
2224/8584	Sintering	2224/85919	Combinations of two or more cleaning methods provided for in at least two different groups from H01L 2224/8591 - H01L 2224/85914
2224/8585	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester	2224/8592	Applying permanent coating, e.g. protective coating
2224/85855	Hardening the adhesive by curing, i.e. thermosetting	2224/8593	Reshaping, e.g. for severing the wire, modifying the wedge or ball or the loop shape
2224/85856	Pre-cured adhesive, i.e. B-stage adhesive	2224/85931	by chemical means, e.g. etching
2224/85859	Localised curing of parts of the connector	2224/85935	by heating means, e.g. reflowing
2224/85862	Heat curing	2224/85937	using a polychromatic heating lamp
2224/85865	Microwave curing	2224/85939	using a laser
2224/85868	Infrared [IR] curing	2224/85941	Induction heating, i.e. eddy currents
2224/85871	Visible light curing	2224/85943	using a flame torch, e.g. hydrogen torch
2224/85874	Ultraviolet [UV] curing	2224/85945	using a corona discharge, e.g. electronic flame off [EFO]
2224/85877	Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes	2224/85947	by mechanical means, e.g. "pull-and-cut", pressing, stamping
2224/8588	Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives	2224/85948	Thermal treatments, e.g. annealing, controlled cooling
2224/85885	Combinations of two or more hardening methods provided for in at least two different groups from H01L 2224/85855 - H01L 2224/8588 , e.g. for hybrid thermoplastic-thermosetting adhesives	2224/85951	Forming additional members, e.g. for reinforcing
2224/8589	using an inorganic non metallic glass type adhesive, e.g. solder glass	2224/85986	. . .	Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
			2224/86	. . .	using tape automated bonding [TAB]
			2224/86001	. . .	involving a temporary auxiliary member not forming part of the bonding apparatus
			2224/86002	being a removable or sacrificial coating
			2224/86005	being a temporary or sacrificial substrate
			2224/86007	. . .	involving a permanent auxiliary member being left in the finished device, e.g. aids for holding or protecting the TAB connector during or after the bonding process

2224/86009	. . .	Pre-treatment of the connector or the bonding area	2224/86186	connecting first outside the semiconductor or solid-state body, i.e. off-chip
2224/8601	Cleaning, e.g. oxide removal step, desmearing	2224/86191	connecting first both on and outside the semiconductor or solid-state body
2224/8603	Reshaping	2224/862	. . .	Applying energy for connecting
2224/86031	by chemical means, e.g. etching, anodisation	2224/86201	Compression bonding
2224/86035	by heating	2224/86203	Thermo-compression bonding
2224/86039	using a laser	2224/86205	Ultrasonic bonding
2224/86045	using a corona discharge, e.g. electronic flame off [EFO]	2224/86207	Thermosonic bonding
2224/86047	by mechanical means, e.g. severing, pressing, stamping	2224/8621	with energy being in the form of electromagnetic radiation
2224/86048	Thermal treatment, e.g. annealing, controlled pre-heating or pre-cooling	2224/86212	Induction heating, i.e. eddy currents
2224/86051	Forming additional members	2224/86214	using a laser
2224/86053	. . .	Bonding environment	2224/8623	Polychromatic or infrared lamp heating
2224/86054	Composition of the atmosphere	2224/86232	using an autocatalytic reaction, e.g. exothermic brazing
2224/86085	being a liquid, e.g. fluidic self-assembly	2224/86234	using means for applying energy being within the device, e.g. integrated heater
2224/8609	Vacuum	2224/86236	using electro-static corona discharge
2224/86091	Under pressure	2224/86237	using electron beam (electron beam in general B23K 15/00)
2224/86095	Temperature settings	2224/86238	using electric resistance welding, i.e. ohmic heating
2224/86096	Transient conditions	2224/8634	. . .	Bonding interfaces of the connector
2224/86097	Heating	2224/86345	Shape, e.g. interlocking features
2224/86098	Cooling	2224/86355	having an external coating, e.g. protective bond-through coating
2224/86099	Ambient temperature	2224/86359	Material
2224/861	. . .	the connector being supplied to the parts to be connected in the bonding apparatus	2224/8636	. . .	Bonding interfaces of the semiconductor or solid state body
2224/8611	. . .	involving protection against electrical discharge, e.g. removing electrostatic charge	2224/86365	Shape, e.g. interlocking features
2224/8612	. . .	Aligning	2224/86375	having an external coating, e.g. protective bond-through coating
2224/86121	Active alignment, i.e. by apparatus steering, e.g. optical alignment using marks or sensors	2224/86379	Material
2224/86122	by detecting inherent features of, or outside, the semiconductor or solid-state body	2224/8638	. . .	Bonding interfaces outside the semiconductor or solid-state body
2224/8613	using marks formed on the semiconductor or solid-state body	2224/86385	Shape, e.g. interlocking features
2224/86132	using marks formed outside the semiconductor or solid-state body, i.e. "off-chip"	2224/86395	having an external coating, e.g. protective bond-through coating
2224/86136	involving guiding structures, e.g. spacers or supporting members	2224/86399	Material
2224/86138	the guiding structures being at least partially left in the finished device	2224/868	. . .	Bonding techniques
2224/86143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium	2224/86801	Soldering or alloying
2224/86148	involving movement of a part of the bonding apparatus	2224/86805	involving forming a eutectic alloy at the bonding interface
2224/86149	being the lower part of the bonding apparatus, i.e. holding means for the bodies to be connected, e.g. XY table	2224/8681	involving forming an intermetallic compound at the bonding interface
2224/8615	Rotational movements	2224/86815	Reflow soldering
2224/8616	Translational movements	2224/8682	Diffusion bonding
2224/86169	being the upper part of the bonding apparatus, e.g. nozzle	2224/86825	Solid-liquid interdiffusion
2224/8617	Rotational movement	2224/8683	Solid-solid interdiffusion
2224/8618	Translational movements	2224/8684	Sintering
2224/86181	connecting first on the semiconductor or solid-state body, i.e. on-chip,	2224/8685	using a polymer adhesive, e.g. an adhesive based on silicone, epoxy, polyimide, polyester
			2224/86855	Hardening the adhesive by curing, i.e. thermosetting
			2224/86856	Pre-cured adhesive, i.e. B-stage adhesive
			2224/86859	Localised curing of parts of the connector
			2224/86862	Heat curing
			2224/86865	Microwave curing

- 2224/86868 Infrared [IR] curing
- 2224/86871 Visible light curing
- 2224/86874 Ultraviolet [UV] curing
- 2224/86877 Moisture curing, i.e. curing by exposing to humidity, e.g. for silicones and polyurethanes
- 2224/8688 Hardening the adhesive by cooling, e.g. for thermoplastics or hot-melt adhesives
- 2224/86885 Combinations of two or more hardening methods provided for in at least two different groups selected from [H01L 2224/86855](#) - [H01L 2224/8688](#), e.g. hybrid thermoplastic-thermosetting adhesives
- 2224/8689 using an inorganic non metallic glass type adhesive, e.g. solder glass
- 2224/86893 Anodic bonding, i.e. bonding by applying a voltage across the interface in order to induce ions migration leading to an irreversible chemical bond
- 2224/86895 Direct bonding, i.e. joining surfaces by means of intermolecular attracting interactions at their interfaces, e.g. covalent bonds, van der Waals forces
- 2224/86896 between electrically conductive surfaces, e.g. copper-copper direct bonding, surface activated bonding
- 2224/86897 between electrically insulating surfaces, e.g. oxide or nitride layers
- 2224/86899 Combinations of bonding methods provided for in at least two different groups from [H01L 2224/868](#) - [H01L 2224/86897](#)
- 2224/869 involving monitoring, e.g. feedback loop
- 2224/86909 Post-treatment of the connector or the bonding area
- 2224/8691 Cleaning, e.g. oxide removal step, desmearing
- 2224/8693 Reshaping
- 2224/86931 by chemical means, e.g. etching, anodisation
- 2224/86935 by heating means
- 2224/86939 using a laser
- 2224/86945 using a corona discharge, e.g. electronic flame off [EFO]
- 2224/86947 by mechanical means, e.g. severing, pressing, stamping
- 2224/86948 Thermal treatments, e.g. annealing, controlled pre-heating or pre-cooling
- 2224/86951 Forming additional members
- 2224/86986 Specific sequence of steps, e.g. repetition of manufacturing steps, time sequence
- 2224/89 using at least one connector not provided for in any of the groups [H01L 2224/81](#) - [H01L 2224/86](#)
- 2224/90 Methods for connecting semiconductor or solid state bodies using means for bonding not being attached to, or not being formed on, the body surface to be connected, e.g. pressure contacts using springs or clips
- 2224/91 Methods for connecting semiconductor or solid state bodies including different methods provided for in two or more of groups [H01L 2224/80](#) - [H01L 2224/90](#)
- 2224/92 Specific sequence of method steps
- 2224/9201 Forming connectors during the connecting process, e.g. in-situ formation of bumps
- 2224/9202 Forming additional connectors after the connecting process
- 2224/9205 Intermediate bonding steps, i.e. partial connection of the semiconductor or solid-state body during the connecting process
- 2224/921 Connecting a surface with connectors of different types
- 2224/9211 Parallel connecting processes
- 2224/9212 Sequential connecting processes
- 2224/92122 the first connecting process involving a bump connector
- 2224/92124 the second connecting process involving a build-up interconnect
- 2224/92125 the second connecting process involving a layer connector
- 2224/92127 the second connecting process involving a wire connector
- 2224/92132 the first connecting process involving a build-up interconnect
- 2224/92133 the second connecting process involving a bump connector
- 2224/92135 the second connecting process involving a layer connector
- 2224/92136 the second connecting process involving a strap connector
- 2224/92137 the second connecting process involving a wire connector
- 2224/92138 the second connecting process involving a TAB connector
- 2224/92142 the first connecting process involving a layer connector
- 2224/92143 the second connecting process involving a bump connector
- 2224/92144 the second connecting process involving a build-up interconnect
- 2224/92147 the second connecting process involving a wire connector
- 2224/92148 the second connecting process involving a TAB connector
- 2224/92152 the first connecting process involving a strap connector
- 2224/92153 the second connecting process involving a bump connector
- 2224/92155 the second connecting process involving a layer connector
- 2224/92157 the second connecting process involving a wire connector
- 2224/92158 the second connecting process involving a TAB connector
- 2224/92162 the first connecting process involving a wire connector
- 2224/92163 the second connecting process involving a bump connector
- 2224/92164 the second connecting process involving a build-up interconnect
- 2224/92165 the second connecting process involving a layer connector
- 2224/92166 the second connecting process involving a strap connector
- 2224/92168 the second connecting process involving a TAB connector

2224/92172	the first connecting process involving a TAB connector	2224/95101	in a liquid medium
2224/92173	the second connecting process involving a bump connector	2224/95102	being a colloidal droplet
2224/92174	the second connecting process involving a build-up interconnect	2224/9511	using a rack or rail
2224/92175	the second connecting process involving a layer connector	2224/95115	using a roll-to-roll transfer technique
2224/92176	the second connecting process involving a strap connector	2224/9512	Aligning the plurality of semiconductor or solid-state bodies
2224/92177	the second connecting process involving a wire connector	2224/95121	Active alignment, i.e. by apparatus steering
2224/922	Connecting different surfaces of the semiconductor or solid-state body with connectors of different types	2224/95122	by applying vibration
2224/9221	Parallel connecting processes	2224/95123	by applying a pressurised fluid flow, e.g. liquid or gas flow
2224/9222	Sequential connecting processes	2224/95133	by applying an electromagnetic field
2224/92222	the first connecting process involving a bump connector	2224/95134	Electrowetting, i.e. by changing the surface energy of a droplet
2224/92224	the second connecting process involving a build-up interconnect	2224/95136	involving guiding structures, e.g. shape matching, spacers or supporting members
2224/92225	the second connecting process involving a layer connector	2224/95143	Passive alignment, i.e. self alignment, e.g. using surface energy, chemical reactions, thermal equilibrium
2224/92226	the second connecting process involving a strap connector	2224/95144	Magnetic alignment, i.e. using permanent magnetic parts in the semiconductor or solid-state body
2224/92227	the second connecting process involving a wire connector	2224/95145	Electrostatic alignment, i.e. polarity alignment with Coulomb charges
2224/92228	the second connecting process involving a TAB connector	2224/95146	by surface tension
2224/92242	the first connecting process involving a layer connector	2224/95147	by molecular lock-key, e.g. by DNA
2224/92244	the second connecting process involving a build-up interconnect	2224/95148	involving movement of a part of the bonding apparatus
2224/92246	the second connecting process involving a strap connector	2224/96	the devices being encapsulated in a common layer, e.g. neo-wafer or pseudo-wafer, said common layer being separable into individual assemblies after connecting
2224/92247	the second connecting process involving a wire connector	2224/97	the devices being connected to a common substrate, e.g. interposer, said common substrate being separable into individual assemblies after connecting
2224/92248	the second connecting process involving a TAB connector	2224/98	Methods for disconnecting semiconductor or solid-state bodies
2224/92252	the first connecting process involving a strap connector	2225/00	Details relating to assemblies covered by the group H01L 25/00 but not provided for in its subgroups	
2224/92253	the second connecting process involving a bump connector	2225/03	All the devices being of a type provided for in the same subgroup of groups H01L 27/00 - H01L 51/00
2224/92255	the second connecting process involving a layer connector	2225/04	the devices not having separate containers
2224/93	Batch processes	2225/065	the devices being of a type provided for in group H01L 27/00
2224/94	at wafer-level, i.e. with connecting carried out on a wafer comprising a plurality of undiced individual devices	2225/06503	Stacked arrangements of devices
2224/95	at chip-level, i.e. with connecting carried out on a plurality of singulated devices, i.e. on diced chips	2225/06506	Wire or wire-like electrical connections between devices
2224/95001	involving a temporary auxiliary member not forming part of the bonding apparatus, e.g. removable or sacrificial coating, film or substrate	2225/0651	Wire or wire-like electrical connections from device to substrate
2224/95053	Bonding environment	2225/06513	Bump or bump-like direct electrical connections between devices, e.g. flip-chip connection, solder bumps
2224/95085	being a liquid, e.g. for fluidic self-assembly	2225/06517	Bump or bump-like direct electrical connections from device to substrate
2224/95091	Under pressure	2225/0652	Bump or bump-like direct electrical connections from substrate to substrate
2224/95092	Atmospheric pressure, e.g. dry self-assembly	2225/06524	Electrical connections formed on device or on substrate, e.g. a deposited or grown layer
2224/95093	Transient conditions, e.g. assisted by a gas flow or a liquid flow	2225/06527	Special adaptation of electrical connections, e.g. rewiring, engineering changes, pressure contacts, layout
2224/951	Supplying the plurality of semiconductor or solid-state bodies			

2225/06531	Non-galvanic coupling, e.g. capacitive coupling	2225/1058	Bump or bump-like electrical connections, e.g. balls, pillars, posts
2225/06534	Optical coupling	2225/1064	Electrical connections provided on a side surface of one or more of the containers
2225/06537	Electromagnetic shielding	2225/107	Indirect electrical connections, e.g. via an interposer, a flexible substrate, using TAB (printed circuits H05K 1/00)
2225/06541	Conductive via connections through the device, e.g. vertical interconnects, through silicon via [TSV] (manufacturing via connections per se H01L 21/76898)	2225/1076	Shape of the containers
2225/06544	Design considerations for via connections, e.g. geometry or layout	2225/1082	for improving alignment between containers, e.g. interlocking features
2225/06548	Conductive via connections through the substrate, container, or encapsulation	2225/1088	Arrangements to limit the height of the assembly
2225/06551	Conductive connections on the side of the device	2225/1094	Thermal management, e.g. cooling
2225/06555	Geometry of the stack, e.g. form of the devices, geometry to facilitate stacking	2227/00		Indexing scheme for devices consisting of a plurality of semiconductor or other solid state components formed in or on a common substrate covered by group H01L 27/00
2225/06558	the devices having passive surfaces facing each other, i.e. in a back-to-back arrangement	2227/32	Devices including an organic light emitting device [OLED], e.g. OLED display
2225/06562	at least one device in the stack being rotated or offset	2227/323	Multistep processes for AMOLED
2225/06565	the devices having the same size and there being no auxiliary carrier between the devices	2227/326	Use of temporary substrate, e.g. for manufacturing of OLED displays having an inorganic driving circuit
2225/06568	the devices decreasing in size, e.g. pyramidal stack	2229/00		Indexing scheme for semiconductor devices adapted for rectifying, amplifying, oscillating or switching, or capacitors or resistors with at least one potential-jump barrier or surface barrier, for details of semiconductor bodies or of electrodes thereof, or for multistep manufacturing processes thereof
2225/06572	Auxiliary carrier between devices, the carrier having an electrical connection structure	2251/00		Indexing scheme relating to organic semiconductor devices covered by group H01L 51/00
2225/06575	Auxiliary carrier between devices, the carrier having no electrical connection structure	2251/10	Processes specially adapted for the manufacture or treatment of organic semiconductor devices
2225/06579	TAB carriers; beam leads	2251/105	Patterning of a layer by embossing, e.g. to form trenches in an insulating layer
2225/06582	Housing for the assembly, e.g. chip scale package [CSP]	2251/30	Materials
2225/06586	Housing with external bump or bump-like connectors	2251/301	Inorganic materials
2225/06589	Thermal management, e.g. cooling	2251/303	Oxides, e.g. metal oxides
2225/06593	Mounting aids permanently on device; arrangements for alignment (use of temporary supports H01L 21/6835)	2251/305	Transparent conductive oxides [TCO]
2225/06596	Structural arrangements for testing (testing or measuring during manufacture or treatment H01L 22/00 ; testing electrical properties or locating electrical faults G01R 31/00)	2251/306	composed of tin oxides, e.g. F doped SnO ₂
2225/10	the devices having separate containers	2251/308	composed of indium oxides, e.g. ITO
2225/1005	the devices being of a type provided for in group H01L 27/00	2251/50	Organic light emitting devices
2225/1011	the containers being in a stacked arrangement	2251/53	Structure
2225/1017	the lowermost container comprising a device support	2251/5307	specially adapted for controlling the direction of light emission
2225/1023	the support being an insulating substrate	2251/5315	Top emission
2225/1029	the support being a lead frame	2251/5323	Two-side emission, i.e. TOLED
2225/1035	the device being entirely enclosed by the support, e.g. high-density interconnect [HDI]	2251/533	End-face emission
2225/1041	Special adaptations for top connections of the lowermost container, e.g. redistribution layer, integral interposer	2251/5338	Flexible OLED
2225/1047	Details of electrical connections between containers	2251/5346	Graded composition
2225/1052	Wire or wire-like electrical connections	2251/5353	Inverted OLED
			2251/5361	OLED lamp
			2251/5369	Nanoparticles used in whatever layer except emissive layer, e.g. in packaging
			2251/5376	Combination of fluorescent and phosphorescent emission
			2251/5384	Multiple hosts in the emissive layer
			2251/5392	Short-circuit prevention
			2251/55	characterised by parameters
			2251/552	HOMO-LUMO-EF

2251/554	. . . Oxidation-reduction potential	2924/01028	. . Nickel [Ni]
2251/556	. . . Temperature	2924/01029	. . Copper [Cu]
2251/558	. . . Thickness	2924/0103	. . Zinc [Zn]
2251/56	. . Processes specially adapted for the manufacture or treatment of OLED	2924/01031	. . Gallium [Ga]
2251/562	. . . Aging	2924/01032	. . Germanium [Ge]
2251/564	. . . Application of alternating current	2924/01033	. . Arsenic [As]
2251/566	. . . Division of substrate, e.g. for manufacturing of OLED displays	2924/01034	. . Selenium [Se]
2251/568	. . . Repairing	2924/01035	. . Bromine [Br]
		2924/01036	. . Krypton [Kr]
		2924/01037	. . Rubidium [Rb]
2924/00	Indexing scheme for arrangements or methods for connecting or disconnecting semiconductor or solid-state bodies as covered by H01L 24/00	2924/01038	. . Strontium [Sr]
2924/0001	. Technical content checked by a classifier	2924/01039	. . Yttrium [Y]
	NOTE	2924/0104	. . Zirconium [Zr]
	Codes H01L 2924/0001 - H01L 2924/0002 are used to describe the status of reclassification; they do not relate to technical features as such	2924/01041	. . Niobium [Nb]
2924/00011	. . Not relevant to the scope of the group, the symbol of which is combined with the symbol of this group	2924/01042	. . Molybdenum [Mo]
2924/00012	. . Relevant to the scope of the group, the symbol of which is combined with the symbol of this group	2924/01043	. . Technetium [Tc]
2924/00013	. . Fully indexed content	2924/01044	. . Ruthenium [Ru]
2924/00014	. . the subject-matter covered by the group, the symbol of which is combined with the symbol of this group, being disclosed without further technical details	2924/01045	. . Rhodium [Rh]
2924/00015	. . the subject-matter covered by the group, the symbol of which is combined with the symbol of this group, being disclosed as prior art	2924/01046	. . Palladium [Pd]
2924/0002	. . Not covered by any one of groups H01L 24/00 , H01L 24/00 and H01L 2224/00	2924/01047	. . Silver [Ag]
2924/01	. Chemical elements	2924/01048	. . Cadmium [Cd]
2924/01001	. . Hydrogen [H]	2924/01049	. . Indium [In]
2924/01002	. . Helium [He]	2924/0105	. . Tin [Sn]
2924/01003	. . Lithium [Li]	2924/01051	. . Antimony [Sb]
2924/01004	. . Beryllium [Be]	2924/01052	. . Tellurium [Te]
2924/01005	. . Boron [B]	2924/01053	. . Iodine [I]
2924/01006	. . Carbon [C]	2924/01054	. . Xenon [Xe]
2924/01007	. . Nitrogen [N]	2924/01055	. . Cesium [Cs]
2924/01008	. . Oxygen [O]	2924/01056	. . Barium [Ba]
2924/01009	. . Fluorine [F]	2924/01057	. . Lanthanum [La]
2924/0101	. . Neon [Ne]	2924/01058	. . Cerium [Ce]
2924/01011	. . Sodium [Na]	2924/01059	. . Praseodymium [Pr]
2924/01012	. . Magnesium [Mg]	2924/0106	. . Neodymium [Nd]
2924/01013	. . Aluminum [Al]	2924/01061	. . Promethium [Pm]
2924/01014	. . Silicon [Si]	2924/01062	. . Samarium [Sm]
2924/01015	. . Phosphorus [P]	2924/01063	. . Europium [Eu]
2924/01016	. . Sulfur [S]	2924/01064	. . Gadolinium [Gd]
2924/01017	. . Chlorine [Cl]	2924/01065	. . Terbium [Tb]
2924/01018	. . Argon [Ar]	2924/01066	. . Dysprosium [Dy]
2924/01019	. . Potassium [K]	2924/01067	. . Holmium [Ho]
2924/0102	. . Calcium [Ca]	2924/01068	. . Erbium [Er]
2924/01021	. . Scandium [Sc]	2924/01069	. . Thulium [Tm]
2924/01022	. . Titanium [Ti]	2924/0107	. . Ytterbium [Yb]
2924/01023	. . Vanadium [V]	2924/01071	. . Lutetium [Lu]
2924/01024	. . Chromium [Cr]	2924/01072	. . Hafnium [Hf]
2924/01025	. . Manganese [Mn]	2924/01073	. . Tantalum [Ta]
2924/01026	. . Iron [Fe]	2924/01074	. . Tungsten [W]
2924/01027	. . Cobalt [Co]	2924/01075	. . Rhenium [Re]
		2924/01076	. . Osmium [Os]
		2924/01077	. . Iridium [Ir]
		2924/01078	. . Platinum [Pt]
		2924/01079	. . Gold [Au]
		2924/0108	. . Mercury [Hg]
		2924/01081	. . Thallium [Tl]
		2924/01082	. . Lead [Pb]
		2924/01083	. . Bismuth [Bi]
		2924/01084	. . Polonium [Po]
		2924/01085	. . Astatine [At]
		2924/01086	. . Radon [Rn]
		2924/01087	. . Francium [Fr]
		2924/01088	. . Radium [Ra]

2924/01089	. . Actinium [Ac]	2924/0425	. . 5th Group
2924/0109	. . Thorium [Th]	2924/0426	. . 6th Group
2924/01091	. . Protactinium [Pa]	2924/0427	. . 7th Group
2924/01092	. . Uranium [U]	2924/0428	. . 8th Group
2924/01093	. . Neptunium [Np]	2924/0429	. . 9th Group
2924/01094	. . Plutonium [Pu]	2924/044	. . 10th Group
2924/011	. Groups of the periodic table	2924/0441	. . 11th Group
2924/01101	. . Alkali metals	2924/0442	. . 12th Group
2924/01102	. . Alkali earth metals	2924/0443	. . 13th Group
2924/01103	. . Transition metals	2924/0444	. . 14th Group
2924/01104	. . Refractory metals	2924/0445	. . Lanthanides
2924/01105	. . Rare earth metals	2924/0446	. . Actinides
2924/01106	. . . Lanthanides, i.e. Ce, Pr, Nd, Pm, Sm, Eu, Gd, Tb, Dy, Ho, Er, Tm, Yb, Lu	2924/0449	. . being a combination of two or more materials provided in the groups H01L 2924/0421 - H01L 2924/0446
2924/01107	. . . Actinides, i.e. Th, Pa, U, Np, Pu, Am, Cm, Bk, Cf, Es, Fm, Md, No, Lr	2924/04491	. . having a monocrystalline microstructure
2924/01108	. . Noble metals	2924/04492	. . having a polycrystalline microstructure
2924/01109	. . Metalloids or Semi-metals	2924/04494	. . having an amorphous microstructure, i.e. glass
2924/0111	. . Chalcogens	2924/045	. Carbides composed of metals from groups of the periodic table
2924/01111	. . Halogens	2924/0451	. . 1st Group
2924/01112	. . Noble gases	2924/0452	. . 2nd Group
2924/012	. Semiconductor purity grades	2924/0453	. . 3rd Group
2924/01201	. . 1N purity grades, i.e. 90%	2924/0454	. . 4th Group
2924/01202	. . 2N purity grades, i.e. 99%	2924/04541	. . . TiC
2924/01203	. . 3N purity grades, i.e. 99.9%	2924/0455	. . 5th Group
2924/01204	. . 4N purity grades, i.e. 99.99%	2924/0456	. . 6th Group
2924/01205	. . 5N purity grades, i.e. 99.999%	2924/04563	. . . WC
2924/01206	. . 6N purity grades, i.e. 99.9999%	2924/0457	. . 7th Group
2924/01207	. . 7N purity grades, i.e. 99.99999%	2924/0458	. . 8th Group
2924/01208	. . 8N purity grades, i.e. 99.999999%	2924/0459	. . 9th Group
2924/013	. Alloys	2924/046	. . 10th Group
2924/0132	. . Binary Alloys	2924/0461	. . 11th Group
2924/01321	. . . Isomorphous Alloys	2924/0462	. . 12th Group
2924/01322	. . . Eutectic Alloys, i.e. obtained by a liquid transforming into two solid phases	2924/0463	. . 13th Group
2924/01323 Hypoeutectic alloys i.e. with compositions lying to the left of the eutectic point	2924/0464	. . 14th Group
2924/01324 Hypereutectic alloys i.e. with compositions lying to the right of the eutectic point	2924/04642	. . . SiC
2924/01325	. . . Peritectic Alloys, i.e. obtained by a liquid and a solid transforming into a new and different solid phase	2924/0465	. . Lanthanides
2924/01326	. . . Monotectics, i.e. obtained by a liquid transforming into a solid and a new and different liquid phase	2924/0466	. . Actinides
2924/01327	. . . Intermediate phases, i.e. intermetallics compounds	2924/0469	. . being a combination of two or more materials provided in the groups H01L 2924/0451 - H01L 2924/0466
2924/0133	. . Ternary Alloys	2924/04691	. . having a monocrystalline microstructure
2924/0134	. . Quaternary Alloys	2924/04692	. . having a polycrystalline microstructure
2924/0135	. . Quinary Alloys	2924/04694	. . having an amorphous microstructure, i.e. glass
2924/014	. . Solder alloys	2924/047	. . Silicides composed of metals from groups of the periodic table
2924/01402	. . Invar, i.e. single-phase alloy of around 36% nickel and 64% iron	2924/0471	. . 1st Group
2924/01403	. . Kovar, i.e. FeNiCo alloys	2924/0472	. . 2nd Group
2924/01404	. . Alloy 42, i.e. FeNi42	2924/0473	. . 3rd Group
2924/01405	. . Inovco, i.e. Fe-33Ni-4.5Co	2924/0474	. . 4th Group
2924/042	. Borides composed of metals from groups of the periodic table	2924/0475	. . 5th Group
2924/0421	. . 1st Group	2924/0476	. . 6th Group
2924/0422	. . 2nd Group	2924/0477	. . 7th Group
2924/0423	. . 3rd Group	2924/0478	. . 8th Group
2924/0424	. . 4th Group	2924/0479	. . 9th Group
		2924/048	. . 10th Group
		2924/0481	. . 11th Group
		2924/0482	. . 12th Group
		2924/0483	. . 13th Group
		2924/0484	. . 14th Group
		2924/0485	. . Lanthanides

2924/0486	. . Actinides	2924/0532	. . 2nd Group
2924/0489	. . being a combination of two or more materials provided in the groups H01L 2924/0471 - H01L 2924/0486	2924/0533	. . 3rd Group
2924/04891	. . having a monocrystalline microstructure	2924/0534	. . 4th Group
2924/04892	. . having a polycrystalline microstructure	2924/05341	. . . TiO ₂
2924/04894	. . having an amorphous microstructure, i.e. glass	2924/05342	. . . ZrO ₂
2924/049	. Nitrides composed of metals from groups of the periodic table	2924/0535	. . 5th Group
2924/0491	. . 1st Group	2924/0536	. . 6th Group
2924/0492	. . 2nd Group	2924/0537	. . 7th Group
2924/0493	. . 3rd Group	2924/0538	. . 8th Group
2924/0494	. . 4th Group	2924/05381	. . . FeOx
2924/04941	. . . TiN	2924/0539	. . 9th Group
2924/0495	. . 5th Group	2924/054	. . 10th Group
2924/04953	. . . TaN	2924/0541	. . 11th Group
2924/0496	. . 6th Group	2924/0542	. . 12th Group
2924/0497	. . 7th Group	2924/0543	. . 13th Group
2924/0498	. . 8th Group	2924/05432	. . . Al ₂ O ₃
2924/0499	. . 9th Group	2924/0544	. . 14th Group
2924/05	. . 10th Group	2924/05442	. . . SiO ₂
2924/0501	. . 11th Group	2924/0545	. . Lanthanides
2924/0502	. . 12th Group	2924/0546	. . Actinides
2924/0503	. . 13th Group	2924/0549	. . being a combination of two or more materials provided in the groups H01L 2924/0531 - H01L 2924/0546
2924/05032	. . . AlN	2924/05491	. . having a monocrystalline microstructure
2924/0504	. . 14th Group	2924/05492	. . having a polycrystalline microstructure
2924/05042	. . . Si ₃ N ₄	2924/05494	. . having an amorphous microstructure, i.e. glass
2924/0505	. . Lanthanides	2924/055	. Chalcogenides other than oxygen i.e. sulfides, selenides and tellurides composed of metals from groups of the periodic table
2924/0506	. . Actinides	2924/0551	. . 1st Group
2924/0509	. . being a combination of two or more materials provided in the groups H01L 2924/0491 - H01L 2924/0506	2924/0552	. . 2nd Group
2924/05091	. . having a monocrystalline microstructure	2924/0553	. . 3rd Group
2924/05092	. . having a polycrystalline microstructure	2924/0554	. . 4th Group
2924/05094	. . having an amorphous microstructure, i.e. glass	2924/0555	. . 5th Group
2924/051	. Phosphides composed of metals from groups of the periodic table	2924/0556	. . 6th Group
2924/0511	. . 1st Group	2924/0557	. . 7th Group
2924/0512	. . 2nd Group	2924/0558	. . 8th Group
2924/0513	. . 3rd Group	2924/0559	. . 9th Group
2924/0514	. . 4th Group	2924/056	. . 10th Group
2924/0515	. . 5th Group	2924/0561	. . 11th Group
2924/0516	. . 6th Group	2924/0562	. . 12th Group
2924/0517	. . 7th Group	2924/0563	. . 13th Group
2924/0518	. . 8th Group	2924/0564	. . 14th Group
2924/0519	. . 9th Group	2924/0565	. . Lanthanides
2924/052	. . 10th Group	2924/0566	. . Actinides
2924/0521	. . 11th Group	2924/0569	. . being a combination of two or more materials provided in the groups H01L 2924/0551 - H01L 2924/0566
2924/0522	. . 12th Group	2924/05691	. . having a monocrystalline microstructure
2924/0523	. . 13th Group	2924/05692	. . having a polycrystalline microstructure
2924/0524	. . 14th Group	2924/05694	. . having an amorphous microstructure, i.e. glass
2924/0525	. . Lanthanides	2924/057	. Halides composed of metals from groups of the periodic table
2924/0526	. . Actinides	2924/0571	. . 1st Group
2924/0529	. . being a combination of two or more materials provided in the groups H01L 2924/0511 - H01L 2924/0526	2924/0572	. . 2nd Group
2924/05291	. . having a monocrystalline microstructure	2924/0573	. . 3rd Group
2924/05292	. . having a polycrystalline microstructure	2924/0574	. . 4th Group
2924/05294	. . having an amorphous microstructure, i.e. glass	2924/0575	. . 5th Group
2924/053	. Oxides composed of metals from groups of the periodic table	2924/0576	. . 6th Group
2924/0531	. . 1st Group	2924/0577	. . 7th Group
		2924/0578	. . 8th Group
		2924/0579	. . 9th Group

2924/058	. . 10th Group	2924/09701	. . . Low temperature co-fired ceramic [LTCC]
2924/0581	. . 11th Group	2924/10	. Details of semiconductor or other solid state devices to be connected
2924/0582	. . 12th Group	2924/1011	. . Structure
2924/0583	. . 13th Group	2924/1015	. . Shape
2924/0584	. . 14th Group	2924/10155	. . . being other than a cuboid
2924/0585	. . Lanthanides	2924/10156 at the periphery
2924/0586	. . Actinides	2924/10157 at the active surface
2924/0589	. . being a combination of two or more materials provided in the groups H01L 2924/0571 - H01L 2924/0586	2924/10158 at the passive surface
2924/05891	. . having a monocrystalline microstructure	2924/1016	. . . being a cuboid
2924/05892	. . having a polycrystalline microstructure	2924/10161 with a rectangular active surface
2924/05894	. . having an amorphous microstructure, i.e. glass	2924/10162 with a square active surface
2924/059	. Being combinations of any of the materials from the groups H01L 2924/042 - H01L 2924/0584 , e.g. oxynitrides	2924/1017	. . . being a sphere
2924/05991	. . having a monocrystalline microstructure	2924/102	. . Material of the semiconductor or solid state bodies
2924/05992	. . having a polycrystalline microstructure	2924/1025	. . . Semiconducting materials
2924/05994	. . having an amorphous microstructure, i.e. glass	2924/10251 Elemental semiconductors, i.e. Group IV
2924/06	. Polymers (polymers per se C08 ; polymer adhesives C09J)	2924/10252 Germanium [Ge]
2924/061	. . Polyolefin polymer	2924/10253 Silicon [Si]
2924/0615	. . Styrenic polymer	2924/10254 Diamond [C]
2924/062	. . Halogenated polymer	2924/1026 Compound semiconductors
2924/0625	. . Polyvinyl alcohol	2924/1027 IV
2924/063	. . Polyvinyl acetate	2924/10271 Silicon-germanium [SiGe]
2924/0635	. . Acrylic polymer	2924/10272 Silicon Carbide [SiC]
2924/064	. . Graft polymer	2924/1032 III-V
2924/0645	. . Block copolymer	2924/10321 Aluminium antimonide [AlSb]
2924/065	. . ABS	2924/10322 Aluminium arsenide [AlAs]
2924/0655	. . Polyacetal	2924/10323 Aluminium nitride [AlN]
2924/066	. . Phenolic resin	2924/10324 Aluminium phosphide [AlP]
2924/0665	. . Epoxy resin	2924/10325 Boron nitride [BN], e.g. cubic, hexagonal, nanotube
2924/067	. . Polyphenylene	2924/10326 Boron phosphide [BP]
2924/0675	. . Polyester	2924/10327 Boron arsenide [BAs, B ₁₂ As ₂]
2924/068	. . Polycarbonate	2924/10328 Gallium antimonide [GaSb]
2924/0685	. . Polyether	2924/10329 Gallium arsenide [GaAs]
2924/069	. . Polyurethane	2924/1033 Gallium nitride [GaN]
2924/0695	. . Polyamide	2924/10331 Gallium phosphide [GaP]
2924/07	. . Polyamine or polyimide	2924/10332 Indium antimonide [InSb]
2924/07001	. . . Polyamine	2924/10333 Indium arsenide [InAs]
2924/07025	. . . Polyimide	2924/10334 Indium nitride [InN]
2924/0705	. . Sulfur containing polymer	2924/10335 Indium phosphide [InP]
2924/0715	. . Polysiloxane	2924/10336 Aluminium gallium arsenide [AlGaAs]
2924/078	. . Adhesive characteristics other than chemical	2924/10337 Indium gallium arsenide [InGaAs]
2924/07802	. . . not being an ohmic electrical conductor	2924/10338 Indium gallium phosphide [InGaP]
2924/0781	. . . being an ohmic electrical conductor	2924/10339 Aluminium indium arsenide [AlInAs]
2924/07811 Extrinsic, i.e. with electrical conductive fillers	2924/1034 Aluminium indium antimonide [AlInSb]
2924/07812 Intrinsic, e.g. polyaniline [PANI]	2924/10341 Gallium arsenide nitride [GaAsN]
2924/0782	. . . being pressure sensitive	2924/10342 Gallium arsenide phosphide [GaAsP]
2924/095	. with a principal constituent of the material being a combination of two or more materials provided in the groups H01L 2924/013 - H01L 2924/0715	2924/10343 Gallium arsenide antimonide [GaAsSb]
2924/0951	. . Glass epoxy laminates	2924/10344 Aluminium gallium nitride [AlGaN]
2924/09511	. . . FR-4	2924/10345 Aluminium gallium phosphide [AlGaP]
2924/09512	. . . FR-5	2924/10346 Indium gallium nitride [InGaN]
2924/09522	. . . G10	2924/10347 Indium arsenide antimonide [InAsSb]
2924/09523	. . . G11	2924/10348 Indium gallium antimonide [InGaSb]
2924/096	. . Cermets, i.e. composite material composed of ceramic and metallic materials	2924/10349 Aluminium gallium indium phosphide [AlGaInP]
2924/097	. . Glass-ceramics, e.g. devitrified glass	2924/1035 Aluminium gallium arsenide phosphide [AlGaInP]
		2924/10351 Indium gallium arsenide phosphide [InGaAsP]
		2924/10352 Indium gallium arsenide antimonide [InGaAsSb]

2924/10353	Indium arsenide antimonide phosphide [InAsSbP]	2924/1068	Lithium niobate [LiNbO ₃]
2924/10354	Aluminium indium arsenide phosphide [AlInAsP]	2924/10681	Lanthanum copper oxide [La ₂ CuO ₄]
2924/10355	Aluminium gallium arsenide nitride [AlGaAsN]	2924/1072	Layered
2924/10356	Indium gallium arsenide nitride [InGaAsN]	2924/10721	Lead(II)iodide [PbI ₂]
2924/10357	Indium aluminium arsenide nitride [InAlAsN]	2924/10722	Molybdenum disulfide [MoS ₂]
2924/10358	Gallium arsenide antimonide nitride [GaAsSbN]	2924/10723	Gallium selenide [GaSe]
2924/10359	Gallium indium nitride arsenide antimonide [GaInNAsSb]	2924/10724	Tin sulfide [SnS]
2924/1036	Gallium indium arsenide antimonide phosphide [GaInAsSbP]	2924/10725	Bismuth sulfide [Bi ₂ S ₃]
2924/1037	II-VI	2924/1077	Magnetic diluted [DMS]
2924/10371	Cadmium selenide [CdSe]	2924/10771	Gallium manganese arsenide [GaMnAs]
2924/10372	Cadmium sulfide [CdS]	2924/10772	Indium manganese arsenide [InMnAs]
2924/10373	Cadmium telluride [CdTe]	2924/10773	Cadmium manganese telluride [CdMnTe]
2924/10375	Zinc selenide [ZnSe]	2924/10774	Lead manganese telluride [PbMnTe]
2924/10376	Zinc sulfide [ZnS]	2924/10775	Lanthanum calcium manganate [La _{0.7} Ca _{0.3} MnO ₃]
2924/10377	Zinc telluride [ZnTe]	2924/10776	Iron(II)oxide [FeO]
2924/10378	Cadmium zinc telluride, i.e. CZT [CdZnTe]	2924/10777	Nickel(II)oxide [NiO]
2924/10379	Mercury cadmium telluride [HgZnTe]	2924/10778	Europium(II)oxide [EuO]
2924/1038	Mercury zinc telluride [HgZnSe]	2924/10779	Europium(II)sulfide [EuS]
2924/10381	Mercury zinc selenide [HgZnSe]	2924/1078	Chromium(III)bromide [CrBr ₃]
2924/1042	I-VII	2924/1082	Other
2924/10421	Cuprous chloride [CuCl]	2924/10821	Copper indium gallium selenide, CIGS [CuInGaSe ₂]
2924/1047	I-VI	2924/10822	Copper zinc tin sulfide, CZTS [Cu ₂ ZnSnS ₄]
2924/10471	Copper sulfide [CuS]	2924/10823	Copper indium selenide, CIS [CuInSe ₂]
2924/1052	IV-VI	2924/10824	Silver gallium sulfide [AgGaS ₂]
2924/10521	Lead selenide [PbSe]	2924/10825	Zinc silicon phosphide [ZnSiP ₂]
2924/10522	Lead(II)sulfide [PbS]	2924/10826	Arsenic selenide [As ₂ S ₃]
2924/10523	Lead telluride [PbTe]	2924/10827	Platinum silicide [PtSi]
2924/10524	Tin sulfide [SnS, SnS ₂]	2924/10828	Bismuth(III)iodide [BiI ₃]
2924/10525	Tin telluride [SnTe]	2924/10829	Mercury(II)iodide [HgI ₂]
2924/10526	Lead tin telluride [PbSnTe]	2924/1083	Thallium(I)bromide [TlBr]
2924/10527	Thallium tin telluride [Tl ₂ SnTe ₅]	2924/10831	Selenium [Se]
2924/10528	Thallium germanium telluride [Tl ₂ GeTe ₅]	2924/10832	Silver sulfide [Ag ₂ S]
2924/1057	V-VI	2924/10833	Iron disulfide [FeS ₂]
2924/10571	Bismuth telluride [Bi ₂ Te ₃]	2924/11	Device type
2924/1062	II-V	2924/12	Passive devices, e.g. 2 terminal devices
2924/10621	Cadmium phosphide [Cd ₃ P ₂]	2924/1203	Rectifying Diode
2924/10622	Cadmium arsenide [Cd ₃ As ₂]	2924/12031	PIN diode
2924/10623	Cadmium antimonide [Cd ₃ Sb ₂]	2924/12032	Schottky diode
2924/10624	Zinc phosphide [Zn ₃ P ₂]	2924/12033	Gunn diode
2924/10625	Zinc arsenide [Zn ₃ As ₂]	2924/12034	Varactor
2924/10626	Zinc antimonide [Zn ₃ Sb ₂]	2924/12035	Zener diode
2924/1067	Oxide	2924/12036	PN diode
2924/10671	Titanium dioxide, anatase, rutile, brookite [TiO ₂]	2924/12037	Cat's whisker diode
2924/10672	Copper(I)oxide [Cu ₂ O]	2924/12038	Point contact
2924/10673	Copper(II)oxide [CuO]	2924/1204	Optical Diode
2924/10674	Uranium dioxide [UO ₂]	2924/12041	LED
2924/10675	Uranium trioxide [UO ₃]	2924/12042	LASER
2924/10676	Bismuth trioxide [Bi ₂ O ₃]	2924/12043	Photo diode
2924/10677	Tin dioxide [SnO ₂]	2924/12044	OLED
2924/10678	Barium titanate [BaTiO ₃]	2924/1205	Capacitor
2924/10679	Strontium titanate [SrTiO ₃]	2924/1206	Inductor
			2924/1207	Resistor
			2924/13	Discrete devices, e.g. 3 terminal devices
			2924/1301	Thyristor
			2924/13011	Anode Gate Thyristor [AGT]
			2924/13013	Bidirectional Control Thyristor [BCT]
			2924/13014	Breakover Diode [BOD]
			2924/13015	DIAC - Bidirectional trigger device

2924/13016	Dynistor - Unidirectional switching device	2924/1307	Organic Field-Effect Transistor [OFET]
2924/13017	Shockley diode - Unidirectional trigger and switching device	2924/13071	Ballistic transistor
2924/13018	SIDAC - Bidirectional switching device	2924/13072	Sensor FET
2924/13019	Trisil, SIDACtor - Bidirectional protection devices	2924/13073	ion-sensitive field-effect transistor [ISFET]
2924/1302	GTO - Gate Turn-Off thyristor	2924/13074	Electrolyte-oxide-semiconductor field effect transistor [EOSFET], e.g. Neurochip
2924/13021	DB-GTO - Distributed Buffer Gate Turn-Off thyristor	2924/13075	Deoxyribonucleic acid field-effect transistor [DNAFET]
2924/13022	MA-GTO - Modified Anode Gate Turn-Off thyristor	2924/13076	DEPFET
2924/13023	IGCT - Integrated Gate Commutated Thyristor	2924/13078	Unijunction transistors
2924/13024	LASCR - Light Activated SCR, or LTT - Light triggered thyristor	2924/13079	Single-electron transistors [SET]
2924/13025	Light Activated Semiconducting Switch [LASS]	2924/1308	Nanofluidic transistor
2924/13026	MCT - MOSFET Controlled Thyristor - It contains two additional FET structures for on/off control	2924/13081	Multigate devices
2924/13027	BRT - Base Resistance Controlled Thyristor	2924/13082	Tetrode transistor
2924/13028	RCT - Reverse Conducting Thyristor	2924/13083	Pentode transistor
2924/13029	PUT or PUJT - Programmable Unijunction Transistor - A thyristor with gate on n-type layer near to the anode used as a functional replacement for unijunction transistor	2924/13084	Trigate transistor
2924/1303	SCS - Silicon Controlled Switch or Thyristor Tetrode - A thyristor with both cathode and anode gates	2924/13085	Dual gate FETs
2924/13032	SITh - Static Induction Thyristor, or FCTh - Field Controlled Thyristor - containing a gate structure that can shut down anode current flow	2924/13086	Junctionless Nanowire Transistor [JNT]
2924/13033	TRIAC - Triode for Alternating Current - A bidirectional switching device containing two thyristor structures with common gate contact	2924/13087	Vertical-Slit Field-Effect Transistor [VeSFET]
2924/13034	Silicon Controlled Rectifier [SCR]	2924/13088	Graphene Nanoribbon Field-Effect Transistor [GNRFET]
2924/13035	Asymmetrical SCR [ASCR]	2924/13089	Nanoparticle Organic Memory Field-Effect Transistor [NOMFET]
2924/1304	Transistor	2924/1309	Modulation-Doped Field Effect Transistor [MODFET]
2924/1305	Bipolar Junction Transistor [BJT]	2924/13091	Metal-Oxide-Semiconductor Field-Effect Transistor [MOSFET]
2924/13051	Heterojunction bipolar transistor [HBT]	2924/13092	Dual Gate Metal-Oxide-Semiconductor Field-Effect Transistor [DGMOSFET]
2924/13052	Schottky transistor	2924/14	Integrated circuits
2924/13053	Avalanche transistor	2924/141	Analog devices
2924/13054	Darlington transistor	2924/142	HF devices
2924/13055	Insulated gate bipolar transistor [IGBT]	2924/1421	RF devices
2924/13056	Photo transistor	2924/14211	Voltage-controlled oscillator [VCO]
2924/1306	Field-effect transistor [FET]	2924/14215	Low-noise amplifier [LNA]
2924/13061	Carbon nanotube field-effect transistor [CNFET]	2924/1422	Mixer
2924/13062	Junction field-effect transistor [JFET]	2924/14221	Electronic mixer
2924/13063	Metal-Semiconductor Field-Effect Transistor [MESFET]	2924/14222	Frequency mixer
2924/13064	High Electron Mobility Transistor [HEMT, HFET [heterostructure FET], MODFET]	2924/1423	Monolithic Microwave Integrated Circuit [MMIC]
2924/13066	Inverted-T field effect transistor [ITFET]	2924/1424	Operational amplifier
2924/13067	FinFET, source/drain region shapes fins on the silicon surface	2924/1425	Converter
2924/13068	Fast-reverse epitaxial diode field-effect transistor [FREDFET]	2924/14251	Frequency converter
2924/13069	Thin film transistor [TFT]	2924/14252	Voltage converter
			2924/14253	Digital-to-analog converter [DAC]
			2924/1426	Driver
			2924/1427	Voltage regulator [VR]
			2924/143	Digital devices
			2924/1431	Logic devices
			2924/1432	Central processing unit [CPU]
			2924/1433	Application-specific integrated circuit [ASIC]
			2924/14335	Digital signal processor [DSP]
			2924/1434	Memory
			2924/1435	Random access memory [RAM]
			2924/1436	Dynamic random-access memory [DRAM]
			2924/14361	Synchronous dynamic random access memory [SDRAM]

2924/14362	RAS Only Refresh [ROR]	2924/15312	being a pin array, e.g. PGA
2924/14363	CAS before RAS refresh [CBR]	2924/15313	being a land array, e.g. LGA
2924/14364	Multibank DRAM [MDRAM]	2924/1532	the connection portion being formed on the die mounting surface of the substrate
2924/14365	Video DRAM [VRAM]	2924/15321	being a ball array, e.g. BGA
2924/14366	Window DRAM [WRAM]	2924/15322	being a pin array, e.g. PGA
2924/14367	Fast page mode DRAM [FPM DRAM]	2924/15323	being a land array, e.g. LGA
2924/14368	Extended data out DRAM [EDO DRAM]	2924/1533	the connection portion being formed both on the die mounting surface of the substrate and outside the die mounting surface of the substrate
2924/14369	Burst EDO DRAM [BEDO DRAM]	2924/15331	being a ball array, e.g. BGA
2924/1437	Static random-access memory [SRAM]	2924/15332	being a pin array, e.g. PGA
2924/1438	Flash memory	2924/15333	being a land array, e.g. LGA
2924/1441	Ferroelectric RAM [FeRAM or FRAM]	2924/156	. . .	Material
2924/1442	Synchronous graphics RAM [SGRAM]	2924/157	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2924/1443	Non-volatile random-access memory [NVRAM]	2924/15701	the principal constituent melting at a temperature of less than 400 C
2924/1444	PBRAM	2924/15717	the principal constituent melting at a temperature of greater than or equal to 400 C and less than 950 C
2924/145	Read-only memory [ROM]	2924/15724	Aluminium [Al] as principal constituent
2924/1451	EPROM	2924/15738	the principal constituent melting at a temperature of greater than or equal to 950 C and less than 1550 C
2924/14511	EEPROM	2924/15747	Copper [Cu] as principal constituent
2924/1453	PROM	2924/1576	Iron [Fe] as principal constituent
2924/146	. .	Mixed devices	2924/15763	the principal constituent melting at a temperature of greater than 1550 C
2924/1461	. . .	MEMS	2924/15786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2924/15	. .	Details of package parts other than the semiconductor or other solid state devices to be connected	2924/15787	Ceramics, e.g. crystalline carbides, nitrides or oxides
2924/151	. .	Die mounting substrate	2924/15788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2924/1511	. . .	Structure	2924/1579	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2924/1515	. . .	Shape	2924/15791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2924/15151	the die mounting substrate comprising an aperture, e.g. for underfilling, outgassing, window type wire connections	2924/15793	with a principal constituent of the material being a solid not provided for in groups H01L 2924/157 - H01L 2924/15791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2924/15153	the die mounting substrate comprising a recess for hosting the device	2924/15798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2924/15155	the shape of the recess being other than a cuboid	2924/161	. . .	Cap
2924/15156	Side view	2924/1611	. . .	Structure
2924/15157	Top view	2924/1615	. . .	Shape
2924/15158	the die mounting substrate being other than a cuboid	2924/16151	Cap comprising an aperture, e.g. for pressure control, encapsulation
2924/15159	Side view	2924/16152	Cap comprising a cavity for hosting the device, e.g. U-shaped cap
2924/15162	Top view			
2924/15165	. . .	Monolayer substrate			
2924/1517	. . .	Multilayer substrate			
2924/15172	Fan-out arrangement of the internal vias			
2924/15173	in a single layer of the multilayer substrate			
2924/15174	in different layers of the multilayer substrate			
2924/15182	Fan-in arrangement of the internal vias			
2924/15183	in a single layer of the multilayer substrate			
2924/15184	in different layers of the multilayer substrate			
2924/15192	Resurf arrangement of the internal vias			
2924/152	. . .	Disposition			
2924/153	. . .	Connection portion			
2924/1531	the connection portion being formed only on the surface of the substrate opposite to the die mounting surface			
2924/15311	being a ball array, e.g. BGA			

2924/16153	Cap enclosing a plurality of side-by-side cavities [e.g. E-shaped cap]	2924/16587	Ceramics, e.g. crystalline carbides, nitrides or oxides
2924/1616	Cavity shape	2924/16588	Glasses, e.g. amorphous oxides, nitrides or fluorides
2924/1617	Cavity coating	2924/1659	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2924/16171	Material	2924/16593	with a principal constituent of the material being a solid not provided for in groups H01L 2924/157 - H01L 2924/15791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2924/16172	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2924/16598	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2924/16173	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2924/166	. . .	Material
2924/16174	Ceramics, e.g. crystalline carbides, nitrides or oxides (glass ceramics H01L 2224/16175)	2924/167	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof
2924/16175	Glasses, e.g. amorphous oxides, nitrides or fluorides	2924/16701	the principal constituent melting at a temperature of less than 400 C
2924/16176	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2924/16717	the principal constituent melting at a temperature of greater than or equal to 400 C and less than 950 C
2924/16177	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2924/16724	Aluminium [Al] as principal constituent
2924/16178	with a principal constituent of the material being a solid not provided for in groups H01L 2924/157 - H01L 2924/15791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2924/16738	the principal constituent melting at a temperature of greater than or equal to 950 C and less than 1550 C
2924/16179	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2924/16747	Copper [Cu] as principal constituent
2924/1619	Cavity coating shape	2924/1676	Iron [Fe] as principal constituent
2924/16195	Flat cap [not enclosing an internal cavity]	2924/16763	the principal constituent melting at a temperature of greater than 1550 C
2924/16196	Cap forming a cavity, e.g. being a curved metal foil	2924/16786	with a principal constituent of the material being a non metallic, non metalloid inorganic material
2924/162	. . .	Disposition	2924/16787	Ceramics, e.g. crystalline carbides, nitrides or oxides
2924/16235	Connecting to a semiconductor or solid-state bodies, i.e. cap-to-chip	2924/16788	Glasses, e.g. amorphous oxides, nitrides or fluorides
2924/16251	Connecting to an item not being a semiconductor or solid-state body, e.g. cap-to-substrate	2924/1679	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy
2924/1626	Cap-in-cap assemblies	2924/16791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene
2924/1627	stacked type assemblies, e.g. stacked multi-cavities	2924/16793	with a principal constituent of the material being a solid not provided for in groups H01L 2924/167 - H01L 2924/16791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond
2924/163	. . .	Connection portion, e.g. seal	2924/16798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams
2924/1631	Structure	2924/171	. . .	Frame
2924/16315	Shape	2924/1711	. . .	Structure
2924/1632	Disposition	2924/1715	. . .	Shape
2924/164	Material	2924/17151	Frame comprising an aperture, e.g. for pressure control, encapsulation
2924/165	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2924/172	. . .	Disposition
2924/16586	with a principal constituent of the material being a non metallic, non metalloid inorganic material			

2924/173	. . .	Connection portion, e.g. seal	2924/1903	. . .	including wave guides
2924/176	. . .	Material	2924/19031	being a strip line type
2924/177	with a principal constituent of the material being a metal or a metalloid, e.g. boron [B], silicon [Si], germanium [Ge], arsenic [As], antimony [Sb], tellurium [Te] and polonium [Po], and alloys thereof	2924/19032	being a microstrip line type
			2924/19033	being a coplanar line type
			2924/19038	being a hybrid line type
			2924/19039	impedance transition between different types of wave guides
2924/17701	the principal constituent melting at a temperature of less than 400 C	2924/1904	. . .	Component type
2924/17717	the principal constituent melting at a temperature of greater than or equal to 400 C and less than 950 C	2924/19041	being a capacitor
			2924/19042	being an inductor
			2924/19043	being a resistor
2924/17724	Aluminium [Al] as principal constituent	2924/1905	. .	Shape
2924/17738	the principal constituent melting at a temperature of greater than or equal to 950 C and less than 1550 C	2924/19051	. . .	Impedance matching structure [e.g. balun]
			2924/191	. .	Disposition
2924/17747	Copper [Cu] as principal constituent	2924/19101	. . .	of discrete passive components
2924/1776	Iron [Fe] as principal constituent	2924/19102	in a stacked assembly with the semiconductor or solid state device
2924/17763	the principal constituent melting at a temperature of greater than 1550 C	2924/19103	interposed between the semiconductor or solid-state device and the die mounting substrate, i.e. chip-on-passive
2924/17786	with a principal constituent of the material being a non metallic, non metalloid inorganic material	2924/19104	on the semiconductor or solid-state device, i.e. passive-on-chip
2924/17787	Ceramics, e.g. crystalline carbides, nitrides or oxides	2924/19105	in a side-by-side arrangement on a common die mounting substrate
2924/17788	Glasses, e.g. amorphous oxides, nitrides or fluorides	2924/19106	in a mirrored arrangement on two different side of a common die mounting substrate
2924/1779	with a principal constituent of the material being a polymer, e.g. polyester, phenolic based polymer, epoxy	2924/19107	off-chip wires
2924/17791	The principal constituent being an elastomer, e.g. silicones, isoprene, neoprene	2924/20	. .	Parameters
			2924/201	. .	Temperature ranges
2924/17793	with a principal constituent of the material being a solid not provided for in groups H01L 2924/177 - H01L 2924/17791 , e.g. allotropes of carbon, fullerene, graphite, carbon-nanotubes, diamond	2924/20101	. . .	Temperature range $T < 0\text{ C}$, $T < 273.15\text{ K}$
			2924/20102	. . .	Temperature range $0\text{ C} = < T < 60\text{ C}$, $273.15\text{ K} = < T < 333.15\text{ K}$
			2924/20103	. . .	Temperature range $60\text{ C} = < T < 100\text{ C}$, $333.15\text{ K} = < T < 373.15\text{ K}$
2924/17798	with a principal constituent of the material being a combination of two or more materials in the form of a matrix with a filler, i.e. being a hybrid material, e.g. segmented structures, foams	2924/20104	. . .	Temperature range $100\text{ C} = < T < 150\text{ C}$, $373.15\text{ K} = < T < 423.15\text{ K}$
			2924/20105	. . .	Temperature range $150\text{ C} = < T < 200\text{ C}$, $423.15\text{ K} = < T < 473.15\text{ K}$
			2924/20106	. . .	Temperature range $200\text{ C} = < T < 250\text{ C}$, $473.15\text{ K} = < T < 523.15\text{ K}$
			2924/20107	. . .	Temperature range $250\text{ C} = < T < 300\text{ C}$, $523.15\text{ K} = < T < 573.15\text{ K}$
2924/181	. .	Encapsulation	2924/20108	. . .	Temperature range $300\text{ C} = < T < 350\text{ C}$, $573.15\text{ K} = < T < 623.15\text{ K}$
2924/1811	. . .	Structure	2924/20109	. . .	Temperature range $350\text{ C} = < T < 400\text{ C}$, $623.15\text{ K} = < T < 673.15\text{ K}$
2924/1815	. . .	Shape	2924/2011	. . .	Temperature range $400\text{ C} = < T < 450\text{ C}$, $673.15\text{ K} = < T < 723.15\text{ K}$
2924/1816	Exposing the passive side of the semiconductor or solid-state body	2924/20111	. . .	Temperature range $450\text{ C} = < T < 500\text{ C}$, $723.15\text{ K} = < T < 773.15\text{ K}$
2924/18161	of a flip chip	2924/202	. .	Electromagnetic wavelength ranges [W]
2924/18162	of a chip with build-up interconnect	2924/20201	. . .	Gamma radiation, i.e. wavelength less than 0.01 nm
2924/18165	of a wire bonded chip	2924/20202	. . .	X-ray radiation, i.e. wavelength 0.01 to 10 nm
2924/182	. . .	Disposition	2924/2021	. . .	Ultraviolet radiation
2924/183	. . .	Connection portion, e.g. seal	2924/20211	UV-C $100 = < W < 280\text{ nm}$
2924/18301	being an anchoring portion, i.e. mechanical interlocking between the encapsulation resin and another package part	2924/20212	UV-B $280 = < W < 315\text{ nm}$
			2924/20213	UV-A $315 = < W < 400\text{ nm}$
2924/186	. . .	Material	2924/2024	. . .	Visible spectrum wavelength $390 = < W < 700\text{ nm}$, i.e. 400-790 THz
2924/19	. .	Details of hybrid assemblies other than the semiconductor or other solid state devices to be connected	2924/2026	. . .	Infrared radiation $700 = < W < 3000\text{ nm}$
2924/1901	. .	Structure	2924/20261	IR-A $700 = < W < 1400\text{ nm}$, i.e. 215 THz-430 THz
2924/19011	. . .	including integrated passive components			
2924/19015	. . .	including thin film passive components			
2924/1902	. . .	including thick film passive components			

2924/20262	IR-B 1400=<W<3000 nm, i.e. 100THz-215 THz	2924/20752	. . .	larger or equal to 20 microns less than 30 microns
2924/20263	IR-C 3000 nm =<W<1 mm, i.e. 300 GHz-100THz	2924/20753	. . .	larger or equal to 30 microns less than 40 microns
2924/2027	. . .	Radio 1 mm - km 300 GHz - 3 Hz	2924/20754	. . .	larger or equal to 40 microns less than 50 microns
2924/20271	Microwave radiation 1 mm - 1 meter, i.e 300 GHz - 300 MHz	2924/20755	. . .	larger or equal to 50 microns less than 60 microns
2924/203	. .	Ultrasonic frequency ranges, i.e. KHz	2924/20756	. . .	larger or equal to 60 microns less than 70 microns
2924/20301	. . .	Ultrasonic frequency [f] f<25 kHz	2924/20757	. . .	larger or equal to 70 microns less than 80 microns
2924/20302	. . .	Ultrasonic frequency [f] 25 KHz=<f< 50 KHz	2924/20758	. . .	larger or equal to 80 microns less than 90 microns
2924/20303	. . .	Ultrasonic frequency [f] 50 KHz=<f< 75 KHz	2924/20759	. . .	larger or equal to 90 microns less than 100 microns
2924/20304	. . .	Ultrasonic frequency [f] 75 KHz=<f< 100 KHz	2924/2076	. . .	equal to or larger than 100 microns
2924/20305	. . .	Ultrasonic frequency [f] 100 KHz=<f< 125 KHz	2924/30	. .	Technical effects
2924/20306	. . .	Ultrasonic frequency [f] 125 KHz=<f< 150 KHz	2924/301	. .	Electrical effects
2924/20307	. . .	Ultrasonic frequency [f] 150 KHz=<f< 175 KHz	2924/30101	. . .	Resistance
2924/20308	. . .	Ultrasonic frequency [f] 175 KHz=<f< 200 KHz	2924/30105	. . .	Capacitance
2924/20309	. . .	Ultrasonic frequency [f] f>=200 KHz	2924/30107	. . .	Inductance
2924/206	. .	Length ranges	2924/3011	. . .	Impedance
2924/2064	. . .	larger or equal to 1 micron less than 100 microns	2924/30111	matching
2924/20641	. . .	larger or equal to 100 microns less than 200 microns	2924/302	. . .	Electrostatic
2924/20642	. . .	larger or equal to 200 microns less than 300 microns	2924/30201	Charge
2924/20643	. . .	larger or equal to 300 microns less than 400 microns	2924/30205	Discharge
2924/20644	. . .	larger or equal to 400 microns less than 500 microns	2924/3025	. . .	Electromagnetic shielding
2924/20645	. . .	larger or equal to 500 microns less than 600 microns	2924/35	. .	Mechanical effects
2924/20646	. . .	larger or equal to 600 microns less than 700 microns	2924/351	. . .	Thermal stress
2924/20647	. . .	larger or equal to 700 microns less than 800 microns	2924/3511	Warping
2924/20648	. . .	larger or equal to 800 microns less than 900 microns	2924/3512	Cracking
2924/20649	. . .	larger or equal to 900 microns less than 1000 microns	2924/35121	Peeling or delaminating
2924/2065	. . .	larger or equal to 1000 microns less than 1500 microns	2924/36	. .	Material effects
2924/20651	. . .	larger or equal to 1500 microns less than 2000 microns	2924/364	. . .	Polymers
2924/20652	. . .	larger or equal to 2000 microns less than 2500 microns	2924/3641	Outgassing
2924/20653	. . .	larger or equal to 2500 microns less than 3000 microns	2924/365	. . .	Metallurgical effects
2924/20654	. . .	larger or equal to 3000 microns less than 4000 microns	2924/3651	Formation of intermetallics
2924/20655	. . .	larger or equal to 4000 microns less than 5000 microns	2924/36511	Purple plague
2924/20656	. . .	larger or equal to 5000 microns less than 6000 microns	2924/3656	Formation of Kirkendall voids
2924/20657	. . .	larger or equal to 6000 microns less than 7000 microns	2924/37	. .	Effects of the manufacturing process
2924/20658	. . .	larger or equal to 7000 microns less than 8000 microns	2924/37001	. . .	Yield
2924/207	. .	Diameter ranges	2924/37002	. . .	Shelf life
2924/2075	. . .	larger or equal to 1 micron less than 10 microns	2924/3701	. . .	increased through put
2924/20751	. . .	larger or equal to 10 microns less than 20 microns	2924/38	. .	Effects and problems related to the device integration
			2924/381	. . .	Pitch distance
			2924/384	. . .	Bump effects
			2924/3841	Solder bridging
			2924/386	. . .	Wire effects
			2924/3861	Sag
			2924/3862	Sweep
			2924/40	. .	Details of apparatuses used for either manufacturing connectors or connecting the semiconductor or solid-state body
			2924/401	. .	LASER
			2924/40101	. . .	Mode
			2924/40102	being pulsed
			2924/40103	being continous
			2924/40105	. . .	Beam details
			2924/4015	Shape
			2924/402	. . .	Type

H01L

- 2924/40201 being a chemical
- 2924/40202 Deuterium Flouride [DF] LASER
- 2924/40203 Hydrogen Flouride [HF] LASER
- 2924/40207 Dye laser
- 2924/4025 being a gas
- 2924/40251 argon-ion LASER
- 2924/40252 CO₂ LASER
- 2924/40253 HeAg LASER
- 2924/40254 HeNe LASER
- 2924/40255 NeCu LASER
- 2924/403 being an Excimer
- 2924/40301 ArF LASER
- 2924/40302 F2 LASER
- 2924/40303 KrCl LASER
- 2924/40304 KrF LASER
- 2924/40305 XeCl LASER
- 2924/40306 XeF LASER
- 2924/4035 being a fiber hosted LASER
- 2924/404 being a solid state
- 2924/40401 Free electron LASER
- 2924/40402 Photonic crystal LASER
- 2924/40403 Fiber solid state LASER
- 2924/40404 Yttrium Aluminium Garnet Nd:YAG LASER
- 2924/40405 Yttrium Lithium Flouride Nd:YLF LASER
- 2924/40406 Ruby LASER
- 2924/40407 Yb:YAG LASER
- 2924/405 Wavelength
- 2924/40501 UV spectrum
- 2924/40502 Visible spectrum
- 2924/40503 IR spectrum

2933/00 Details relating to devices covered by the group [H01L 33/00](#) but not provided for in its subgroups

- 2933/0008 . . Processes
- 2933/0016 . . relating to electrodes
- 2933/0025 . . relating to coatings
- 2933/0033 . . relating to semiconductor body packages
- 2933/0041 . . . relating to wavelength conversion elements
- 2933/005 . . . relating to encapsulations
- 2933/0058 . . . relating to optical field-shaping elements
- 2933/0066 . . . relating to arrangements for conducting electric current to or from the semiconductor body
- 2933/0075 . . . relating to heat extraction or cooling elements
- 2933/0083 . . Periodic patterns for optical field-shaping in or on the semiconductor body or semiconductor body package, e.g. photonic bandgap structures
- 2933/0091 . . Scattering means in or on the semiconductor body or semiconductor body package ([H01L 33/22](#) takes precedence)